

Development of a portable electrochemical instrument for the monitoring of heavy metals.

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DEVELOPMENT OF A PORTABLE ELECTROCHEMICAL
INSTRUMENT FOR THE MONITORING OF HEAVY METALS

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requirements of
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for the degree of the Master of Philosophy

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Abstract

This report describes the development of a novel, portable, electrochemical instrument capable of gathering real-time quantitative data on a range of heavy metal contaminants. The unit is being developed for use on the site of contaminated land or water and is also able to determine the oxidation state of a metal, which is a measure of the metal's toxicity. The system provides the facilities found in a traditional lab based instrument, in a hand held design. In contrast to existing commercial systems, it can stand alone without the need of a computer and expert operators.

At the present stage of development, the instrument is capable of detecting and identifying six different toxic environmental pollutants, lead, cadmium, mercury, zinc, nickel and copper with good sensitivity and precision. Two different identification techniques have been developed. The first technique is based on the statistical profile (probability density function) of oxidation potential. The second method is based on an artificial neural network. The instrument with the combination of a Geographical Position System (GPS) is capable of storing the geographical position of the sample under test. Software has been developed to combine pollutant results with geographical position, in order to produce a cartographical presentation of the pollution of an area.

Summary

Heavy metals in land and natural water may have a detrimental effect on both human health and the environment. Apart from direct health or environmental problems, water or land contamination can cause economic and financial damage. The Confederation of British Industry has estimated that as much as 200,000 hectares of land is contaminated in the UK and remediation of these areas could cost up to £20 billion. Such land includes sites previously used for heavy industries such as steel making and shipbuilding.

Monitoring heavy metals at various points in industrial processes, in natural water and at agricultural, urban and industrial sites is highly important. At present, a great deal of manpower is employed by different companies to screen for them, which usually requires numerous sample collections and the use of dedicated laboratories. The existing analytical techniques that are used for heavy metal identification require highly trained personnel to undertake time consuming data analysis and interpretation of sample collections. Furthermore, existing detection instruments are generally complicated to operate, bulky, expensive, impractical to use for on-site monitoring and often involve sample pre-treatment before measurement. A fast, reliable, relatively inexpensive portable (hand held) instrument capable of direct monitoring of heavy metal contaminants *in-situ*, which can stand alone without the need of a computer, is consequently very desirable.

This report describes the development of a portable electrochemical instrument for detecting, identifying and measuring concentrations of heavy metals in soil or water. In contrast to existing commercial systems, it is portable, easy to use, avoids expensive and time-consuming procedures, and can stand alone without the need of a computer and expert operators. The instrument at present can detect and identify six different toxic metals, namely lead, cadmium, mercury, zinc, nickel and copper. Two different identification techniques have been developed. The first technique is based on the statistical profile (probability density function) of oxidation potential. The second method is based on an artificial neural network. The instrument, combined with a Geographical Position System (GPS) is capable of storing the geographical

position of the sample under test. Software has been developed to produce a cartographical presentation of the pollution of an area. The instrument's capability of detecting metals in multi-element solutions and in soil samples has also been examined, demonstrating good results.

Publications

Patents

- [1] K. Christidis, P.Robertson, K.Gow and P.Pollard: 'Heavy Metal Sensor: Measurement Apparatus', British Patent Application, No:0514081.9, 8 July 2005.

Peer Reviewed Journal Papers

- [1] K. Christidis, K.Gow, P.Robertson and P.Pollard: 'Intelligent Potentiostat for Identification of Heavy Metals in Situ', *Review of Scientific Instruments*, Vol. 77, 2006 .
- [2] K. Christidis, P.Robertson, K.Gow and P.Pollard: 'On-Site Monitoring and Cartographical Mapping of Heavy Metals', *Instrumentation Science and Technology*, Vol. 34, 2006.
- [3] K. Christidis, P.Robertson, K.Gow and P.Pollard: 'Acidity Compensation of Electrochemical Measurements for Monitoring of Heavy Metals', *Transactions of The Instrumentation Society and Control*, (Accepted on 6/12/05).
- [4] K. Christidis, K.Gow, P.Robertson and P.Pollard: 'Intelligent Potentiostat for Identification of Heavy Metals in Situ', *Virtual Journal of Biological Research*, Feb. (2006).
- [5] K. Christidis, K.Gow, P.Robertson and P.Pollard: 'Hand-held Voltammetric Analyser for Real-Time Monitoring of Heavy Metals', Submitted on 28/9/05 to: *IEEE Transactions on Instrumentation and Measurements*.
- [6] K. Christidis, K.Gow, P.Robertson and P.Pollard: 'Computer-Based Identification of Heavy Metal Contaminants in Real-Time Using Anodic Stripping Voltammetry', Submitted on 26/1/06 to: *Environmental Modelling and Software*.
- [7] K. Christidis, K.Gow, P.Robertson and P.Pollard: 'Analysis of Soil samples in Situ', Submitted on 21/2/06 to: *Review of Scientific Instruments*.

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- [1] K. Christidis, P.Robertson, K.Gow and P.Pollard, "Electrochemical Hand-held Instrument for Measuring of Heavy Metals in Situ", *Best SET Britain*, House of Commons, 13 March 2006, London, UK.
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Conference on Electroanalysis, ESEAC 2004, National University of Ireland, Galway, Ireland.

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List of Key Symbols

T_D	deposition time of the excitation signal
ΔI	differential current
E_p	oxidation potential
R_D	digital-to-analogue converter resolution
R_G	signal generator resolution
V_{DACF}	signal generator full-scale output voltage
V_P	excitation signal start potential
V_F	excitation signal final potential
V_S	step potential
P_A	pulse amplitude
P_P	pulse period
P_D	pulse duration
$\Delta\phi_w$	voltage potential across the working electrode-solution interface
$\Delta\phi_r$	voltage potential across the reference electrode-solution interface
I_{FS}	potentiostat full-scale output current
R_f	feedback resistor
V_{OS}	offset voltage
I_B	bias current
V_{DAFS}	data acquisition system full-scale voltage
R_P	potentiostat resolution
$p(f)$	probability density function of f
σ	standard deviation
μ	mean value
I_P	peak current
E_P'	normalised oxidation potential (neural network input)
I_P'	normalised peak current (neural network input)
R_{ON}	ON resistance of the analogue multiplexer
min_{E_P}	the minimum input value of E_P used for the training of the neural network
min_{I_P}	the minimum input value of I_P used for the training of the neural network
max_{E_P}	the maximum input value of E_P used for the training of the neural network
max_{I_P}	the maximum input value of I_P used for the training of the neural network

$bias_{Nn}$	bias value of n^{th} neuron
N_{ni}	input of n^{th} neuron
N_{no}	output of n^{th} neuron
w_{jk}	weight of k^{th} neuron of j^{th} layer
O_{ni}	input of n^{th} neuron of output layer
O_{no}	output of n^{th} neuron of output layer
ϕ	longitude
λ	latitude
h	altitude
$\Delta\phi$	longitude offset (from base pixel)
$\Delta\lambda$	latitude offset (from base pixel)
$\Delta x'$	longitude offset (from base pixel) converted into metres
$\Delta y'$	latitude offset (from base pixel) converted into metres
$P(x,y)$	pixel in the raster
P_B	base pixel
P_{ID}	pixel's identification number
A_M	physical size of a map
A_V	virtual size of a map
R_{xy}	virtual size of a pixel

Chapter One

Introduction

1.1. Threats Posed by Heavy Metals

The presence of heavy metals in land and natural water systems has in some instances caused significant ecosystem degradation because of their toxicity to human and other biological life[1-3]. The pathways for heavy metal introduction into soil and aquatic environments are numerous[2,4-8], and include the land application of sewage sludge and municipal composts[9-11], mine wastes[12-14], dredged materials, fly ash[15,16], and atmospheric deposits[17-19]. In addition to these anthropogenic sources, heavy metals can be introduced to soils naturally as reaction products via the dissolution of metal-bearing minerals that are found in concentrated deposits[20-22]. New European Community directives, proposed in 1993, have demanded that member countries in future enforce even stricter controls on water quality, in order to protect the environment and associated biological life. Apart from the direct health or environmental problems, water or land contamination can cause economic and financial damage. The Confederation of British Industry has estimated that as much as 200,000 hectares of land is contaminated in the UK and remediation of these areas could cost up to £20 billion.

The necessity of monitoring pollutant levels at various points in industrial and recycling processes, in natural water, and at agricultural, urban and industrial sites is highly important[23].

1.2 Present Techniques for Detecting Heavy Metals

At present a great deal of highly trained personnel are employed by different companies and organisations in the assessment of different polluted areas. Usually this process requires a large number of sample collection and dedicated laboratories[24]. Among the most popular methods used for the analysis[25] of aquatic or soil samples are atomic absorption spectrometry (AAS)[26-28], inductively coupled plasma-atomic emission spectrometry (ICP-AES)[29], X-ray fluorescence (XRF)[30-33], liquid chromatography mass-spectrometry (LC-MS)[34], energy dispersive analysis (EDAX)[35,36] and electroanalysis[37,38]. The instruments used for the analysis are expensive bench-top units (Fig. 1.1) and require trained personnel to perform the analysis and to interpret the results[24,39]. These analytical systems are too bulky to be used in the field[40,41]. In a number of applications, the long time delays associated with this process are unacceptable. In addition, the majority of samples are typically negative, yet are subjected to costly laboratory analysis[42].

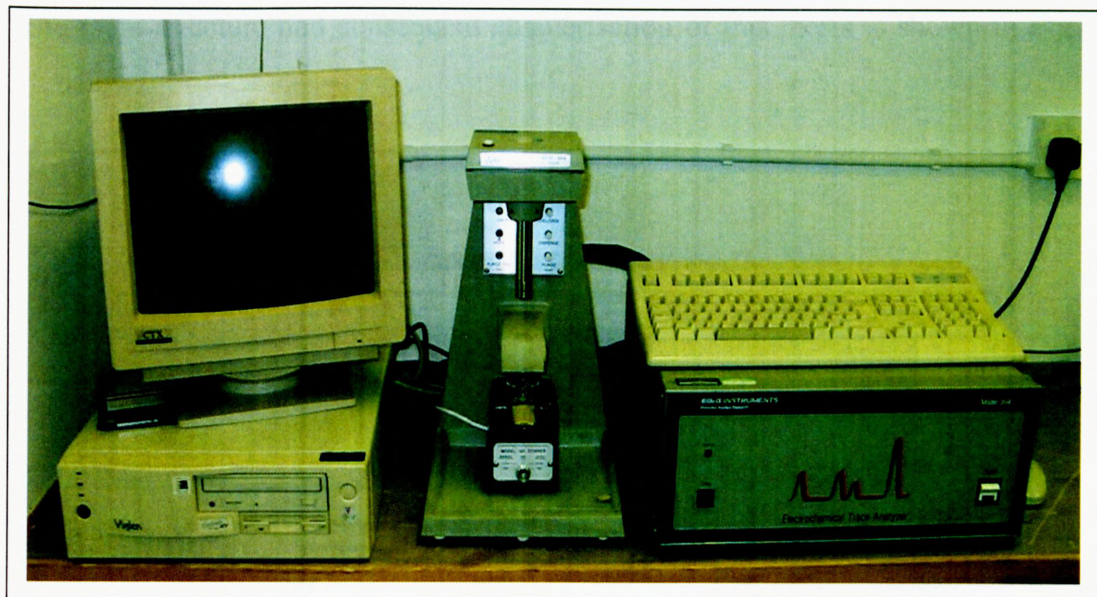


Figure 1.1: Electroanalytical instrument for analysis of heavy metals

In summary, existing detection techniques are generally complicated to use, expensive, and time consuming. An inexpensive portable (hand-held) instrument capable of direct monitoring of heavy metal contaminants in the field, which can stand alone without the need of a computer, is consequently very desirable.

1.3 New Hand-Held Electrochemical Instrument

This report describes the development of an electrochemical instrument capable of gathering real-time quantitative data on a range of heavy metal contaminants. The unit is being developed for use on the site of contaminated land or water and is also able to determine the oxidation state of a metal, which is a measure of the metal's toxicity. This was the main task of this project which involved research into the following three main aspects, namely:

1. The development of a portable electrochemical instrumentation for detection of heavy metals in situ.
2. The formulation of an appropriate classification strategy for the characterisation of heavy metals in situ.
3. Cartographical mapping of the pollution

The main structure and consequent chapterisation of this thesis is shown in Fig. 1.2 below.

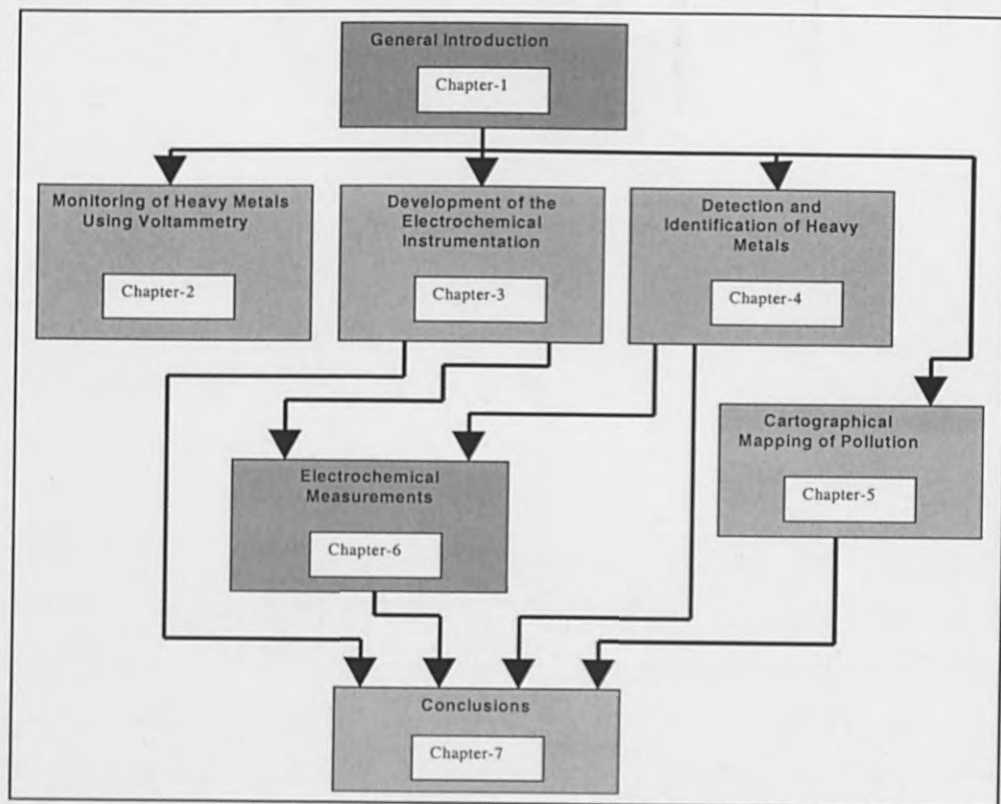


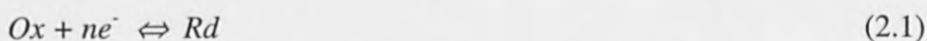
Figure 1.2: Structure of the thesis.

Chapter Two

Monitoring of Heavy Metals Using Electroanalytical Methods

2.1. Introduction

Analytical voltammetry has recently become a very important technique for metal analysis[43,44]. Ions in a solution can be measured by introducing a time-dependent potential between submerged working and reference electrodes and then measuring the current which flows through the working electrode. This current is the sum of Faradaic and non-Faradaic (background) components. The latter is the current of interest, which is the result of Redox reactions at the electrode surface:



Where, “Ox” are the oxidised species and “Rd” are the reduced species.

Electrons either leave the electrode by reducing some oxidised species or enter the electrode by oxidising reduced species. The total Faradaic current that flows through the working electrode will therefore indicate the total rate of all such reactions occurring at the surface.

There are two main categories of voltammetric techniques, namely, potential sweep and pulse voltammetry. Potential sweep techniques consist of scanning a chosen region of potential and measuring the current response arising from the electron transfer and associated reaction. Two of the most popular potential sweep techniques used in analytical applications are cyclic voltammetry (CV)[45-47] and anodic linear-scan stripping voltammetry (ALSV)[48]. Pulse techniques are based on the

application of a succession of potential steps of varying height and in forward or reverse directions. These techniques were developed largely to provide enhanced sensitivity in analytical applications as compared to potential sweep voltammetry[49-51]. Some of the most popular pulse techniques are normal pulse voltammetry (NPV)[47,51], differential pulse anodic stripping voltammetry (DPASV)[49] and square wave voltammetry (SWV)[53].

Of the different voltammetric techniques that might have been used in the development of the portable electrochemical instrument, DPASV was chosen in preference to other techniques. DPASV is a precise electrochemical method for heavy metal detection[54,55] which delivers extremely low detection limits, owing to an extremely favourable Faradaic-to-charging current ratio. Furthermore, this technique is ideally suited for this task because of its inherent simplicity and compatibility with digital microcomputer-based instruments[56].

2.2 Differential Pulse Anodic Stripping Voltammetry

The DPASV technique is a two-step process (Fig. 2.1). The first step is a fixed time pre-concentration stage (deposition), where metal ions in solution are reduced by electrolysis at a suitable applied potential to form an amalgam with the working electrode.

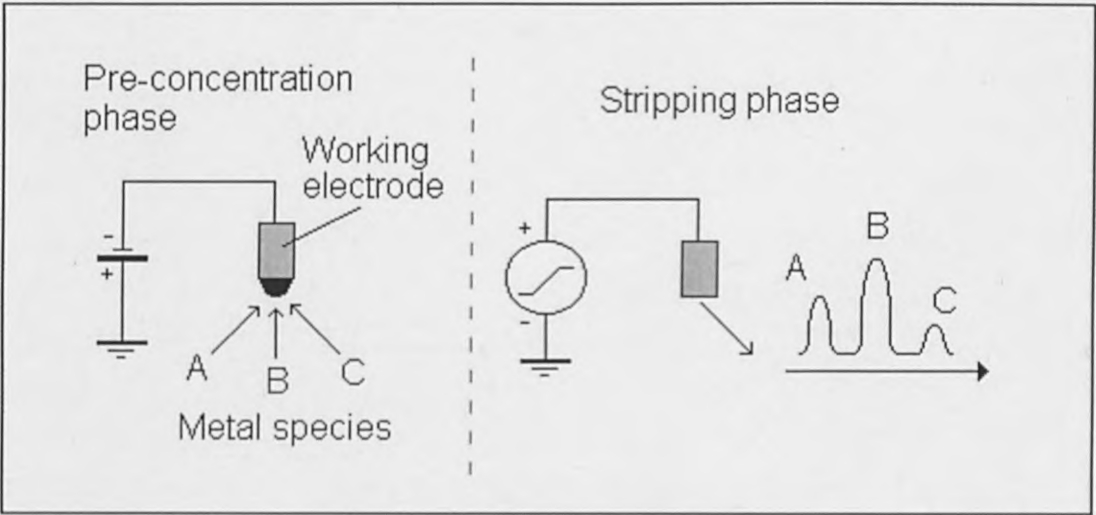


Figure 2.1: Two stages (phases) of differential pulse anodic stripping voltammetry

The second stage is a stripping stage, in which the metal is oxidised back into solution by means of a time-controlled excitation waveform imposed between the working and the counter electrode. The excitation signal consists of small pulses of constant amplitude superimposed upon a staircase waveform (Fig. 2.2).

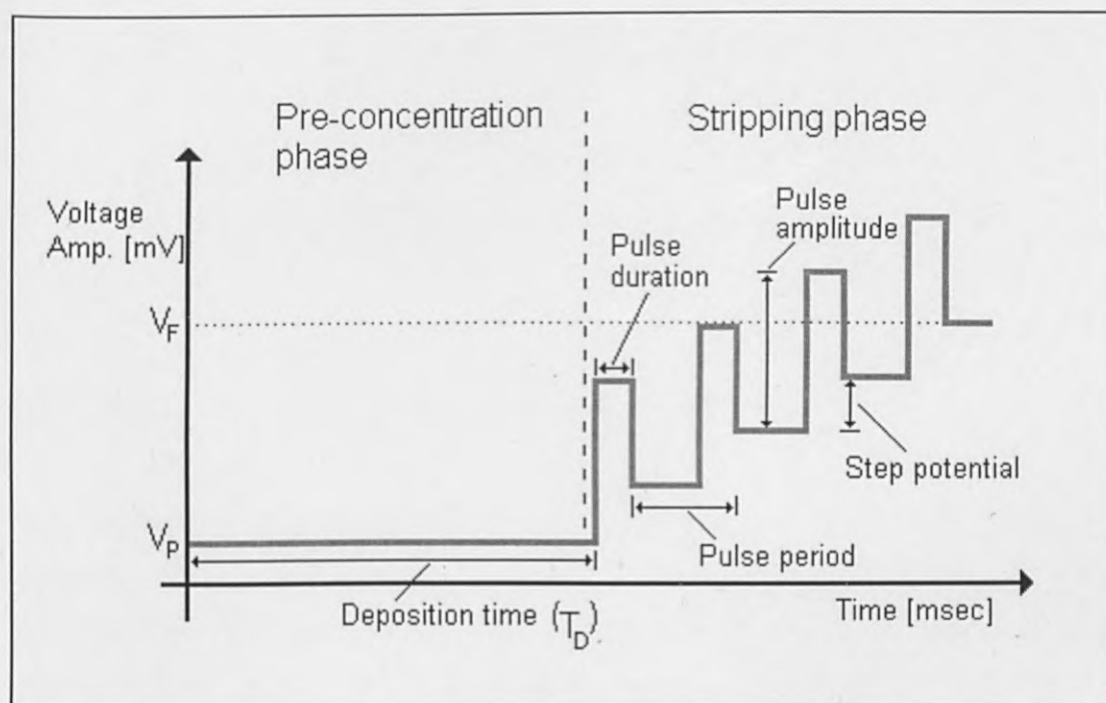


Figure 2.2: Differential pulse anodic stripping voltammetry - excitation signal

The current is sampled twice in each pulse period (once before the potential step, and then again just at the end of the pulse). The difference between these two current samples ($s_{2i} - s_{1i} = \Delta I$) is recorded and displayed (Fig. 2.3). This process is repeated for all of the signal pulses. As the potential approaches the lowest oxidation potential of those metals dissolved onto the electrode surface, the ions of that metal pass into solution from the electrode. The current increases rapidly and reaches a maximum value when the potential has a value corresponding to the metal's oxidation potential. As the anodic potential rises, other peaks will be observed at the oxidation potentials of the other metals which are present in the sample.

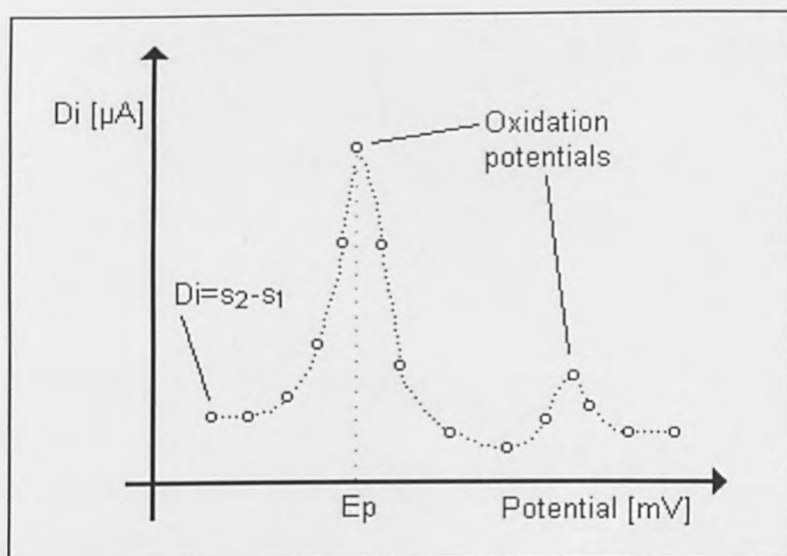


Figure 2.3: Voltammogram – Differential current versus potential

2.3 Sensors

The electrochemical sensor (cell) is a circuit element with electrical properties that influence the performance of the overall instrument[57]. It consists of three electrodes: the working electrode (WE), the counter electrode (CE) and a reference electrode (RE). The WE is the interface of interest and ideally, measurements would be limited to changes of this interface alone. The CE is used as an electrode from which current will pass to the WE. The RE is a non-polarisable interface that is used to measure/control the potential of the WE.

Traditional voltammetric methods involve the use of mercury based electrodes, usually in the form of a hanging mercury drop electrode (HMDE)[40,52,58], static mercury drop electrode (SMDE)[51,59] or more recently the mercury film electrode (MFEs)[60,61]. The extensive use of these electrodes is based on the advantageous analytical properties of mercury in the negative potential range[62]. However, HMDE and SMDE electrode systems have a large size due to their associated heavy motors and large mercury reservoirs[40,63]. They require careful cleaning, prolonged oxygen removal, solution stirring during the deposition, standard additions and frequent solution replacement[63]. Apart from the large size and high cost, an important disadvantage of all mercury electrodes is the use of toxic mercury[64]. The

considerable toxicity of mercury has led some countries to ban its use completely and, as a result, alternative electrode materials are sought for use in stripping analysis[65,66]. For the present application, glassy carbon[67,68] and screen printed[64,69] solid electrodes were chosen in preference to HMDE, SMDE and MFEs.

2.3.1 Electrochemical Cell with Glassy Carbon Electrode

This cell consists of three solid electrodes (Fig. 2.4). The working electrode is glassy carbon, the counter electrode is platinum and the reference electrode silver/silver chloride (3 M *NaCl*). These electrodes are commercially available and have been provided by Bioanalytical Systems Inc., (BAS) Indiana.

The working electrode is made of a carbon wire embedded in glass within a plastic rod. The sensitive portion of the electrode is a tiny circle of glassy material with surface area of 7.1mm^2 in the centre of the electrode rod. Despite its very small surface area, this electrode is very sensitive and rugged, providing reproducible results. The reference electrode is a simple system comprising of a silver wire in silver chloride solution within a glass rod. This electrode is always kept wet, usually in 3 M *NaCl* solution. The counter electrode is simply a platinum wire attached to a plastic rod with a soldered gold connector.

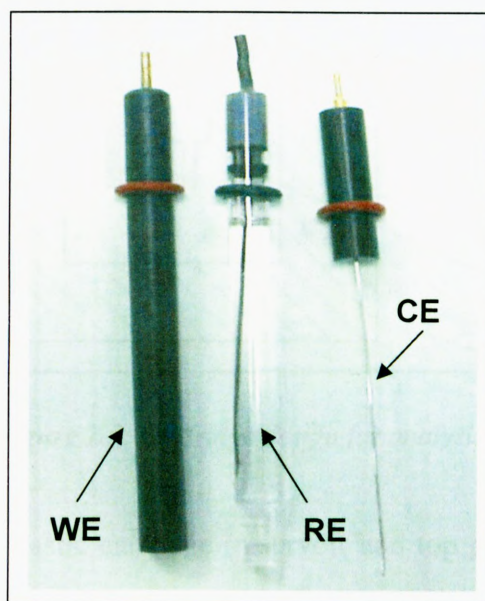


Figure 2.4: Three electrode cell with glassy carbon working electrode, platinum counter electrode and silver/silver chloride reference electrode.

A plastic cartridge has been designed (Fig. 2.5) to support the three electrodes for use in the field. The cartridge consists of two main parts. The top part provides the mechanical support to the electrodes and the second part (base) is the sample reservoir. The reservoir has been designed to accommodate either soil or aquatic samples.

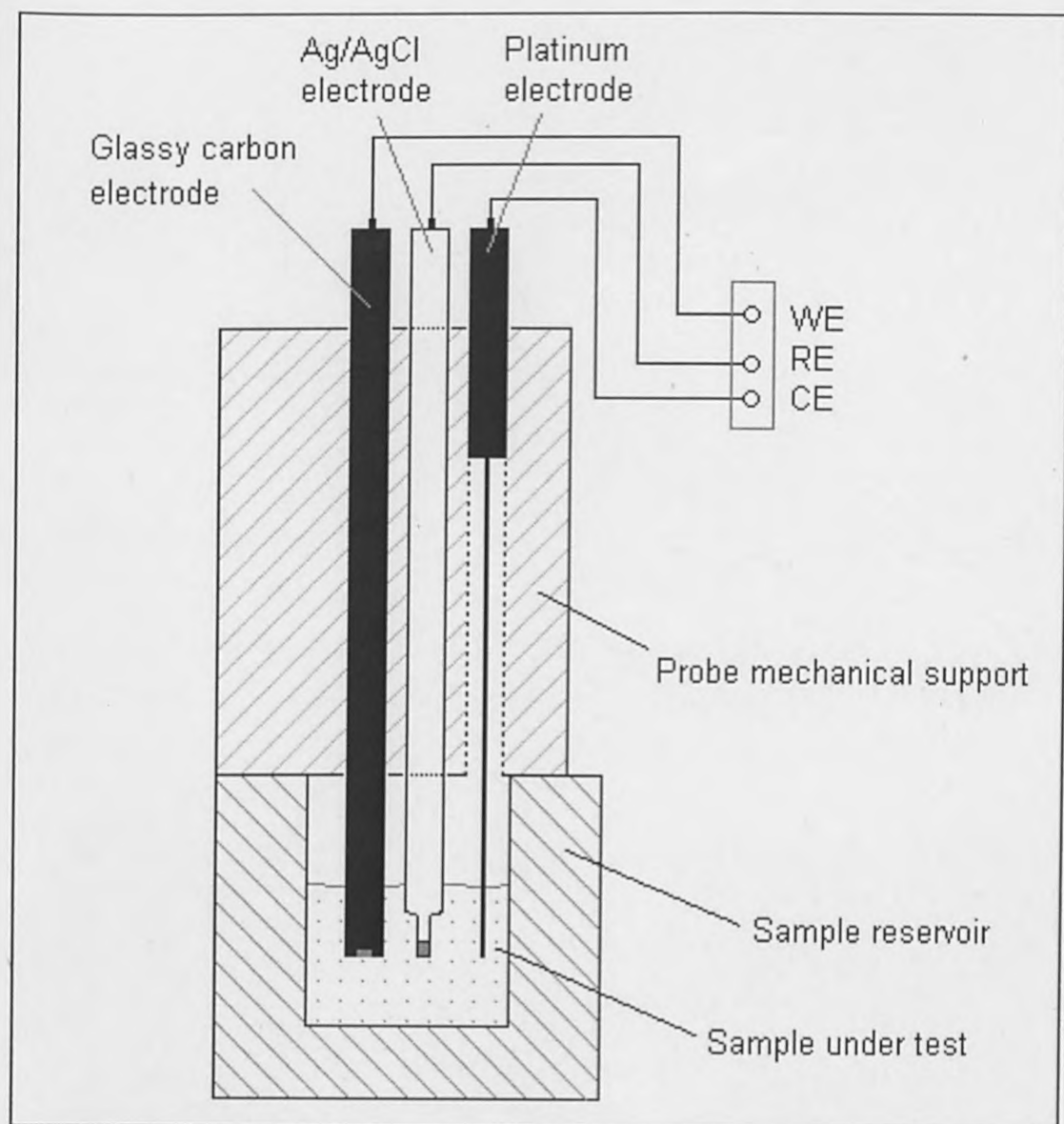
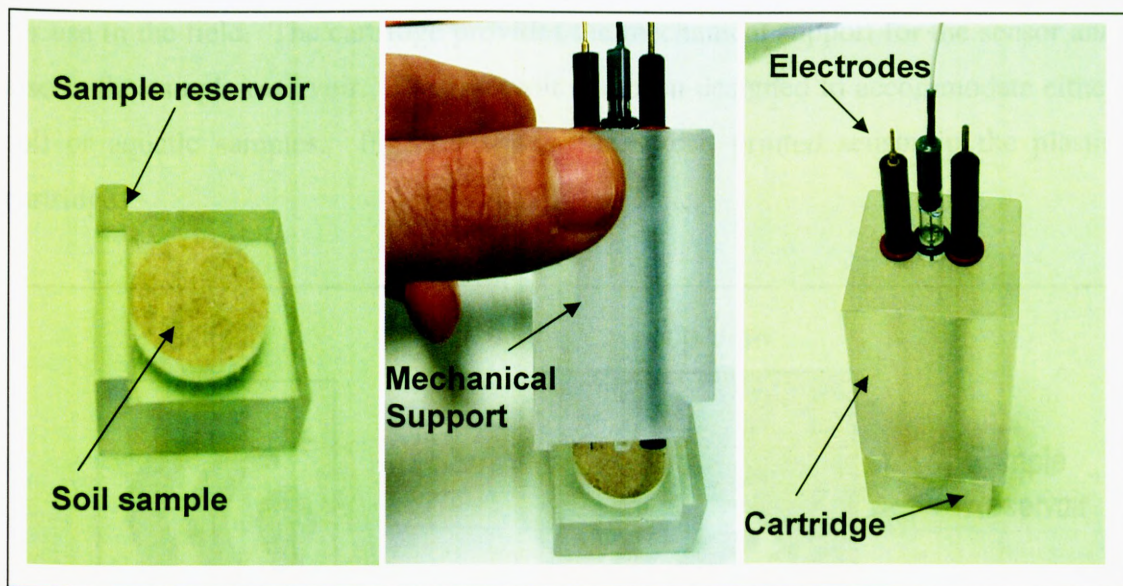


Figure 2.5: Cartridge design for analysis in the field

Fig. 2.6 shows the plastic cartridge (reservoir and top part) with the three electrodes and a soil test sample.



(a)

(b)

(c)

Figure 2.6: (a) sample reservoir with sample under test, (b) mechanical support, (c) plastic cartridge with the three electrodes ready for analysis

2.3.2 Screen Printed Sensor

The three electrodes of the screen printed cell are made with specially manufactured carbon inks and are printed on ceramic plates (Fig. 2.7). These cells are inexpensive, disposable and easy to store as they have no need for special storage conditions.

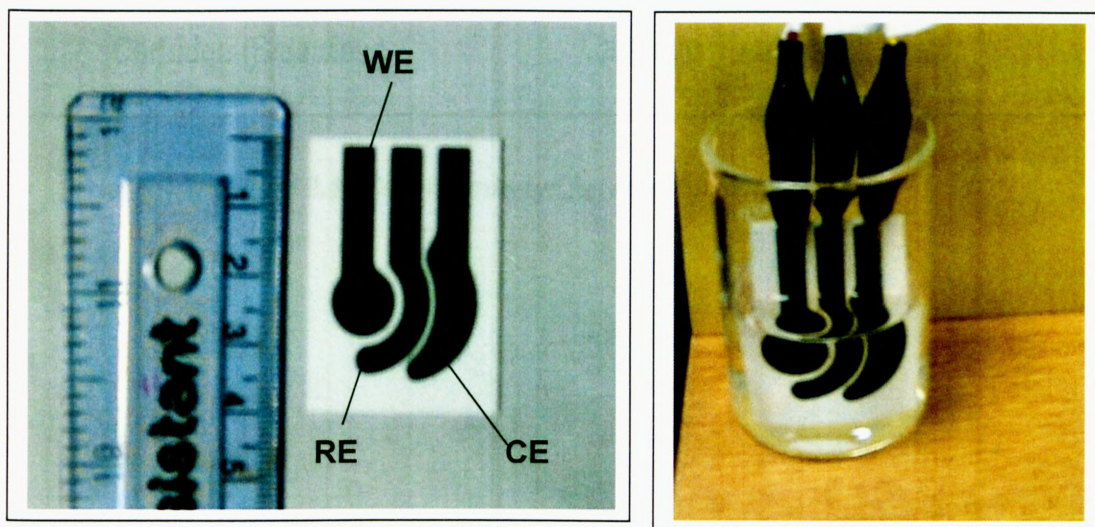


Figure 2.7: Screen printed carbon sensor

A plastic cartridge has been designed (Fig. 2.8) to support the screen printed sensor for use in the field. The cartridge provides the mechanical support for the sensor and also is the sample reservoir. The reservoir has been designed to accommodate either soil or aquatic samples. Fig. 2.9 shows the screen printed sensor in the plastic cartridge.

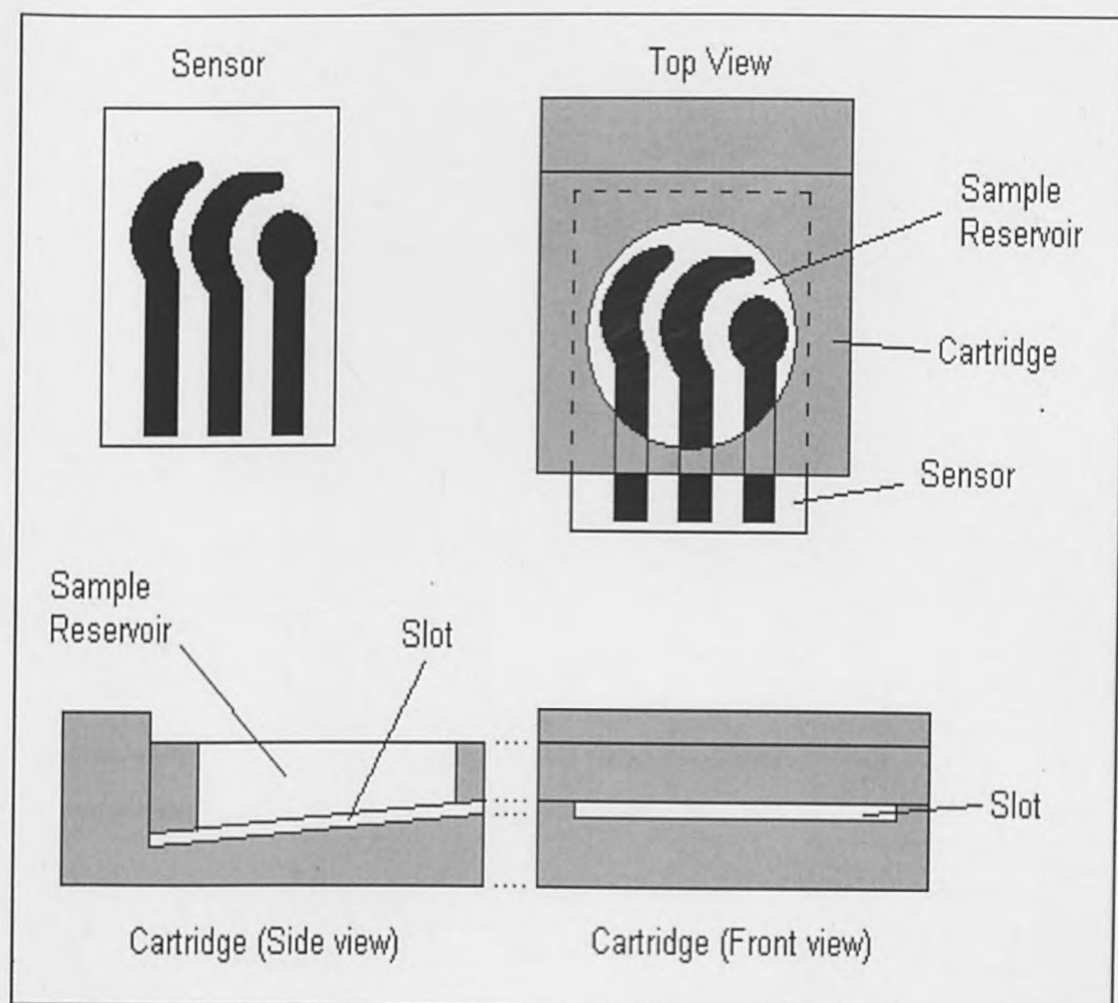


Figure 2.8: Cartridge design for screen printed sensor

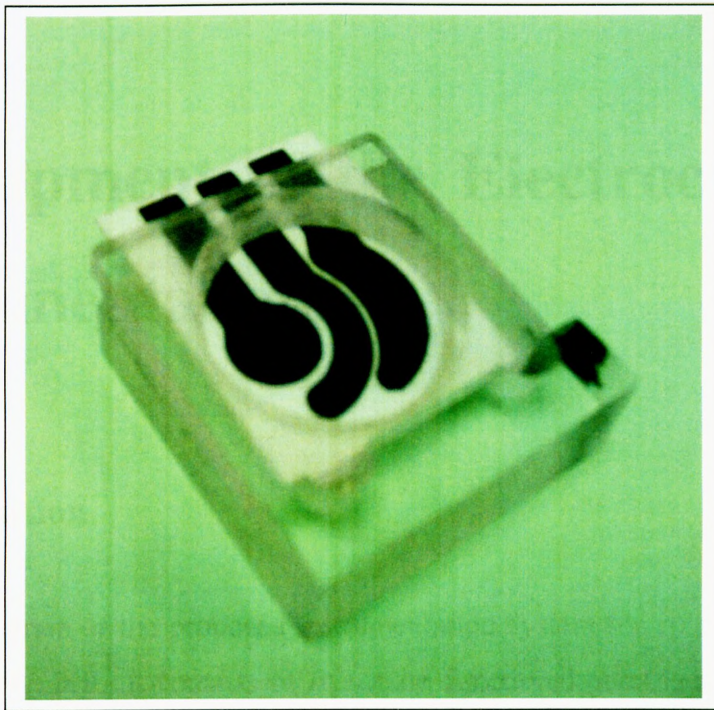


Figure 2.9: Plastic cartridge with the screen printed sensor

Chapter Three

Development of the Electrochemical Instrumentation

3.1 Introduction

The block diagram of the proposed instrumentation system for voltammetric analysis is shown in Fig. 3.1. It consists of five main functional parts, a signal generator, a potentiostat, a data acquisition unit, a microcontroller and a display unit.

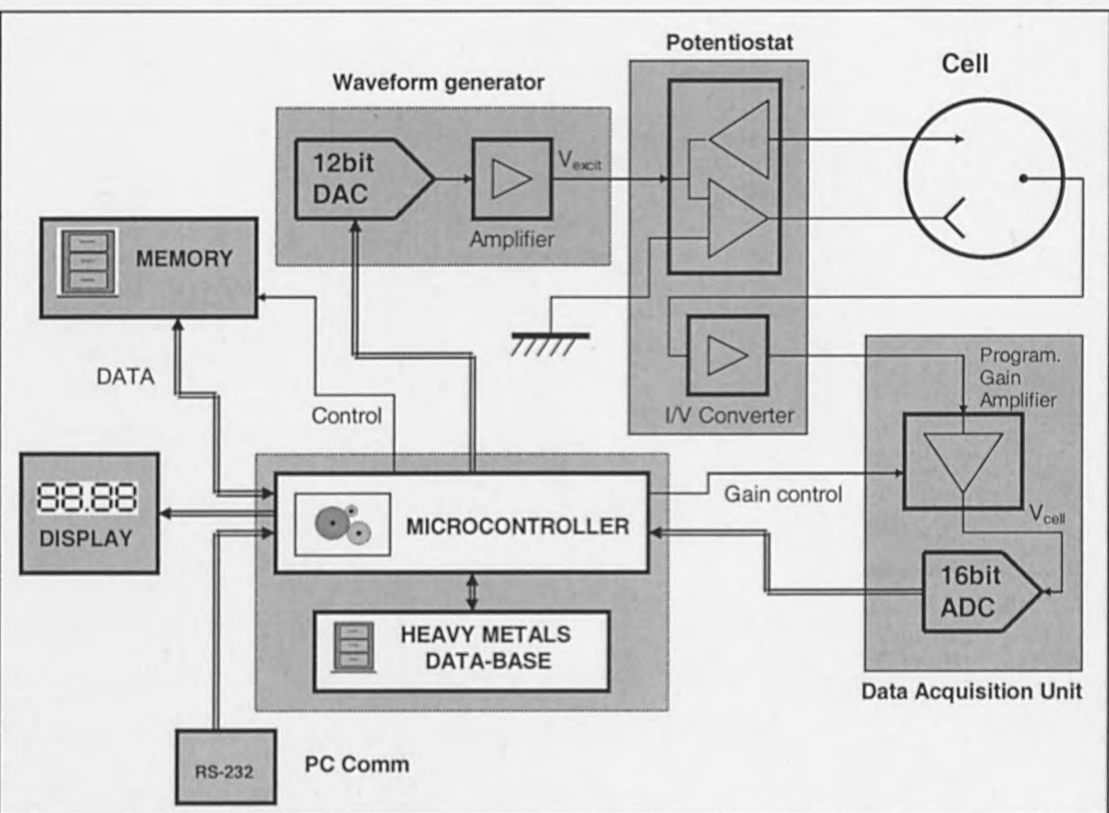


Figure 3.1: Block diagram of the electrochemical instrumentation system

More detailed examination of the design, construction, and operation of each functional part is given in the following sections.

3.2 Signal Generator

The signal generator provides the appropriate potential waveform (DPASV-excitation signal) for the cell. Fig.3.2 illustrates the circuitry of the signal generator. The heart of the system is a 16-bit microcontroller (MC68HCS12) which produces (synthesises) the excitation signal. With the use of the microcontroller (μC) the signal generator becomes very flexible. All of the parameters of the signal can be re-programmed and a complex waveform can be generated very easily. The signal is generated by the μC in digital form and is then converted to analogue form using a digital to analogue converter (DAC). The resolution of the DAC (R_D) is 12 bit.

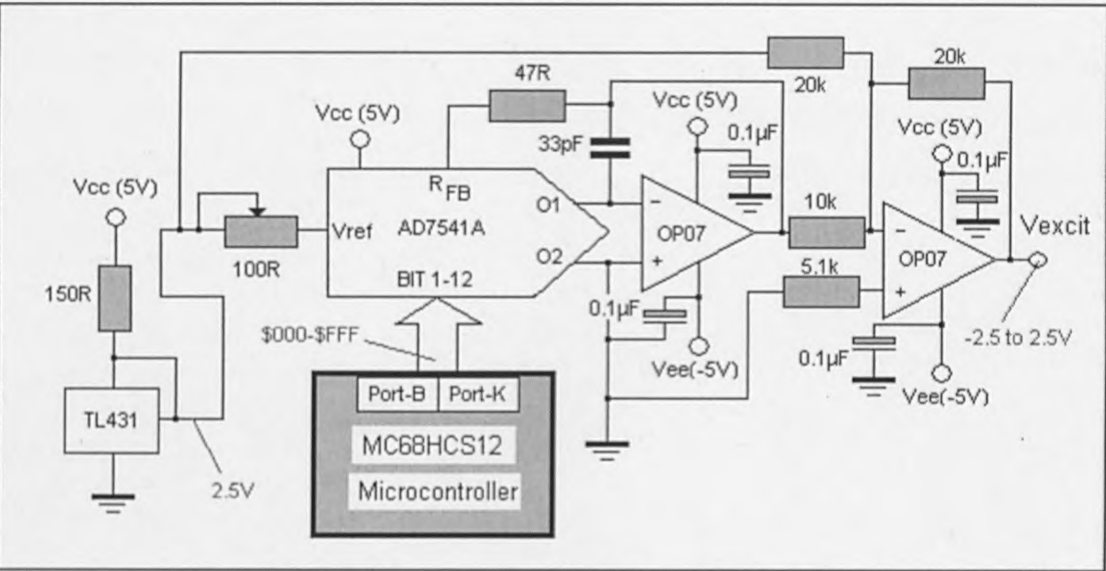


Figure 3.2: Circuitry and of the signal generator

The reference voltage (V_{ref}) which is needed to define the DAC full scale (V_{DACF}) is 2.5V, which is provided by a programmable precision reference device (TL431). Table 3.1 shows the code relationship of the DAC operation.

Table 3.1: DAC operation ($V_{ref} = 2.5\text{ V}$).

Binary Number in DAC	Analogue Output
1111 1111 1111	$V_{ref} \times (4096/2) = +2.5\text{ V}$
1000 0000 0000	$V_{ref} \times 0 = 0\text{ V}$
0000 0000 0000	$-V_{ref} \times (4096/2) = -2.5\text{ V}$

Full-scale trimming can be accomplished by adjusting the value of $20\text{ k}\Omega$ feedback resistor of the second operational amplifier. The 33 pF capacitor is used for phase compensation in order to provide stability. The generator resolution (R_G) is given by:

$$R_G = \frac{V_{DACF}}{2^{(R_D)}} = \frac{5V}{2^{12}} = 1.22\text{ mV} \tag{3.1}$$

Where, V_{DACF} is the full scale voltage and R_D the resolution of the DAC.

Table 3.2 shows the connection between the pins of the microcontroller ports (Port-PB and Port-PK of the evaluation T-board) and the AD7541A DAC device. Datasheets with all technical information of the DAC (AD7541A), operational amplifier (OP07), and programmable reference voltage device (TL431) are given in Appendices D1, D2 and D3 respectively.

Table 3.2: Connection between microcontroller pins and DAC device.

Microcontroller		AD7541A - DAC	
PORT	T-Board Pin	Signal	Pin
PB(0)	H1-24	D(0)LSB	15
PB(1)	H1-25	D(1)	14
PB(2)	H1-26	D(2)	13
PB(3)	H1-27	D(3)	12
PB(4)	H1-28	D(4)	11
PB(5)	H2-01	D(5)	10
PB(6)	H2-02	D(6)	09
PB(7)	H2-03	D(7)	08
PK(0)	H1-08	D(8)	07
PK(1)	H1-07	D(9)	06
PK(2)	H1-06	D(10)	05
PK(3)	H1-05	D(11)MSB	04

The assembly program developed to produce the ASVDP excitation signal with deposition time (T_D) of 60 sec, starting potential (V_P) -1100 mV, last potential (V_F) +500 mV, step potential (V_S) 2 mV, pulse amplitude (P_A) 25 mV, pulse period (P_P) 100 ms and pulse duration (P_D) 50 ms, is listed in Appendix B.1. The flow chart of this program is shown in Fig. 3.3 below.

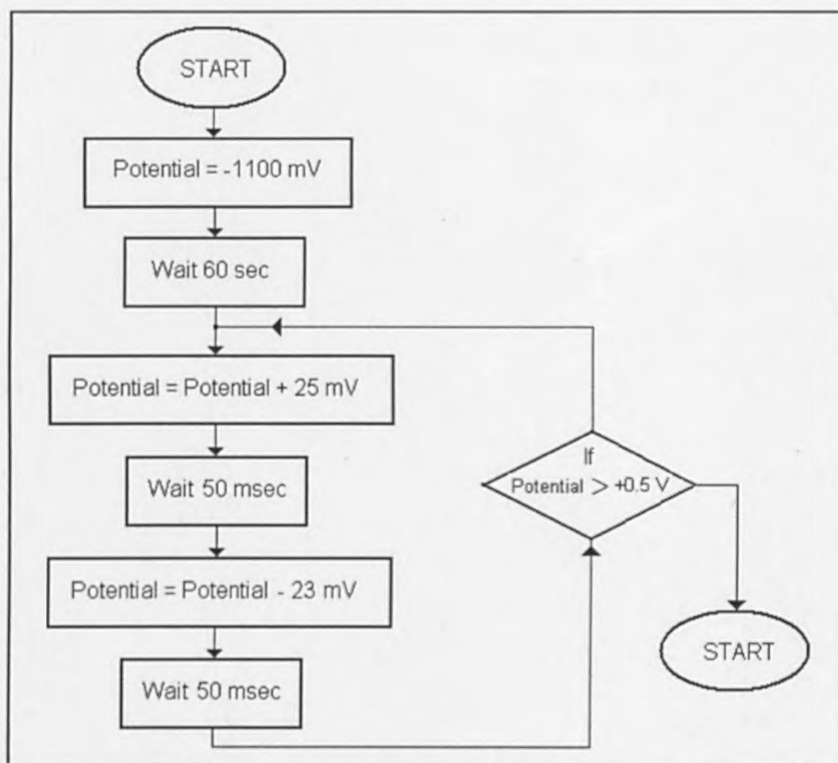


Figure 3.3: Flow chart of signal generator program

3.3 Potentiostat

In a potentiostat, the potential of the working electrode (vs RE) is controlled and the current flowing through the cell (via the CE) is measured. Fig. 3.4(a) shows the basic circuit for the three electrode potential control. As can be seen from this figure, E is the applied potential measured between RE and WE. I is the resulting current measured in WE. The CE allows current to flow through the cell. The RE maintains constant interfacial potential difference regardless of the current. It is also used to monitor the potential difference[70] to control $\Delta\phi_w$ relative to its own $\Delta\phi_r$ [71-73] [see Fig. 3.4(b)]. The resistor R_2 is the sum of resistance of the counter electrode separator and the solution resistance between the counter and the reference electrodes. The

resistor R_3 , is the sum of resistance of the measuring electrode and the solution resistance between the reference and measuring electrodes[74,75]. The resistance R_2 is also referred to the literature as the uncompensated cell resistance (R_{un}). The use of the feedback control [Fig. 3.4(a)] is to compare $\Delta\phi_r$ with E . If there is a difference (error) the potential is adjusted until balance (no error) is achieved [76,77].

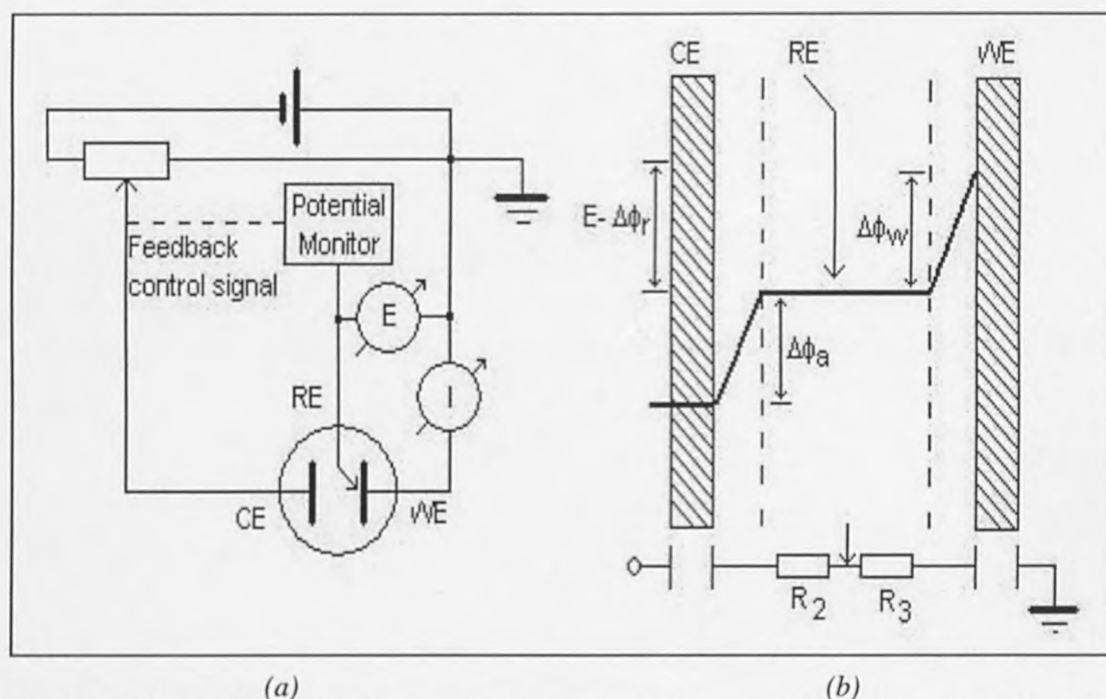


Figure 3.4: (a) Basic circuit for the three electrode potential control, (b) schematic representation of potential gradients.

The potentiostat operation is as follows: The potentiometer [Fig.3.4(a)] is adjusted to a value to initiate reaction at WE. The potential at which reaction ensues (E with respect to RE) is monitored with the voltmeter. The current through the cell will decrease, as the reactive species is consumed at WE. This current decrease will cause E to increase. Monitoring the increase of E on the voltmeter, the potentiometer is adjusted to decrease the voltage applied to the CE until $E' = E$. The desired control point and actual control point are now very close. Fig. 3.5 shows a basic potentiostat circuit, that can be used for controlling the potential on the WE, implemented by using an operational amplifier[78-80].

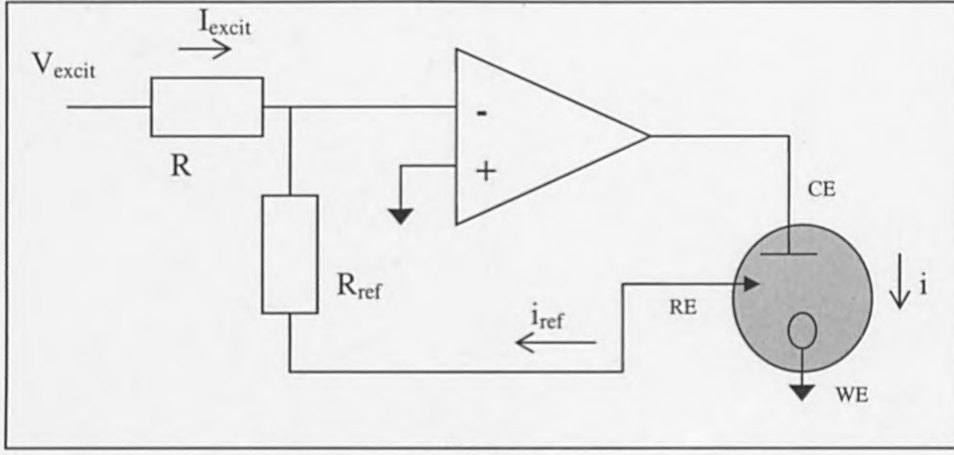


Figure 3.5: Basic circuitry of potentiostat

The virtual ground at the inverting input forces all currents to be zero at this point, therefore:

$$-i_{ref} = i_{excit} \quad \text{and} \quad -e_{ref} = e_{excit} \left(\frac{R_{ref}}{R_1} \right) \quad (3.2)$$

This simple arrangement has two drawbacks:

- The need to measure the current flowing into the WE
- The flow of current in RE is excessive

These are remedied using a current follower, and a voltage follower respectively[81], as shown in Fig. 3.6. The voltages e_f and V_{cell} are available for connection (to a data acquisition system, where:

$$e_f = -V_{excit} \quad \text{and} \quad V_{cell} = -iR_f \quad (3.3)$$

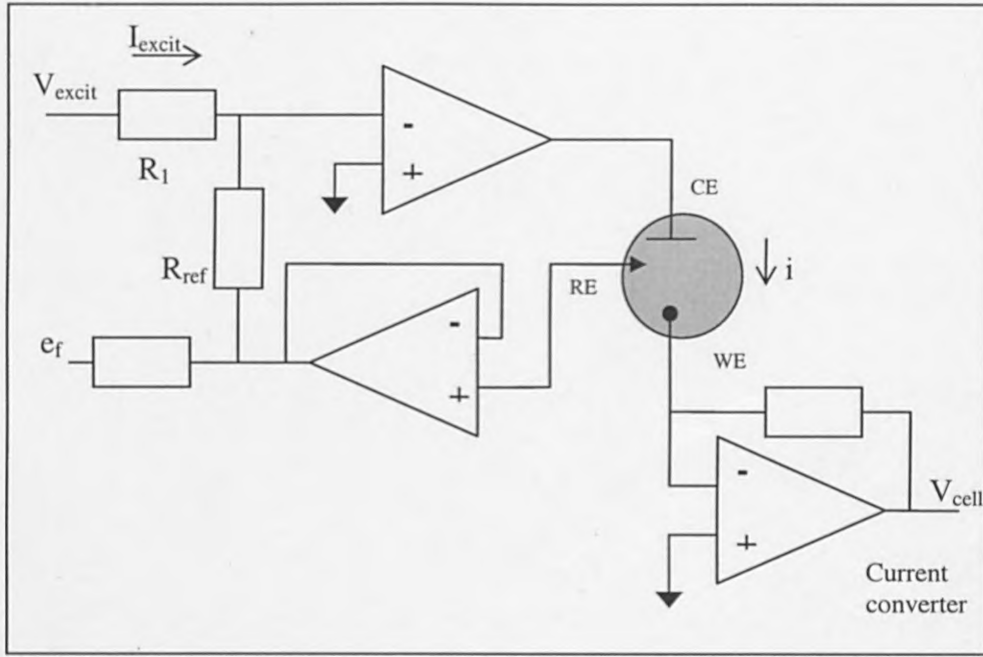


Figure 3.6: Potentiostat circuitry

Fig. 3.7 shows the complete circuit of the potentiostat designed for the system. The full scale current (I_{FS}) is $400 \mu\text{A}$ ($-200 \mu\text{A}$ to $+200 \mu\text{A}$). The current measuring stage consists of two operational amplifiers. The first op-amp is a current to voltage converter with a gain of 10×10^{-3} ($R_f = 10 \text{ k}\Omega$). The 10 nF capacitor in the feedback loop provides some low-pass filtering (time constant, $100 \mu\text{sec}$). The output of the op-amp (full scale) is given by:

$$V_{ol}(FS) = I_{FS} \cdot R_f = 400[\mu\text{A}] \cdot 10 \times 10^3 [\Omega] = 4 \text{ V } (-2 \text{ V to } +2 \text{ V}) \quad (3.4)$$

where, I_{FS} is the current full scale and R_f is the feedback resistor.

The second op-amp is a voltage amplifier with a gain of 5. The output of the op-amp (full scale) is given by:

$$V_{cell}(FS) = V_{ol}(FS) \cdot \text{Gain} = 4[\text{V}] \cdot 5 = 20 \text{ V } (-10 \text{ V to } +10 \text{ V}) \quad (3.5)$$

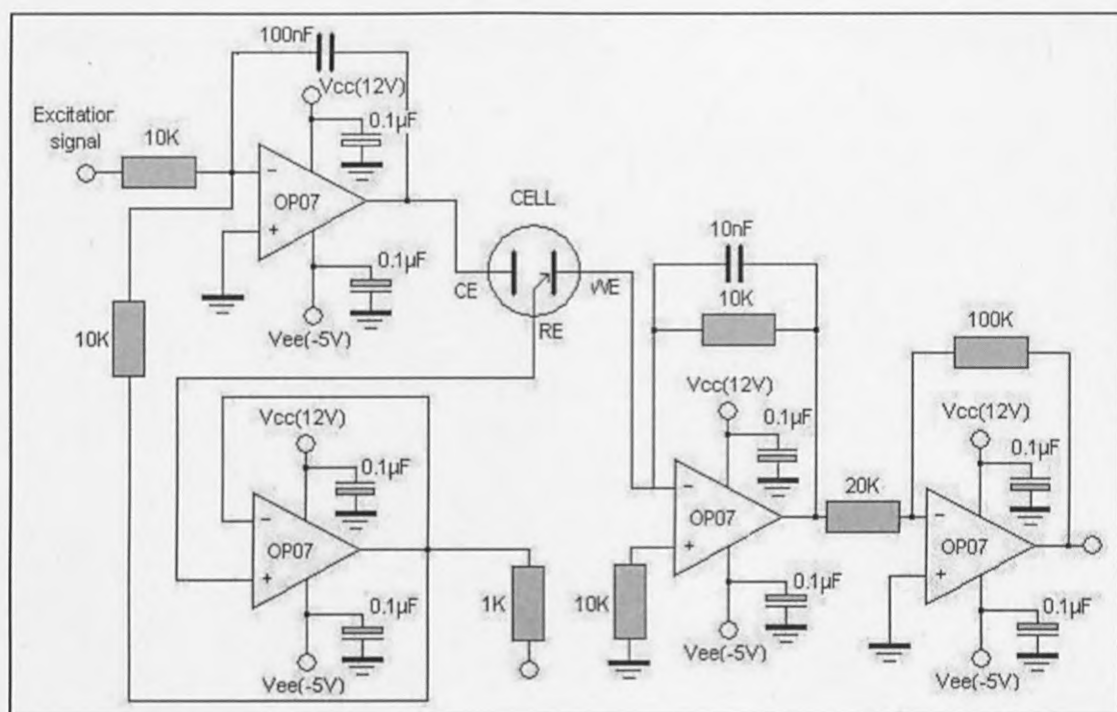


Figure 3.7: Complete circuit of the potentiostat

The specific type of the op-amps (OP07) used in the design have been chosen because of their very low offset voltage (V_{os}) and low bias current (I_B). More technical information of this device is given in Appendix D.2. In order to minimise supply noise effects all operated amplifier supply connections are decoupled[82-84] using 0.1μF ceramic capacitors.

3.3.1 Variable Gain

In the previous section it has been seen that the full scale current I_{FS} is 400 μA (-200 μA to +200 μA). For low metal concentrations the amplitude of the differential (ΔI) current is very low compared to the full-scale current; I_{FS} , of the system. Therefore, the resolution R_P of the system for measuring low concentrations of metals is poor ($R_P = I_{FS} / 2^{16}$). In order to improve the resolution R_P the I_{FS} need to be decreased. In the opposite case, for measuring high concentrations of metals, the I_{FS} of the system should be high enough to fit the large current of the chemical reaction.

In order to overcome this problem, the single current-to-voltage converter (CVC) of the potentiostat (shown on Fig. 3.7) was replaced with a CVC with variable gain (Fig. 3.8).

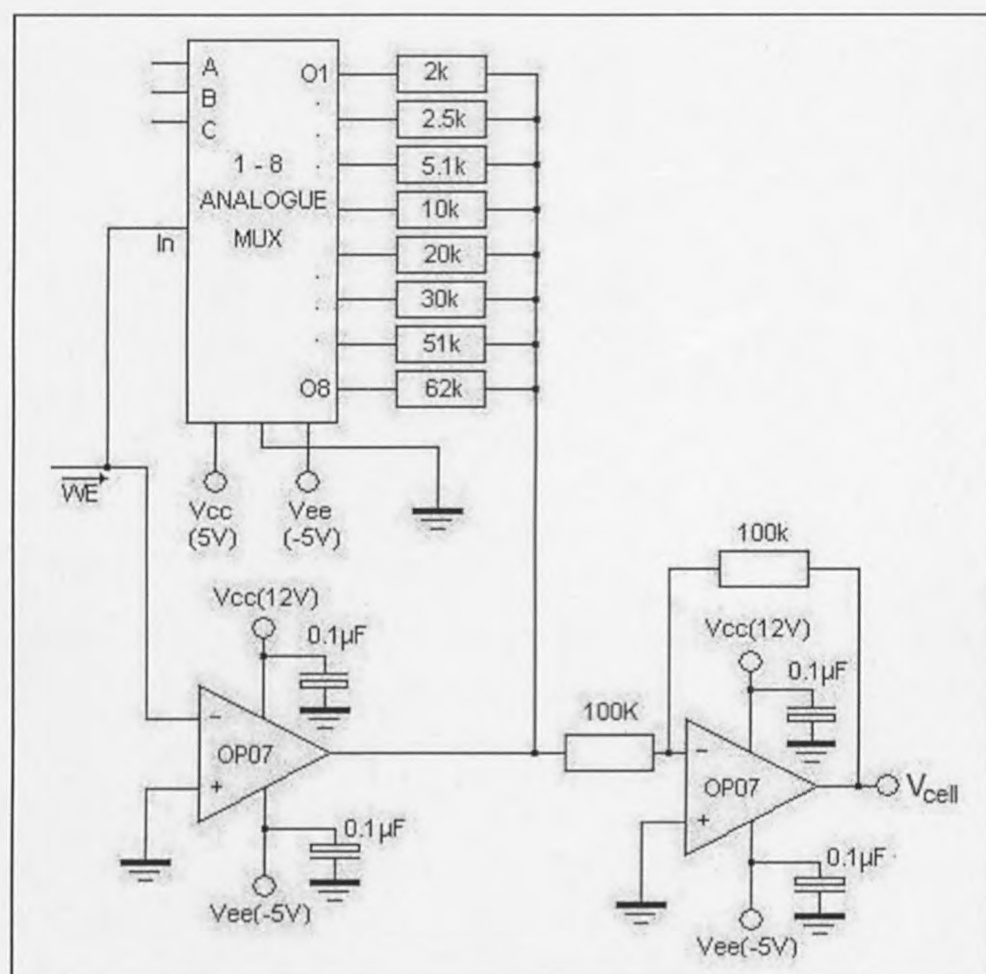


Figure 3.8: Circuit diagram of the variable gain amplifier

The gain of the CVC is determined by one of the eight different resistors connected to the output of the analogue multiplexer (4052B). The appropriate resistor (out of eight) that is used by the CVC (according to the amplitude of the measured signal) is selected by the microcontroller by controlling the analogue multiplexer. Each resistor has an associated parallel capacitor of a value chosen to preserve the 100 μ sec filter time constant of this stage. (These capacitors are omitted from Fig. 3.8 to avoid unnecessary complexity). Therefore, for high current amplitude, the microcontroller will set a low gain (decrease of I_{FS}), and for a low current it will set a high gain (increase of I_{FS}). Table 3.3 shows the different values of I_{FS} (of the system) that can be set by the microcontroller. The maximum ON resistance (R_{ON}) of the analogue multiplexer (4052B) is 240 Ω . Therefore the maximum error occurs when the first

resistor (2 kΩ) is selected which is 12%. The change of resistance is taken into account and compensated for within the software (for all resistors of the multiplexer).

Table 3.3: Different I_{FS} values as set by the microcontroller.

Resistor [k]	Full Scale [μ A]	R_P [nA]
2	\pm 5000	152.6
2.5	\pm 4000	122.1
5.1	\pm 1961	61.0
10	\pm 1000	30.5
20	\pm 500	15.3
30	\pm 333	10.2
51	\pm 196	6.1
62	\pm 161	4.9

Fig. 3.9 shows the algorithm for the selection of the appropriate gain of the variable gain CVC by the microcontroller. The assembly program developed for the automatic gain control is listed in Appendix B.3. Technical information of the 4052B analogue multiplexer is given in Appendix D.4.

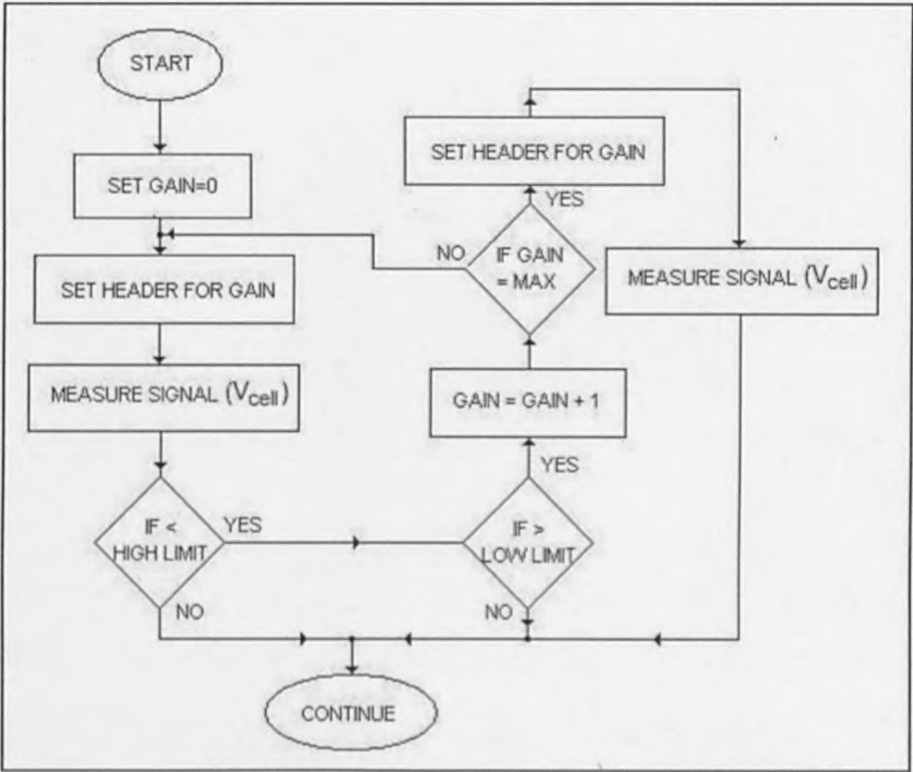


Figure 3.9: flow chart for the variable gain amplifier

3.4 Data Acquisition

In data acquisition, the electrochemical response, (current) is recorded at fixed time intervals by digitising it with an analogue to digital converter (ADC). Fig. 3.10 illustrates the circuitry of the data acquisition sub-system. For the signal conversion a 16-bit ADC device is used (LTC1605). The input to the ADC (output voltage from potentiostat current measuring stage) produces a 16-bit binary number each time a conversion is triggered. These numbers are stored in the microcontroller memory. The ADC operation is controlled by the microcontroller.

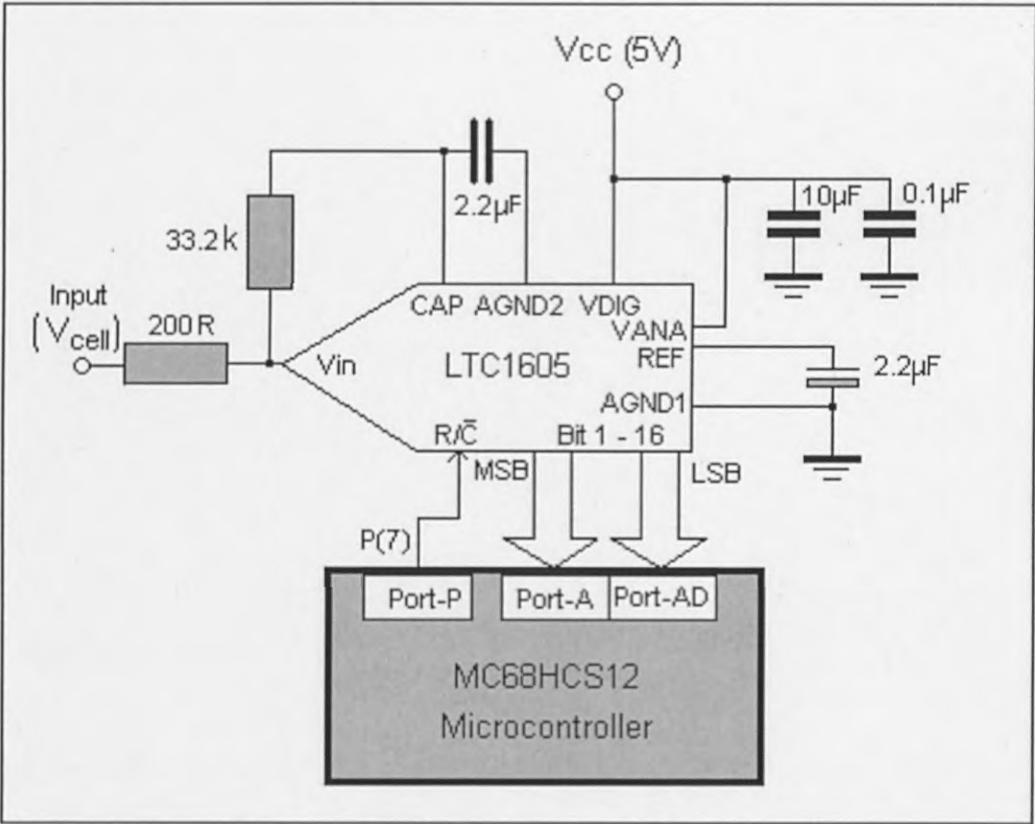


Figure 3.10: Circuitry for data acquisition

The ADC uses an internal reference voltage of 2.5 V. The full-scale range (V_{DAFS}) is equal to ($\pm 4 \times V_{ref} = \pm 10$ V). Conversion start is controlled by the R/\bar{C} input. A falling edge on R/\bar{C} puts the internal sample-and-hold into the hold the state and starts a conversion. A rising edge on R/\bar{C} enables the output data bits. Table 3.4

shows the connection between the pin of the microcontroller ports (Port-PAD1, Port-PA AND Port –PP) of the evaluation T-board) and the LTC1605 ADC device.

Timing diagrams for the ADC operation and more technical information for the device are given in Appendix D.5. The assembly program developed for the ADC operation is listed in Appendix B.2.

Table 3.4: Connection between microcontroller pins and ADC device.

Microcontroller		LTC1605 - ADC	
PORT	T-Board Pin	Signal	Pin
PAD1(0)	H3-12	D0(LSB)	22
PAD1(1)	H3-14	D1	21
PAD1(2)	H3-16	D2	20
PAD1(3)	H3-18	D3	19
PAD1(4)	H3-20	D4	18
PAD1(5)	H3-22	D5	17
PAD1(6)	H3-24	D6	16
PAD1(7)	H3-26	D7	15
PA(0)	H3-01	D8	13
PA(1)	H3-02	D9	12
PA(2)	H3-03	D10	11
PA(3)	H3-04	D11	10
PA(4)	H3-05	D12	09
PA(5)	H3-06	D13	08
PA(6)	H3-07	D14	07
PA(7)	H3-08	D15(MSB)	06
PP(7)	H4-25	R/C	24

3.5 Keypad Input

A keypad with three push buttons is used as an input to the microcontroller (Fig. 3.11). The ENTER button (key) is used to execute a command, or to start a specific process. The RIGHT and LEFT keys are used to increase/decrease the value of a parameter or to move to the next or previous command/operation. The switch bounce problem[85,86] was avoided with the addition of 10 msec delay, as shown in Fig. 3.11(b).

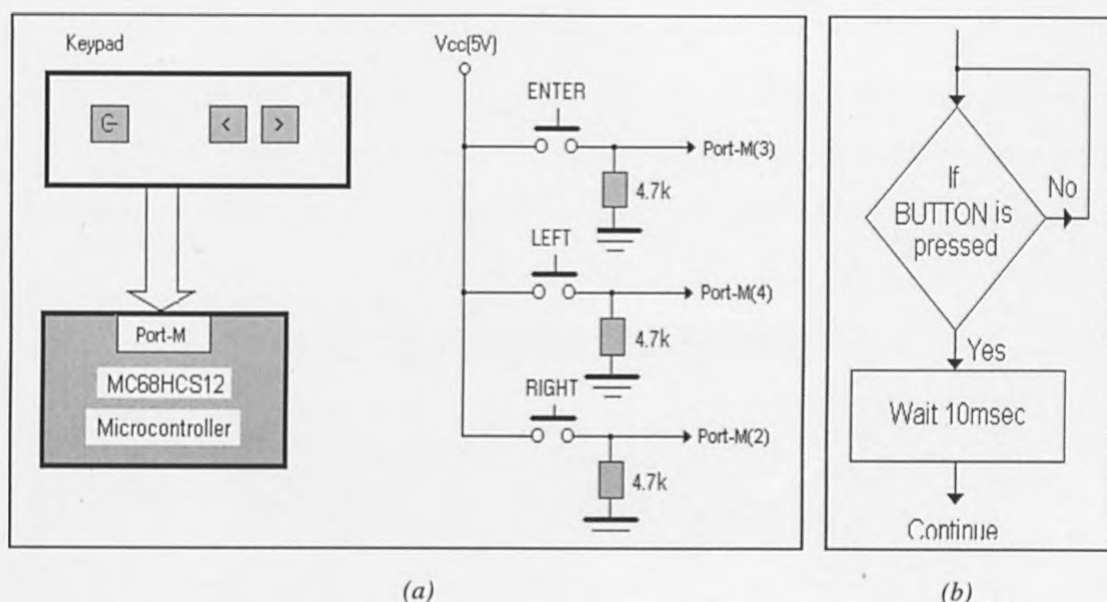


Figure 3.11(a): keypad input, (b)Timing strategy to counter switch bounce

Table 3.5 shows the connection between the pins of the microcontroller port (Port-M of the evaluation T-board) and the key pad board.

Table 3.5: Connection between microcontroller pin-outs and key pad board.

Microcontroller		Key pad
PORT	T-Board Pin	
PM(2)	H4-19	Right
PM(4)	H4-17	Left
PM(3)	H4-18	Enter

3.6 Display Output

Two types of display have been used with the instrument, a simple alphanumerical display and a graphic Liquid Crystal Display (LCD). More detailed examination of the design and operation of the two displays is given in the following sections.

3.6.1 Alphanumerical Display

An LCD (TRIMODS 1543) of 2 x 20 characters (2 lines, 20 characters/line) is used to inform the user of the different stages of the process. The LCD is fully controlled by the microcontroller. Fig. 3.12 shows the LCD interface with the microcontroller.

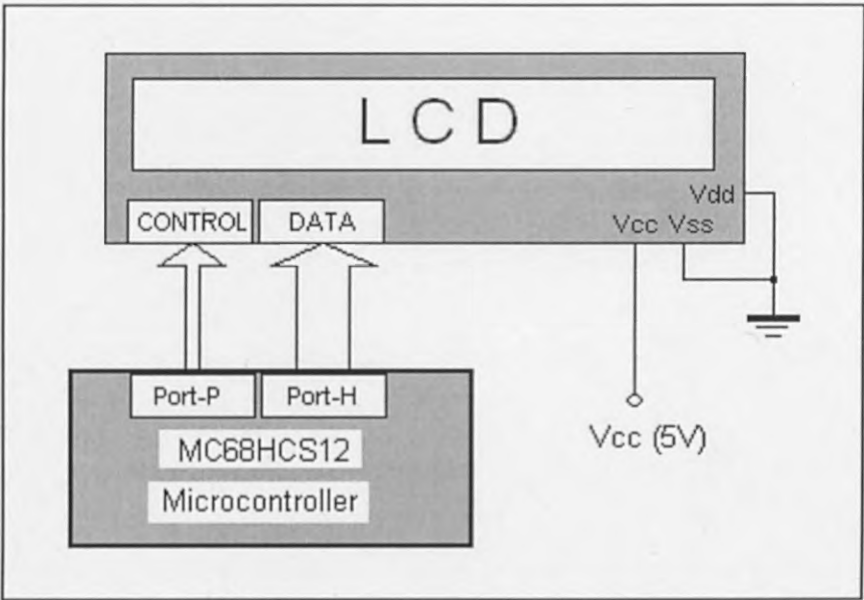


Figure 3.12: LCD interface with the microcontroller

Table 3.6 shows the connection between the pins of the microcontroller ports (Port-PH and Port-PP of the evaluation T-board) and the TRIMODS 1543 display.

Table 3.6: Connection between microcontroller pins and TRIMODS display

Microcontroller		TRIMODS 1543	
PORT	T-Board Pin	Signal	Pin
PH(0)	H2-24	Data-0	07
PH(1)	H2-23	Data-1	08
PH(2)	H2-22	Data-2	09
PH(3)	H2-21	Data-3	10
PH(4)	H2-07	Data-4	11
PH(5)	H2-06	Data-5	12
PH(6)	H2-05	Data-6	13
PH(7)	H2-04	Data-7	14
PP(2)	H1-02	RS	04
PP(4)	H4-28	R/W	06

Fig. 3.13 shows the flow chart for the initialisation of the LCD (control words and timing) to operate in 2-line increment mode, with the cursor on, and character resolution of 5x7 dots.

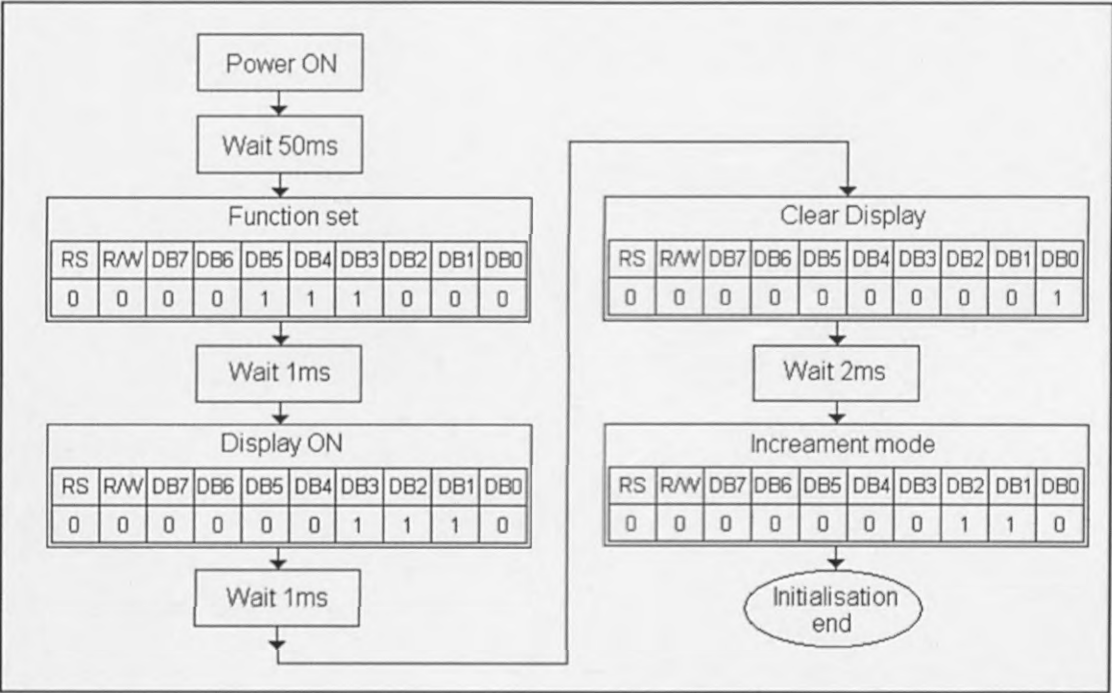


Figure 3.13: Flow chart for LCD initialisation

For displaying a character on the display, the “RS” control signal should be set to logic high and the “R/W” should be set to logic low. After 1 μsec, the data byte corresponding to the character to be displayed is sent to the display in ASCII format while the enable signal (E) is ‘high’. The minimum time for displaying consecutive characters should be at least 500 nsec. Therefore, after sending a character byte to the display there is always 1 μsec delay before sent the next character is sent. This process is described by the flow chart of Fig. 3.14.

A datasheet with all technical information relating to the TRIMODS 1543 LCD is given in Appendix D.6. The assembly program developed for the operation of the LCD is given in Appendix B.5.

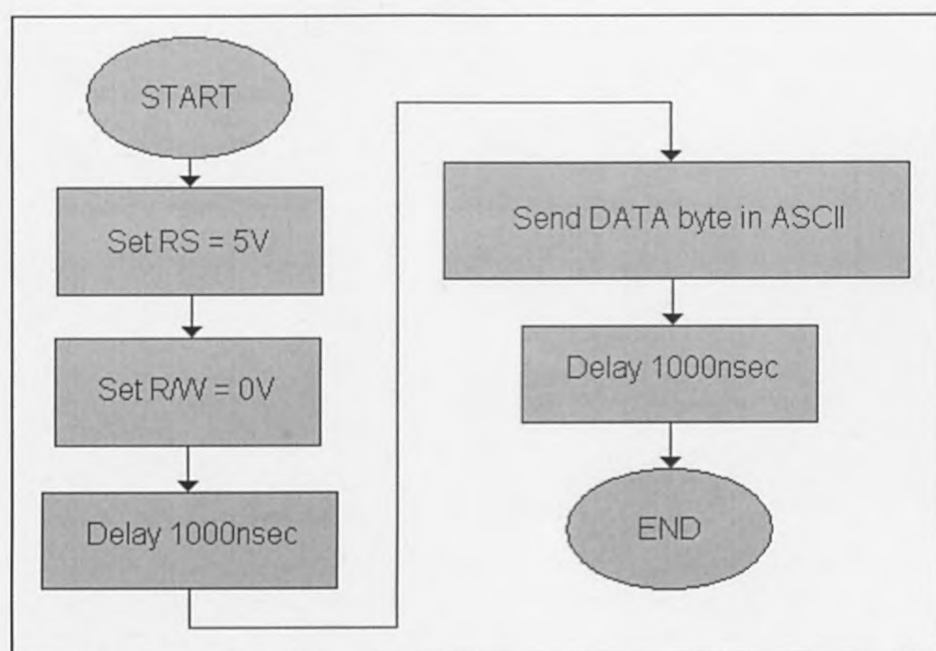


Figure 3.14: Flow chart for displaying a character on the display

3.6.2 Graphic Display

A Graphic liquid crystal display (POWERTIP, PG12864ERS) is used to inform the user of the different stages of the process. The advantages of using a graphic display are as follows:

- It allows the display of graphics and animations for user friendly operation
- It allows the display of the voltammogram in real time (for verification of correct operation)

The display adds flexibility to the system since the user can see the different commands/operations and can change the value of a parameter using a MENU-based operation. The GLCD (64 x 128 pixels with 8 Kbyte video RAM) is fully controlled by the microcontroller. Fig. 3.15 shows the GLCD interface with the microcontroller. Table 3.7 shows the connection between the pins of the microcontroller ports (Port-PH and Port-PP of the evaluation T-board) and the POWERTIP (PG12864ERS) display.

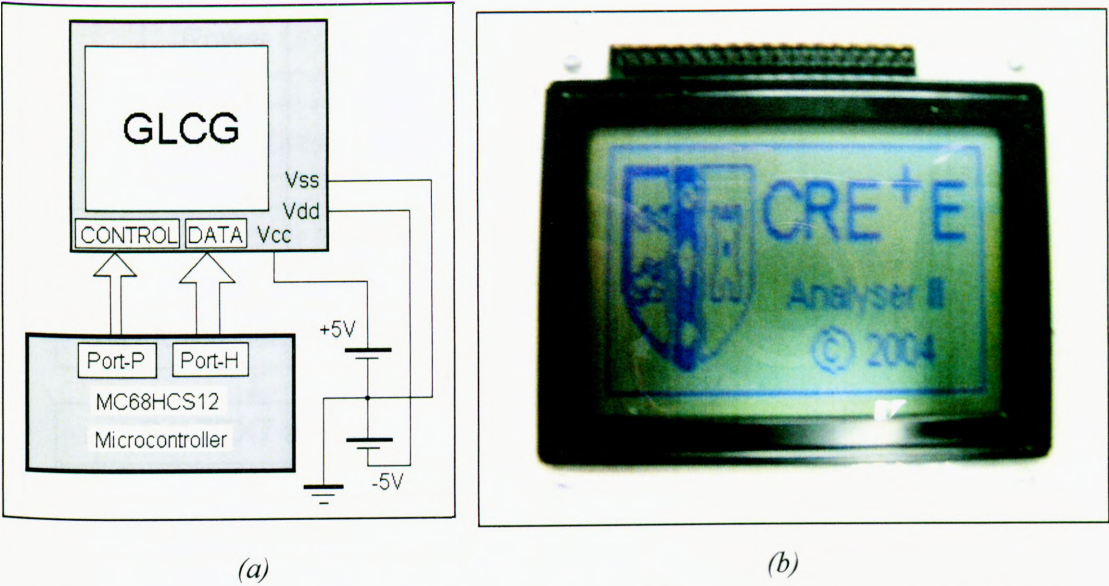


Figure 3.15: (a) GLCD interface with the microcontroller, (b) GLCD graphic output

Table 3.7: Connection between microcontroller pins and graphic display.

Microcontroller		PG 12864ERS	
PORT	T-Board Pin	Signal	Pin
PH(0)	H2-24	Data-0 (LSB)	10
PH(1)	H2-23	Data-1	11
PH(2)	H2-22	Data-2	12
PH(3)	H2-21	Data-3	13
PH(4)	H2-07	Data-4	14
PH(5)	H2-06	Data-5	15
PH(6)	H2-05	Data-6	16
PH(7)	H2-04	Data-7 (MSB)	17
PP(1)	H1-03	/WR	05
PP(2)	H1-02	/RD	06
PP(3)	H1-01	/CE	07
PP(4)	H4-28	C/D	08
PP(5)	H4-27	/RST	09
PP(6)	H4-26	/FS	18

Fig. 3.16 shows the flow chart for the initialisation of the GLCD.

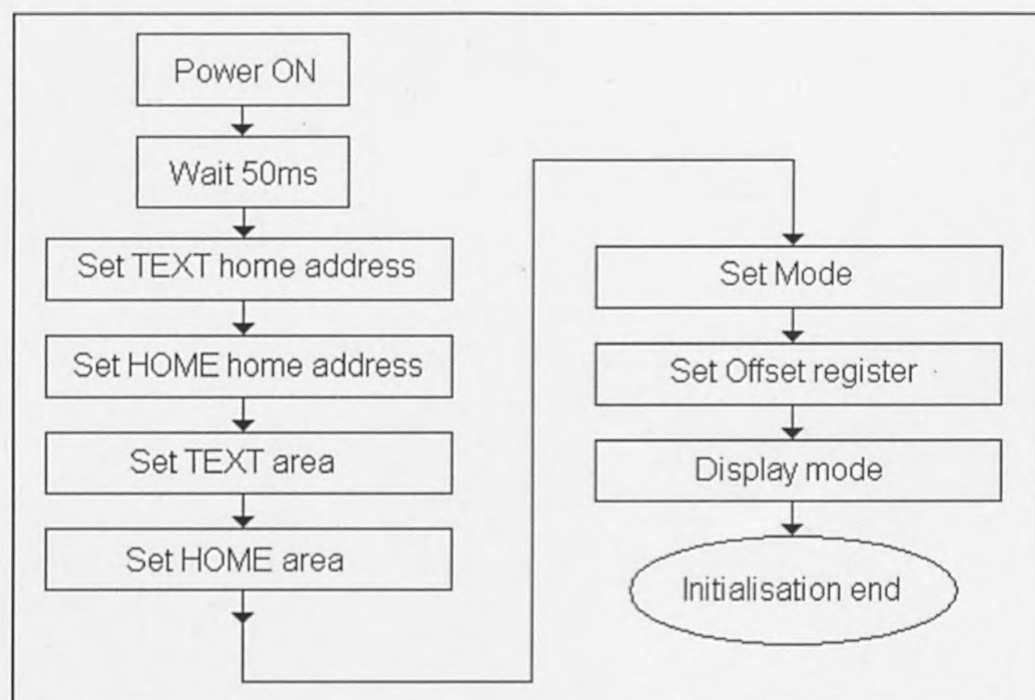


Figure 3.16: Flow chart for GLCD initialisation

The HOME address for the graphics was set to \$0000 with \$0010 area (characters per line). The TEXT address for text display was set to \$0400 with \$0010 area. The display was set to “OR” mode, with both graphics and text enabled and without cursor.

A datasheet with all technical information of the POWERTIP PG12864ERS LCD is given in Appendix D.7. The assembly program developed for the operation of the LCD is given in Appendix B.6.

3.7 External Memory Device

An external memory device of 64 Kbytes storage space has been designed in order to store the results during sample assessment. Since the average size of a sample is approximately 1 Kbyte, the memory device can store up to 60 samples. The heart of the memory device is a I²C serial EEPROM (24AA512) of 512 Kbit (64 K x 8) capacity. Fig. 3.17 shows the circuitry of the memory device.

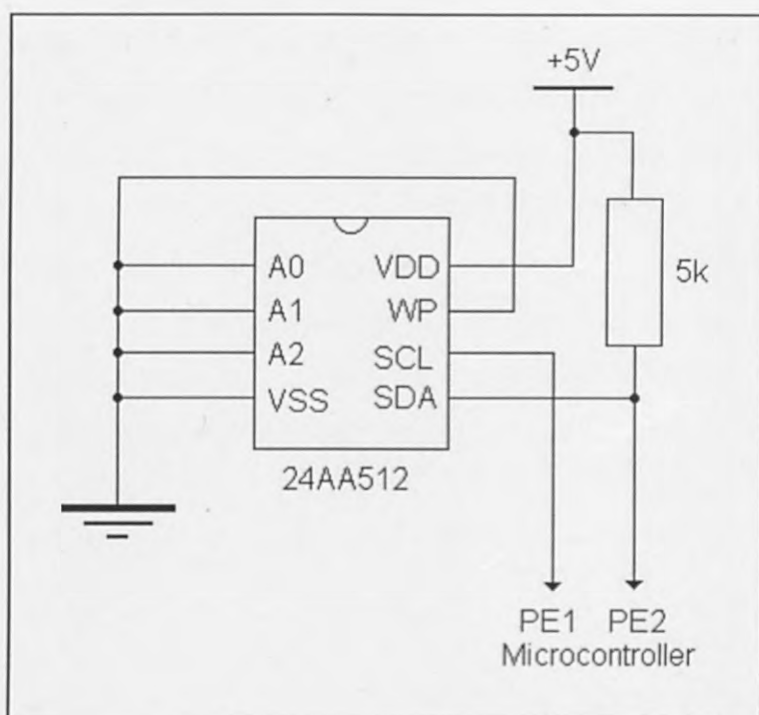


Figure 3.17: Circuitry of the external memory unit

Table 3.8 shows the connection between the pins of the microcontroller ports (Port-PJ of the evaluation T-board) and the 24AA512 serial EEPROM.

Table 3.8: Connection between microcontroller pins and serial EEPROM

Microcontroller		24AA512 - MEM	
PORT	T-Board Pin	Signal	Pin
PJ(0)	H1-22	DATA	05
PJ(1)	H1-21	CLK	06

The 24AA512 memory supports a bi-directional 2-wire bus I²C protocol. The SDA terminal is used to transfer addresses and data into and data out of the device. It is an open-drain terminal, therefore, it requires a pull-up resistor to Vcc (5 kΩ for 200 kHz operation). The bus is controlled by the microcontroller (MASTER) which generates the serial clock (SCL), controls the bus access, and generates the START and STOP conditions while the serial EEPROM works as SLAVE. Both master and slave can operate as a transmitter or receiver, but the master device determines which mode is activated.

Fig. 3.18(a) shows the appropriate data format (protocol) for transmitting a byte from the microcontroller to the serial memory device. Following the START condition, the control code (four bits), the chip-select (three bits), and R/W bit (which is a logic low) are clocked onto the bus by the master transmitter (microcontroller). This indicates to the memory that the address high (most significant) byte will follow after it has generated an acknowledge bit. The next byte is the least significant address byte. After receiving another acknowledge signal from the memory, the microcontroller will transmit the data word to be written into the addressed memory location. The memory acknowledges again and the microcontroller generates a STOP condition.

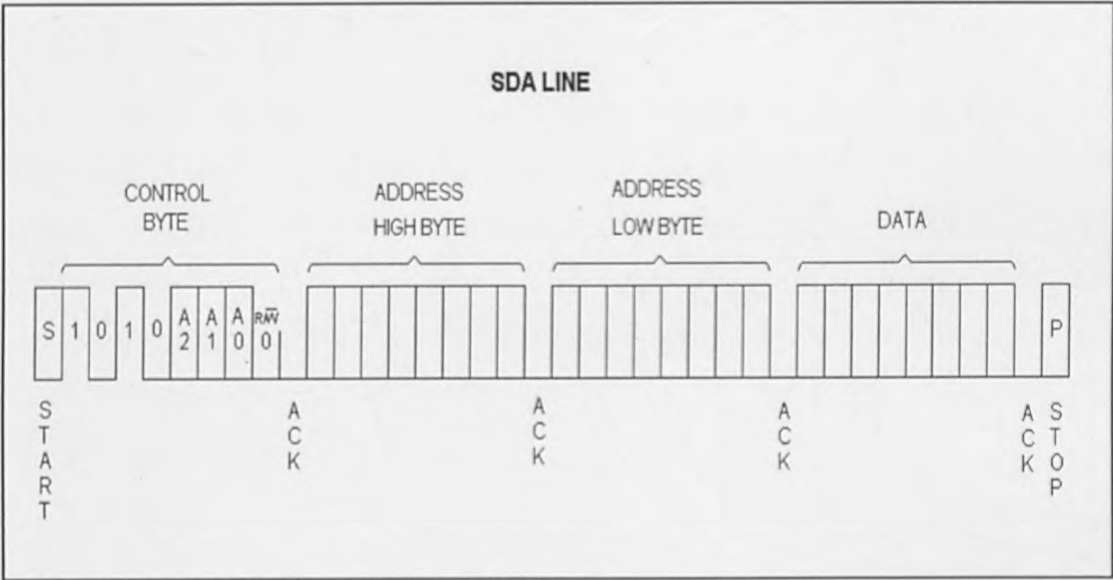


Figure 3.18: (a) Data format (protocol) for transmitting a byte from the microcontroller to the serial memory.

Fig. 3.18(b) shows the appropriate data format (protocol) for transmitting a byte from the serial memory device to the microcontroller using the Sequential Reading Mode. It also shows the selection of the memory location (address) where the reading of the data is going to start. The process of the selection of the address (most significant and least significant bytes) is exactly the same as the write operation.

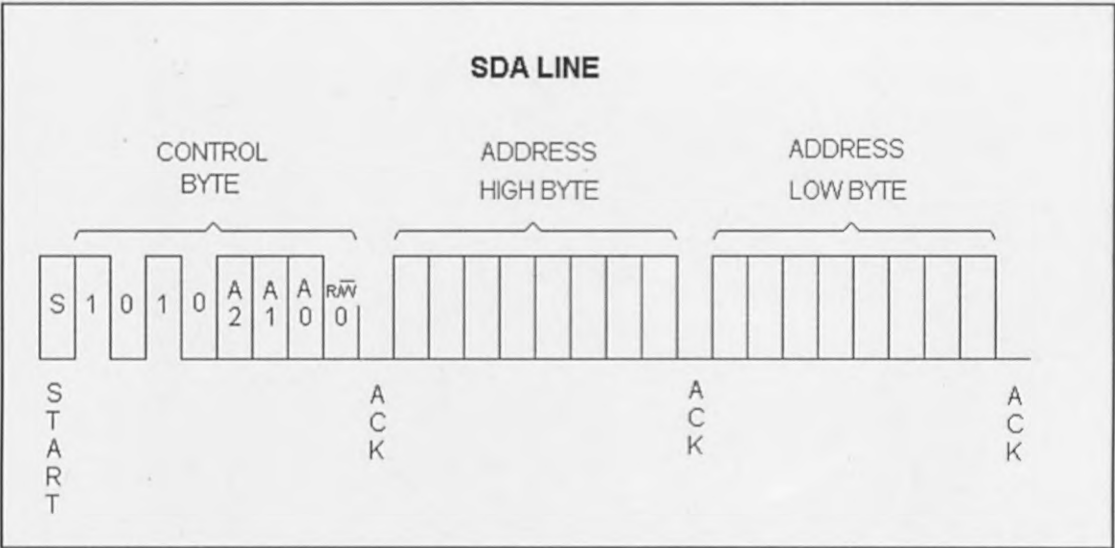


Figure 3.18: (b) Selection of memory location (addressing)

Fig. 3.18(c) shows the reading operation. The reading operation is initiated in the same way as the write operation, with the exception that the R/W bit of the control byte is set to '1'. The memory will then issue an acknowledge bit and transmit the eight bit data word. The memory will then issue another acknowledge bit and will transmit the sequentially addressed eight bit data. Following the final byte transmitted to the microcontroller, the microcontroller will not generate an acknowledge bit but will generate a STOP condition.

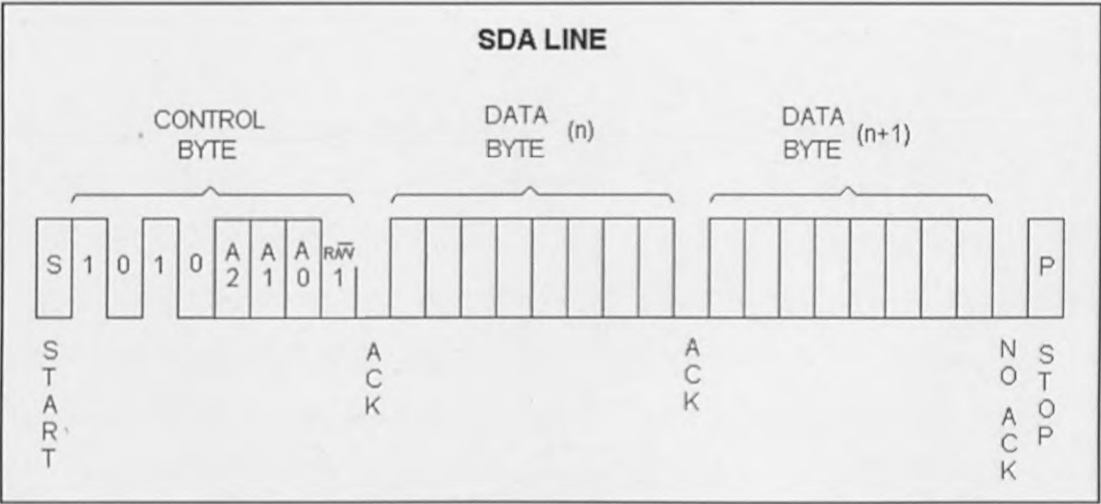


Figure 3.18:(c) Reading operation

Fig. 3.19 shows the physical size (5 cm by 2 cm) of the external memory device designed for the storage of the samples' measurements (voltammograms).

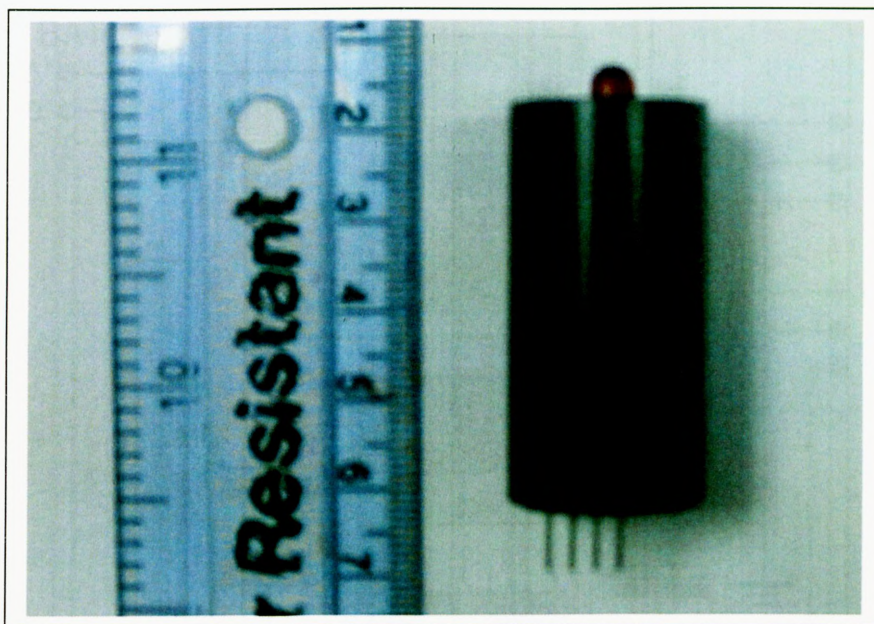


Figure 3.19: Miniature external memory device

A datasheet with all technical information of the 24AA512 memory device is given in Appendix D.8. The assembly program developed for the operation of this memory module is listed in Appendix B.7.

3.8 Portable Power Supply

An important characteristic of the system is its portability, which is made possible by its battery operation. The power consumption of the system is approximately 2 W (0.17 A at 12V). A TRACO TEL 3-0522 DC-to-DC converter was used to provide ± 12 V supplies while LM2950 and 79LM05 regulators were used in conjunction to provide ± 5 V supplies. The circuit diagram of the converter is shown in Fig. 3.20 below. A 7.2 V, 1.4 Ah battery was used for powering the two converter/inverters. The 1.4 Ah capacity of the battery is capable of providing approximately eight hours of continuous operation.

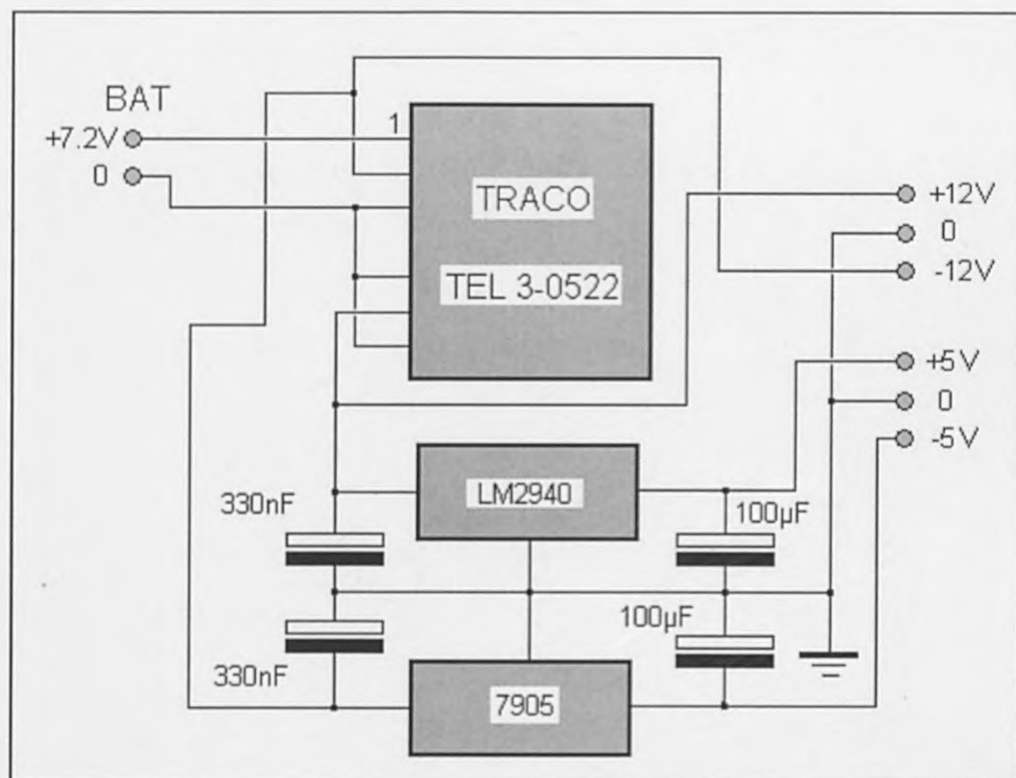


Figure 3.20: Circuit diagram of the converter / inverter

A datasheet with all technical information of the LM2940 and 7905 voltage regulators and TRACO TEL 3-0522 DC-to-DC converter device are given in Appendix D.9, D.10 and D.11 respectively

3.9 System Integration and Miniaturisation

Fig. 3.21 shows the development of the electrochemical instrumentation system with all units (power supply, microcontroller, display, keypad, potentiostat, digital-to-analogue converter, analogue-to-digital converter, and external memory module) connected together.

Fig. 3.22 shows the algorithm (flow chart) of the software which was developed for system operation. The program in assembly language is listed in appendix B.9. The program in C language for uploading and monitoring the voltammogram data on the PC is listed in appendix C.

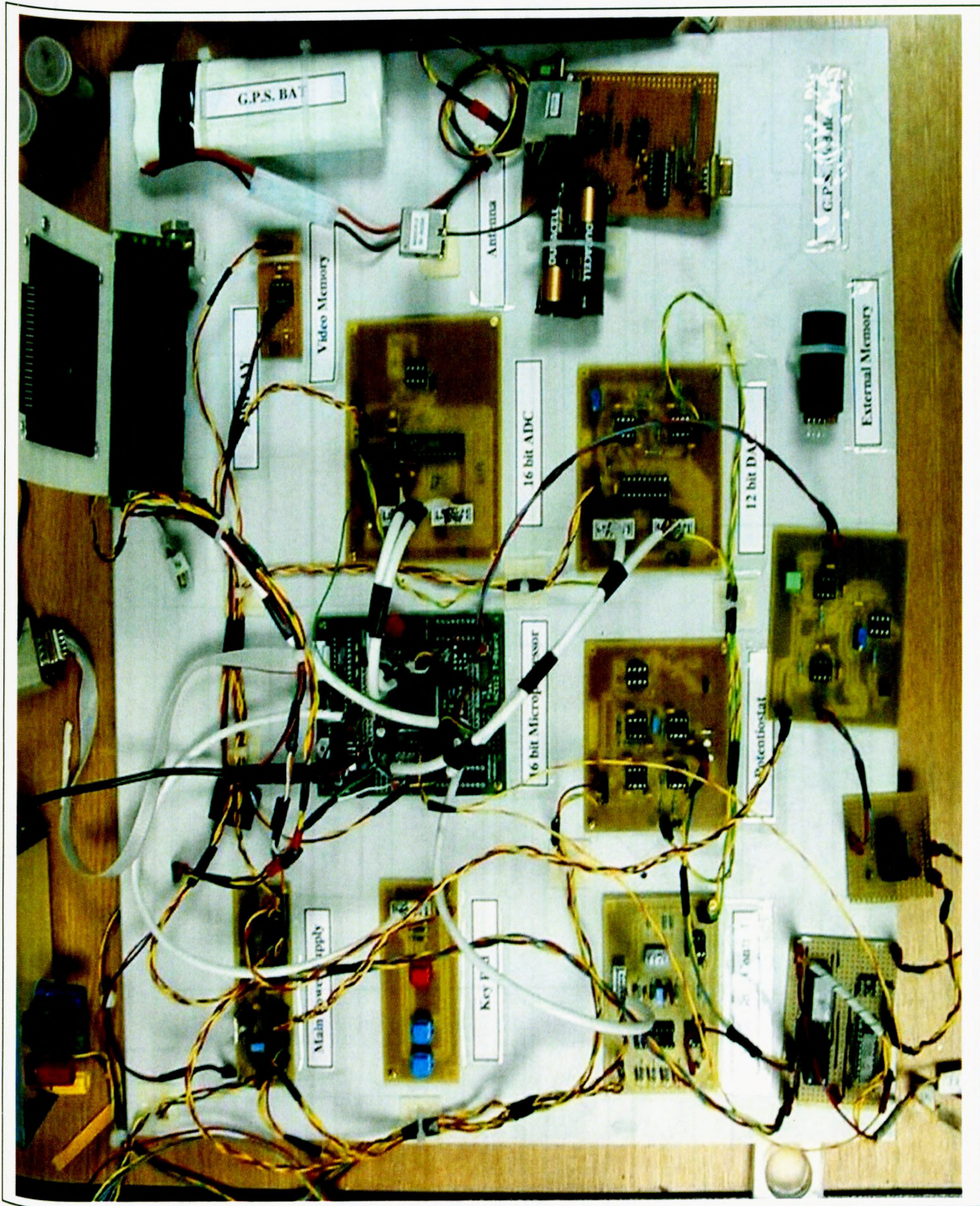


Figure 3.21: Final development of the electrochemical instrumentation system.

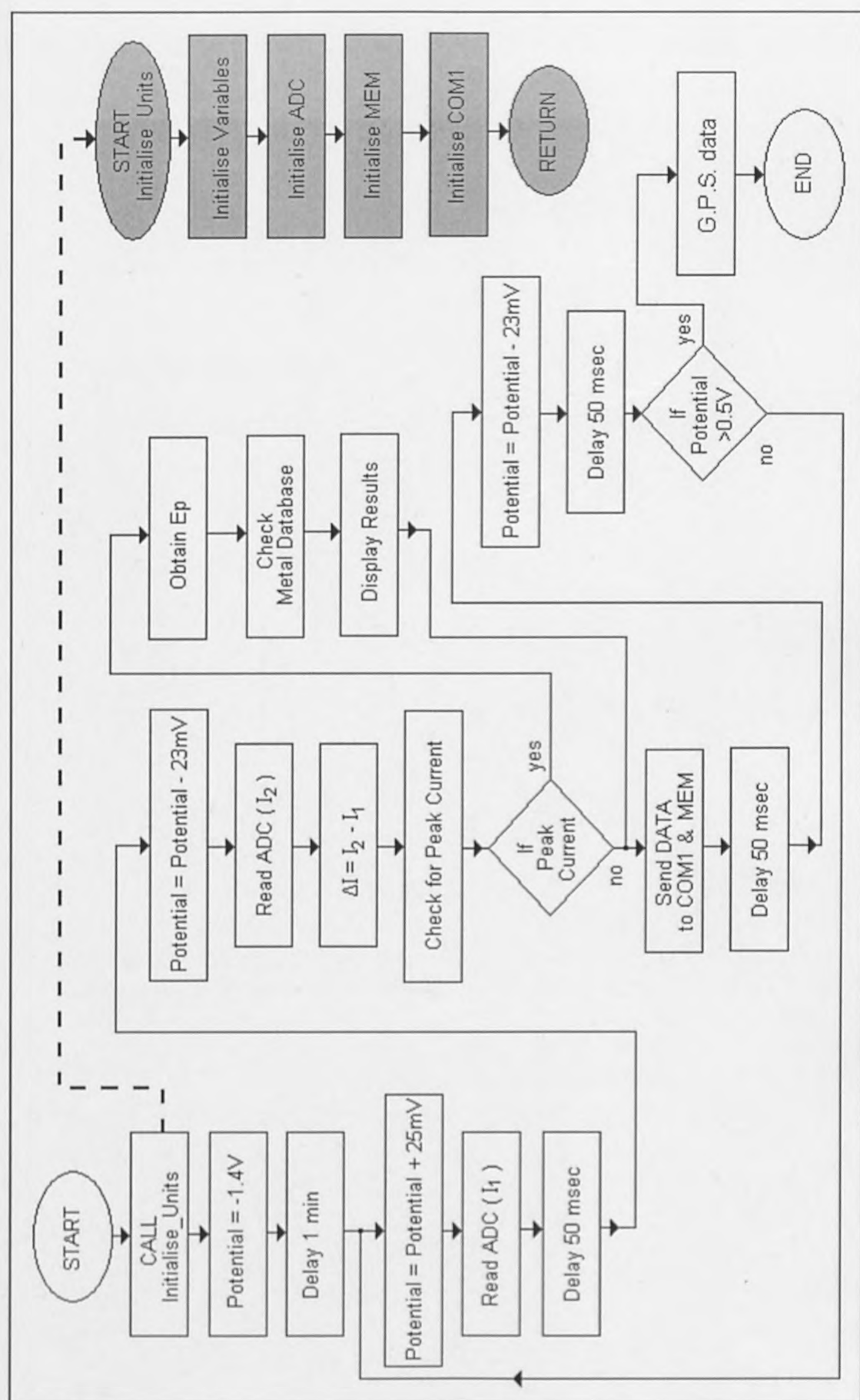


Figure 3.22: Algorithm of the software for the system's operation

Fig. 3.23 shows the design of the plastic box which is used to accommodate all units of the instrument, the battery and the electrochemical sensor.

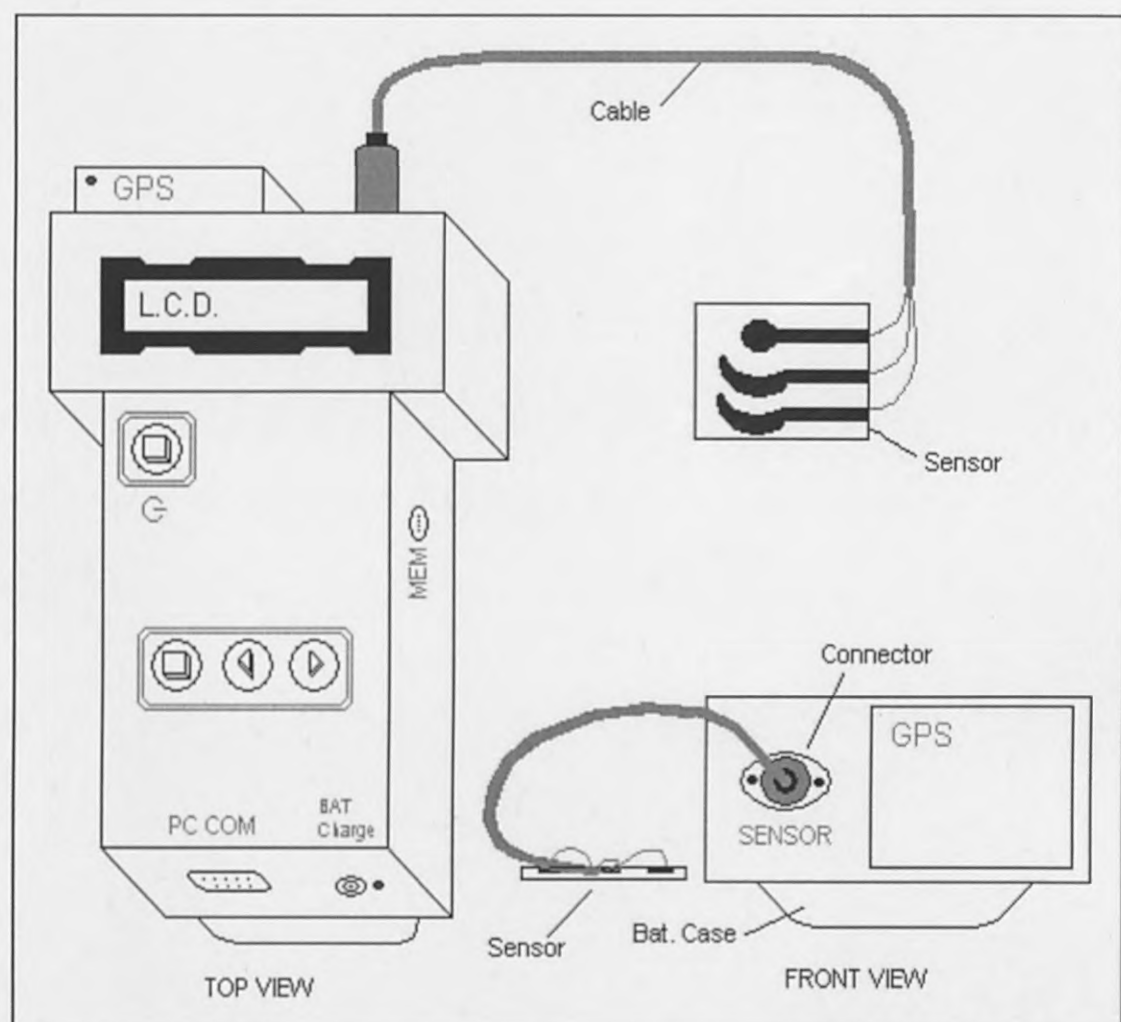


Figure 3.23: Design of the plastic box to accommodate all units of the instrument

The next step of the design was to integrate the whole system shown in Fig.3.21 using only one Prototype Circuit Board (PCB). Fig. 3.24 shows the PCB design of the electrochemical system. The PCB is 17 cm long and 10.2 cm wide.

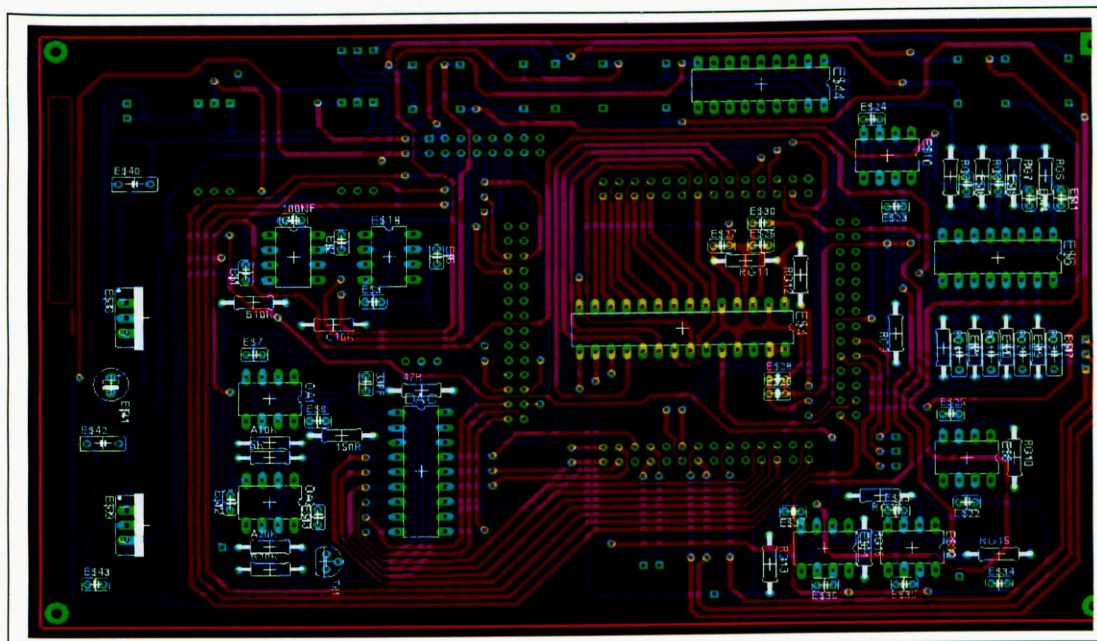


Figure 3.24: PCB design of the electrochemical system

Fig. 3.25 shows the miniaturised version of the system assembled in the plastic box.

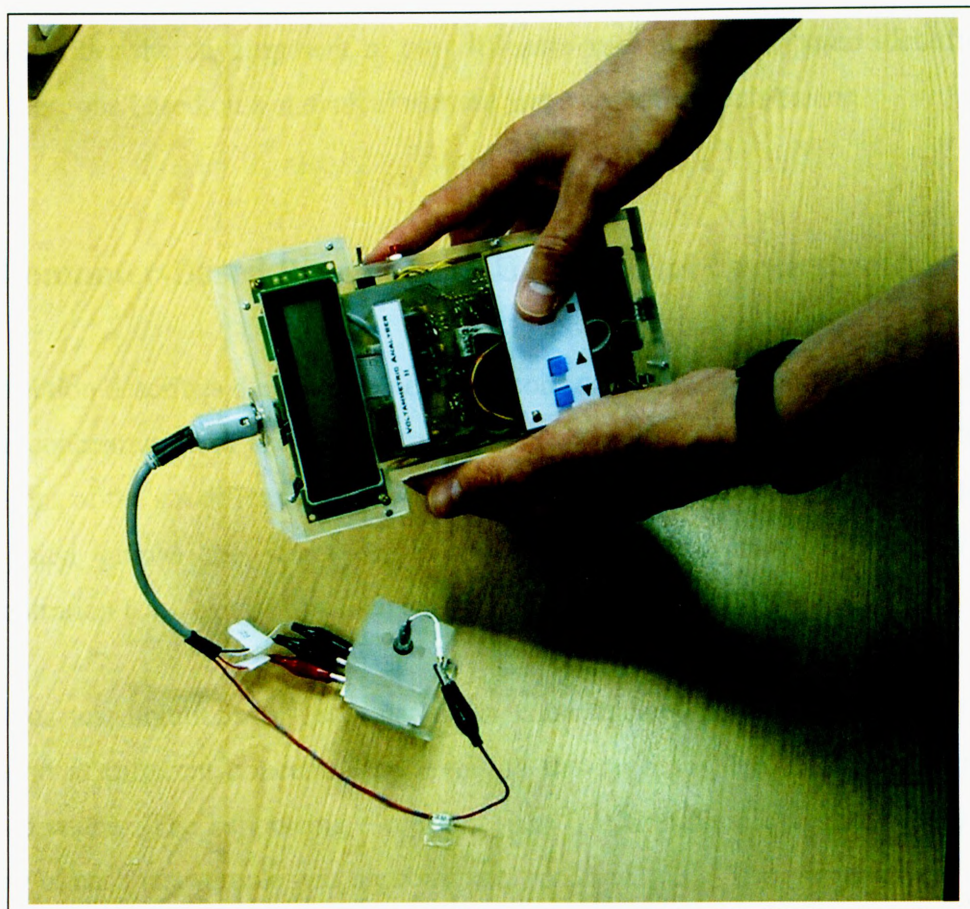


Figure 3.25: Electrochemical instrumentation system prototype

Chapter Four

Microprocessor-Based Detection and Identification of Heavy Metals

4.1 Introduction

This chapter deals with the development of the appropriate microprocessor-based methods for the prediction of the concentration of six different metals namely lead, cadmium, zinc, nickel, mercury and copper. These six ions were initially chosen for examination due to their importance as environmental pollutants[87-92]. The chapter also describes the development of two different microprocessor-based identification strategies, one based on a statistical method and a second on data fusion.

4.2 Computer-Based Prediction of Heavy Metal Concentrations

This section describes the development of a computer-based method for the prediction of the concentration of six different metals. This method is based on the calibration equations of the six different metals. The coefficients of the curve-fitting equations of calibration graphs are stored in system memory; if a metal is identified, its concentration level can be obtained using these equations[93,94].

Aqueous test solutions of lead, cadmium, zinc, nickel, mercury and copper were prepared at different concentration levels in the range of 1 to 100 ppm using de-ionised water. The supporting electrolyte was 0.1 M sodium chloride (*NaCl*). The acidity of each test sample was approximately 1.35 pH[63]. The samples were placed in a glass sample reservoir of 40 ml capacity. The pre-concentration time used for

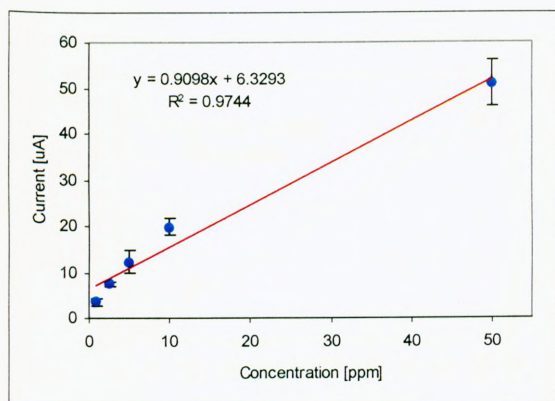
these experiments was 60 sec and the scanning voltage was in the range -1400 to +1000 mV.

Thirty two independent measurements of the electrical potential and peak current amplitude of all six metals were recorded. The instrument was also connected to a personal computer, and the results were monitored for comparison with the values obtained from the liquid-crystal display. This procedure was carried out using both electrochemical sensors (glassy carbon and screen printed).

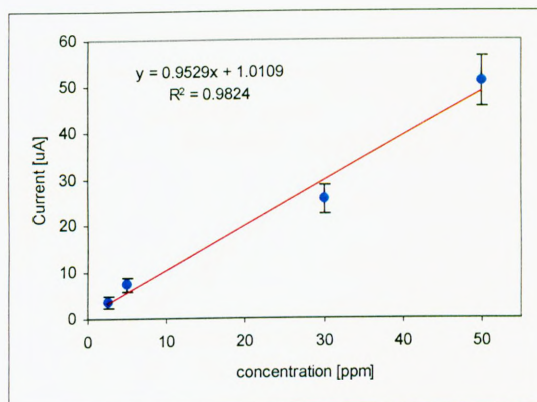
Fig. 4.1(a) to (f) shows the calibration graphs of lead, cadmium, mercury, zinc, copper and nickel respectively using the cell with the glassy carbon electrode. The full set of measurements are given in Appendix A(1-6).

Fig. 4.2(a) to (f) shows the calibration graphs of lead, cadmium, mercury, zinc, copper and nickel respectively using the screen printed cell. The full set of measurements are given in Appendix A(7-12).

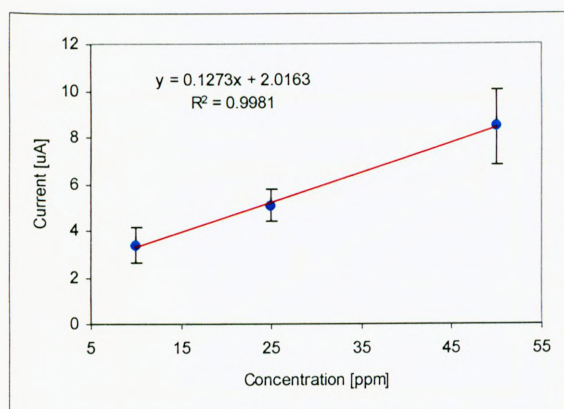
As the calibration graphs for all the metals examined are approximately linear (as shown in Fig. 4.1 and Fig. 4.2) and thus relatively reproducible, the concentration of a particular species can be obtained from the measured peak current. The calibration coefficients of the calibration equations were stored in the microcontroller memory. When a test is carried out, the metal is first identified using the identification algorithm. The amplitude of the peak current (corresponding to the oxidation potential of the identified metal) is then used with the calibration equation in order to predict the level of concentration.



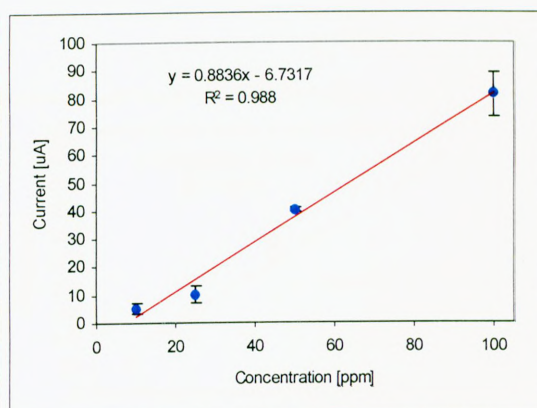
(a) Lead(ii)



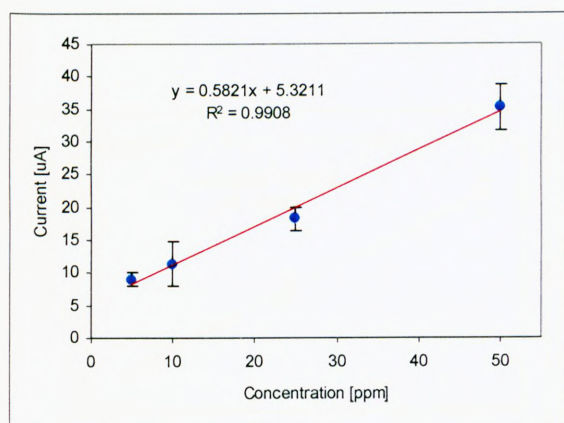
(b) Cadmium(ii)



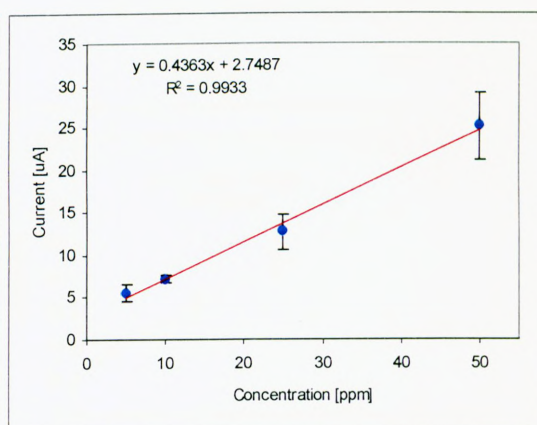
(c) Mercury(ii)



(d) Zinc(ii)

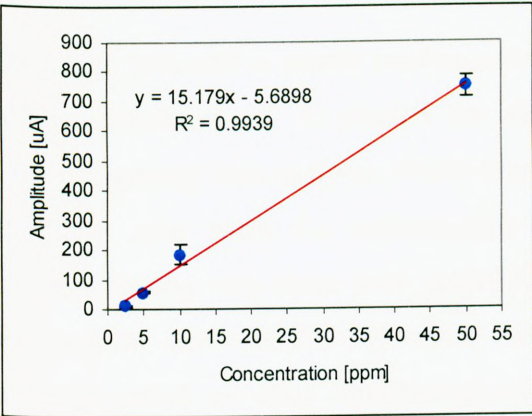


(e) Copper(ii)

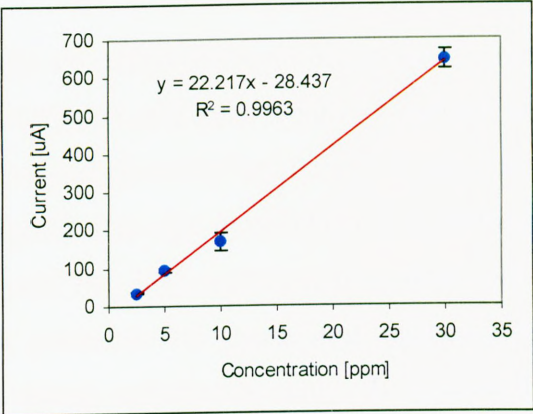


(f) Nickel(ii)

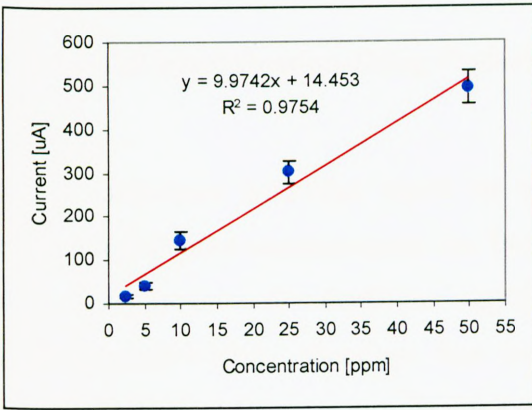
Figure 4.1: Calibration curves of all metals using the glassy carbon electrode



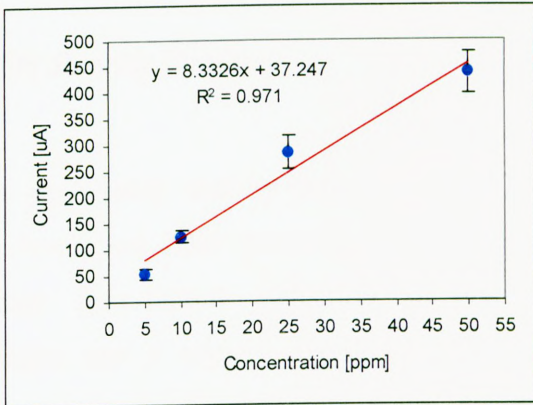
(a) Lead(ii)



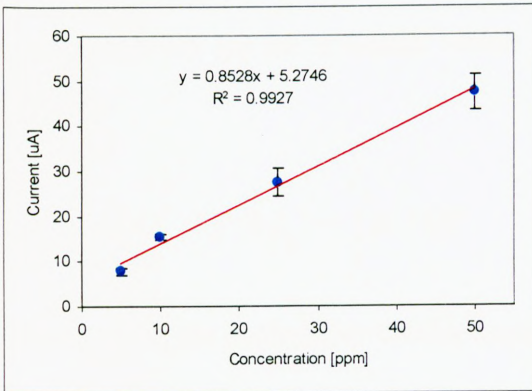
(b) Cadmium(ii)



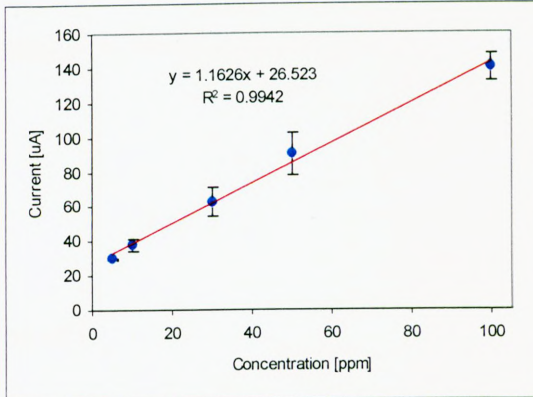
(c) Zinc(ii)



(d) Copper(ii)



(e) Nickel(ii)



(f) Mercury(ii)

Figure 4.2: Calibration curves of the six metals using the screen printed sensor

4.3 Identification of Heavy Metals Using a Statistical Method

Oxidation potential is widely used as a feature extraction method for the identification of electro-active ions. At present, the identification of metals requires laborious and time consuming data analysis, which must be carried out by highly trained personnel. Problems arise when the voltammetric signals relevant to neighbouring elements overlap, having very close peak potentials and very high concentration ratios. Most working in this field[95-98] solve such problems by employing mathematical methods, which are often complicated and difficult to follow or apply. To achieve the same goal, two alternative computer-based techniques, which are simple and quick to apply, have been developed. Using these techniques, six different metals can be identified.

4.3.1 Metal Identification Using Probability Density Function

An identification technique based on the probability density functions (*PDF*) of oxidation potential measurements has been developed. PDF curves have been used in the development of decision algorithms for feature selection in various applications[99-101]. Data are first arranged into a numerical order from which various statistical features are obtained, such as *minimum*, *maximum*, *mean*, *median*, and *standard deviation*. These are then used as a basis for classification.

The probability (*p*) for a feature which assumes a value between f_1 and f_2 is given by[102]:

$$p(f_1 \leq f \leq f_2) = \int_{f_1}^{f_2} p(f)df \tag{4.1}$$

where, $p(f)$ is the probability density function of f .

In the case of Gaussian distribution[103], the probability density function $p(f)$ is given by:

$$p(f) = \left[1/(\sigma\sqrt{2\cdot\pi}) \right] \cdot e^{-(f-\mu)^2/2\cdot\sigma^2} \quad (4.2)$$

$$\mu = \sum_{i=1}^N (f_i / N) \quad (4.2.a)$$

$$\sigma = (1/N) \sum_{i=1}^N (f_i - \mu) \quad (4.2.b)$$

where, μ is the mean value and σ is the standard deviation.

Fig. 4.3 shows an example of probability density function curves for a two-class classification problem. Features 1 and 2 are limited in their capability for classifying the feature as either class 1 or 2. Feature 3 provides a clearer differentiation between class 1 and 2. Feature 4 provides an excellent marker for differentiating the two classes with 100% probability.

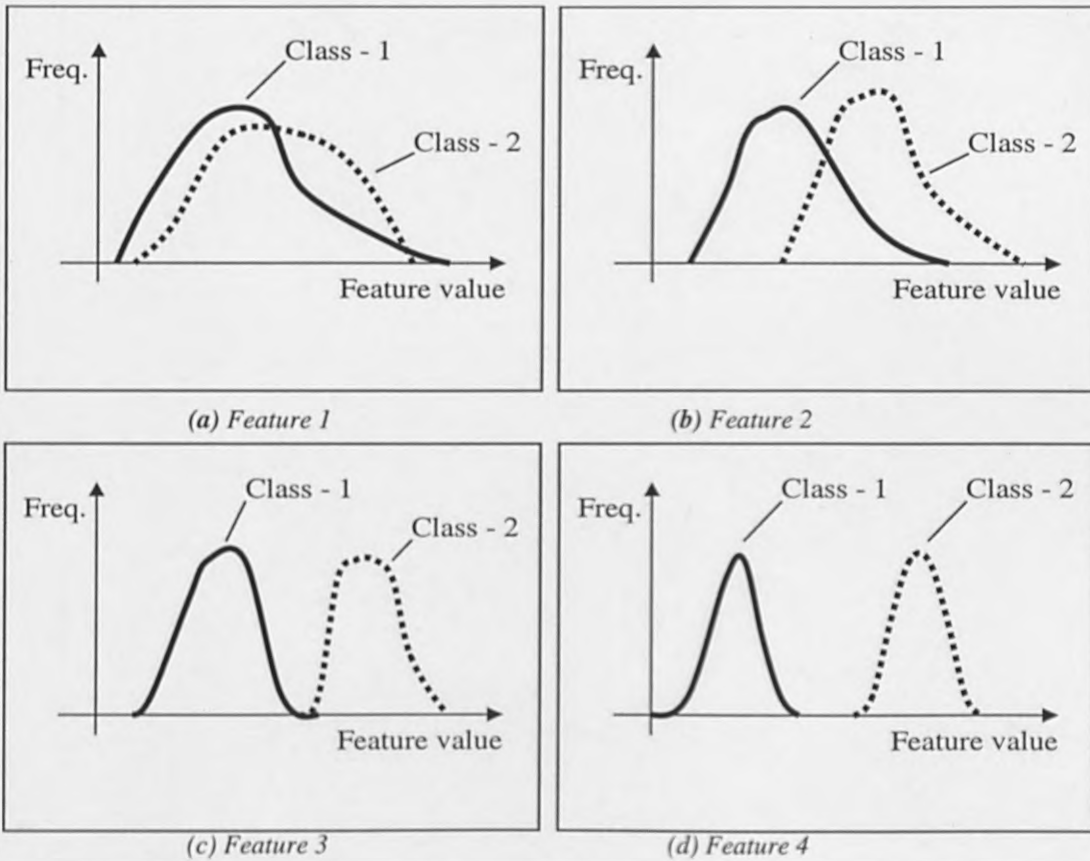


Figure 4.3: Sample probability density function curves for a typical two-class classification

Considering the application of the PDF-based method to the heavy metal identification problem, as the potential of the excitation signal approaches the oxidation potential of one of the metals dissolved onto the electrode surface, the ions of that metal pass into the solution from the electrode. The current increases rapidly and reaches a maximum value (peak current) when the applied potential approximates to the metal's oxidation potential (E_p). When an actual test is carried out, the oxidation potential E_p is assessed and examined against a PDF to determine the probability of membership of that analyte with all analytes stored in a database of PDF measurements. The analyte representing the highest probability of likelihood is thus identified. Analytes identified in this way are automatically given a probability of likelihood, indicating the prediction accuracy.

Fig. 4.4 shows a block diagram for the whole process of identification by this means.

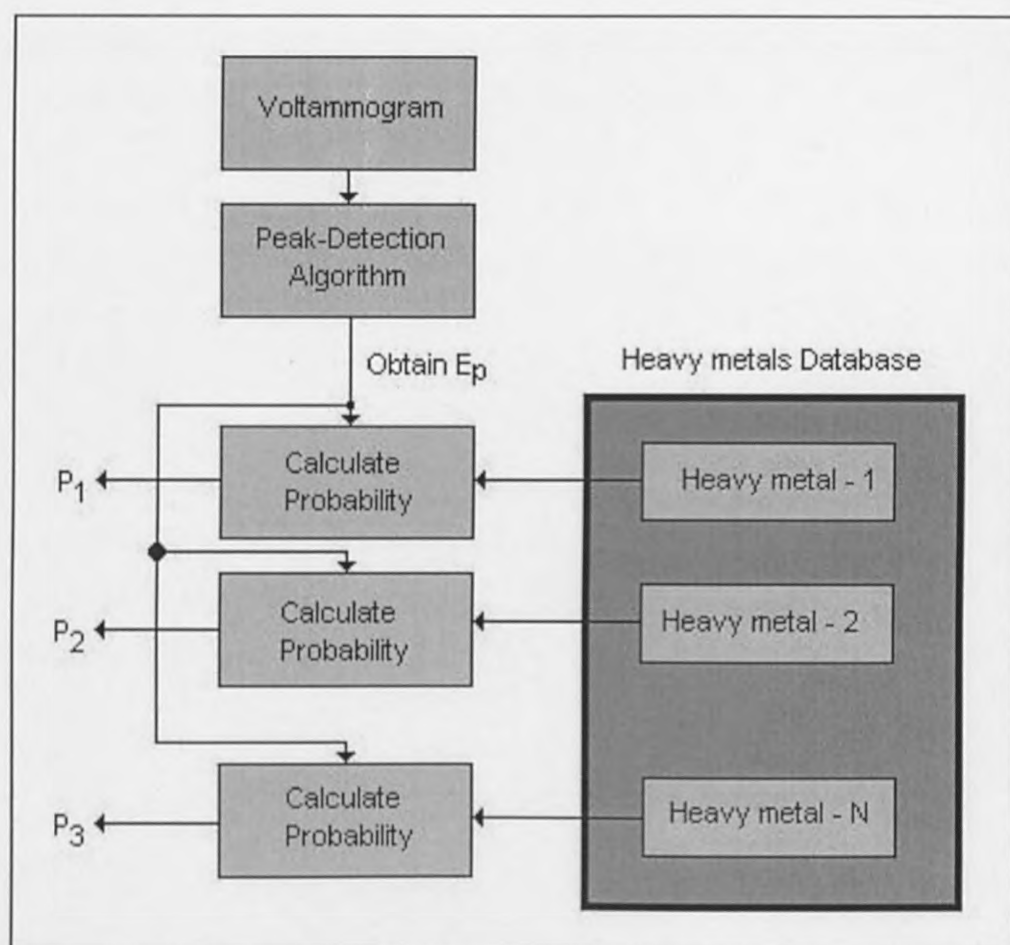


Figure 4.4: Process for the identification of heavy metals

4.3.2 Development of the Statistical Method

Aqueous test solutions of lead, cadmium, zinc, nickel, mercury and copper were prepared at different concentration levels in the range of 1 to 100 ppm. These six ions were initially chosen for examination due to their importance as environmental pollutants. The solutions were prepared using de-ionised water. The supporting electrolyte was 0.1 M sodium chloride (*NaCl*). The acidity of each test sample was approximately 1.35 pH. The samples were placed in a glass sample reservoir of 40 ml capacity. The pre-concentration time used for these experiments was 60 sec and the scanning voltage was in the range -1400 to +1000 mV.

Thirty two independent measurements of the electrical potential and peak current amplitude of all six metals were recorded. The instrument was also connected to a personal computer, and the results were monitored for comparison with the values obtained from the liquid-crystal display. This procedure was carried out using both electrochemical sensor (glassy carbon and screen printed).

Fig. 4.5 shows the resultant probability density functions of the electrical potential measurements which were estimated for the six different metals using the glassy carbon electrode. The statistical parameters are shown in table 4.1. The full set of measurements are given in Appendix A(1-6).

Fig. 4.6 shows the resultant probability density functions of the electrical potential measurements which were estimated for the six different metals using the screen printed sensor. The statistical parameters are shown in table 4.2. The full set of measurements are given in Appendix A(7-12).

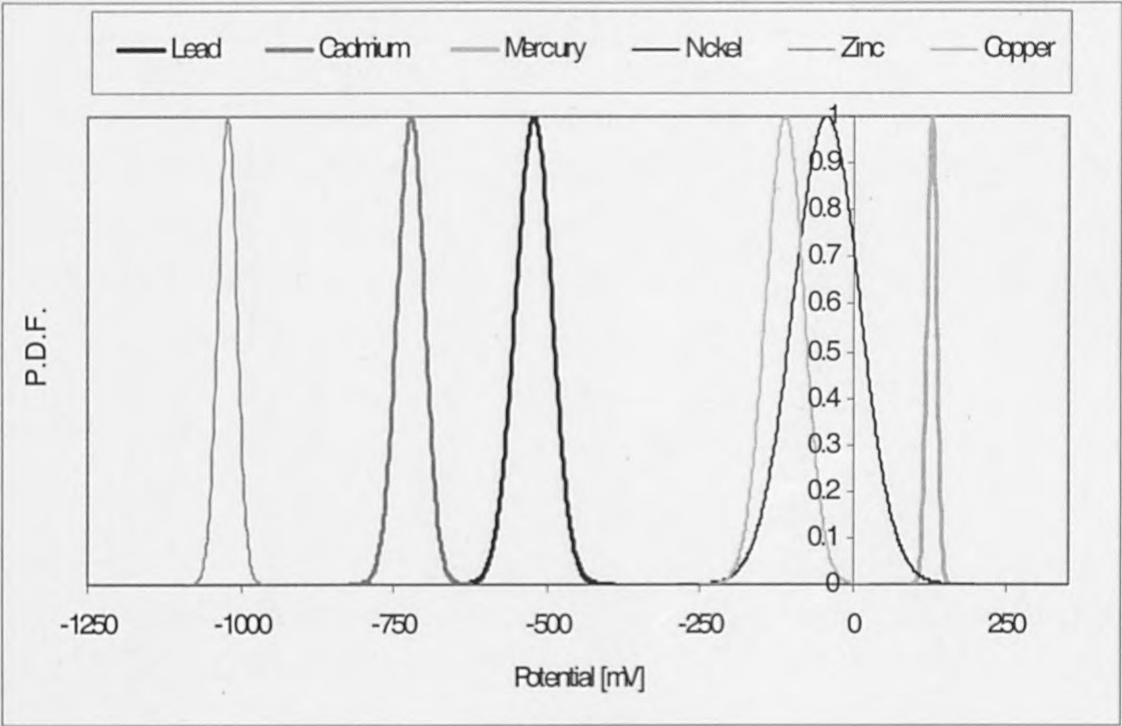


Figure 4.5: Probability density functions of the electrical potentials of the six different metals (glassy carbon electrode).

Table 4.1: Statistical parameters of electrical potential measurements at acidity of ~1.35pH (glassy carbon electrode)

Heavy metal	Oxidation potential [mV]	
	Mean μ_E	Std σ_E
Zinc (Zn^{II})	-1022	15.24
Cadmium (Cd^{II})	-722	22.27
Lead (Pb^{II})	-522	29.36
Copper (Cu^{II})	-112	31.42
Nickel (Ni^{II})	-44	54.40
Mercury (Hg^{II})	128	7.75

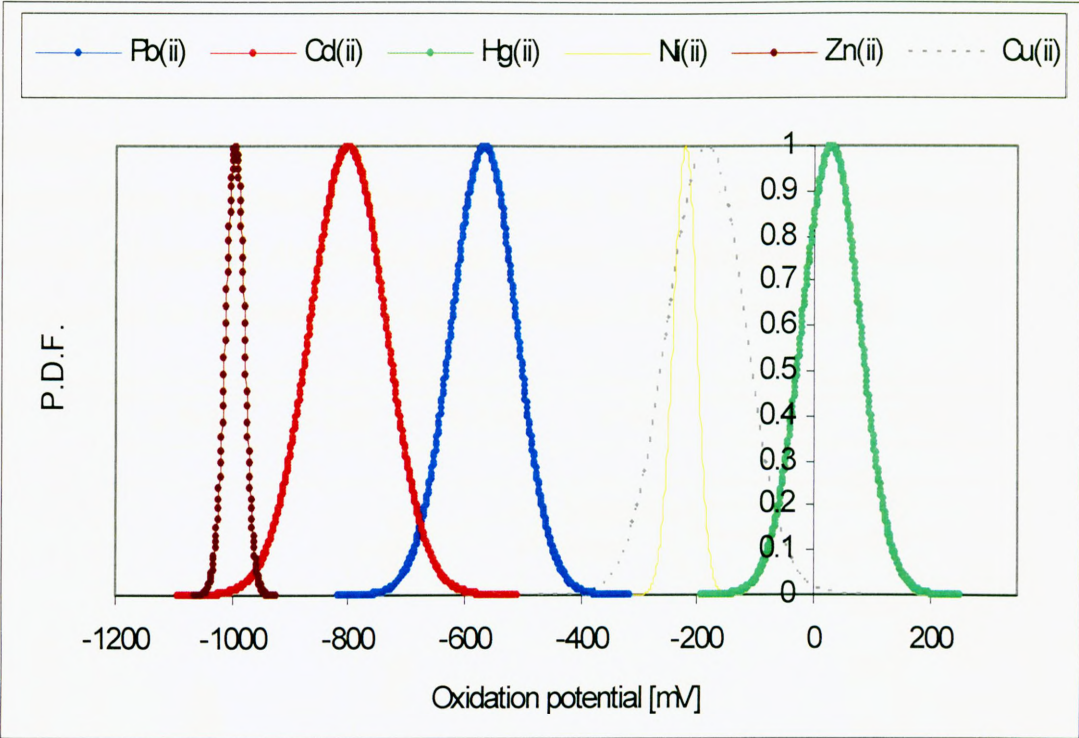


Figure 4.6: Probability density functions of the electrical potentials of the six different metals (screen printed sensor).

Table 4.2: Statistical parameters of electrical potential measurements at acidity of ~1.35pH (screen printed sensor)

Heavy metal	Oxidation potential [mV]	
	Mean μ_E	Std σ_E
Zinc (Zn ^{II})	-1002	25.42
Cadmium (Cd ^{II})	-821	67.99
Lead (Pb ^{II})	-568	56.31
Copper (Cu ^{II})	-183	64.82
Nickel (Ni ^{II})	-211	28.39
Mercury (Hg ^{II})	57	51.74

4.4 Identification of Metals Using Data Fusion

From the dataset obtained from the thirty two measurements described in previous technique, above, the points of peak current amplitude and associated oxidation potential can be extracted. These are plotted in Fig. 4.7. The combination of the current and potential dimensions gives a clearer (two-dimensional) view of separation between the six different metals than the graphs of Fig. 4.5 or Fig. 4.6.

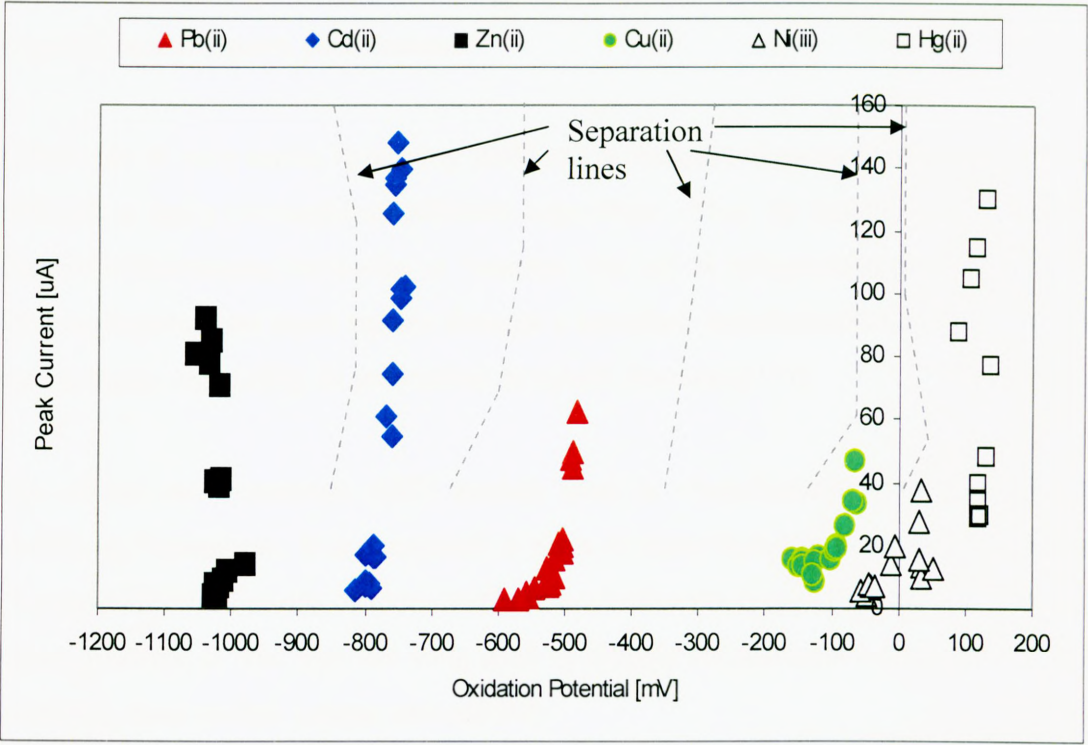


Figure 4.7: Amplitude peak versus oxidation potential for the six different metals

The plot of Fig. 4.7 is called a *space scatter diagram* and is well known in the field of pattern recognition[104]. The plot allows any natural clustering of the data to be seen. Clustering is a process in which a set of data is organised into groups that have strong likeness or similarity, measures described in standard textbooks on pattern recognition[105,106]. Separation problems like the one evidenced on the space scatter diagram of Fig. 4.7 can be easily solved by using artificial neural networks[107,110].

4.4.1 Identification of Heavy Metals Using a Neural Network

Artificial neural networks (ANNs) can be implemented in software, and can be trained to undertake many problems which are amenable to a distributed computational approach of this kind. The training of ANNs is performed with historical data and associated outcomes. The ANN calculates its response to test input data and compares it with a known result. The comparison result is used to adjust internal parameters within the ANN, according to a specified algorithm, in such a way as to improve its subsequent performance.

ANNs can be very useful in solving problems in classification applications where it is difficult to apply conventional software algorithms. They are usually composed of a number of interconnected nodes or 'neurons' that act as independent processing units. Each node processes input signals through a specified transformation and produces an output signal depending on prescribed threshold functions[111].

One of the most common ANN models used in classification applications is the multilayer Perceptron. It is composed of three or more layers of neurons each feeding its outputs forward to one or more nodes in the following layer. For this application, a neural network of this type has been used to classify six different heavy metals, zinc, cadmium, lead, nickel, copper and mercury.

The ANN applied in this instance has three layers of neurons, an input layer, a "hidden layer" and an output layer. The first layer, consists of two input neurons, one for the oxidation potential input and one for the peak current amplitude. The second (hidden) layer consists of seven neurons which are sufficient to solve the classification problem. The third layer consists of six outputs, one each for Lead (Pb^{II}), Cadmium (Cd^{II}), Mercury (Hg^{II}), Zinc (Zn^{II}), Nickel (Ni^{II}) and Copper (Cu^{II}). The neural network was designed and trained using NS32NET ANN development and optimisation software. After training, all weights and bias values for each neuron were obtained.

The input layer (Fig. 4.8) is defined by equations [4.3(a,b)]:

$$E'_p = (E_p - \min_{E_p}) / (\max_{E_p} - \min_{E_p}) \quad (4.3.a)$$

$$I'_p = (I_p - \min_{I_p}) / (\max_{I_p} - \min_{I_p}) \quad (4.3.b)$$

where, E_p and I_p are the inputs of the network, E'_p and I'_p are the normalised inputs, \max_{E_p} and \max_{I_p} are the maximum values of E_p and I_p input respectively used for training, \min_{E_p} and \min_{I_p} are the minimum input values used for training.

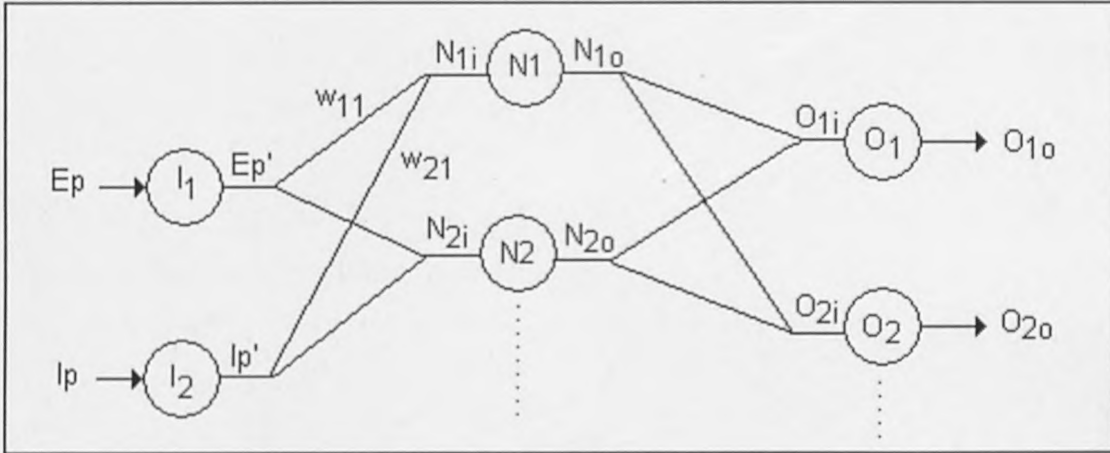


Figure 4.8: Neural network with three layers of neurons

The hidden layer is defined by equations (4.4.a) and (4.4.b):

$$N1_i = (E'_p \times w_1) + (I'_p \times w_2) + \text{bias}_{N1} \quad (4.4.a)$$

where, $N1_i$ is the input of the first neuron of the hidden layer and w_1 and w_2 are the weights.

$$N1_o = 1 / (1 + e^{-N1_i}) \quad (4.4.b)$$

where, $N1_o$ is the output of the first neuron of the hidden layer.

The output layer is defined by equation (4.5):

$$O_{1_o} = \left[\frac{1}{1 + e^{-O_{1_i}}} \right] \times (\max_{O_{1_i}} - \min_{O_{1_i}}) + \min_{O_{1_i}} \quad (4.5)$$

where, O_{1_o} is the output of output layer neuron, $\max_{O_{1_i}}$ is the maximum value of this output for ANN training and $\min_{O_{1_i}}$ is the minimum value of this output for ANN training.

Since the weights, bias, max and min values are known after the ANN design, the next stage is to store these values into microcontroller memory. In addition, appropriate software was developed for the microcontroller which uses equations (4.3), (4.4) and (4.5) and all stored values (weights, bias, max and min) in order to obtain the output of the ANN for a given input pair (E_p , I_p).

Fig. 4.9 shows the flow chart of the operation of the electrochemical instrument for the identification of heavy metals by using a neural network.

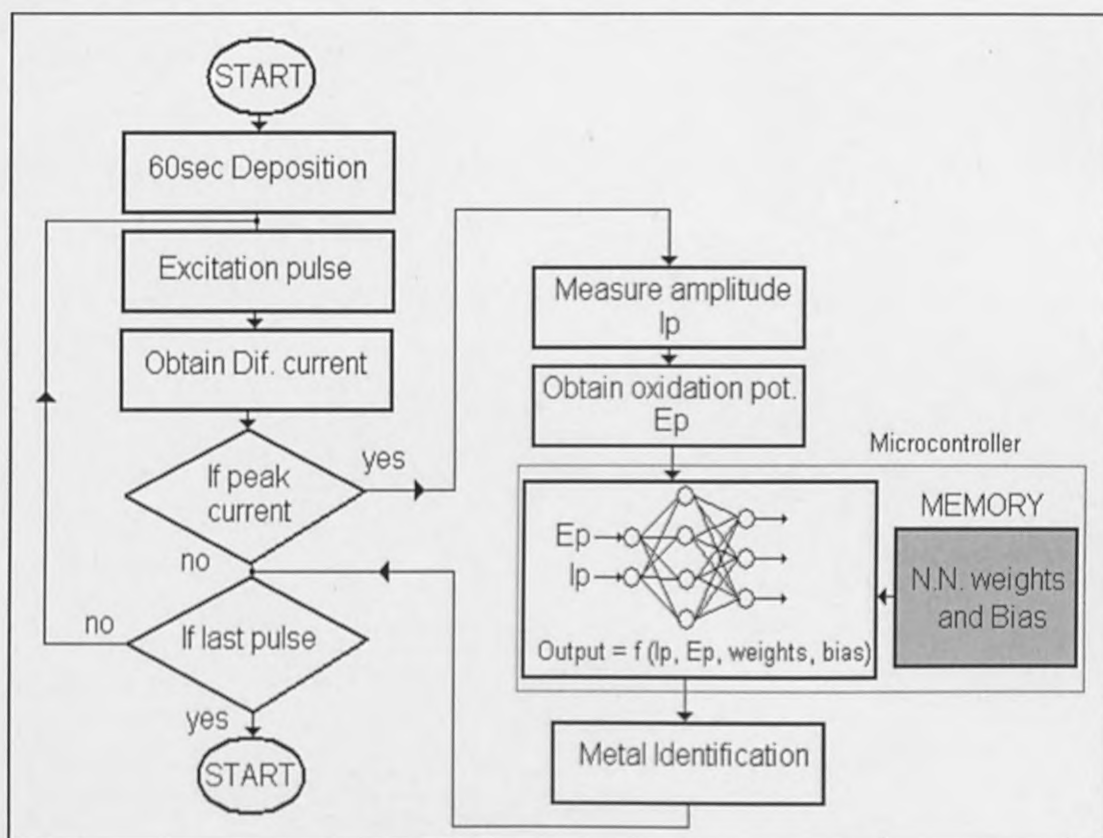


Figure 4.9: Flow chart of the operation of the electrochemical instrument for identification of heavy metals using a neural network.

4.4.2 Development of the Artificial Neural Network

Test solutions of lead, cadmium, zinc, nickel, mercury and copper were prepared at different concentration levels in the range of 1 to 100 ppm. These six ions were chosen to be those for first examination due to their importance as environmental pollutants. The solutions were prepared using ionised water. The supporting electrolyte was 0.1 M sodium chloride (*NaCl*). The samples were placed in a sample reservoir with a 40 ml capacity. The pre-concentration time (deposition) was set to 60s at -1400 mV. The scanning voltage range used was from -1400 to +1000 mV, with step potential of 2 mV and pulse height of 25 mV; the scan rate was 120 ms and the pulse duration was 50 ms.

Thirty two independent measurements of the electrical potential and peak current amplitude of all six metals were recorded. The instrument was also connected to a personal computer, and the results were monitored for comparison with the values obtained from the liquid-crystal display.

The three-layer perceptron ANN was designed and trained using "NS32NET" ANN development software. Fig. 4.10 shows the configuration of the neural network.

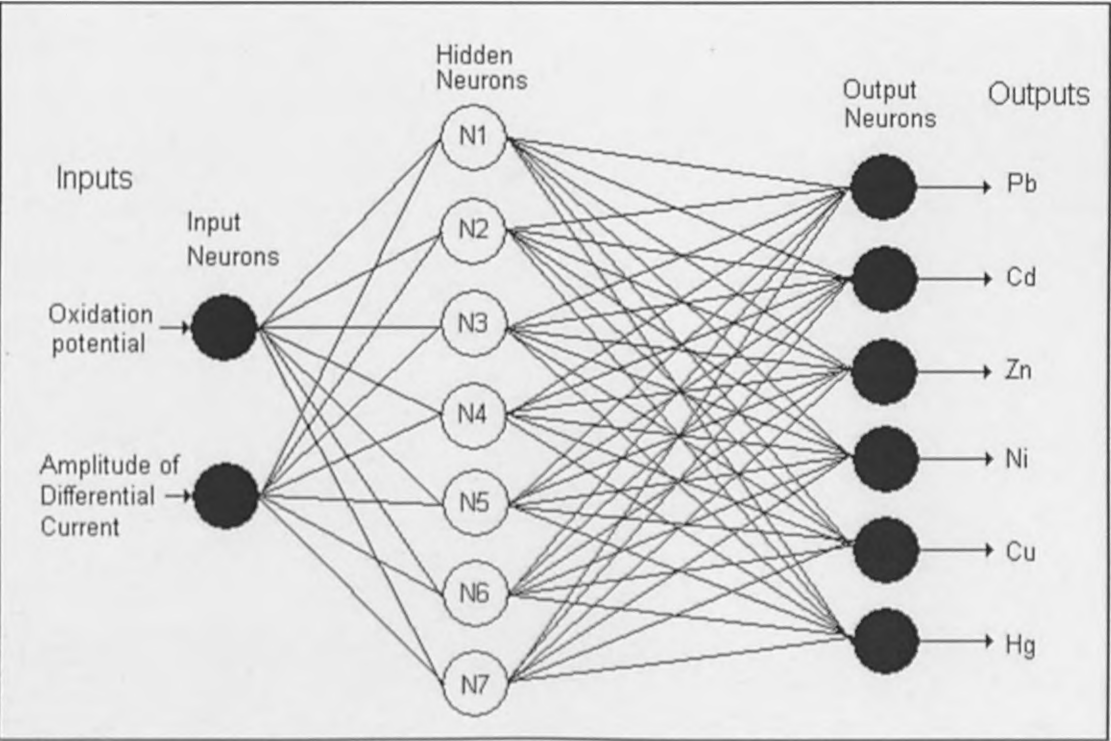


Figure 4.10: Configuration of the neural network

Fig. 4.11 shows the variation of maximum, average, and minimum learning error during training. The training target was 0.012. The neural network reached the target error after 41,000 cycles.

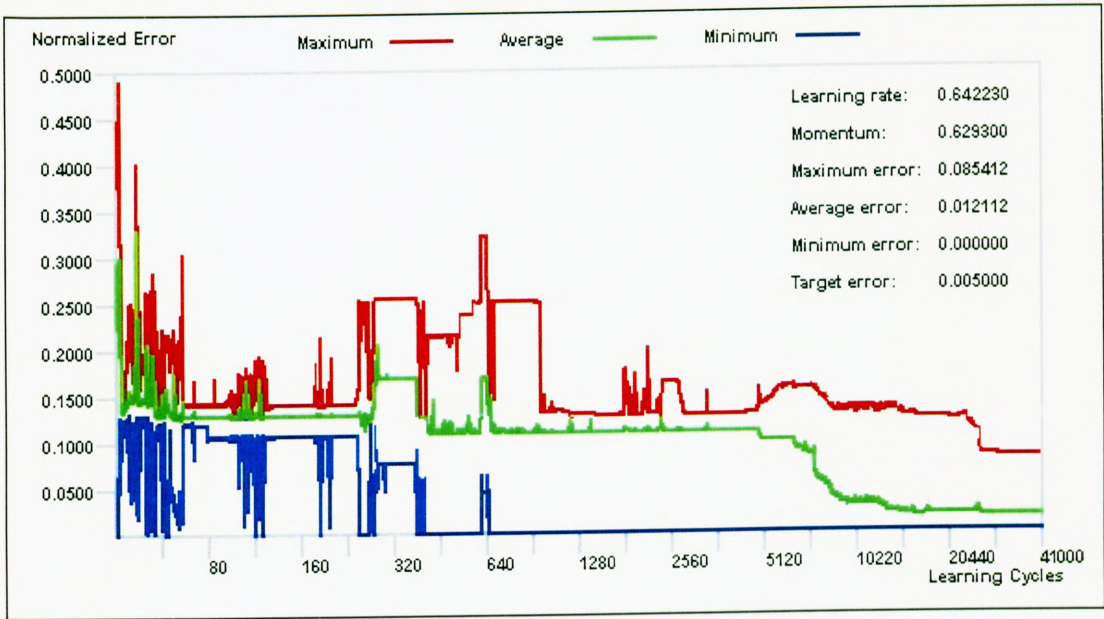


Figure 4.11: Training error during neural network training.

After training, all weights, bias, max and min values of each node of the ANN were obtained. The next stage of the design was to store these values into microcontroller memory. When an actual test is carried out, the peak current amplitude I_p and oxidation potential E_p of the voltammogram are first obtained. Using the I_p and E_p values and the stored weights and bias of each node, the microcontroller applies equations (4.3), (4.4) and (4.5) to obtain the outputs of the ANN, which indicate the presence of any of the six different heavy metals.

The probability of classification results, obtained from the application of the neural network, are given in Table 4.3.

Table 4.3: Probability of classification

Heavy Metal	Lead	Cadmium	Zinc	Nickel	Mercury	Copper
Probability [%]	100	100	100	89	100	92

As expected, lead, cadmium, zinc and mercury are classified with very good certainty (100%). For copper and nickel, the probability of identification was 92% and 89% respectively. This may be due to the network requiring refinement as it may be possible that it has converged with false minima. Such refinements would normally be carried out on a trial and error basis with parameters being gradually adjusted, but the type of software available did not allow such fine adjustments.

Chapter Five

Cartographical Mapping of Pollution

5.1. Introduction

A Global Positioning System (GPS) receiver has been added to the system. With the GPS, it is possible to store the exact geographical position of an assessed sample in the field. The GPS device is connected to the microcontroller via the serial port and uses the NMEA GPS protocol. Geographical Information System (GIS) software has been developed which combines the pollutant results obtained by the analyser, the geographical position where the sample was taken and the map of the area of interest, so as to produce a cartographical presentation of the pollution of this area.

5.2 Global Positioning System - An overview

The Global Positioning System (GPS) is a satellite-based navigation system made up of a network of currently 27 satellites placed into orbit (approximately 20 km above earth's surface) by the U.S. Department of Defense[112,113]. It was originally intended for military applications, but in the 1980s, the government made the system available for civilian use. GPS satellites circle the earth twice a day in a very precise orbit and transmit signal information to earth. GPS receivers take this information and use triangulation to calculate the user's exact location[114]. Essentially, the GPS receiver compares the time a signal was transmitted by a satellite with the time it was received. The time difference tells the GPS receiver how far away the satellite is. With distance measurements from a few satellites, the receiver can determine the user's position and display it on the unit's electronic map.

GPS satellites transmit two low power radio signals (50 Watt or less), designated L1 and L2. Civilian GPS uses the L1 frequency of 1575.42 MHz in the UHF band. This signal contains three different bits of information, namely pseudorandom code, ephemeris data and almanac data[115,116]. The pseudo random code (PRN) is simply an I.D. code that identifies which satellite is transmitting information. Ephemeris data informs the receiver where each satellite should be at any time throughout the day. Each satellite transmits ephemeris data showing the orbital information for that satellite and for every other satellite in the system. Almanac data, which is constantly transmitted by each satellite, contains important information about the status of the satellite (healthy or unhealthy), current date and time. This part of the signal is essential for determining a position.

A GPS receiver must be locked on to the signal of at least three satellites to calculate latitude and longitude (two-dimensional position) and track movement. With four or more satellites in view, the receiver can determine the user's latitude, longitude and altitude (three-dimensional position)[117].

Each satellite transmits its current position x,y,z and its current time t . The message is received by a (station) GPS unit located at some unknown position X,Y,Z at a time $t+\Delta t$. Thus if the satellite transmits a signal at $t=0$ s and this signal is received 80 ms later at time $t+\Delta t = 80$ ms, it follows that the receiver is at distance of $c\Delta t$ from the satellite, where c is the speed of light, i.e at a distance of 3×10^8 m/s $\times 80\times10^{-3}$ s = 2.4×10^7 m. The satellites are equipped with highly stable clocks while each receiver has a less expensive quartz clock. This means that the clock on the receiver may run fast or slow. If fast by δ , it must subtracted from each of the Δt transit times to obtain the true transit time[118].

It is not difficult to show that three-dimensional navigation demands a minimum of four satellites. If their signalling positions are (x_1,y_1,z_1) , (x_2,y_2,z_2) , (x_3,y_3,z_3) and (x_4,y_4,z_4) and the measured signals $(\Delta t_1-\delta)$, $(\Delta t_2-\delta)$, $(\Delta t_3-\delta)$ and $(\Delta t_4-\delta)$, respectively (Fig.5.1), then:

$$(x_1-X)^2 + (y_1-Y)^2 + (z_1-Z)^2 = c^2 (\Delta t_1 - \delta)^2 \tag{5.1}$$

$$(x_2 - X)^2 + (y_2 - Y)^2 + (z_2 - Z)^2 = c^2 (\Delta t_2 - \delta t)^2 \quad (5.2)$$

$$(x_3 - X)^2 + (y_3 - Y)^2 + (z_3 - Z)^2 = c^2 (\Delta t_3 - \delta t)^2 \quad (5.3)$$

$$(x_4 - X)^2 + (y_4 - Y)^2 + (z_4 - Z)^2 = c^2 (\Delta t_4 - \delta t)^2 \quad (5.4)$$

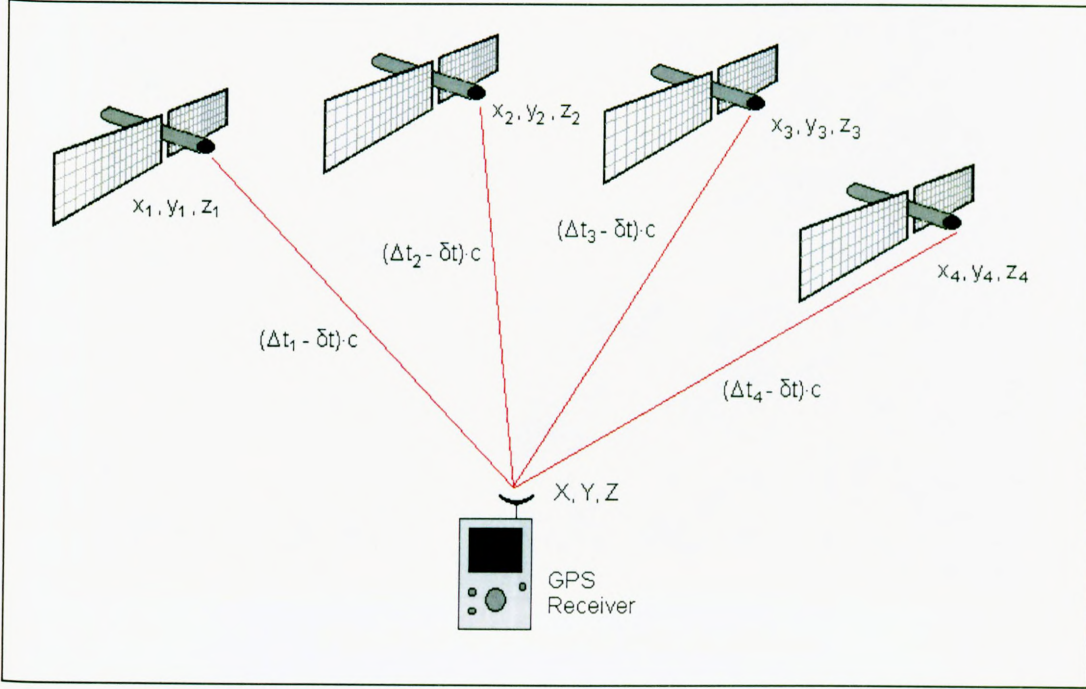


Figure 5.1: Calculating locations using GPS

Once the user's position has been determined [geodetic latitude (ϕ), longitude (λ) and altitude (h)], the GPS unit can calculate other information, such as speed, bearing, track, trip distance, distance to destination, sunrise and sunset times and more.

5.3 The Embedded GPS Receiver

This section deals with the use of an embedded GPS receiver, and the development of the appropriate hardware peripheral and software for its communication with the microcontroller of the electrochemical instrument.

5.3.1 Hardware Design

The Lassen SQ receiver[119] is ideal for this application because of its small size (2.5 x 2.5 cm), its low power consumption (100 mW at 3.3 V) and its compatibility with a

small compact antenna (2.5 x 2.5 cm). Fig. 5.2 shows the GPS receiver with the small compact antenna.

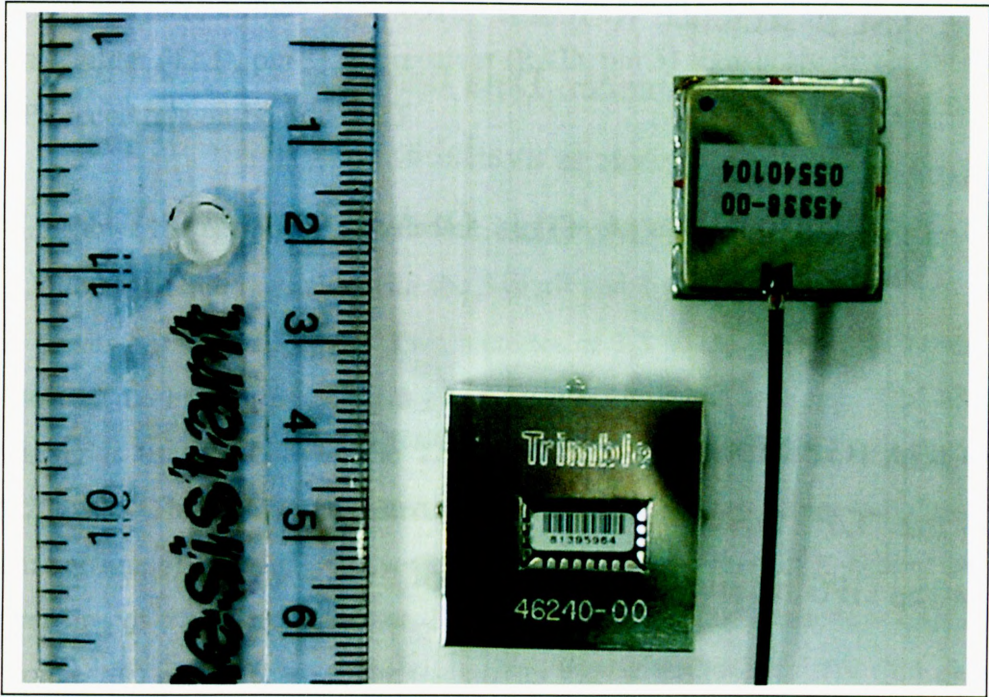


Figure 5.2: GPS receiver with the antenna

The receiver uses a single 8-pin (2 x 4) male header connector for both power and data I/O. The connector pin-out information is listed in table 5.1.

Table 5.1: GPS receiver’s connector signals

Pin number	Function	Description
1	TXD A	Serial data transmit
2	GND	Ground, power signal
3	RXD A	Serial data receive
4	PPS	Pulse-per-second
5	Reserve	Not connected
6	Reserve	Not connected
7	VCC (Prime Power)	+3.0 V to 3.3 V
8	Battery backup power	+2.5 V to +3.6 V

The receiver requires +3.3 V power supply which is supplied through pin 7 (VCC) of the I/O connector. A 3 V backup battery (supplied through pin 8) is used to keep the

module's RAM memory alive and to power the real-time clock when the receiver's prime power is turned off. The RAM memory is used to store the GPS almanac, ephemeris and last position. The receiver provides direct CMOS/TTL level serial I/O. The transmitter (TXD, pin 1) and receiver (RXD, pin 3) signals are driven directly by the GPS receiver's on-board UART.

Fig. 5.3 shows the peripheral circuit that was developed to support the GPS receiver. The LM7803 voltage regulator with the 330 nF and 1 μ F capacitors provides +3.0 V to the power primer (VCC pin). Two batteries of 1.5 V each connected in series are used to provide backup power (pin 8) to the internal RAM memory. The MAX232 line driver is used to convert the TXD and RXD CMOS/TTL level serial data to RS232 levels. The receiver is connected to a microcontroller via the serial port. The transmitter line of the GPS receiver (pin 2 of the D-9 connector) is connected to the receiver line of the microcontroller UART device and the receiver line (pin 3 of the D-9 connector) is connected to the transmitter line of the UART. The D-9 connector can also be used to connect the GPS unit with a PC using a serial RS232 (three-wire) cable. A datasheet with all technical information of the MAX232 line driver is given in Appendix D.12.

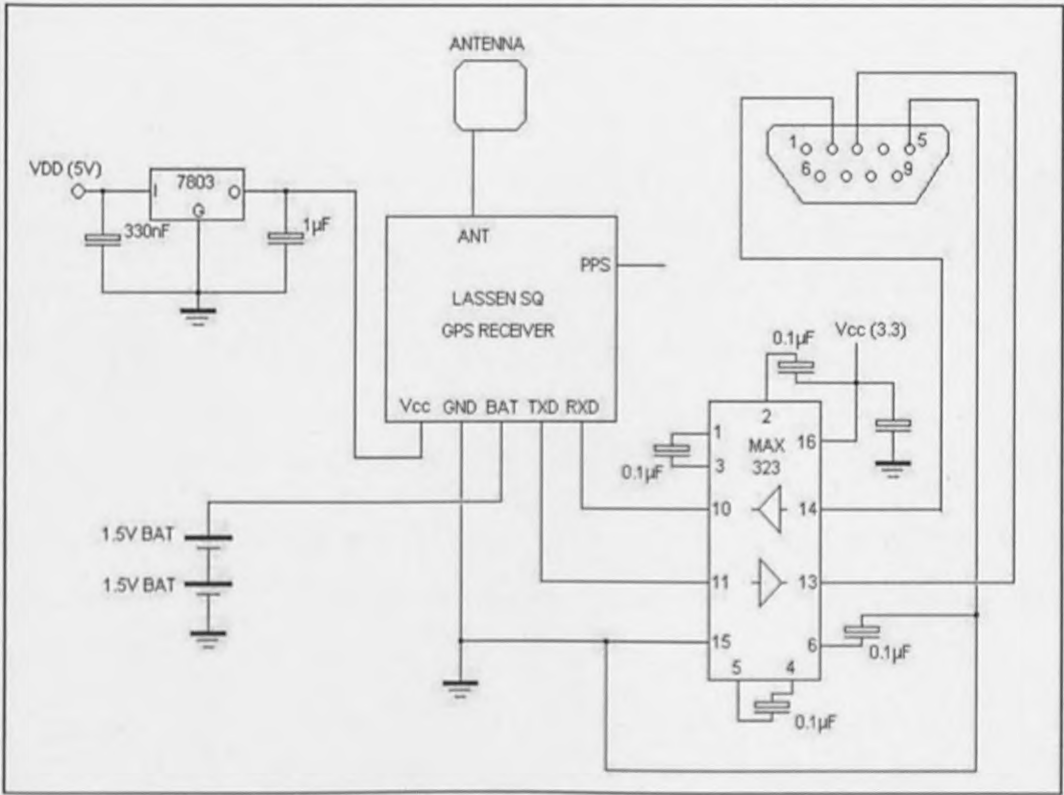


Figure 5.3: Circuit diagram of the graphical position system

5.3.2 Communication Protocol

The Lassen SQ GPS receiver uses the National Marine Electronics Association (NMEA 0183) protocol[119] which is an industry standard. NEMEA allows a single source to transmit serial data over a single twisted wire pair to one or more receivers. Table 5.2 lists the standard characteristics of the data transmission.

Table 5.2: NEMEA 0183 standard characteristics

Signal Characteristic	NEMEA Standard
Baud Rate	4800
Data bits	8
Parity	None
Stop bits	1

NMEA data is output in standard ASCII sentence format. Message identifiers are used to signify what data is contained in each sentence, with data fields being separated by commas. The Lassen SQ receiver is available with firmware that supports a subset of the NMEA 0183 messages: GGA, GLL, GSA, GSV, RMC, VTC and ZDA.

For the current application the GGA (GPS fix data) message is used. This message is sent at 1 second intervals with the “GP” talker ID and checksums and includes time, position and fix related data for the GPS receiver. The format of the GGA message is listed below:

`$GPGGA,time,latitude,longitude,quality,satellites,dilution,altitude,checksum`

The operation of the GPS receiver was examined using the HYPERTERMINAL monitor program. When the receiver was powered up the data displayed on the PC monitor was as listed below:

`$GPGGA,,,0,00,,,0`

After approximately 2 minutes the receiver was able to connect with four different satellites and was able to obtain its geographical position. The data displayed on the PC monitor was as listed below:

```
$GPGGA,122223.02,5708.560,N,00206.080,W,1,04,1.1,56.9,M,0238*0B
```

Software was developed for the microcontroller to read the GGA ASCII data of the GPS receiver and extract the latitude and longitude. Fig. 5.4 shows the algorithm of this process.

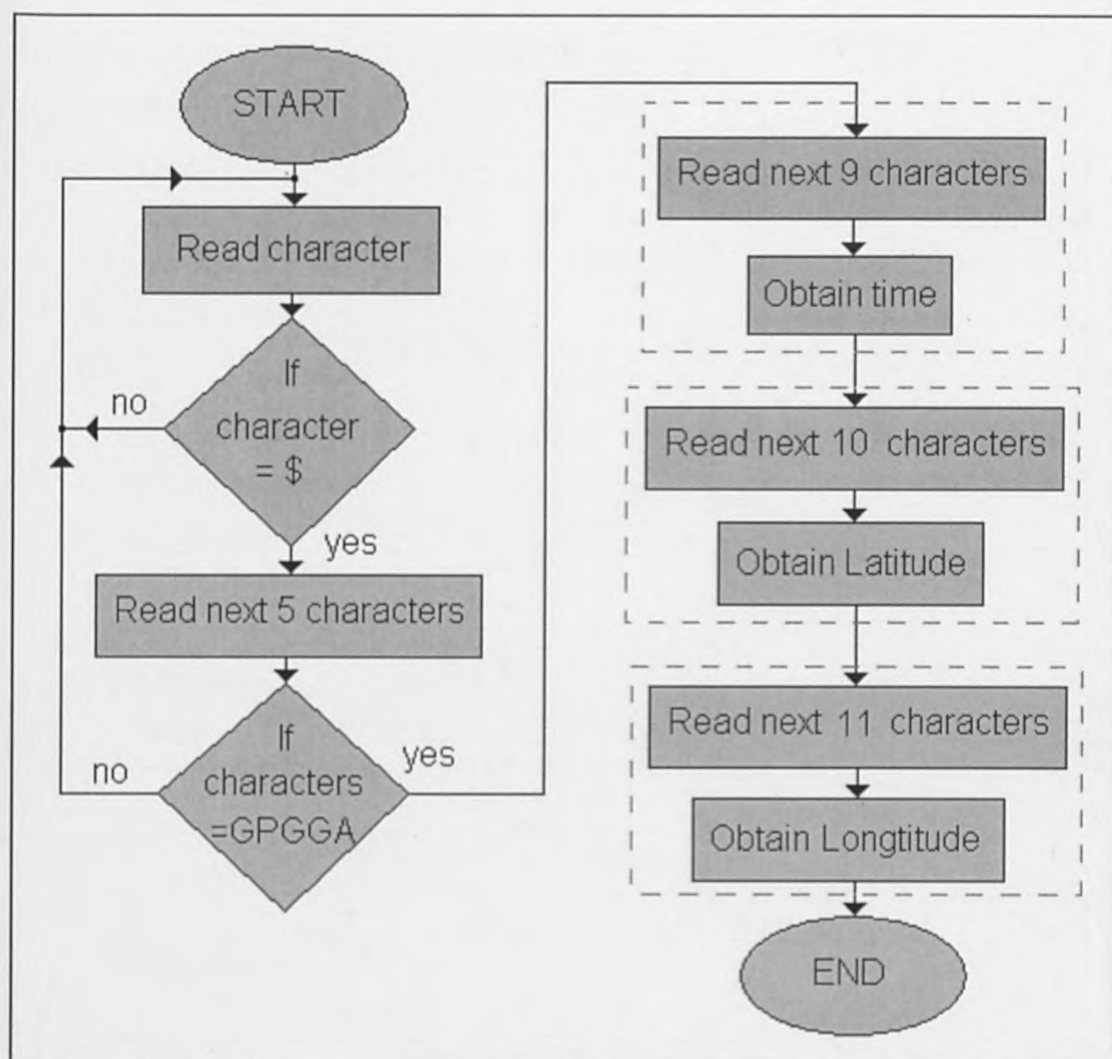


Figure 5.4: Extraction of latitude and longitude data from CGA message.

5.4 The Pollution-Mapping Software

This section deals with the development of the GIS software[120,121] to produce a map on which can be fixed sites of heavy metal pollution. The software combines the pollution results obtained by the analyser, the geographical position of the assessed sample and the map of the assessed area, so as to produce a cartographical presentation of the pollution of the area. The approach is shown in Fig. 5.5. This approach involves four main tasks as follows:

1. Map rasterising[122,123]
2. Correlation of rasterised map with GPS coordinates
3. Database of heavy metal pollution
4. Display of polluted area[124]

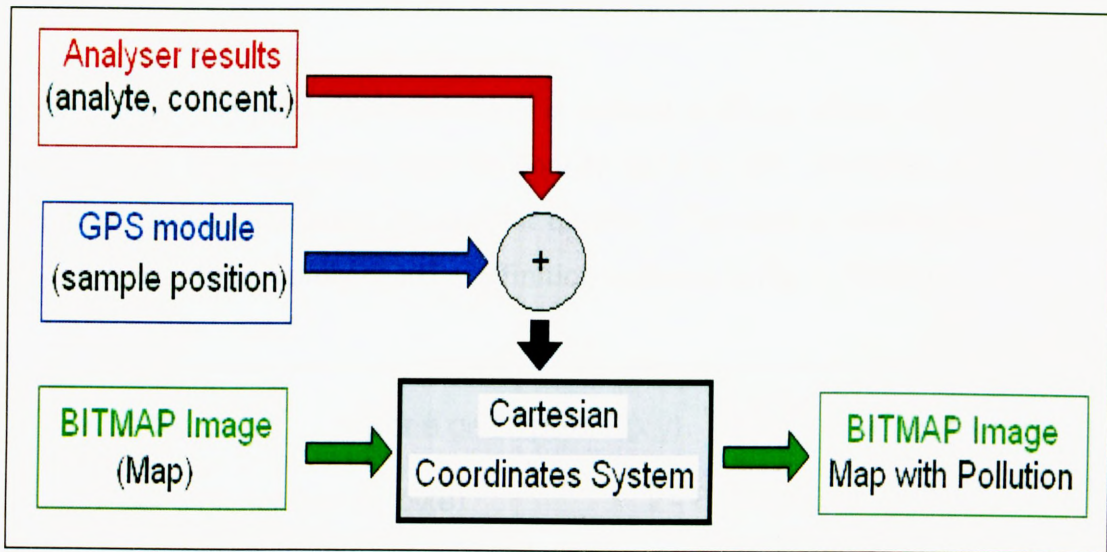


Figure 5.5: Pollution mapping - approach

5.4.1 Map Rasterising

The map of the area under investigation is digitised and stored as a bitmap file. The map in digital form is represented by a two-dimensional array (raster) of size $N \times M$ number of pixels (Fig. 5.6).

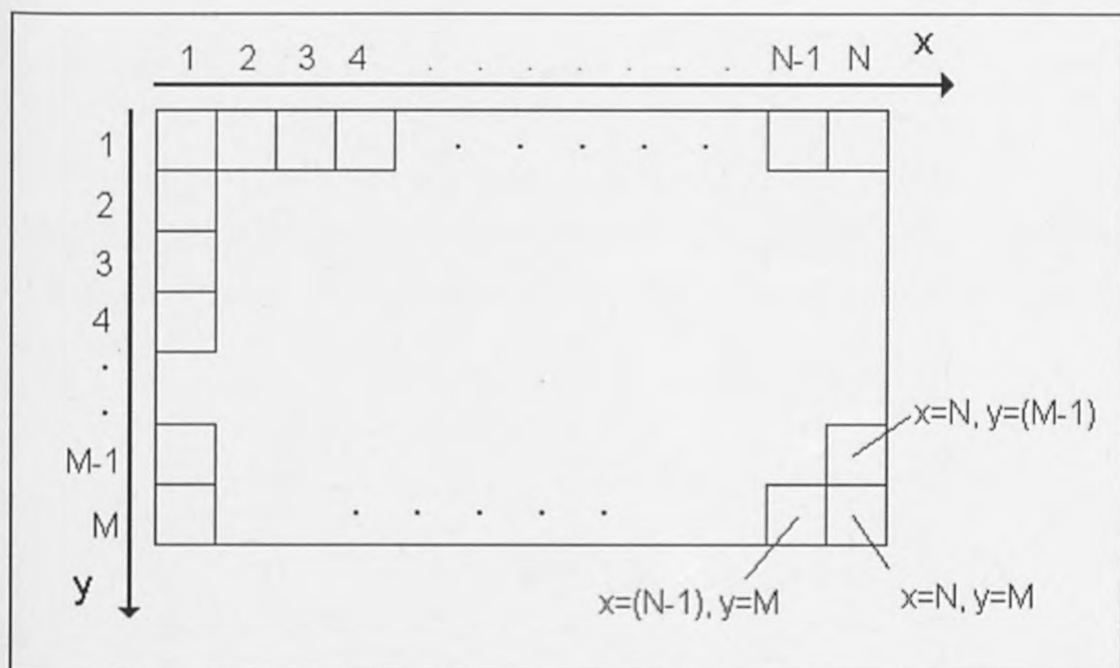


Figure 5.6: Digital image of $N \times M$ pixels

The position of a pixel (P) in the raster is defined as $(P_{x,y})$, where, $x=1,2,3...N$, and $y=1,2,3...M$. The maximum value for both M and N is 255. Therefore, both x and y numbers can be represented by an 8 bit number. The pixel's identification number (P_{ID}) is thus a 16 bit number and its definition is shown in Fig. 5.7 below:

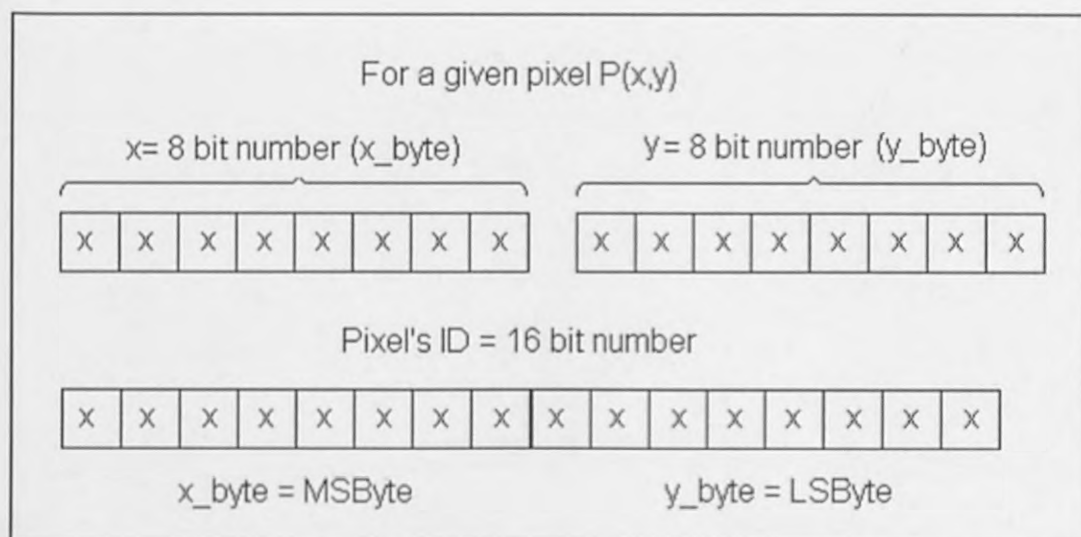


Figure 5.7: Pixel's ID number

This number is unique for every pixel in the image. The first pixel of the digital map is called base pixel P_B (where, $P_B = P(x, y)|_{x=1, y=1}$). The P_{ID} number of the base pixel is $257_{(10)}$ or $0101_{(hex)}$.

The graphic scale (F_s) of the digital map is defined as the ratio of a distance on the displayed map (A_M) to the corresponding distance on the ground (A_v). The graphical size of a pixel (R_{xy}) is defined by the number of pixels of the image ($N \times M$) over A_v (Fig. 5.8).

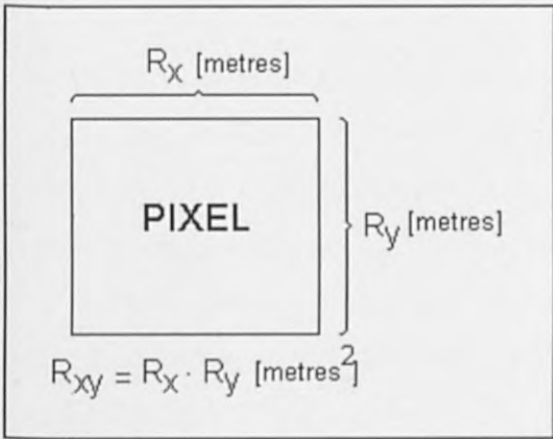


Figure 5.8: Pixel's virtual size in metres

5.4.2 Correlation of Rasterised Map with the GPS Coordinates

When a test is carried out in the field, the GPS receiver will obtain the geographical position (latitude and longitude) of the assessed sample. The differential latitude ($\Delta\phi$) and differential longitude ($\Delta\lambda$) are obtained from equations 5.8(a) and (b), thus:

$$\Delta\phi = \phi_s - \phi_o \tag{5.8a}$$

$$\Delta\lambda = \lambda_s - \lambda_o \tag{5.8b}$$

Where, ϕ_s is the latitude of the sample, ϕ_o is the latitude of the base pixel, λ_s is the longitude of the sample, and λ_o is the longitude of the base pixel.

The position (x, y) of the pixel $P(x, y)$ in the digital map related to the geographical position obtained by the GPS unit, can be calculated thus:

$$x = \Delta x' [m] / R_x [m]$$

(5.9a)

$$y = \Delta y' [m] / R_y [m]$$

(5.9b)

Where, $\Delta x'$ and $\Delta y'$ are the $\Delta \lambda$ and $\Delta \phi$ values in metres, and R_x and R_y define the geographical size of the pixel as shown in Fig. 5.8. By calculating the x and y co-ordinates of the pixel, its identification number P_{ID} can be obtained (Fig. 5.7).

5.4.3 Database of Heavy Metal Pollution

When a pixel of the digital map (consistent with GPS data) has been identified and its P_{ID} number is known, the user can add all appropriate heavy metal pollution-related information of this geographical point by referring it to the pixel's P_{ID} number. Table 5.3 shows the heavy metal pollution (database) created for an area under assessment. The database at the present stage has 12 fields, six for each metal and six for their concentration state. In future more fields can be added in the database for storing more information.

Table 5.3: Database of an assessed area.

Pixel ID	Pb	Con. [ppm]	Cd	Con. [ppm]	Zn	Con. [ppm]	Hg	Con. [ppm]	Ni	Con. [ppm]	Cu	Con. [ppm]
0112 _(hex)	yes	12	no	0	no	0	No	0	no	0	no	0
0113 _(hex)	yes	14	no	0	no	0	No	0	no	0	no	0
0114 _(hex)	yes	15	no	0	no	0	No	0	no	0	no	0
0115 _(hex)	yes	14	no	0	no	0	No	0	no	0	no	0

5.4.4 Display of Polluted Area

The user using the database is able to plot the map of the assessed area and to display any information from the database. For example, a map might show the presence of lead pollutant with green colour (dark green low concentration, light green high concentration), and the presence of other heavy metals with other colour scales.

Fig. 5.9 shows an example of a cartographical mapping of heavy metal pollution of an assessed area (Aberdeen centre, Robert Gordon University). The green colour represents “NO” pollution and the black colour is pollution. As can be seen from this figure there is no heavy metal pollution in the database therefore there is no black area visible on the map.



Figure 5.9: Example of a cartographical mapping of heavy metal pollution of an area under test.

Chapter Six

Measurements

6.1 Introduction

This section deals with test analyses of soil and aqueous samples. The investigations were carried out using the portable analyser and the two different (glassy carbon and screen printed) electrochemical sensors with their new supporting plastic cartridges. All sample tests were carried out in the laboratory in ideal conditions.

6.2 Procedure for Analysing Soil and Aquatic Samples

Analysis Approach for Aquatic Samples

Fig. 6.1 illustrates the steps used for the analysis of aqueous samples. The analysis process consists of two phases, namely, sample pre-treatment and sample analysis.

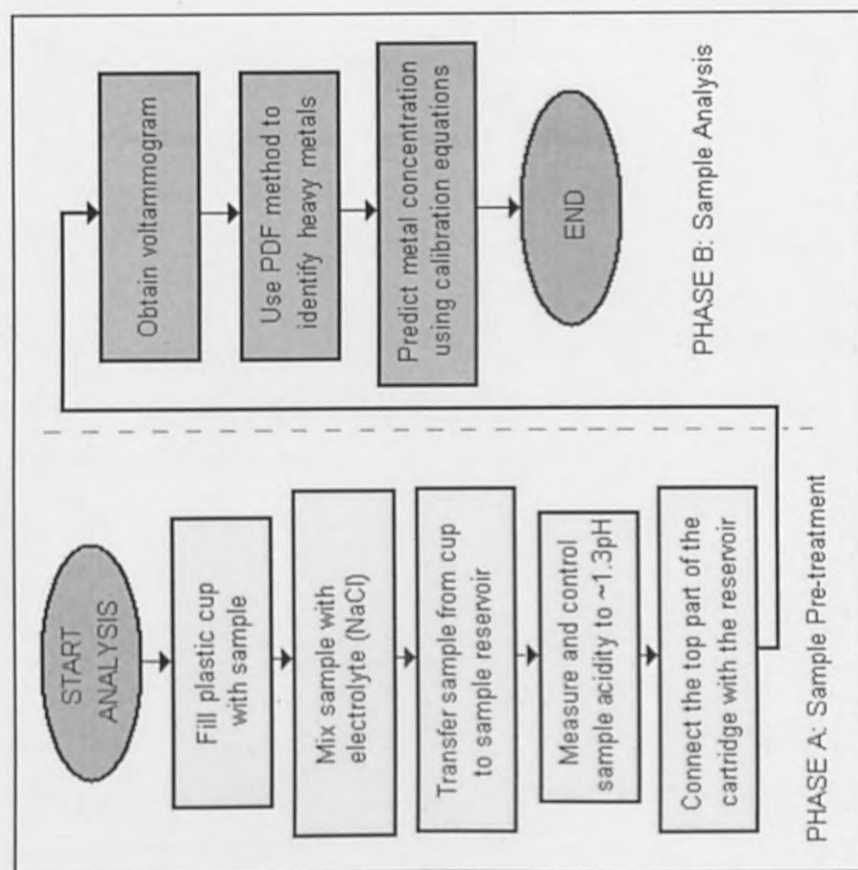


Figure 6.1: Steps in the analysis of aqueous sample

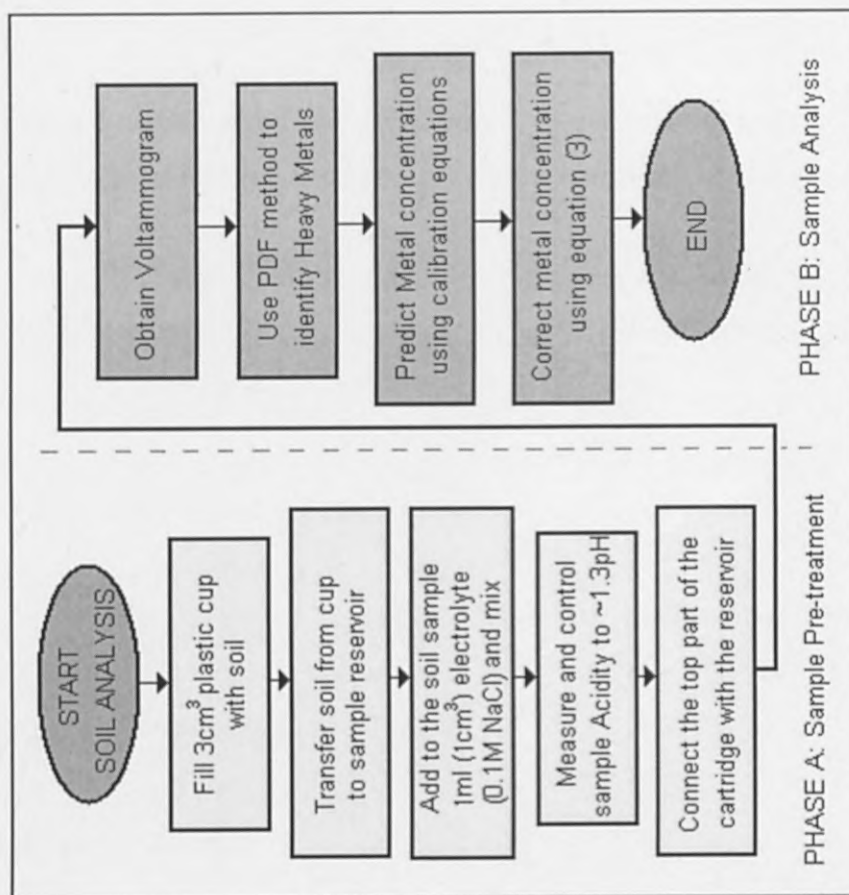


Figure 6.2: Steps in the analysis of a soil sample

Fig. 6.2 illustrates the steps used for the analysis of soil samples. The analysis process consists of two phases, namely, sample pre-treatment and sample analysis.

Using the procedure shown in Fig. 6.2 for soil analysis, the concentrations of metals will be changed (diluted) with the extra addition of supporting electrolyte by a factor C_e , such as:

$$C_e = V_{\text{sample}} / (V_{\text{sample}} + V_{\text{electrolyte}}) \quad (6.1)$$

Where, V_{sample} is the volume of the soil sample in cm^3 and $V_{\text{electrolyte}}$ is the volume of the electrolyte in cm^3 . Therefore, in order to predict the real concentration of metals a correction equation needs to be used such as:

$$C_M' = C_M \times (1 / C_e) \quad (6.2)$$

where, C_M' is the corrected metal concentration, and C_M is the concentration of a metal (M) obtain by the system before correction.

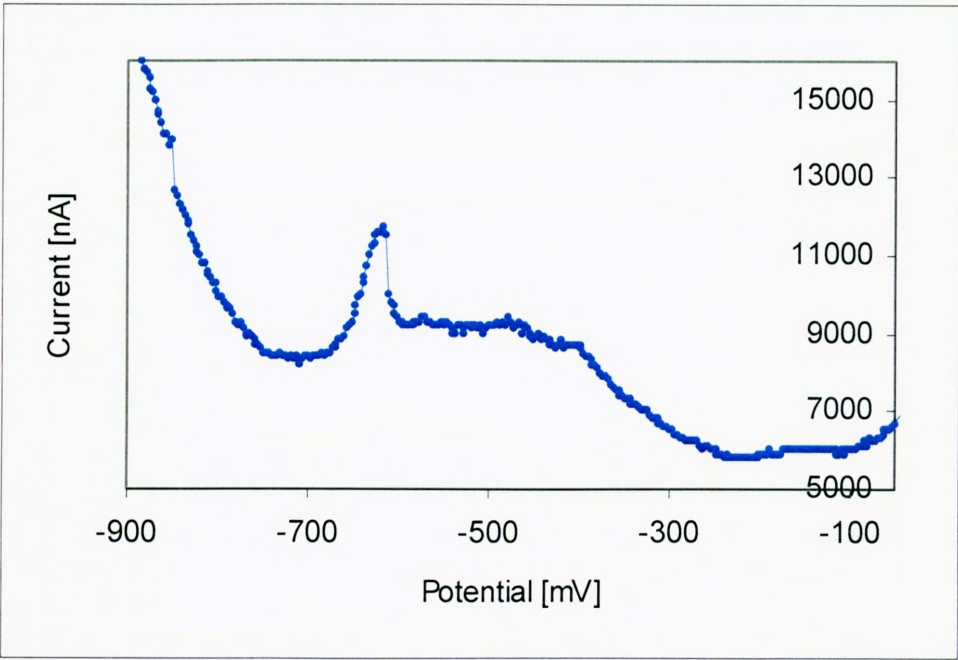
6.3 Analysis of Aqueous Samples

Test solutions of lead, cadmium, zinc, copper, nickel and mercury were prepared at different concentration levels in the range of 250 ppb to 50 ppm. The six ions selected for examination were chosen due to their importance as environmental pollutants. These solutions were diluted from a commercially available standard solution (1000 ppm in 1 M Nitric Acid). The solutions were prepared using de-ionised water with a supporting electrolyte of 0.1 M sodium chloride (NaCl). The pre-concentration (deposition) time was 60sec at -1400 mV potential. The scanning voltage range used was from -1400 to +1000 mV, with step potential of 2 mV, pulse height of 25 mV, with a scan rate of 120 ms and pulse duration of 50 ms. The acidity for test samples was 1.35 pH.

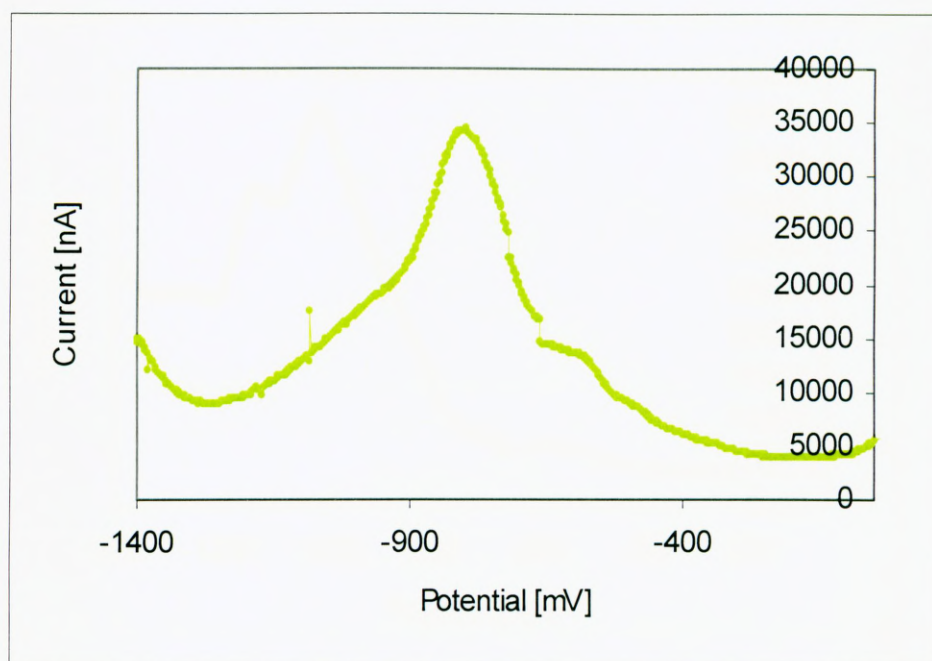
Thirty two independent measurements of the electrical potential and peak amplitude of all six metals were recorded. The instrument was also connected to a personal computer, and the results were monitored for comparison with the values obtained from the liquid-crystal display. This procedure was carried out using both the glassy carbon and screen printed electrochemical sensors.

6.3.1 Sensitivity

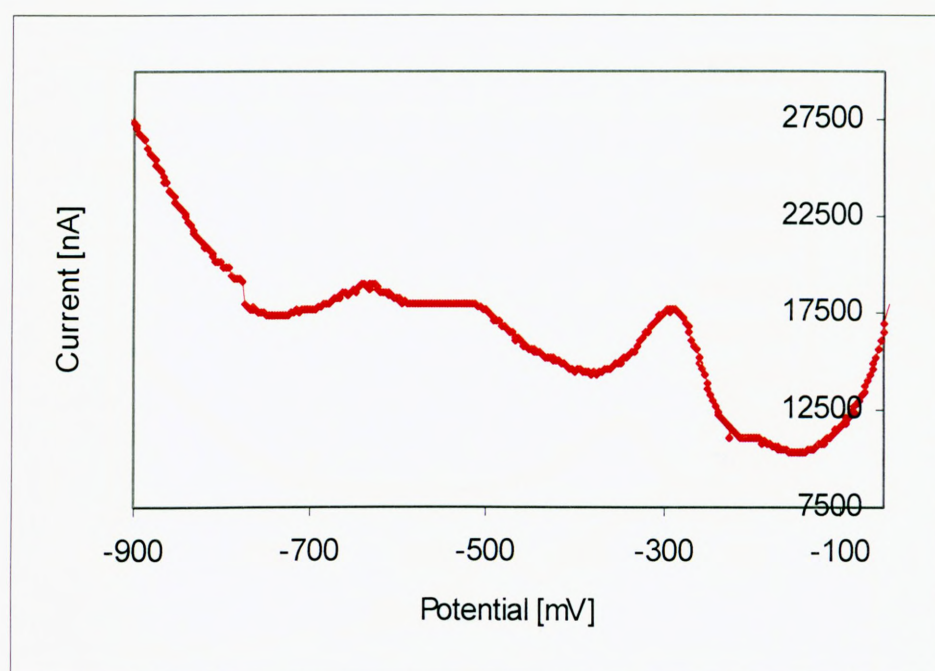
It was found that the lowest possible concentrations of metals that can be detected by the instrument using the screen printed sensor are 1 ppm for Lead(II), 1 ppm for Cadmium(II), 3 ppm for Zinc(II), 1 ppm for Copper(II), 2 ppm for Nickel(II) and 3 ppm for Mercury(II). Fig. 6.3 shows the differential-current voltammogram using the screen printed sensor for each of the above metals at their lower detectable concentration level.



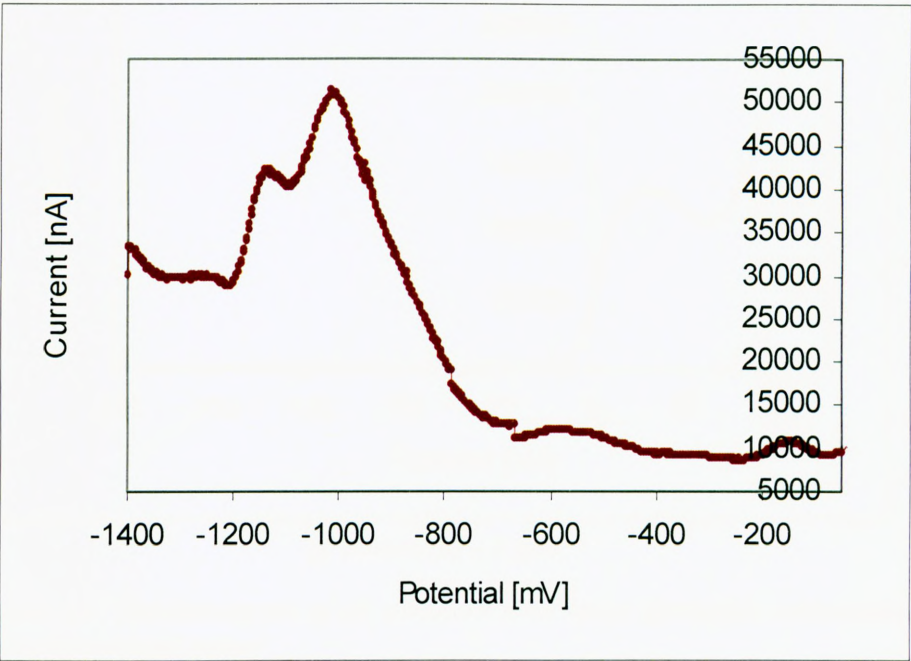
(a) Lead(II) – 1 ppm



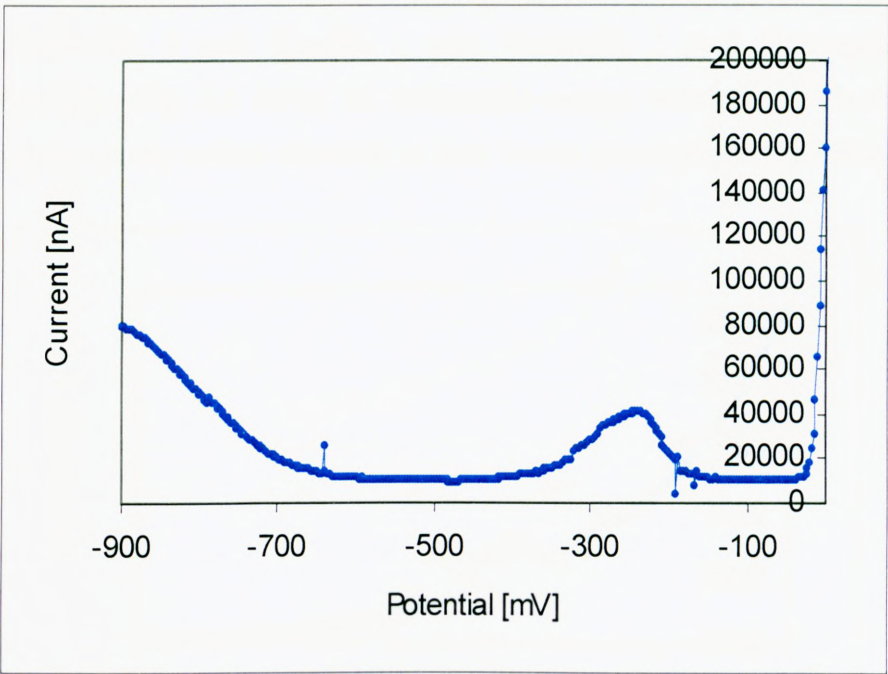
(b) Cadmium(II) – 2 ppm



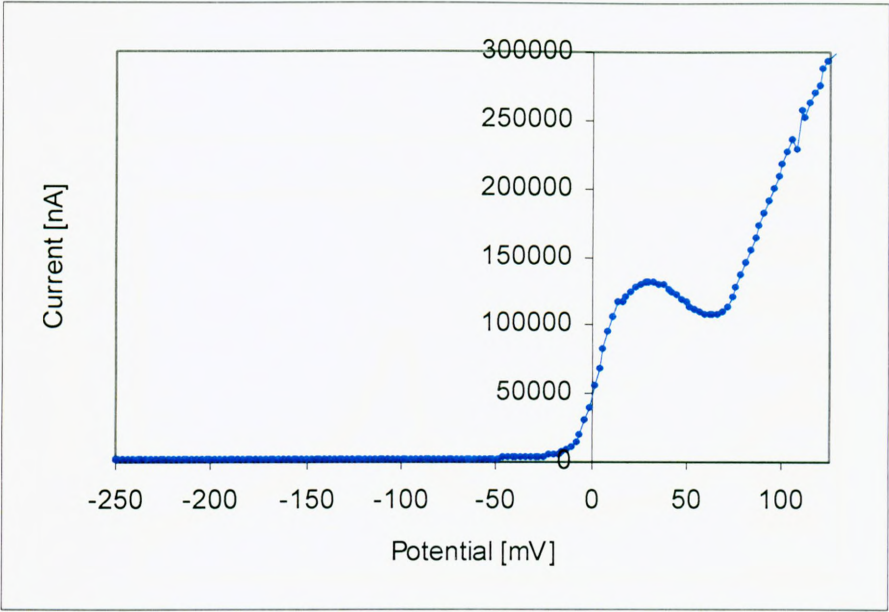
(c) Copper (II) – 1 ppm



(d) Zinc(II) – 3 ppm



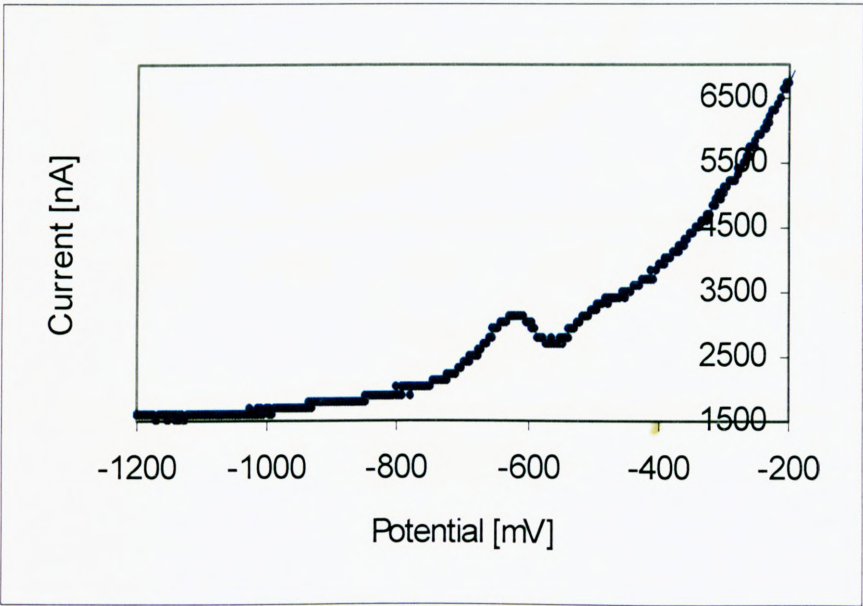
(e) Nickel(II) – 2 ppm



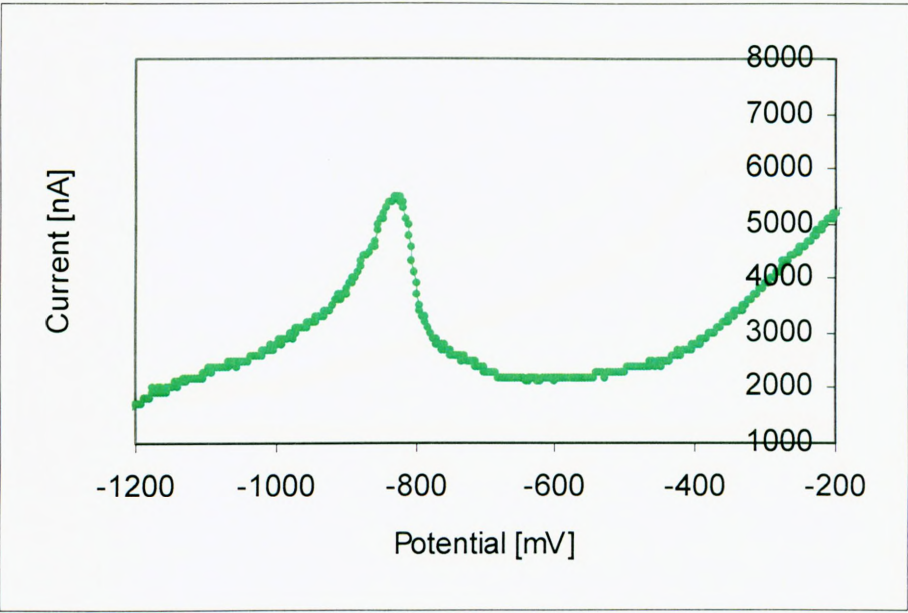
(f) Mercury(II) – 3 ppm

Figure 6.3: Voltammogram of six metals at their lower detectable concentration level using the screen printed sensor

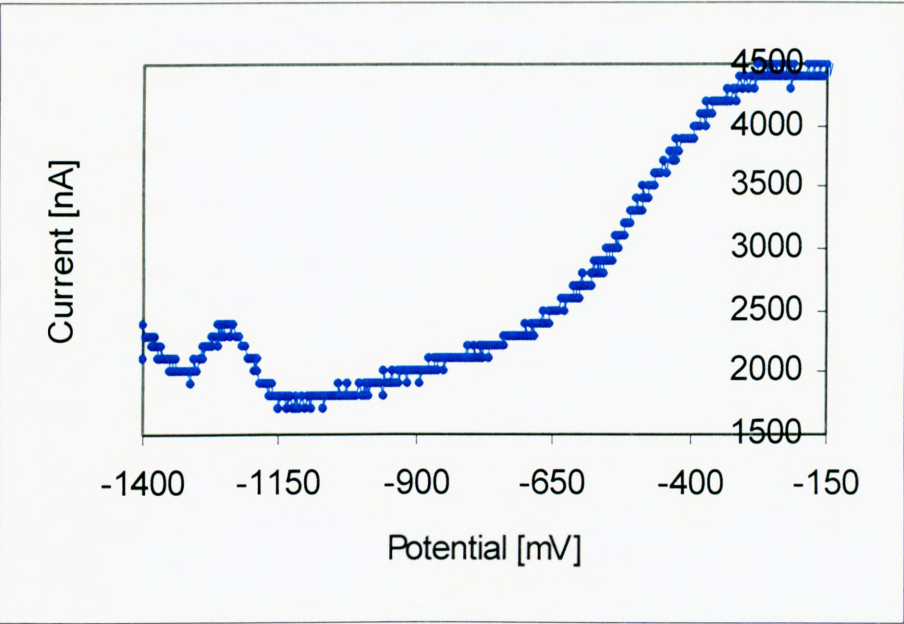
It was found that the lower possible concentrations of metals that can be detected by the instrument using the glassy carbon electrode are 500 ppb for Lead(II), 750 ppb Cadmium(II), 2 ppm Zinc(II), 1 ppm Nickel(II), 2 ppm Mercury(II) and 2 ppm Copper(II). Fig. 6.4 shows the differential-current voltammograms of all six metals using the glassy carbon electrode at their lowest possible detectable concentration.



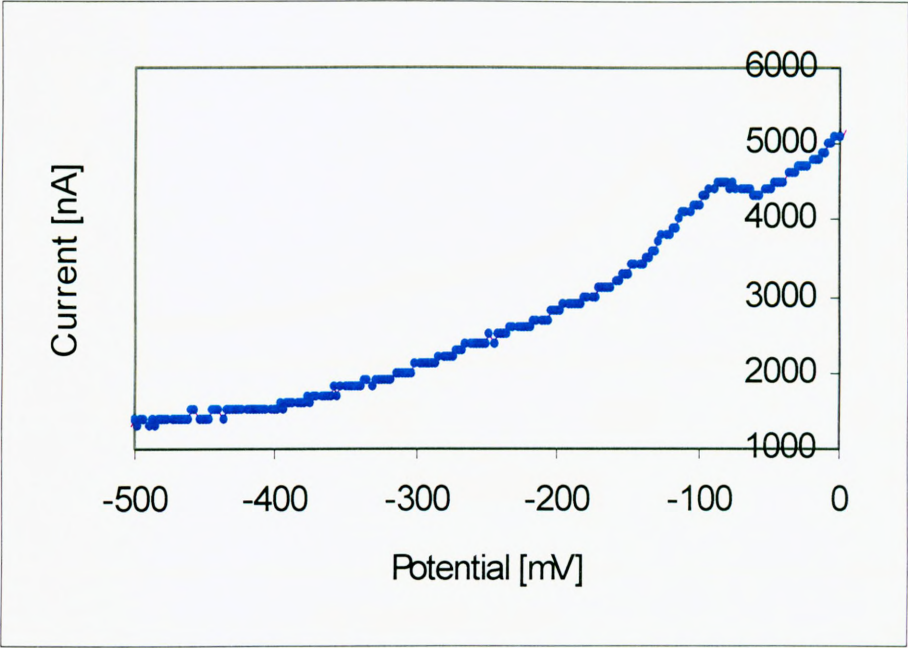
(a) Lead(II) – 500 ppb



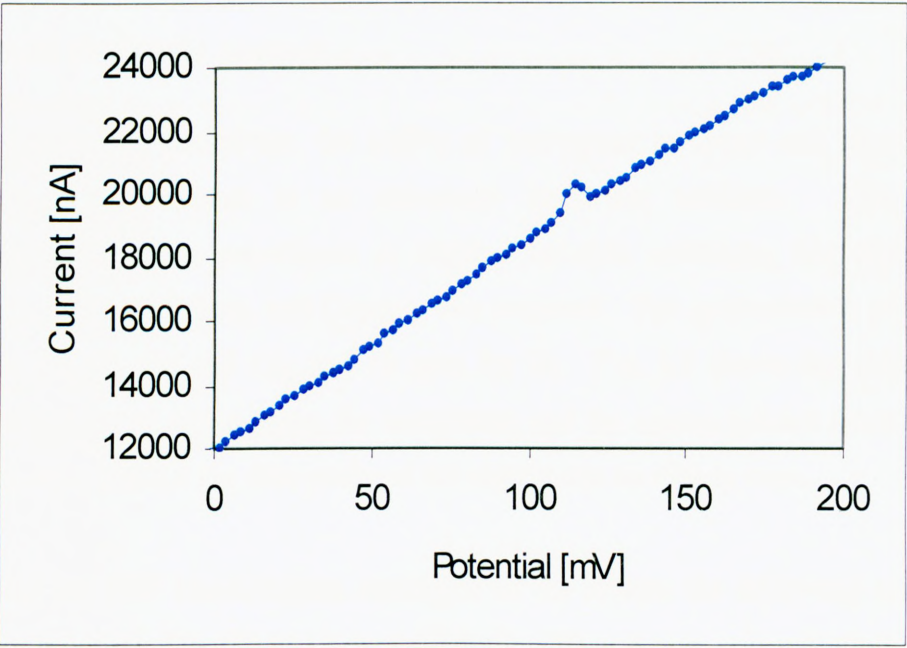
(b) Cadmium(II) – 750 ppb



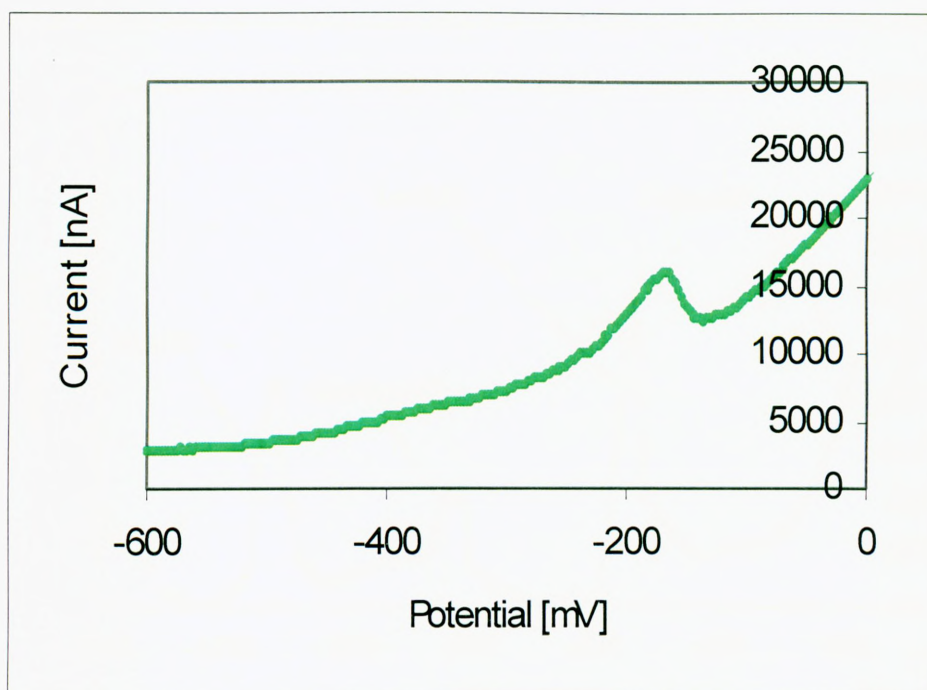
(c) Zinc(II) – 2 ppm



(d) Nickel(II) – 1 ppm



(e) Mercury(II) – 2 ppm



(b) Copper(II) – 2 ppm

Figure 6.4: Differential-current voltammogram of six metals at lower possible detectable concentration using the glassy carbon sensor

6.3.2 Multi-Metal Analysis

In addition to sensitivity, the ability of instrument to detect and identify metals in multi-metal mixtures is an extremely important attribute. This ability was investigated in an experiment in which a solution containing four different metals, Zinc, Lead, Cadmium, and Copper, was prepared. The concentration of metals was 5 ppm for *Pb*, *Cd* and *Cu*, and 10 ppm for *Zn*. Fig. 6.5 shows the differential pulse voltammogram taken using the instrument and the screen printed sensor. As can be seen from Fig.6.5 the four peaks of the metals can be clearly seen.

Using the PDF identification algorithm of the system the following results (metals) were reported: Zinc(II) at 12 ppm, Cadmium(II) at 4 ppm concentration, Lead(II) at 6 ppm concentration and Copper(II) at 3 ppm concentration. The four metals have been easily identified by the instrument and their concentration has been obtained with maximum error of 2 ppm.

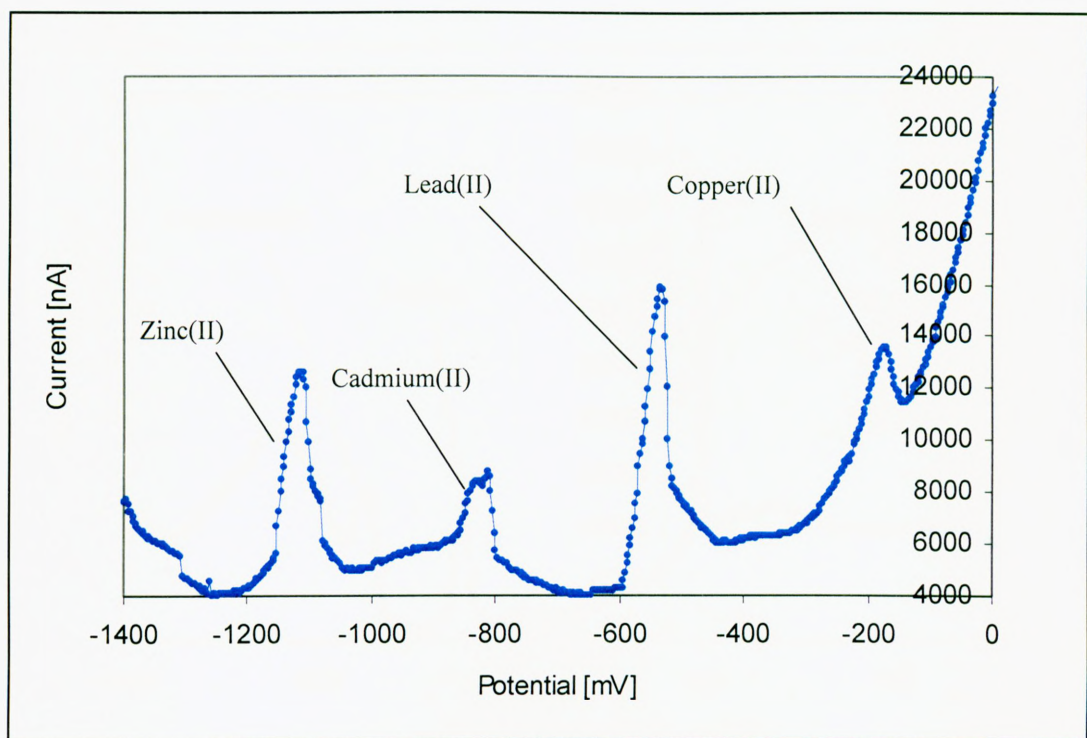


Figure 6.5: Voltammogram for a solution with a multi-metal mixture containing Lead, Cadmium, Copper at 5 ppm and Zinc at 10 ppm.

Another solution was prepared, containing three different metals, Lead, Cadmium, and Mercury. The concentration of all three metals was 10 ppm. Fig. 6.6 shows the differential pulse voltammogram obtained using the instrument and the glassy carbon electrode. As can be seen from the figure, a peak corresponding to each of the three metals can be clearly seen. Using the system’s PDF identification algorithm, the following results were reported: Cadmium(II) at 12 ppm concentration, Lead(II) at 7 ppm concentration and Mercury(II) at 13 ppm concentration. In summary, it was found that the three metals were clearly identified by the instrument and their concentrations were reported with a maximum error of 3 ppm.

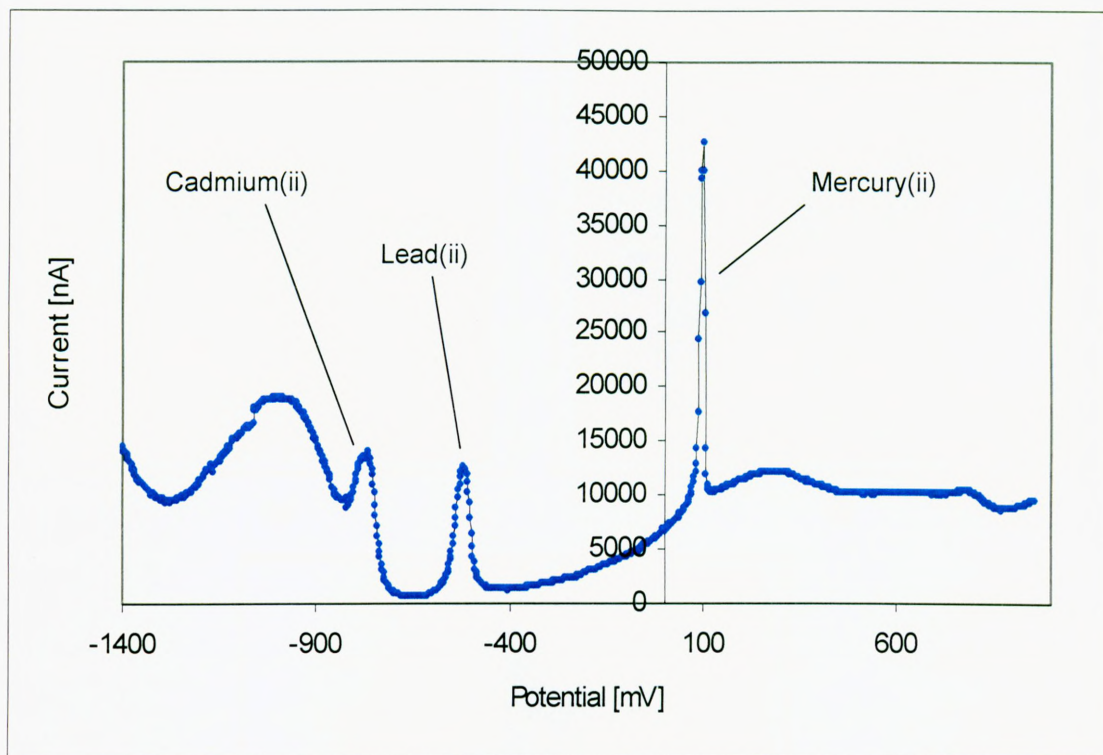


Figure 6.6: Differential pulse voltammogram for a solution with a multi-metal mixture containing Cadmium, Lead and Mercury at 10 ppm

6.4 Analysis of Soil Samples

6.4.1 Preparation of Soil Samples

Three 10 ml metal solutions of lead, cadmium, and zinc were prepared at concentrations of 30 ppm [Fig. 6.7(a)]. The solutions were made up using de-ionised water and standard metal solutions. The supporting electrolyte was 0.1 M sodium chloride ($NaCl$). 10 cm³ of clear sand was added to each of the three different bottles of metal solutions. The aqueous solution and sand in each bottle were mixed well [Fig. 6.7(b)], and then left to dry as shown in Fig. 6.7(c).

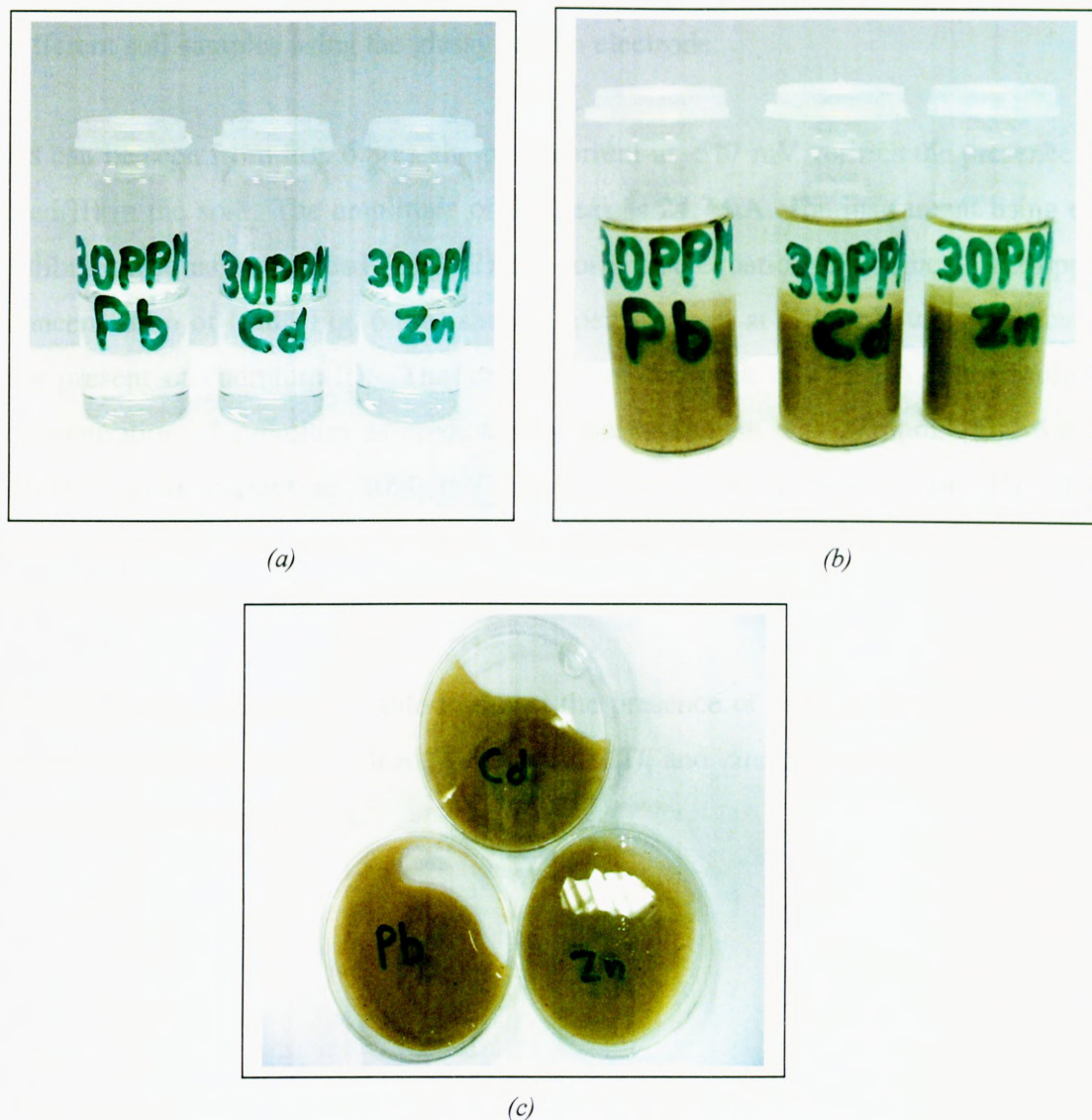


Figure 6.7: (a) Three 10 ml aqueous solutions of 30 ppm lead, cadmium and zinc, (b) aqueous solutions mixed with clear sand, (c) dried soil samples.

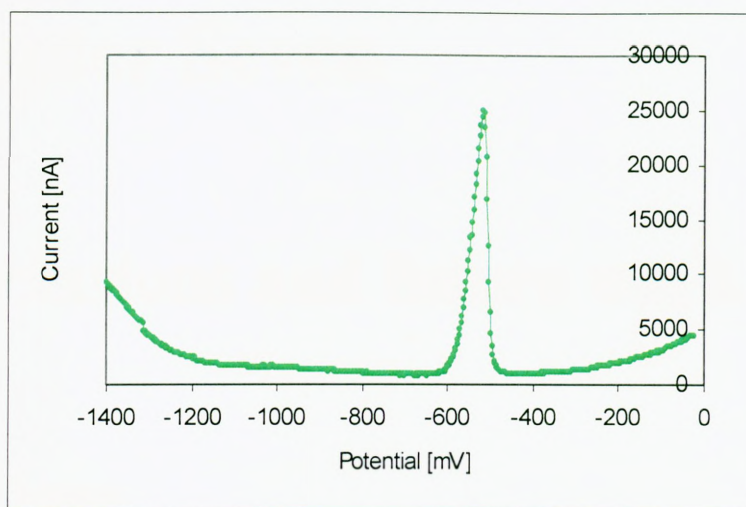
6.4.2 Analysis

3 cm³ volume of the first soil sample (lead) was measured by using a 3 cm³ plastic cup and transferred to the sample reservoir. 1 ml (1 cm³) of 0.1 M NaCl electrolyte was then added and mixed with the sample in the reservoir. The acidity of the sample was controlled to approximately 1.35 pH by adding a few drops of 1M nitric acid. The pre-concentration time used for the analysis was 60 sec and the scanning voltage was in the range -1400 to +1000 mV. The same process was repeated for sample two (cadmium) and three (zinc).

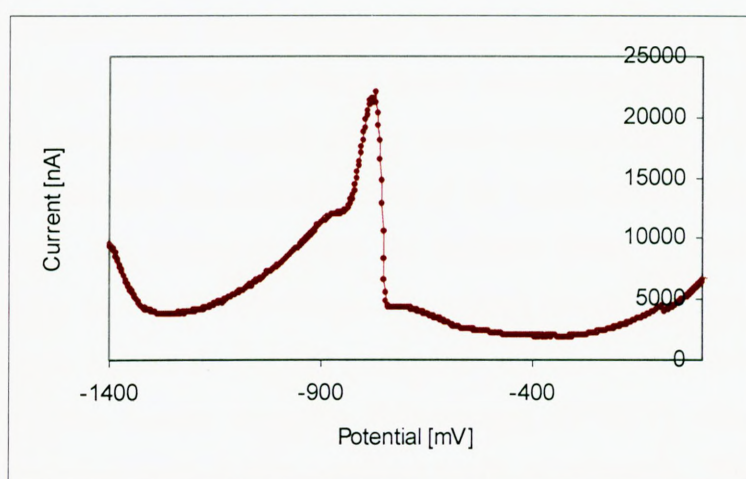
Fig. 6.8 (a),(b) and (c) shows the voltammograms from the analysis of the three different soil samples using the glassy carbon electrode.

As can be seen from Fig. 6.8(a), the peak current at -517 mV verifies the presence of lead(II) in the soil. The amplitude of the peak is 24.7 μ A. The instrument using the calibration equation for lead (Table 2) and correction equation (3) predicted a 26 ppm concentration of lead. Fig. 6.8(b) shows a peak current at -774 mV which indicates the present of cadmium(II). The amplitude of the peak is 21.2 μ A. The resultant concentration of cadmium as predicted by the instrument was 27 ppm. Fig. 6.8(c) shows a peak current at -1090 mV which indicates the present of zinc(II). The amplitude of the zinc peak is 11.3 μ A. The resultant concentration of zinc as predicted by the instrument was 27 ppm.

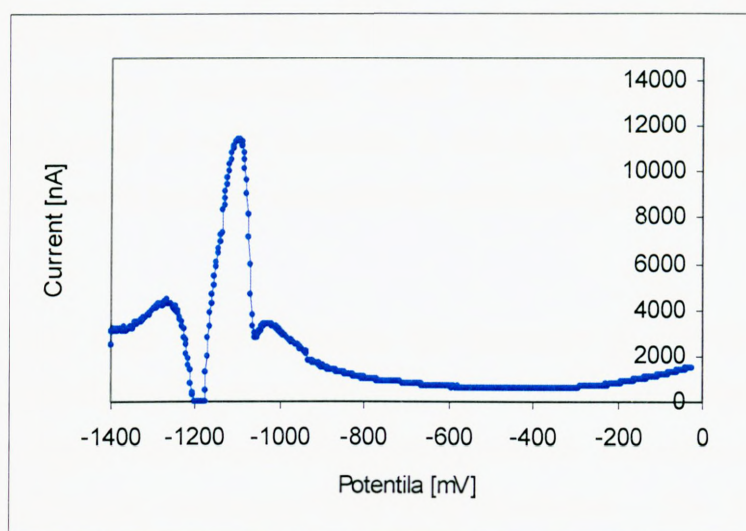
Therefore, the analyser was able to detect the presence of each of the three different metals in the soil samples [lead(II), cadmium(II), and zinc(II)] and also was able to predict their concentrations.



(a) Lead



(b) Cadmium



(c) Zinc

Figure 6.8: Voltammograms from the three different soil samples using the glassy carbon electrode.

Chapter Seven

Conclusions and future work

7.1 Conclusions

A portable (hand-held) electrochemical instrument capable of gathering real-time quantitative data on a range of heavy metal contaminants has been developed. The unit is being developed to identify heavy metals contamination of land or water and is also able to determine the oxidation state of the target metals, which is a measure of their toxicity. The system provides the facilities found in a traditional lab based instrument, but in a hand held design. In contrast to existing commercial systems, it can stand alone without the need of a computer and expert operators. The system uses Differential Pulse Anodic Stripping Voltammetry (DPASV) which is a precise and sensitive analytical method with excellent limits of detection. The sensor (cell) uses solid (screen-printed and glassy carbon) working electrodes rather than the more common Hanging Mercury Drop Electrodes (HMDE) which are used by most traditional laboratory instruments. Apart from the size and cost difference, an important advantage of solid electrodes is that they do not require the use of toxic mercury. This work has been submitted for publication[125].

At the present stage of development, the instrument is capable of detecting and identifying six different toxic environmental pollutants, lead, cadmium, mercury, zinc, nickel and copper, with good sensitivity and precision. Two different microprocessor-based identification techniques have been developed. The first identification technique is based on statistical information (Probability Density Function) of oxidation potentials of the above six metals. When an actual test is carried out, the oxidation potential E_p is assessed and examined against a PDF to determine the probability of membership of that analyte with all analytes stored in a database of

PDF measurements. The analyte representing the highest probability of likeliness is thus identified. Analytes identified in this way are automatically given a probability of likeliness, indicating the prediction accuracy. A database has been created from practical measurements which contains statistical information of the six different heavy metals. At present there are two sets of data, one set using the glassy carbon electrode and a second set using the screen printed sensor. This work has been submitted for publication[126].

The second identification technique is based on an intelligent machine-based-method using a multi-layer perceptron neural network consisting of three layers of neurons. The artificial neural network was implemented using a 16-bit microcontroller and was trained to identify the six different metals. The probability of classification was very good (100%) for lead, cadmium, zinc and mercury. For copper and nickel was 92% and 89% respectively. This work has been published[127,128].

The instrument with the combination of a Geographical Position System (GPS) is capable of storing the geographical position of the sample under test. Software has been developed to combine pollutant results with geographical position, in order to produce a cartographical presentation of the pollution of an area. The instrument's capability of detecting metals in multi-element solutions and in soil samples has also been examined, demonstrating good results. This work has been published[129].

Finally, other parts of this research have been submitted for publication to various peer reviewed journals[130,131]. All aspects of the research have been patented[132].

7.2 Future work

At present, the instrument has been used successfully to analyse both soil and aqueous samples in laboratory conditions. The next stage of this project is the use of the instrument in the field. This will require some further development of the sampling chamber and further miniaturisation of the instrument for in situ usage.

The instrument will be taken to various contaminated places in order to assess its capability to detect and to identify different types of heavy metals, in situ. At that stage the instrument (hardware and software) and the sensor cartridge will be in their final form. Therefore, the final clarifications and additions to the patent application will be made at that point.

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Appendix A: Tables with Results

A.1. Peak current amplitude and oxidation potential, for lead(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	1	3.10	-592
02	1	4.65	-558
03	1	3.80	-553
04	1	3.50	-568
05	1	2.70	-568
06	2.5	6.68	-546
07	2.5	7.20	-529
08	2.5	7.25	-524
09	2.5	7.93	-537
10	2.5	7.12	-525
11	5	10.48	-522
12	5	10.15	-516
13	5	12.19	-523
14	5	15.55	-528
15	5	12.75	-527
16	10	17.70	-524
17	10	19.52	-517
18	10	21.70	-518
19	10	20.00	-522
20	10	20.38	-526
21	50	49.35	-516
22	50	51.01	-519
23	50	47.52	-502
24	50	44.72	-504
25	50	62.18	-502
26	100	98.53	-509
27	100	100.89	-505
28	100	110.65	-487
29	100	92.32	-482
30	100	93.45	-490
31	100	102.21	-487
32	100	108.87	-486

A.2. Peak current amplitude and oxidation potential, for cadmium(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	2.5	3.6	-768
02	2.5	3.4	-768
03	2.5	2.5	-770
04	2.5	3	-779
05	2.5	2.5	-775
06	2.5	3.9	-773
07	2.5	6.1	-769
08	5	8.02	-762
09	5	6.05	-763
10	5	5.48	-759
11	5	8.55	-760
12	5	6.9	-751
13	5	8.23	-758
14	5	8.91	-755
15	30	32.1	-741
16	30	20.6	-746
17	30	22.7	-732
18	30	25.5	-742
19	30	28.15	-739
20	30	26.45	-725
21	30	25.34	-732
22	50	51.2	-712
23	50	59.8	-703
24	50	43.5	-708
25	50	45.63	-712
26	50	56.82	-715
27	50	51.6	-720
28	50	49.3	-709
29	100	105.72	-722
30	100	101.28	-720
31	100	98.3	-710
32	100	94.7	-711

A.3. Peak current amplitude and oxidation potential, for zinc(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	10	4.4	-1002
02	10	4.9	-1005
03	10	3.5	-1009
04	10	7.2	-980
05	10	7.18	-1007
06	10	4	-1024
07	10	3.9	-1019
08	25	14.25	-1012
09	25	12	-1019
10	25	9.02	-1012
11	25	6.75	-1019
12	25	7.3	-1022
13	25	13.11	-1022
14	25	7.9	-1029
15	50	40.43	-1004
16	50	40.2	-1007
17	50	38.75	-1024
18	50	41.3	-1019
19	50	40.1	-1012
20	50	39.01	-1019
21	50	41.4	-1024
22	50	39.33	-1019
23	50	40.72	-1017
24	100	85.05	-1022
25	100	71.03	-1031
26	100	77.7	-1019
27	100	92.32	-1034
28	100	80.45	-1041
29	100	84.2	-1032
30	100	78.02	-1048
31	100	72.01	-1034
32	100	91.5	-1034

A.4. Peak current amplitude and oxidation potential, for mercury(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	5	29.17	120
02	5	29.65	122
03	5	29.42	128
04	5	29.12	132
05	5	29.34	129
06	5	29.23	131
07	5	29.52	129
08	5	29.49	130
09	5	29.12	132
10	10	39.67	118
11	10	35.45	127
12	10	40.53	132
13	10	33.24	134
14	10	38.11	128
15	10	39.09	136
16	10	42.34	129
17	10	32.03	129
18	10	37.42	130
19	30	60.78	132
20	30	51.55	137
21	30	74.02	128
22	30	65.87	133
23	30	63.12	128
24	30	60.02	132
25	50	95.54	105
26	50	88.34	88
27	50	104.21	134
28	50	76.27	137
29	100	145.39	115
30	100	132.06	130
31	100	148.78	132
32	100	134.12	130

A.5. Peak current amplitude and oxidation potential, for copper(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	10	8.43	-158
02	10	11.23	-150
03	10	10.02	-143
04	10	8.5	-143
05	10	8.2	-127
06	10	8.1	-144
07	10	8.8	-132
08	10	8.01	-143
09	10	18.52	-135
10	10	8.48	-129
11	10	10.42	-118
12	25	9.5	-119
13	25	12.45	-125
14	25	9.02	-126
15	25	12.22	-123
16	25	10.22	-125
17	25	15.68	-122
18	25	17.34	-121
19	25	19.9	-118
20	25	18.8	-124
21	25	17.61	-116
22	25	18.36	-123
23	50	22.01	-97
24	50	16.34	-94
25	50	33.12	-92
26	50	39.12	-80
27	50	33.3	-65
28	50	34.08	-63
29	50	40.99	-65
30	50	31.12	-62
31	50	36.24	-64
32	50	32.16	-63

A.6. Peak current amplitude and oxidation potential, for nickel(II): Using glassy carbon electrode.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	5	6.82	-48
02	5	6.11	-41
03	5	6.02	-4
04	5	4.81	-22
05	5	5.79	-59
06	5	5.09	-52
07	5	4.92	-47
08	5	4.82	-35
09	10	6.86	-6
10	10	7.74	-7
11	10	7.75	-11
12	10	7.07	-4
13	10	7.34	-30
14	10	7.12	-34
15	10	6.77	-6
16	10	6.79	-12
17	25	13.62	-156
18	25	15.82	-178
19	25	12.91	-176
20	25	14.35	-145
21	25	11.24	-102
22	25	11.34	-123
23	25	10.56	-23
24	25	10.26	-12
25	50	22.98	-4
26	50	19.02	-6
27	50	27.48	-10
28	50	32.99	-23
29	50	24.23	-18
30	50	23.49	-11
31	50	24.56	-3
32	50	24.98	-12

A.7. Peak current amplitude and oxidation potential, for lead(II): Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	2.5	7.6	-602
02	2.5	15.1	-623
03	2.5	14.1	-616
04	2.5	8.1	-622
05	2.5	12.32	-612
06	2.5	12.8	-622
07	2.5	11.6	-602
08	2.5	11.6	-608
09	5	55.65	-611
10	5	59.42	-612
11	5	56.73	-609
12	5	60.25	-611
13	5	56.11	-601
14	5	55.31	-602
15	5	59.09	-598
16	5	60.22	-592
17	10	153	-521
18	10	226.1	-522
19	10	167.1	-521
20	10	224.3	-526
21	10	223.4	-523
22	10	160	-523
23	10	159.1	-533
24	10	162.3	-522
25	50	747.9	-501
26	50	747.8	-502
27	50	796.3	-504
28	50	700.1	-511
29	50	710.2	-511
30	50	780.2	-502
31	50	709.5	-504
32	50	782.7	-503

A.8. Peak current amplitude and oxidation potential, for cadmium(II): Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	2.5	37.22	-755
02	2.5	32.91	-760
03	2.5	36.25	-776
04	2.5	31.05	-745
05	2.5	31.98	-746
06	2.5	35.66	-739
07	2.5	37.26	-722
08	2.5	32.11	-728
09	5	94.82	-777
10	5	94.82	-756
11	5	100.1	-799
12	5	89.23	-782
13	5	90.34	-789
14	5	102.7	-774
15	5	91.73	-782
16	5	95.03	-824
17	10	168.7	-845
18	10	168.7	-848
19	10	143	-833
20	10	187	-834
21	10	139	-856
22	10	198	-869
23	10	190	-857
24	10	152	-877
25	30	648.4	-914
26	30	639.2	-902
27	30	679	-916
28	30	611	-927
29	30	612	-900
30	30	654	-909
31	30	678	-918
32	30	630	-922

A.9. Peak current amplitude and oxidation potential, for zinc(II): Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	5	47.21	-1002
02	5	68.12	-1048
03	5	58.67	-1011
04	5	44.27	-1016
05	5	62.78	-1023
06	5	45.87	-1029
07	5	43.78	-1036
08	5	56.11	-1026
09	10	124.6	-961
10	10	122.1	-964
11	10	139.8	-965
12	10	112.6	-959
13	10	240.1	-971
14	10	109.9	-957
15	10	132.8	-968
16	10	112.7	-958
17	25	302.8	-995
18	25	304.2	-1009
19	25	243.2	-1003
20	25	327.2	-1011
21	25	249.9	-994
22	25	271.2	-1012
23	25	272.6	-1008
24	25	312.7	-1021
25	50	398.9	-997
26	50	389.2	-1016
27	50	446.1	-1023
28	50	420.1	-1013
29	50	486.2	-1005
30	50	478.2	-1009
31	50	470.9	-1021
32	50	396.8	-1022

A.10. Peak current amplitude and oxidation potential, for mercury: Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	5	30.22	19
02	5	32.56	11
03	5	29.67	13
04	5	33.52	25
05	5	31.08	23
06	5	31.12	11
07	10	40.98	21
08	10	41.34	14
09	10	37.56	13
10	10	36.67	15
11	10	42.78	12
12	10	36.78	11
13	30	50.31	29
14	30	55.22	23
15	30	51.27	21
16	30	65.12	34
17	30	71.06	23
18	30	72.32	64
19	50	72.66	87
20	50	73.99	64
21	50	74.72	83
22	50	92.25	78
23	50	89.2	78
24	50	71.01	61
25	50	97.99	73
26	100	136.6	122
27	100	155.2	132
28	100	141.1	138
29	100	134	145
30	100	149	132
31	100	151.1	127
32	100	140	129

A.11. Peak current amplitude and oxidation potential, for copper(II): Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	2.5	14.11	-268
02	2.5	21.09	-256
03	2.5	15.54	-261
04	2.5	20.03	-269
05	2.5	12.64	-264
06	2.5	22.42	-262
07	5	47.12	-243
08	5	32.05	-256
09	5	46.23	-252
10	5	30.42	-257
11	5	49.56	-261
12	5	32.09	-254
13	10	170.2	-196
14	10	167	-184
15	10	150.6	-189
16	10	134.2	-182
17	10	120.1	-183
18	10	126.7	-181
19	25	320.5	-146
20	25	280.1	-137
21	25	332	-138
22	25	287.5	-148
23	25	334	-139
24	25	269.2	-135
25	25	289.6	-137
26	50	540	-91
27	50	445.1	-92
28	50	546.3	-95
29	50	471.2	-91
30	50	493.6	-98
31	50	479.5	-94
32	50	470.3	-93

A.12. Peak current amplitude and oxidation potential, for nickel: Using the screen printed sensor.

Sample No	Concentration [ppm]	Amplitude [μA]	Oxidation Pot. [mV]
01	5	6.52	-268
02	5	6.32	-255
03	5	8.21	-253
04	5	8.03	-255
05	5	8.79	-259
06	5	8.12	-245
07	5	6.08	-239
08	5	6.23	-235
09	10	16.32	-210
10	10	16.21	-209
11	10	16.98	-211
12	10	16.35	-221
13	10	17.99	-219
14	10	17.82	-223
15	10	17.95	-208
16	10	17.02	-214
17	25	22.08	-198
18	25	21.56	-201
19	25	23.76	-196
20	25	22.05	-183
21	25	27.92	-194
22	25	31.44	-192
23	25	29.28	-199
24	25	35.71	-193
25	50	41.01	-184
26	50	43.29	-188
27	50	41.56	-182
28	50	47.92	-186
29	50	55.99	-188
30	50	59.12	-183
31	50	58.09	-175
32	50	43.25	-179

Appendix B

Software developed in ASSEMBLY language

B.1. Excitation Signal

```
.....
*
*      School of Engineering
*      The Robert Gordon University, Aberdeen
*.....
*      File name: excitation.asm (ok)
*      Author:      KONSTANTINOS CHRISTIDIS
*      Created:     02/03/2004
*.....
*      M68HCS12 Assembler Source File
*
* Description : Produce excitation signal
*               PON=50mS and POFF=70ms
*               Range:-1.4 to +1.0V
*.....
* DAC:
*      PORT B - [DDDD DDDD], LSB DATA for DAC
*      PORT K - [XXXX DDDD], MSB DATA for DAC
*.....
COPCTL      EQU      $003C      ; COP Control Register
*.....
* STARTING ADDRESS FOR DATA
*.....
ORG          $3700      ; DATA: RAM starting address
*.....
* I/O PORTS
*.....
PORTB       EQU      $0001      ; DAC: LSB DATA
DDRB        EQU      $0003
PORTK       EQU      $0032      ; DAC: MSB DATA
DDRK        EQU      $0033
*.....
* DAC DATA
*.....
VOLT_M      DB        #0        ;$3000: Voltage variable for DAC (MSByte)
VOLT_L      DB        #0        ;$3001: Voltage variable for DAC (LSByte)
VOLT_M_AUX  DB        #0        ;Voltage var. to support Sensor MASK control
VOLT_L_AUX  DB        #0        ;Voltage var. to support Sensor MASK control
*.....
* STARTING ADDRESS FOR THE PROGRAM
*.....
ORG          $1000      ; PROGRAM: RAM starting address
*.....
* Initialisation - Set variables
*.....
START:      CLR        COPCTL    ; Clear COP
            LDS        #$3BFF    ; Set STAC register
*.....
* Set I/O ports
*.....
            BSET       DDRB,$%11111111    ; Set port-B OUTPUT
            BSET       DDRK,$%00001111    ; Set port-K OUTPUT
*.....
* Initial voltage (-1.4V) (#0901)
*.....
            LDD        #0901
            STD        VOLT_M
            STD        VOLT_M_AUX
            BSET       VOLT_M_AUX,$%00010000    ; Connect sensor-1 (S1)
            LDD        VOLT_M_AUX
            STAA        PORTK      ; Sent also Control (S1=1)
            STAB        PORTB
```

```

*****
;* Deposition timer for 1 min
*****
LOOP50:      LDD      #1200          ; 1200 x 50msec = 1min DELAY
             JSR      DELAY10
             DEC
             CPD      #0
             BHI      LOOP50
             RTS
*****
;* REPEAT PROCESS
*****
LOOP:         NOP
*****
;* 50 msec step up (21bits -1.22 x 21 = 25.62mV)
*****
             LDD      VOLT_M
             ADDD     #21
             STD      VOLT_M
             STD      VOLT_M_AUX
             BSET     VOLT_M_AUX,##00010000 ; Connect sensor-1 (S1)
             LDD      VOLT_M_AUX
             STAA     PORTK           ; Sent also Control (S1=1)
             STAB     PORTB
             JSR      DELAY50
*****
;* 50 sec step down (19 bit 1.22x19=23.18)
*****
             LDD      VOLT_M          ; Load current voltage potential
             SUBD     #19             ; Add 20bits to current potential
             STD      VOLT_M          ; Store new potential
             STD      VOLT_M_AUX
             BSET     VOLT_M_AUX,##00010000 ; Connect sensor-1 (S1)
             LDD      VOLT_M_AUX
             STAA     PORTK           ; Sent also Control (S1=1)
             STAB     PORTB           ; LSB DAC output
             JSR      DELAY50         ; Wait for 50msec
             JSR      DELAY10
             JSR      DELAY10
*****
;* Check if reach potential +0.0V (2048) or +1.0V (2867)
*****
             LDD      VOLT_M          ; Load current voltage potential
             CPD      #2867           ; 1.0V Step potential 2 = 1.0V
             LBLO     LOOP            ; If no, repeat process GO to LOOP
                                     ; If yes, continue
*****
*****      END OF MAIN      *****
*****
LOOPGQ:       BRA      LOOPGQ         ; Continuously repeat, END
*****
;*
;* SUBROUTINE: DELAY50
;* INFO:      Delay for 50ms
;* PASS:      No
;* RETURNE:   No
*****
DELAY50:      PSHA
             LDAA     #5              ; 5 x 10msec DELAY
             JSR      DELAY10
             DECA
             CMPA     #0
             BHI      LOOP50
             PULA
             RTS
*****
;*
;* SUBROUTINE: DELAY10
;* INFO:      Delay for 10ms
;* PASS:      No
;* RETURNE:   No
*****
DELAY10:      LDX      #40625         ; 10msec execution time
LOOP10:       DEX
             CPX      #0
             BHI      LOOP10
             LDX      #REGBS
             RTS
*****
*****      END OF CODE      *****
*****

```

B.2. Data acquisition

```

*****
*           School of Engineering
*           The Robert Gordon University, Aberdeen
*****
*           File name: adc.asM
*           Author:      KONSTANTINOS CHRISTIDIS
*           Created:     14/02/2004
*****
*           M68HCS12 Assembler Source File
* Description : ADC driver and Data acquisition
*****
* ADC:      PORT A - [DDDD DDDD], MSB DATA for ADC
*           PORT AD1 - [DDDD DDDD], LSB DATA for ADC
*           PORT P7 - CONTROL DATA for ADC
*****

COPCTL      EQU      $003C          ; COP Control Register
*****
* I/O PORTS
*****
PORTAD1      EQU      $012F          ; ADC: LSB DATA
ENBL_AD1 EQU      $012D
PORTA      EQU      $0000          ; ADC: MSB DATA
DDRA      EQU      $0002
PORTP      EQU      $0258          ; ADC: CONTROL
DDRP      EQU      $025A
*****
; * STARTING ADDRESS FOR THE PROGRAM
; *****
; ORG      $1000          ; PROGRAM: RAM starting address
; *****
; * Initialisation - Set variables
; *****
START:      CLR      COPCTL          ; Clear COP
            LDS      #$3BFF          ; Set STAC register
; *****
; * Set I/O ports
; *****
            CLR      DDRA            ; Set port-A INPUT
            BSET     ENBL_AD1,$$11111111 ; Enable port-AD1 (INPUT)
            BSET     DRP,$$11111100    ; Set port-P OUTPUT
LOOP:      JSR      READADC
            JSR      DELAY50
            JMP      LOOP            ; Continuously read ADC
; *****
; * SUBROUTINE: DELAY50
; * INFO:      Delay for 50ms
; * PASS:      No
; * RETURNE:   No
; *****
DELAY50:    PSHA
            LDAA     #5              ; 5 x 10msec DELAY
            JSR      DELAY10
            DECA
            CMPA     #0
            BHI      LOOP50
            PULA
            RTS
; *****
; * SUBROUTINE: DELAY10
; * INFO:      Delay for 10ms
; * PASS:      No
; * RETURNE:   No
; *****
DELAY10:    LDX      #40625          ; 10msec execution time
LOOP10:    DEX
            CPX      #$00
            BHI      LOOP10
            LDX      #REGBS
            RTS
; *****
; * SUBROUTINE: READADC
; * INFO:      Read ADC Converter
; * PASS:      No
; * RETURNE:   Register-D
; *****
READADC:    BSET     PORTP,$$10000000 ; Initial stage (Conversion=OFF)
            JSR      DELAY01
            BCLR     PORTP,$$10000000 ; Conversion=ON

```



```

NOP
NOP
NOP
BSET PORTP,##10000000 ; Conversion=OFF
JSR DELAY01 ; Wait for BUSY signal
LDAA PORTA ; Read MSByte
LDAB PORTAD1 ; Read LSByte
RTS
;*****
;* SUBROUTINE: DELAY01
;* INFO: Wait for 100usec
;* PASS: No
;* RETURNE: No
;*****
DELAY01: LDX #1016 ; 100 usec execution time
LOOP25: DEX
CPX #500
BHI LOOP25
RTS
;*****
;* END OF CODE
;*****

```

B.3. Gain control

```

;*****
;*
;* School of Engineering
;* The Robert Gordon University, Aberdeen
;*****
;* File name: gain_cnt.asm
;* Author: KONSTANTINOS CHRISTIDIS
;* Created: 12/08/2004
;*****
;* M68HCS12 Assembler Source File
;* Description : Gain
;*****
;* ADC: PORT A - [DDDD DDDD], MSB DATA for ADC
;* PORT AD1 - [DDDD DDDD], LSB DATA for ADC
;* PORT P7 - CONTROL DATA for ADC
;* GAIN: PORT T - [XXAB CXXX] 3bits Input KEYPAD
;*****
COPCTL EQU $003C ; COP Control Register
;*****
;* STARTING ADDRESS FOR DATA
;*****
ORG $3700 ; DATA: RAM starting address
;*****
;* I/O PORTS
;*****
PORTAD1 EQU $012F ; ADC: LSB DATA
ENBL_AD1 EQU $012D
PORTA EQU $0000 ; ADC: MSB DATA
DDRA EQU $0002
PORTP EQU $0258 ; LCD:3-BIT CONTROL
DDRP EQU $025A
PORTT EQU $0240 ; GAIN: 3-BIT DATA
DDRT EQU $0242
;*****
;* ADC DATA
;*****
SMP_16M DW #0 ;$0802: ADC sample storage (MSWord)
SMP_16L DW #0 ;
SAMPLE_M DW #0
;*****
;* AUTOMATIC GAIN
;*****
GN_PNT1 DB #0
GN_PNT2 DB #0
GAIN DB #0 ;$0870
GAIN0 DB ##00000000
GAIN1 DB ##00001000 ;$0870
GAIN2 DB ##00010000 ;$0870
GAIN3 DB ##00011000 ;$0870
GAIN4 DB ##00100000 ;$0870
GAIN5 DB ##00101000 ;$0870
GAIN6 DB ##00110000 ;$0870
GAIN7 DB ##00111000 ;$0870
GN_RES DW #0 ;$0000
GN_RES0 DW #31623 ;$0872

```

```

GN_RES1      DW      #25914      ;$0872
GN_RES2      DW      #14698      ;$0872
GN_RES3      DW      #7722       ;$0872
GN_RES4      DW      #2959       ;$0872
GN_RES5      DW      #2322       ;$0872
GN_RES6      DW      #1722       ;$0872
GN_RES7      DW      #811        ;$0872
X_SAMPLA DW      #0              ;$0874
X_SAMPLB DW      #0              ;$0874
X_SAMPL0 DW      #0              ;$0874
X_SAMPL1 DW      #0              ;$0874
X_SAMPL2 DW      #0              ;$0874
X_SAMPL3 DW      #0              ;$0874
X_SAMPL4 DW      #0              ;$0874
X_SAMPL5 DW      #0              ;$0874
X_SAMPL6 DW      #0              ;$0874
X_SAMPL7 DW      #0              ;$0874
SMP_M16M DW      #0              ;
SMP_M16L DW      #0              ;
SAMPL_MM dw      #0              ;
DIV_FLG1 DB      #0              ;1=div10, 10=div1000
DIV_FLG2 DB      #0              ;0=Less than 500.00uA,1=Higher than 500.00uA
RES_PPM      DW      #0
;*****
;* STARTING ADDRESS FOR THE PROGRAM
;*****
ORG          $1000                ; PROGRAM: RAM starting address
;*****
;* Initialisation - Set variables
;*****
START:      CLR      COPCTL        ; Clear COP
            LDS      #3BFF        ; Set STAC register
;*****
;* Set I/O ports
;*****
            CLR      DDRA          ; Set port-A INPUT
            BSET     ENBL_AD1, #01111111 ; Enable port-AD1 (INPUT)
            BSET     DDRP, #01111100    ; Set port-P OUTPUT
            BSET     DDRT, #00111000    ; Set port-T OUTPUT
LOOPGQ:     NOP
;*****
;* GAIN CONTROL
;* Read ADC, HIGH sample
;*****
            JSR      GN_CNT2
;*****
;* GAIN CONTROL
;* Find best tuning
;*****
            LDAA     GN_PNT2
            LSLA
            STAA     GN_PNT1
            LDY      #X_SAMPL0
            LDAA     GN_PNT1
NTXT2:      CMPA     #0
            BEQ      VELE2
            DECA
            INY
            BRA      NTXT2
VELE2:      LDD      0,Y
            STD      X_SAMPLA
            LDY      #GN_RES0
            LDAA     GN_PNT1
NTXT3:      CMPA     #0
            BEQ      VELE3
            DECA
            INY
            BRA      NTXT3
VELE3:      LDD      0,Y
            STD      GN_RES
;*****
;* MULTIPLY SAMPLE A WITH RESOLUTION
;*****
            LDD      X_SAMPLA
            LDY      GN_RES
            EMUL                     ;X_SAMPLA*GAIN_RES*100=(Y:D)
            STD      SMP_M16L
            STY      SMP_M16M
;*****
;* MULTIPLY SAMPLE B WITH RESOLUTION
;*****
            LDD      X_SAMPLB
            LDY      GN_RES
            EMUL                     ;X_SAMPLB*GAIN_RES*100=(Y:D)
            STD      C_SMP16L
            STY      C_SMP16M
;*****
;* Calculate difference NUMBER 1 - NUMBER 2 [method II]
;*****

```

```

LDD     SMP_M16L
SUBD    C_SMP16L
STD     SMP_16L
BCC     NEXT
LDD     C_SMP16M
ADDD    #1
STD     C_SMP16M
NEXT:   LDD     SMP_M16M
        SUBD    C_SMP16M
        STD     SMP_16M
;*****
;* Multiply sample with resolution
;*****
LDY     SMP_16M
LDD     SMP_16L
LDX     #10000
EDIV                      ; (Y:D)/100=Y.D
STY     SAMPLE_M          ; Store results
STY     SAMPL_MM
movb    #100,DIV_FLG1     ; Set division /100
ldd     SAMPLE_M
;*****
; Repeat Process
;*****
BRA     LOOPGQ            ; Continuously repeat
;*****
;* Subroutine: GN_ADC
;* Note: Gain control for ADC
;*****
GN_ADC: STAA    PORTT
        JSR     DELAY001    ; Delay 200nsec
        JSR     READADC     ; Read ADC for gain 000
        JSR     NEGPOS     ; Negative and positive shift results on D-REGISTER
        RTS
;*****
;* Subroutine: GAIN_CNT
;* Note: Gain control for ADC FOR FIRST SAMPLE
;*****
GAIN_CNT: MOVB   #0,GN_PNT1
        LDAA    GAIN0
        JSR     GN_ADC
        STD     X_SAMPLE0    ; Store sample for gain 000
        CPD     #51491      ; +9.8(*0.8)
        LBHS    NO_GN
        CPD     #14044      ; -9.8(*0.8)
        LBLS    NO_GN
        MOVB    #1,GN_PNT1
        LDAA    GAIN1
        JSR     GN_ADC
        STD     X_SAMPL1    ; Store sample for X gain
        CPD     #43375      ; +5(*0.8)
        LBHS    NO_GN
        CPD     #22160      ; -5(*0.8)
        LBLS    NO_GN
        MOVB    #2,GN_PNT1
        LDAA    GAIN2
        JSR     GN_ADC
        STD     X_SAMPL2    ; Store sample for X gain
        CPD     #38174      ; +2.5(*0.7)
        LBHS    NO_GN
        CPD     #27361      ; -2.5(*0.7)
        LBLS    NO_GN
        MOVB    #3,GN_PNT1
        LDAA    GAIN3
        JSR     GN_ADC
        STD     X_SAMPL3    ; Store sample for X gain
        CPD     #34888      ; +0.98(*0.7)
        LBHS    NO_GN
        CPD     #30647      ; -0.98(*0.7)
        LBLS    NO_GN
        MOVB    #4,GN_PNT1
        LDAA    GAIN4
        JSR     GN_ADC
        STD     X_SAMPL4    ; Store sample for X gain
        CPD     #34358      ; +0.735(*0.7)
        LBHS    NO_GN
        CPD     #31177      ; -0.735(*0.7)
        LBLS    NO_GN
        MOVB    #5,GN_PNT1
        LDAA    GAIN5
        JSR     GN_ADC
        STD     X_SAMPL5    ; Store sample for X gain
        CPD     #33849      ; +0.5(*0.7)
        LBHS    NO_GN
        CPD     #31686      ; -0.5(*0.7)
        LBLS    NO_GN
        MOVB    #6,GN_PNT1
        LDAA    GAIN6
        JSR     GN_ADC

```

```

STD      X_SAMPL6      ; Store sample for X gain
CPD      #33308        ; +0.25(*0.7)
LBHS     NO_GN
CPD      #32227        ; -0.25(*0.7)
LBLS     NO_GN
MOVB     #7,GN_PNT1
LDAA     GAIN7
JSR      GN_ADC
STD      X_SAMPL7      ; Store sample for X gain
NO_GN:   RTS
;*****
;* Subroutine:  GN_CNT2
;* Note:  Gain control for ADC FOR SECOND SAMPLE
;*****
GN_CNT2: MOVB     #0,GN_PNT2
LDAA     GAIN0
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #51491        ; +9.8(*0.8)
LBHS     NO_GN1
CPD      #14044        ; -9.8(*0.8)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #1,GN_PNT2
LDAA     GAIN1
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #43375        ; +5(*0.8)
LBHS     NO_GN1
CPD      #22160        ; -5(*0.8)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #2,GN_PNT2
LDAA     GAIN2
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #38174        ; +2.5(*0.7)
LBHS     NO_GN1
CPD      #27361        ; -2.5(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #3,GN_PNT2
LDAA     GAIN3
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #34888        ; +0.98(*0.7)
LBHS     NO_GN1
CPD      #30647        ; -0.98(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #4,GN_PNT2
LDAA     GAIN4
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #34358        ; +0.735(*0.7)
LBHS     NO_GN1
CPD      #31177        ; -0.735(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #5,GN_PNT2
LDAA     GAIN5
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #33849        ; +0.5(*0.7)
LBHS     NO_GN1
CPD      #31686        ; -0.5(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #6,GN_PNT2
LDAA     GAIN6
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #33308        ; +0.25(*0.7)
LBHS     NO_GN
CPD      #32227        ; -0.25(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1

```



```

        CMPA    GN_PNT2
        LBL5    NO_GN1
        MOV5    #7,GN_PNT2
        LDAA    GAIN7
        JSR     GN_ADC
        STD     X_SAMPLB    ; Store sample for X gain
NO_GN1:
        RTS
;*****
;*      SUBROUTINE: DELAY50
;*      INFO:      Delay for 50ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY50:
        PSHA
        LDAA    #5          ; 5 x 10msec DELAY
        JSR     DELAY10
        DECA
        CMPA    #0
        BHI     LOOP50
        PULA
        RTS
;*****
;*      SUBROUTINE: DELAY10
;*      INFO:      Delay for 10ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY10:
        LDX     #40625      ;10msec execution time
LOOP10:
        DEX
        CPX     #$00
        BHI     LOOP10
        LDX     #REGB5
        RTS
;*****
;*      SUBROUTINE: READADC
;*      INFO:      Read ADC Converter
;*      PASS:      No
;*      RETURNE:   Register-D
;*****
READADC:
        BSET    PORTP,%%10000000    ; Initial stage (Conversion=OFF)
        JSR     DELAY01
        BCLR    PORTP,%%10000000    ; Conversion=ON
        NOP
        NOP
        BSET    PORTP,%%10000000    ; Conversion=OFF
        JSR     DELAY01              ; Wait for BUSY signal
        LDAA    PORTA                ; Read MSByte
        LDAB    PORTAD1              ; Read LSByte
        RTS
;*****
;*      SUBROUTINE: DELAY01
;*      INFO:      Wait for 100usec
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY01:
        LDX     #1016              ; 100 usec execution time
LOOP25:
        DEX
        CPX     #$00
        BHI     LOOP25
        RTS
;*****
;*      END OF CODE
;*****

```

B.4. Keypad control

```

;*****
;*
;*      School of Engineering
;*      The Robert Gordon University, Aberdeen
;*****
;*      File name:  keypad.asm
;*      Author:     KONSTANTINOS CHRISTIDIS
;*      Created:    21/09/2004
;*****
;*      M68HCS12 Assembler Source File
;*      Description : Keypad operation (drivers)
;*****
;*      KEYPAD:    PORT M - [XXX(<) (E)(>)XX] 3bits Input KEYPAD
;*****
COPCTL    EQU     $003C    ; COP Control Register
;*****

```

```

* STARTING ADDRESS FOR DATA
*****
ORG      $3700          ; DATA: RAM starting address
*****
* I/O PORTS
*****
PORTM    EQU      $0250
DDRM     EQU      $0252          ; KEYPAD: 3-BIT DATA
*****
* STARTING ADDRESS FOR THE PROGRAM
*****
ORG      $1000          ; PROGRAM: RAM starting address
*****
* Initialisation - Set variables
*****
START:    CLR      COPCTL          ; Clear COP
          LDS      #$3BFF          ; Set STAC register
*****
* Set I/O ports
*****
          BCLR     DDRM,$%00011100 ; Set M2,M3,M4 INPUTS
*****
LOOP:     LDAA     #$00
          JSR      ENT_BTN          ; Read ENTER bout-on
          JSR      DELAY10
          LDAA     #$FF
          JSR      ENT_BTN          ; Read ENTER bout-on
          JSR      DELAY10
          BRA      LOOPQG          ; Continuously repeat, END
*****
* SUBROUTINE: DELAY10
* INFO:      Delay for 10ms
* PASS:      No
* RETURNE:   No
*****
DELAY10:  LDX      #40625          ;10msec execution time
LOOP10:   DEX
          CPX      #$00
          BHI      LOOP10
          LDX      #REGBS
          RTS
*****
* SUBROUTINE: ENT_BTN
* INFO:      Wait to press Enter button
*****
ENT_BTN:  NOP
INTROD8:  LDAA     PORTM          ; Read ENTER bout-on
          ANDA     %%00001000      ; READ M4 PIN
          CMPA     %%00001000
          BNE      INTROD8
          RTS
*****
* END OF CODE
*****

```

B.5. Alphanumerical display

```

*****
* School of Engineering
* The Robert Gordon University, Aberdeen
*****
* File name:  display_1.asm
* Author:     KONSTANTINOS CHRISTIDIS
* Created:    21/05/2004
*****
* M68HCS12 Assembler Source File
* Description : Alphanumerical display drivers
*****
* LCD:        PORT H - [DDDD DDDD], DATA for LCD
*             PORT P - [XXC CCxx], CONTROL FOR LCD
*****
COPCTL    EQU      $003C          ; COP Control Register
*****
* STARTING ADDRESS FOR DATA
*****
ORG      $3700          ; DATA: RAM starting address
*****
* I/O PORTS
*****

```

```

PORTH      EQU      $0260      ; LCD: 8-BIT DATA
DDRH       EQU      $0262
PORTP      EQU      $0258      ; LCD:3-BIT CONTROL
DDRP       EQU      $025A
;*****
; * STARTING ADDRESS FOR THE PROGRAM
;*****
ORG         $1000      ; PROGRAM: RAM starting address
;*****
; * Initialisation - Set variables
;*****
START:      CLR      COPCTL      ; Clear COP
            LDS      #$3BFF      ; Set STAC register
;*****
; * Set I/O ports
;*****
            MOV     #$FF,DDRH      ; Set port-H OUTPUT
            BSET    DDRP,$%1111100 ; Set port-P OUTPUT
;*****
; * Initialise LCD
;*****
            LDAA    #%00111000      ; 8bit, 2line 5x7dot
            JSR     CNTLCT
            LDAA    #%00000110      ; Display control
            JSR     CNTLCT
            LDAA    #%00000001      ; Clear LCD
            JSR     CNTLCT
            LDAA    #%00000110      ; Increment
            JSR     CNTLCT
;*****
; * Print Welcome on LCD
;*****
            JSR     CLR_LCD      ; Clear LCD
            LDY     #MSG_Wa
            JSR     CHAR_STR
            JSR     LINE_LCD      ; Next line
            LDY     #MSG_Wb
            JSR     CHAR_STR
;*****
LOOP:        BRA      LOOP
;*****
; * SUBROUTINE: D_CHAR
; * FUNCTION:
;*****
D_CHAR:      JSR     PRNLCD
            RTS
;*****
; * SUBROUTINE: CLR_LCD
; * INFO:      Clear LCD
; * PASS:      No
; * RETURNE:   No
;*****
CLR_LCD:     LDAA    #%00000001      ; Clear LCD
            JSR     CNTLCT
            RTS
;*****
; * SUBROUTINE: LINE_LCD
; * INFO:      Next Line (LCD)
; * PASS:      No
; * RETURNE:   No
;*****
LINE_LCD:    LDAA    #%11000000      ; Next line
            JSR     CNTLCT
            RTS
;*****
; * SUBROUTINE: CNTLCT
; * INFO:      Control output to LCD
; * PASS:      Register-A, data
; * RETURNE:   No
;*****
CNTLCT:      LDAB    #%00000000      ; CONTROL: (E=0,R/W=0,RS=0)
            STAB    PORTP
            STAA    PORTH
            JSR     DELAYLCD
            LDAB    #%00000100      ; CONTROL: (E=1,R/W=0,RS=0)
            STAB    PORTP
            JSR     DELAYLCD
            RTS
;*****
; * SUBROUTINE: PRNLCD
; * INFO:      Data output to LCD
; * PASS:      Register-A, data
; * RETURNE:   No
;*****
PRNLCD:      LDAB    #%00010000      ; CONTROL: (E=0,R/W=0,RS=0)
            STAB    PORTP
            STAA    PORTH
            JSR     DELAYLCD
            LDAB    #%00010100      ; CONTROL: (E=1,R/W=0,RS=1)

```

```

        STAB    PORTP
        JSR     DELAYLCD
        RTS
;*****
;*  SUBROUTINE: DELAYLCD
;*  INFO:      Delay for LCD operation
;*  PASS:      No
;*  RETURNE:   No
;*****
DELAYLCD:    JSR     DELAY10          ;10msec execution time
             RTS
;*****
;* Subroutine: CHAR_STR
;* Description: This subroutine prints
;*              a character string
;*****
CHAR_STR:    NOP
TXT_LOOP:    LDAA    0,Y
             CMPA    #$FF
             BEQ     TXT_END1
             JSR     PRNLCD
             INY
             BRA     TXT_LOOP
TXT_END1:    RTS
;*****
;* CHARACTERS FOR DISPLAY
;*****
MSG_Wa      FCC     "Volt. Analyser-I "
             FCB     $FF
MSG_Wb      FCC     "R.G.U. 2004. "
             FCB     $FF
;*****
;* END OF CODE
;*****

```

B.6. Graphic display

```

;*****
;* School of Engineering
;* The Robert Gordon University, Aberdeen
;*****
;* File name:   glcd.asm
;* Author:      KONSTANTINOS CHRISTIDIS
;* Created:     02/02/2005
;*****
;* M68HCS12 Assembler Source File
;* Description : GLCD drivers and operation example
;* LCD:        PORT C - [DDDD DDDD], DATA for LCD
;*             PORT H - [XXXX XCCC], CONTROL DATA for LCD
;*****
COPCTL      ORG     $F000          ; Starting Address inchip EEPROM
             EQU     $0016          ; COP Control Register
PORTC       EQU     $0004          ; Data for LCD
PORTH       EQU     $0024          ; Control DATA for LCD
REGBS       EQU     $0000          ; REGISTER BASE ADDRESS.
;*****
;* Set I/O ports
;*****
             MOVB    #$FF,$0006    ; Set port-C OUTPUT
             MOVB    #$FF,$0025    ; Set port-H OUTPUT
;*****
;* INITIALISE LCD
;*****
;PREPARE FOR RESET
             LDAB    %%00110110    ; (Rst=OFF,COM=off,E=ON,R=OFF,W=OFF)
             STAB    PORTH          ;CONTROL OUTPUT
             JSR     DELAY50
;SET RESET ON FOR SIX CYCLES
             LDAB    %%00010110    ; (Rst=ON,COM=off,E=ON,R=OFF,W=OFF)
             STAB    PORTH          ;CONTROL OUTPUT
             JSR     DELAY50
;SET RESET OFF
             LDAB    %%00110110    ; (Rst=OFF,COM=off,E=ON,R=OFF,W=OFF)
             STAB    PORTH          ;CONTROL OUTPUT
             JSR     DELAY50
;SET ENABLE OFF
             LDAB    %%00111110    ; (Rst=OFF,COM=off,E=OFF,R=OFF,W=OFF)
             STAB    PORTH          ;CONTROL OUTPUT
;*****

```



```

;*Set GRAPHICS HOME address at $0000
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$00          ;WRITE LS BYTE DATA OF #$0000
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$00          ;WRITE MS BYTE DATA OF #$0000
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$42          ;WRITE COMMAND
        JSR      WR_COMND
;*****
;*Set GRAPHICS AREA SET - $0010
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$10          ;WRITE 1ST BYTE DATA OF #$0010
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$00          ;WRITE 2ND BYTE DATA OF #$0010
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$43
        JSR      WR_COMND
;*****
;*Set TEXT HOME address AT $0400
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$00          ;WRITE 1ST BYTE DATA OF #$0400
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$04          ;WRITE 2ND BYTE DATA OF #$0400
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$40
        JSR      WR_COMND
;*****
;*Set TEXT AREA SET - $0010
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$10          ;WRITE 1ST BYTE DATA OF #$0010
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$00          ;WRITE 2ND BYTE DATA OF #$0010
        JSR      WR_DATA
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$41
        JSR      WR_COMND
;*****
;*Set MODE SET
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$10000000    ;"OR" MODE
        JSR      WR_COMND
;*****
;*Set DISPLAY MODE
;*****
        JSR      ST_CHECK      ;READ STATUS
        LDAA     #$10011100    ;($98),GRAPH=0N,TEXT=0N,CURSOR=OFF
        JSR      WR_COMND
;*****
;* Print Welcome on LCD
;*****
        JSR      CLR_PLOT
        JSR      CLR_SCREEN
        LDD      #$0000
        STD      ADDPNT_M
        JSR      SET_ADD_PNT   ; POINTER ADDRESS
        JSR      ST_CHECK      ; READ STATUS
        LDAA     #$B0          ; AUTO WRITE MODE ON
        JSR      WR_COMND
        LDY      #$F59D        ; STARTING ADDRESS OF GRAPH DATA
        LDx      #1024         ; 1024 POSITIONS
LOP_1B:  pshx
        JSR      ST_CH_2       ; READ STATUS 2
        LDAA     0,Y
        JSR      WR_DATA
        INY
        pulx
        dex
        CPx      #$00
        BHI      LOP_1B
        JSR      ST_CH_2       ; READ STATUS 2
        LDAA     #$B2          ; AUTO WRUTE MODE RESET
        JSR      WR_COMND
LOOPG    BRA      LOOPG        ; Continuously repeat, END
;*****
;* SUBROUTINE: DELAY50
;* INFO:      Delay for 50ms
;* PASS:      No

```

```

;*      RETURNE:   No
;*****
DELAY50:      LDX      #65000          ;50 msec execution time
LOOP50:       DEX
              CPX      #$00
              BHI      LOOP50
              LDX      #REGBS
              RTS
;*****
;*      SUBROUTINE: DELAY_01
;*      INFO:      Delay for 50ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY_01:     LDX      #1300          ;1 msec execution time
LOOP_010:    DEX
              CPX      #$00
              BHI      LOOP_010
              LDX      #REGBS
              RTS
;*****
;*      SUBROUTINE: DELAY01
;*      INFO:      Wait for 100usec
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY01:     LDX      #325            ; 100 usec execution time
LOOP25:      DEX
              CPX      #$00
              BHI      LOOP25
              RTS
;*****
;*      SUBROUTINE: DELAY02
;*      INFO:      Wait for 770usec
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY02:     LDX      #1000           ; 770 usec execution time
LOOP77:      DEX
              CPX      #$00
              BHI      LOOP77
              RTS
;*****
* Subroutine: CHAR_STR
* Description: This subroutine prints
*              a character string
;*****
CHAR_STR:    LDD      #$0430          ;start at 3rd line
              STD      ADDPNT_M
              JSR      SET_ADD_PNT
              JSR      ST_CHECK       ;READ STATUS
              LDAA     #$B0           ;AUTO WRITE MODE ON
TXT_LOOP:    JSR      WR_COMND
              LDAA     0,Y
              CMPA     #$FF
              BEQ      TXT_END1
              JSR      ST_CH_2        ;READ STATUS 2
              LDAA     0,Y
              JSR      WR_DATA
              INY
              BRA      TXT_LOOP
TXT_END1:    JSR      ST_CH_2         ;READ STATUS 2
              LDAA     #$B2           ;AUTO WRUTE MODE RESET
              JSR      WR_COMND
              RTS
;*****
;*      SUBROUTINE: ST_CH_2
;*      INFO:      Status check 2
;*****
ST_CH_2:     MOVB     #$00,$0006      ; Set port-A INPUT
              LDX      #$0000
              BSET     #$24,X,%%00010000 ;SET COM OFF (1)
              BCLR     #$24,X,%%00000100 ;SET RD ON (0)
              BCLR     #$24,X,%%00001000 ;SET CE ON (0)
LOOP_N2:     LDAA     PORTC
              ANDA     %%00001000
              CMPA     %%00001000
              BNE      LOOP_N2
              BSET     #$24,X,%%00001000 ;SET CE OFF (1)
              BSET     #$24,X,%%00000100 ;SET RD OFF (1)
              MOVB     #$FF,$0006      ;Set port-A OUTPUT
              RTS
;*****
;*      SUBROUTINE: ST_CHECK
;*      INFO:      Status check
;*****
ST_CHECK:    MOVB     #$00,$0006      ;Set port-A INPUT
              LDX      #$0000
              BSET     #$24,X,%%00010000 ;SET COM OFF (1)

```

```

LOOP_N1:      BCLR      #$24,X,#%00000100      ;SET RD ON (0)
              BCLR      #$24,X,#%00001000      ;SET CE ON (0)
              NOP
              NOP
              NOP
              LDAA      PORTC
              BSET      #$24,X,#%00001000      ;SET CE OFF (1)
              BSET      #$24,X,#%00000100      ;SET RD OFF (1)
              ANDA      #%00000011
              CMPA      #%00000011
              BNE       LOOP_N1
              MOVB      #$FF,$0006              ;Set port-A OUTPUT
              RTS

```

```

;*****
;*      SUBROUTINE: WR_DATA
;*      INFO:      Write data
;*****

```

```

WR_DATA:      LDX       #$0000
              STAA      PORTC                  ;DATA OUTPUT
              BCLR      #$24,X,#%00010000      ;SET COM=OFF (0)
              nop
              BCLR      #$24,X,#%00001000      ;SET CE=ON (0)
              nop
              BCLR      #$24,X,#%00000010      ;SET WR=ON (0)
              nop
              nop
              NOP
              BSET      #$24,X,#%00000010      ;SET WR=OFF (1)
              nop
              BSET      #$24,X,#%00001000      ;SET CE=OFF (1)
              BSET      #$24,X,#%00010000      ;SET COM (1)
              RTS

```

```

;*****
;*      SUBROUTINE: WR_COMND
;*      INFO:      Write command
;*****

```

```

WR_COMND:     LDX       #$0000
              STAA      PORTC                  ;DATA OUTPUT
              BSET      #$24,X,#%00010000      ;SET COM=ON (1)
              nop
              BCLR      #$24,X,#%00001000      ;SET CE=ON (0)
              nop
              BCLR      #$24,X,#%00000010      ;SET WR=ON (0)
              nop
              nop
              NOP
              BSET      #$24,X,#%00000010      ;SET WR=OFF (1)
              nop
              NOP
              BSET      #$24,X,#%00001000      ;SET CE=OFF (1)
              RTS

```

```

;*****
;*      SUBROUTINE: SET_ADD_PNT
;*      INFO:      Set ADDRESS POINTER
;*****

```

```

SET_ADD_PNT:  JSR       ST_CHECK              ;READ STATUS
              LDAA      ADDPNT_L
              JSR       WR_DATA
              JSR       ST_CHECK              ;READ STATUS
              LDAA      ADDPNT_M
              JSR       WR_DATA
              JSR       ST_CHECK              ;READ STATUS
              LDAA      #$24
              JSR       WR_COMND
              RTS

```

```

;*****
;*      SUBROUTINE: CLR_SCREEN
;*      INFO:      Set ADDRESS POINTER
;*****

```

```

CLR_SCREEN:   LDD       #$0400
              STD        ADDPNT_M
              JSR       SET_ADD_PNT
              JSR       ST_CHECK              ;READ STATUS
              LDAA      #$B0                  ;AUTO WRITE MODE ON
              JSR       WR_COMND
              LDx        #128                  ;128 POSITIONS = 16 X 8

LOOP_B1:      pshx
              JSR       ST_CH_2              ;READ STATUS 2
              LDAA      #$00
              JSR       WR_DATA
              pulx
              dex
              CPx        #$00
              BHI        LOOP_B1
              JSR       ST_CH_2              ;READ STATUS 2
              LDAA      #$B2                  ;AUTO WRUTE MODE RESET
              JSR       WR_COMND
              RTS

```



```

FCB      $40,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$2
FCB      $40,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$2
FCB      $40,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$2
FCB      $7f,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$ff,$fe
FCB      $0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0,$0

```

B.7. I²C serial EEPROM

```

*****
*
*      School of Engineering
*      The Robert Gordon University, Aberdeen
*
*      File name:      memory.asm
*      Author:         KONSTANTINOS CHRISTIDIS
*      Created:        13/5/2004
*
*****
*      M68HCS12 Assembler Source File
*      PORT F - [xxxx xx(C)(D)], Memory module
*****
ORG      $F000          ; Starting Address in-chip EEPROM
COPCTL   EQU      $0016 ; COP Control Register
PORTF    EQU      $0030 ; Memory module
;*****
POINTER  EQU      $0870
;*
;*      STORE DATA      $0872-76, 77-7B, 7C-80, (80)
;*****
;* Initialisation - Set variables
;*****
START:   CLR      COPCTL ; Clear COP
        LDS      #$0BFF ; Set stac register
;*****
;* Set I/O ports
;*****
        MOVB     #$FF,$0032 ; Set port-F OUTPUT
;*****
;* Write number #10 into Memory module
;*****
        LDD      #10
        JSR      WR_MODULE
LOOPG    BRA      LOOPG ; Continuously repeat, END
;*****
;*
;*      SUBROUTINE: MEM_PC
;*      INFO:      Setting the memory address for sample
;*      PASS:      -
;*      RETURNE:   -
;*****
SHORT_ADD: CLRA
          LDAB     SAMP_MEM ; A:B = 0: SAMPLE
          LDY      #1000
          EMUL
          STD      MEM_ADD_M ; Memory Address Counter
          ADDD     #OFFSET
          STD      ADD_OFST
          RTS
;*****
;*
;*      SUBROUTINE: DELAY50
;*      INFO:      Delay for 50ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY50:  LDX      #65000 ; 50 msec execution time
LOOP50:   DEX
          CPX      #$00
          BHI      LOOP50
          LDX      #REGBS
          RTS
;*****
;*
;*      SUBROUTINE: DELAY01
;*      INFO:      Wait for 100usec
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY01:  LDX      #325 ; 100 usec execution time
LOOP25:   DEX
          CPX      #$00
          BHI      LOOP25
          RTS
;*****

```

```

;* SUBROUTINE: DELAY02
;* INFO: Wait for 770usec
;* PASS: No
;* RETURNE: No
;*****
DELAY02: LDX #1000 ; 770 usec execution time
LOOP77: DEX
CPX #000
BHI LOOP77
RTS
;*****
* Subroutine: WR_MODULE
* Description: Write result to mem. module
;*****
WR_MODULE: LDX #REGBS
JSR STRTBIT ;GOTO STRTBIT SUBROUTINE
LDAA #010100000 ;LOAD CONTROL BYTE INTO
STAA TXBUFF ;TXBUFF FOR OUTPUT TO SEEPROM
JSR TXBYTE ;OUTPUT 1 BYTE TO SEEPROM
LDAA MEM_ADD_M ;GET MSB ADDRESS AND LOAD IN
STAA TXBUFF ;TXBUFF FOR OUTPUT
JSR TXBYTE ;OUTPUT 1 BYTE TO SEEPROM
LDAA MEM_ADD_L ;GET LSB ADDRESS AND LOAD IN
STAA TXBUFF ;TXBUFF FOR OUTPUT
JSR TXBYTE ;OUTPUT 1 BYTE TO SEEPROM
LDAA SAMPLE_M ;DATA BYTE TO OUTPUT IS $A5
STAA TXBUFF
JSR TXBYTE ;OUTPUT 1 BYTE TO SEEPROM
LDAA SAMPLE_L ;DATA BYTE TO OUTPUT IS $A5
STAA TXBUFF
JSR TXBYTE ;OUTPUT 1 BYTE TO SEEPROM
JSR STOPBIT ;SEND STOP BIT TO BEGIN INTERNAL WRITE CYCLE
RTS
;*****
* Subroutine: STARTBIT
* Description: Start bit output subroutine
;*****
STRTBIT: LDAA #00000111
STAA DDRF ;PORT C ALL INPUTS EXCEPT BITS 0,1,2
LDAA #CHIDHI ;SET SCLK AND SDATA HI
STAA PORTF
NOP ;OBEY PROPER START BIT SETUP TIME
NOP
NOP
NOP
NOP
BCLR PFOFF,X,#SDAMASK ;SET DATA LOW FOR STOP BIT
NOP ;OBEY PROPER START BIT HOLD TIME
NOP
NOP
NOP
BCLR PFOFF,X,#SCKMASK ;SET CLK LO
RTS ;END START BIT SUBROUTINE
;*****
* Subroutine: STOPBIT
* Description: Stop bit output subroutine
;*****
STOPBIT: LDAA #00000111
STAA DDRF ;PORT C ALL INPUTS EXCEPT FOR BITS 0,1
BCLR PFOFF,X,#SDAMASK ;MAKE SURE DATA BIT IS LOW
BSET PFOFF,X,#SCKMASK ;CLK BIT HI
NOP ;OBEY PROPER STOP BIT SETUP TIME
NOP
NOP
NOP
BSET PFOFF,X,#SDAMASK ;DATA BIT HI CAUSES STOP BIT
RTS ;END STOP BIT SUBROUTINE
;*****
* Subroutine: INBIT
* Description: This routine reads in one
bit from the data line
;*****
INBIT: LDAA #00000110 ;SET SDATA AS INPUT AND KEEP
STAA DDRF ;SCLK AS OUTPUT
CLR EE_IN ;GUESS INPUT IS A 0
BSET PFOFF,X,#SCKMASK ;SET CLK BIT HI
NOP ;WAIT TO READ INPUT
LDAA PORTF ;GET INPUT FROM SDATA
BCLR PFOFF,X,#SCKMASK ;BRING CLK LO AFTER PORT READ
BITA #DIMASK ;SEE IF INPUT IS 1 OR 0
BEQ DONEIN ;INPUT IS A ZERO
LDAA #00FF ;INPUT BIT IS ACTUALLY A 1
STAA EE_IN ;STORE BACK IN EE_IN
DONEIN: RTS
;*****
* Subroutine: OUTBIT
* Description: This routine writes out one
bit to the sdata line
;*****

```

```

OUTBIT:      LDAA    #00000011
             STAA    DDRF
             LDAA    TXBUFF
             BITA    #DOMASK
             BEQ     LOWOUT
             BSET    PPOFF,X,#SDAMASK
             BRA     CONTOUT
LOWOUT:      BCLR    PPOFF,X,#SDAMASK
CONTOUT: BSET PPOFF,X,#SCKMASK
             NOP
             NOP
             BCLR    PPOFF,X,#SCKMASK
             BCLR    PPOFF,X,#SDAMASK
             RTS

*****
* Subroutine: TXBYTE
* Description: This routine outputs 1 byte
*             of data out the sdata pin
*****
TXBYTE:      LDAB    #8
TXBIT:      JSR     OUTBIT
             ROL     TXBUFF
             DECB
             CMPB    #$00
             BNE     TXBIT
             JSR     INBIT
             LDAA    EE_IN
             BITA    #DIMASK
             BEQ     DONETX
             BSET    PPOFF,X,#LEDMAK
DONETX:      RTS

*****
* Subroutine: RXBYTE
* Description: This subroutine receives
*             1 byte from SEEPROM
*****
RXBYTE:      LDAB    #8
RXBIT:      ROL     RXBUFF
             LDAA    RXBUFF
             ANDA    #%11111110
             STAA    RXBUFF
             JSR     INBIT
             LDAA    EE_IN
             BITA    #DIMASK
             BEQ     CONTRX
             LDAA    RXBUFF
             ORAA    #00000001
             STAA    RXBUFF
CONTRX:      DECB
             CMPB    #$00
             BNE     RXBIT
             RTS

*****
*
*             END OF CODE
*****
             ORG     $FBFE
             DW      START
             ;Reset vector address
             ;Code starting address

```

B.8. Program Vr.1.01

```

*****
*
*       School of Engineering
*       The Robert Gordon University, Aberdeen
*****
*       File name:  pr_vr101.asm
*       Author:     KONSTANTINOS CHRISTIDIS
*       Created:    07/04/2005
*****
*       M68HCS12 Assembler Source File
*       Description : System operation (for prototype)
*
*       PON=50ms and POFF=70ms
*       Range:-1.4 to +1.0V
*****
* LCD:      PORT H - [DDDD DDDD], DATA for LCD
*            PORT P - [XXC CCxx], CONTROL FOR LCD
*            PORT P - [xccc CCxx], CONTROL FOR LCD
*
* KEYPAD:    PORT M - [XXX(<) (E)(>)XX] 3bits Input KEYPAD
* SWEATCH:   PORT M5 - ON=PC, OFF=GPS
* DAC:       PORT B - [DDDD DDDD], LSB DATA for DAC
*            PORT K - [XXXX DDDD], MSB DATA for DAC
* ADC:       PORT A - [DDDD DDDD], MSB DATA for ADC
*            PORT AD1 - [DDDD DDDD], LSB DATA for ADC

```

```

*      PORT P7 - CONTROL DATA for ADC
* GAIN:  PORT T - [XXAB CXXX] 3bits Input KEYPAD
* SCI:   PORT S
* MEMORY: PORT J - [XXXX XX,CLK,DATA], I2C MEMORY MODULE
* RELAYS: PORT K - [XX(S2)(S1) XXXX], CONTROL FOR RELAYS
*****
COPCTL      EQU      $003C      ; COP Control Register
*****
* STARTING ADDRESS FOR DATA
*****
ORG         $3700      ; DATA: RAM starting address
*****
* I/O PORTS
*****
PORTAD1     EQU      $012F      ; ADC: LSB DATA
ENBL_AD1 EQU      $012D
PORTA       EQU      $0000      ; ADC: MSB DATA
DDRA       EQU      $0002
PORTB       EQU      $0001      ; DAC: LSB DATA
DDRB       EQU      $0003
PORTK       EQU      $0032      ; DAC: MSB DATA
DDRK       EQU      $0033
PORTM       EQU      $0250
DDRM       EQU      $0252      ; KEYPAD: 3-BIT DATA
PORTH       EQU      $0260      ; LCD: 8-BIT DATA
DDRH       EQU      $0262
PORTP       EQU      $0258      ; LCD:3-BIT CONTROL
DDRP       EQU      $025A
PORTT       EQU      $0240      ; GAIN: 3-BIT DATA
DDRT       EQU      $0242
PORTJ       EQU      $0268      ; MEMORY
DDRJ       EQU      $026A
PORTS       EQU      $0248
DDRS       EQU      $024A
PORTAD0     EQU      $008F      ; build in ADC
*****
* SCI-0
*****
SC0BDH      EQU      $00C8      ; SCI Baud Rate Control Register High
SC0BDL      EQU      $00C9      ; SCI Baud Rate Control Register Low
SC0CR1      EQU      $00CA      ; SCI Control Register 1
SC0CR2      EQU      $00CB      ; SCI Control Register 2
SC0SR1      EQU      $00CC      ; SCI Status Register 1
SC0SR2      EQU      $00CD      ; SCI Status Register 2
SC0DRH      EQU      $00CE      ; SCI Data Register High
SC0DRL      EQU      $00CF      ; SCI Data Register Low
BIT1        EQU      %00000010  ; SCI - TXD0
BIT0        EQU      %00000001  ; SCI - RXD0
BIT5        EQU      %00100000  ; SCI
BIT7        EQU      %10000000  ; SCI
BIT32       EQU      %00001100  ; SCI
*****
* DAC DATA
*****
VOLT_M      DB        #0        ;$3000: Voltage variable for DAC (MSByte)
VOLT_L      DB        #0        ;$3001: Voltage variable for DAC (LSByte)
VOLT_M_AUX  DB        #0        ;Voltage var. to support Sensor MASK control
VOLT_L_AUX  DB        #0        ;Voltage var. to support Sensor MASK control
*****
* ADC DATA
*****
SMP_16M     DW        #0        ;$0802: ADC sample storage (MSWord)
SMP_16L     DW        #0        ;
SAMPLE_M_DW #0
*****
* NUMBER TO CHARACTER
*****
DIGIT1      DB        #0        ;$0804: 1st Digit Number Address (LSB)
DIGIT2      DB        #0        ;$0805: 2nd Digit Number Address
DIGIT3      DB        #0        ;$0806: 3rd Digit Number Address
DIGIT4      DB        #0        ;$0807: 4th Digit Number Address
DIGIT5      DB        #0        ;$0808: 5th Digit Number Address (MSB - 16bits)
RESULTS     DW        #0        ;$0809: 16 bits result Address (for division)
*****
* PEAK ALGORITHM
*****
AMPLITUDE   DW        #0        ;$080B: PEAK CURRENT
COUNTER     DW        #0        ;$080D: Counter (sample point)?????????????
*****
* CONVERT TO UNSIGNED NUMBER
*****
ADD_M       DB        #0        ;$0810: Aux address for pos - neg shift (MSB)
ADD_L       DB        #0        ;$0811: Aux address for pos - neg shift (LSB)
*****
* CHARACTERISATION
*****
* DBASE-GCE

```



```

*****
PBMX      DW      #9500      ; Pb max rng (14000-5250=8750, +750=9250)
PBMN      DW      #8000      ; Pb min rng (14000-5250=8750, -750=8000)
CDMX      DW      #6860      ; Cd max rng (14000-7740=6260, +600=6860)
CDMN      DW      #5660      ; Cd min rng (14000-7740=6260, -600=5660)
HGMX      DW      #15570     ; Hg max rng (14000+1270=15270, +250=15570)
HGMN      DW      #15020     ; Hg min rng (14000+1270=15270, -250=15020)
ZNMX      DW      #4200      ; Zn max rng (14000-10400=3600, +750=4350)
ZNMN      DW      #3000      ; Zn min rng (14000-10400=3600, -750=2850)
N11MX     DW      #6760      ; Ni1 max rng (14000-8540=5460, +1300=6760)
N11MN     DW      #4160      ; Ni1 min rng (14000-8540=5460, -1300=4160)
N12MX     DW      #15190     ; Ni2 max rng (14000-310=13690, +1500=15190)
N12MN     DW      #12190     ; Ni2 min rng (14000-310=13690, -1500=12190)
CULMX     DW      #6140      ; Cu1 max rng (14000-8610=5390, +1250=6640)
CULMN     DW      #4640      ; Cu1 min rng (14000-8610=5390, -1250=4140)
CU2MX     DW      #10840     ; Cu2 max rng (14000-3410=10590, +250=10840)
CU2MN     DW      #10340     ; Cu2 min rng (14000-3410=10590, -250=10340)
CU3MX     DW      #13530     ; Cu3 max rng (14000-1220=12780, +750=13530)
CU3MN     DW      #12030     ; Cu3 min rng (14000-1220=12780, -750=12030)
CHR_FLG   DB      #0        ; Characterisation flag
POTEN     DW      #0        ; $0820: 16 bit Potential variable
COUNTMAX DW      #0        ; $0822: 16 bit Max Counter (potential)
SINFLAG   DB      #0        ; $0824: Ditermination of sign OFF=-
PEAK      DB      #0        ; $0825:
C_SMP16M  DW      #0        ; $0826: Variable for current sample
C_SMP16L  DW      #0        ;
CNT_ADDR   DW      #0        ; $0828: 16 bit Address counter
TIMER_60  DW      #0        ; $082A: 16 bit Timer variable for deposition
*****
* I2C COMMS
*****
PFOFF     EQU      $0030      ; OFFSET FROM CONTROL REG BEG.
DDRF      EQU      $0032      ; F PORT DIRECTION REGISTER.
REGBS     EQU      $0000      ; REGISTER BASE ADDRESS.
TXBUFF    DB      #0        ; $082C
EE_IN     DB      #0        ; $082D
MEM_ADD_M  DB      #0        ; $082E
MEM_ADD_L  DB      #0        ; $082F
RXBUFF    DB      #0        ; $0830
MEM_DATA_M DB      #0        ; $0831
MEM_DATA_L DB      #0        ; $0832
CNT_2      DW      #0        ; $0833
CHIDHI     EQU      $00000011 SET BOTH CLK AND DATA HI
CHIDLO     EQU      $00000010 SET CLK HI AND DATA LO
CLODHI     EQU      $00000001 SET CLK LO AND DATA HI
CLODLO     EQU      $00000000 SET CLK AND DATA BOTH LO
DIMASK     EQU      $00000001 BIT MASK FOR DATA IN BIT
DOMASK     EQU      $10000000 BIT MASK FOR DATA OUT BIT
SDAMASK    EQU      $00000001 BIT MASK FOR SERIAL DATA
SCKMASK    EQU      $00000010 BIT MASK FOR SERIAL CLOCK
LEDMASK    EQU      $00000100 BIT MASK FOR ACK FAILED LED
OFFSET     EQU      #900
P_2        DB      #0        ; $0835
A_MIN      DW      #0        ; $0836
A_MIN_1    DW      #0        ; $0838
MINPOS     DW      #1        ; $083A
MINPOS_1   DW      #1        ; $083C
P_FLAG     DW      #0        ; $083E
CNT_X      DW      #1        ; $0840
I          DW      #0        ; $0842
DATA_1     DW      #0        ; $0844
DATA_2     DW      #0        ; $0846
DATA_3     DW      #0        ; $0848
DATA_4     DW      #0        ; $084A
OLD_DATA   DW      #0        ; $084C
MIN        DW      #0        ; $084E
MAX        DW      #0        ; $0850
MIN_1      DW      #0        ; $0852
MAX_1      DW      #0        ; $0854
AMP        DW      #0        ; $0856
DEF        DW      #0        ; $0858
AV_MIN     DW      #0        ; $085A
AMP_2      DW      #0        ; $085C
FLAG       DB      #1        ; $085E
P          DB      #1        ; $085F
SAMP_MEM   DB      #0        ; $0860: Sample to store in memory
CNT_1      DW      #0        ; $0861
ADATA_1     DW      #0        ; $0863
ADATA_2     DW      #0        ; $0865
ADATA_3     DW      #0        ; $0867
ADATA_4     DW      #0        ; $0869
CNT_PR     DW      #0        ; $086B
F          DW      #0        ; $086D
ALG1_THR   DW      #40       ; Threshold 4.0uA - Scr. Pr. Sensor II
ALG1_THR   DW      #5        ; Threshold 0.5uA - Carb. Paste Sensor
ADD_OFST   DW      #0        ; $086E: Base Address for counting sample
*****
* AUTOMATIC GAIN
*****

```

```

GN_PNT1      DB      #0
GN_PNT2      DB      #0
GAIN         DB      #0                ;$0870
GAIN0        DB      #000000000
GAIN1        DB      #00001000        ;$0870
GAIN2        DB      #00001000        ;$0870
GAIN3        DB      #00001000        ;$0870
GAIN4        DB      #00100000        ;$0870
GAIN5        DB      #00101000        ;$0870
GAIN6        DB      #00110000        ;$0870
GAIN7        DB      #00111000        ;$0870
GN_RES       DW      #0                ;$0000
GN_RES0      DW      #31623            ;$0872
GN_RES1      DW      #25914            ;$0872
GN_RES2      DW      #14698            ;$0872
GN_RES3      DW      #7722             ;$0872
GN_RES4      DW      #2959             ;$0872
GN_RES5      DW      #2322             ;$0872
GN_RES6      DW      #1722             ;$0872
GN_RES7      DW      #811              ;$0872
X_SAMPLA DW  #0                ;$0874
X_SAMPLB DW  #0                ;$0874
X_SAMPL0 DW  #0                ;$0874
X_SAMPL1 DW  #0                ;$0874
X_SAMPL2 DW  #0                ;$0874
X_SAMPL3 DW  #0                ;$0874
X_SAMPL4 DW  #0                ;$0874
X_SAMPL5 DW  #0                ;$0874
X_SAMPL6 DW  #0                ;$0874
X_SAMPL7 DW  #0                ;$0874
SMP_M16M DW  #0                ;
SMP_M16L DW  #0                ;
SAMPL_MM dw  #0                ;
DIV_FLG1 DB  #0                ;1=div10, 10=div1000
DIV_FLG2 DB  #0                ;0=Less than 500.00uA,1=Higher than 500.00uA
RES_PPM      DW      #0
*****
* ARRAY (RAM) FOR PEAK STORAGE
*****
ORG          $3900
POINTER      DW      #3902            ;STORE DATA $3902-06, 07-0B, 0C-10, (00)
*****
; * STARTING ADDRESS FOR THE PROGRAM
*****
ORG          $1000                ; PROGRAM: RAM starting address
*****
; * Initialisation - Set variables
*****
START:       CLR      COPCTL        ; Clear COP
             LDS      #3BFF        ; Set stac register
*****
; * Set I/O ports
*****
CLR          DDRA                ; Set port-A INPUT
BSET         ENBL_AD1,#01111111    ; Enable port-AD1 (INPUT)
BSET         DDRB,#01111111        ; Set port-B OUTPUT
BSET         DDRK,#00000111        ; Set port-K OUTPUT
MOV          #FF,DDRH              ; Set port-H OUTPUT
BSET         DDRP,#01111100        ; Set port-P OUTPUT
BSET         DDRT,#000111000       ; Set port-T OUTPUT
BSET         DDRJ,#000000011       ; Set J0,J1 OUTPUTS
BCLR         DDRM,#00001100        ; Set M2,M3,M4 INPUTS
BSET         DDRM,#000100000       ; Set M5 OUTPUT
BSET         DDRK,#000110000       ; Set K4,K5 OUTPUTs
*****
; * Initialise LCD
*****
LDAA         #00111000            ; 8bit, 2line 5x7dot
JSR          CNTLCT
LDAA         #00001110            ; Display control
JSR          CNTLCT
LDAA         #00000001            ; Clear LCD
JSR          CNTLCT
LDAA         #00000110            ; Increment
JSR          CNTLCT
*****
; * Parking - Initial voltage (0V) (#2048)
; * DISCONNECT SENSORS
*****
LDD          #2048
STD          VOLT_M
STAA         PORTK                ;S1 and S2 bits of portK are low
STAB         PORTB
*****
; * Initialise Detection Algorithm Variables
*****
LDD          #1                    ;A:B=0:1
STAA         P_2                  ;p_2=0, 0-start 1-peak, 2-high/low
STD          MINPOS                ;minpos=1;

```

```

        STD     MINPOS_1 ;minpos_1=1;
        STD     CNT_X      ;CNT_X=1;
        STAB    P          ;P=1;
        STAB    FLAG       ;FLAG=1;
        STAB    DIV_FLG2   ;Set to higher than 500uA;
        MOVW    #$3902, POINTER
        LDAA    #$FF
        LDY     POINTER
PLACES:  STAA    0,Y        ;One place (8bit) $0000
        INY
        CPY     #$39ff     ;Initialise from $3902 - $39FF
        BLO     PLACES
;*****
;* Clear general variables
;*****
        CLRA
        CLRB
        STD     MAX        ; Clear Maximum sample
        STD     COUNTER    ; Clear Counter
        STD     CNT_ADDR   ; Address counter
        STAA    SAMP_MEM   ; Sample to store in the memory
        STD     MEM_ADD_M  ; Memory Address Counter
;*****
; ***** Main Program *****
;*****
;*****
;* Print Welcome on LCD
;*****
        JSR     CLR_LCD    ; Clear LCD
        LDY     #MSG_Wa
        JSR     CHAR_STR
        JSR     LINE_LCD   ; Next line
        LDY     #MSG_Wb
        JSR     CHAR_STR
        JSR     ENT_BTN    ; Read ENTER bout-on
;*****
;* Initialise SCI-1 to 4800
;*****
        JSR     INIT_SCI   ; Initialise SCI
;*****
;* Print Wait 1 min on LCD
;*****
        JSR     CLR_LCD    ; Clear LCD
        LDY     #MSG_1a
        JSR     CHAR_STR
        JSR     LINE_LCD   ; Next line
        LDY     #MSG_1b
        JSR     CHAR_STR
;*****
;* Initial voltage (-1.4V) (#0901)
;*****
        LDD     #0901
        STD     VOLT_M
        STD     VOLT_M_AUX
        BSET    VOLT_M_AUX, %%00010000 ; Connect sensor-1 (S1)
        LDD     VOLT_M_AUX
        STAA    PORTK      ; Sent also Control (S1=1)
        STAB    PORTB
;*****
;* Deposition timer for 1 min
;*****
        LDD     #60
        STD     TIMER_60   ; Clear deposition timer
LOOP6:  JSR     TIMER
        CLRA
LOOP8:  JSR     DELAY50     ; Clear time counter
        INCA
        CMPA    #15        ; 260ms + 15 x 50ms = ~1s
        BLO     LOOP8
        LDD     TIMER_60
        DECB
        STD     TIMER_60
        CMPB    #0
        BHI     LOOP6
;*****
;* Print on LCD WORKING...
;*****
        JSR     CLR_LCD    ; Clear LCD
        LDY     #MSG_2
        JSR     CHAR_STR
;*****
;* REPEAT PROCESS
;*****
;*****
;* GAIN CONTROL
;* Read ADC, LOW sample
;*****
LOOP:   JSR     GAIN_CNT
;*****

```

```

;* 50 msec step up (21bits -1.22 x 21 = 25.62mV)
;*****
                LDD      VOLT_M
                ADDD     #21
                STD      VOLT_M
                STD      VOLT_M_AUX
                BSET     VOLT_M_AUX, #%00010000      ; Connect sensor-1 (S1)
                LDD      VOLT_M_AUX
                STAA     PORTK                        ; Sent also Control (S1=1)
                STAB     PORTB
                JSR      DELAY50
;*****
;* GAIN CONTROL
;* Read ADC, HIGH sample
;*****
                JSR      GN_CNT2
;*****
;* GAIN CONTROL
;* Find best tuning
;*****
                LDAA     GN_PNT2
                LSLA
                STAA     GN_PNT1
                LDY      #X_SAMPL0
                LDAA     GN_PNT1
NTXT2:          CMPA     #0
                BEQ      VELE2
                DECA
                INY
                BRA      NTXT2
VELE2:          LDD      0,Y
                STD      X_SAMPLA
                LDY      #GN_RES0
                LDAA     GN_PNT1
NTXT3:          CMPA     #0
                BEQ      VELE3
                DECA
                INY
                BRA      NTXT3
VELE3:          LDD      0,Y
                STD      GN_RES
;*****
;* MULTIPLY SAMPLE A WITH RESOLUTION
;*****
                LDD      X_SAMPLA
                LDY      GN_RES
                EMUL                      ; X_SAMPLA*GN_RES*100=(Y:D)
                STD      SMP_M16L
                STY      SMP_M16M
;*****
;* MULTIPLY SAMPLE B WITH RESOLUTION
;*****
                LDD      X_SAMPLB
                LDY      GN_RES
                EMUL                      ; X_SAMPLB*GN_RES*100=(Y:D)
                STD      C_SMP16L
                STY      C_SMP16M
;*****
;* Calculate difference NUMBER 1 - NUMBER 2 [method II]
;*****
                LDD      SMP_M16L
                SUBD     C_SMP16L
                STD      SMP_16L
                BCC      NEXT
                LDD      C_SMP16M
                ADDD     #1
                STD      C_SMP16M
NEXT:           LDD      SMP_M16M
                SUBD     C_SMP16M
                STD      SMP_16M
;*****
;* Multiply sample with resolution
;*****
                LDY      SMP_16M
                LDD      SMP_16L
                LDX      #10000
                EDIV                      ; (Y:D)/100=Y.D
                STY      SAMPLE_M          ; Store results
                STY      SAMPL_MM
                movb     #100, DIV_FLG1    ; Set division /100
;*****
;* Sent result to PC via serial SCI-0
;*****
                LDAA     #11              ; Sent byte 11 (control word to start process)
                JSR      OUT_CHAR
                LDAA     #11              ; Sent byte 11 for second time in case is lost
                JSR      OUT_CHAR
                LDAA     DIV_FLG1         ; Load first byte - gain, to transmit

```

```

JSR     OUT_CHAR
LDD     SAMPL_MM           ; Load 5 digit data - difference
JSR     CONV
LDAA    DIGIT1
JSR     OUT_CHAR
LDAA    DIGIT2
JSR     OUT_CHAR
LDAA    DIGIT3
JSR     OUT_CHAR
LDAA    DIGIT4
JSR     OUT_CHAR
LDAA    DIGIT5
JSR     OUT_CHAR
LDD     GN_RES             ; Load 5 digit data - difference
JSR     CONV
LDAA    DIGIT1
JSR     OUT_CHAR
LDAA    DIGIT2
JSR     OUT_CHAR
LDAA    DIGIT3
JSR     OUT_CHAR
LDAA    DIGIT4
JSR     OUT_CHAR
LDAA    DIGIT5
JSR     OUT_CHAR
LDD     X_SAMPLEB          ; Load 5 digit data - difference
JSR     CONV
LDAA    DIGIT1
JSR     OUT_CHAR
LDAA    DIGIT2
JSR     OUT_CHAR
LDAA    DIGIT3
JSR     OUT_CHAR
LDAA    DIGIT4
JSR     OUT_CHAR
LDAA    DIGIT5
JSR     OUT_CHAR
LDD     X_SAMPLA           ; Load 5 digit data - difference
JSR     CONV
LDAA    DIGIT1
JSR     OUT_CHAR
LDAA    DIGIT2
JSR     OUT_CHAR
LDAA    DIGIT3
JSR     OUT_CHAR
LDAA    DIGIT4
JSR     OUT_CHAR
LDAA    DIGIT5
JSR     OUT_CHAR
;*****
;* Peak detection algorithm
;*****
JSR     ALGO1
;*****
;* 50 sec step down (19 bit 1.22x19=23.18)
;*****
LDD     VOLT_M              ; Load current voltage potential
SUBD    #19                 ; Add 20bits to current potential
STD     VOLT_M              ; Store new potential
STD     VOLT_M_AUX
BSET    VOLT_M_AUX,##00010000 ; Connect sensor-1 (S1)
LDD     VOLT_M_AUX
STAA    PORTK               ; Sent also Control (S1=1)
STAB    PORTB               ; LSB DAC output
JSR     DELAY50              ; Wait for 50msec
JSR     DELAY10
JSR     DELAY10
;*****
;* Counter increment by (2x1.2mV)
;*****
LDD     COUNTER              ; Add 2.4mV
ADDD    #24
STD     COUNTER
;*****
;* Counter for memory module Address
;*****
LDD     MEM_ADD_M            ; Memory address increase 2 positions
ADDD    #2
STD     MEM_ADD_M
;*****
;* Check if reach potential +0.0V (2048) or +1.0V (2867)
;*****
LDD     VOLT_M              ; Load current voltage potential
CPD     #2867                ; 1.0V Step potential 2 = 1.0V
LBLO    LOOP                 ; If no, repeat process GO to LOOP
; If yes, continue
;*****
;* Terminate COMM Module
;*****

```



```

        LDAA    #12
        JSR     OUT_CHAR
        LDAA    #12
        JSR     OUT_CHAR
;*****
;* Disconnect Sensor-1 (CELL)
;*****
        BCLR    PORTK,%00010000 ; Disconnect sensor-1 (S1)
;*****
;* Print on LCD End of Process
;*****
        JSR     CLR_LCD           ; Clear LCD
        LDY     #MSG_3
        JSR     CHAR_STR
        jsr     ENT_BTN           ; Read ENTER bout-on
;*****
;* Print Ready FOR peak search
;*****
        JSR     CLR_LCD           ; Clear LCD
        LDY     #MSG_6a
        JSR     CHAR_STR
        JSR     LINE_LCD          ; Next line
        LDY     #MSG_6b
        JSR     CHAR_STR
        JSR     ENT_BTN           ; Read ENTER bout-on
;*****
;* Print on LCD Results peak & position
;*****
        MOVW    #$3902,POINTER
        CLR     PEAK
TR_AGAIN: LDY     POINTER
        LDAA    0,Y
        CMPA    #$FF
        BEQ     LV_LOOP
        STAA    SINFLAG
        LDD     1,Y
        STD     POTEN
        LDD     3,Y
        STD     AMPLITUDE
        LDD     5,Y
        STD     CNT_PR
        INC     PEAK
        JSR     PRDATA            ; PRINT AMP_2 and CNT_1
        JSR     ENT_BTN           ; Read ENTER bout-on
        JSR     CHARACT          ; Print Characterisation results
        JSR     ENT_BTN           ; Read ENTER bout-on
        LDD     POINTER
        ADDD    #7
        STD     POINTER
        BRA     TR_AGAIN
LV_LOOP: LDAA    PEAK
        BEQ     NO_PEAK
        JSR     CLR_LCD           ; Clear LCD
        LDY     #MSG_3           ; End Message
        JSR     CHAR_STR
        BRA     LOOPGX
NO_PEAK: JSR     CLR_LCD           ; Clear LCD
        LDY     #MSG_TR1         ; Print "No Analyte Match"
        JSR     CHAR_STR
        JSR     ENT_BTN           ; Read ENTER bout-on
LOOPGX: ;*****
;* Print on LCD End of Process
;*****
        JSR     CLR_LCD           ; Clear LCD
        LDY     #MSG_3
        JSR     CHAR_STR
        jsr     ENT_BTN           ; Read ENTER bout-on
;*****
;END OF PROCESS
;*****
LOOPGX:  BRA     LOOPGX           ; Continuously repeat, END
;*****
;* Subroutine: GN_ADC
;*
;* Note: Gain control for ADC
;*****
GN_ADC:  STAA    PORTT
        JSR     DELAY001         ; Delay 200nsec
        JSR     READADC          ; Read ADC for gain 000
        JSR     NEGPOS           ; Negative and positive shift results on D-REGISTER
        RTS
;*****
;* Subroutine: GAIN_CNT
;*
;* Note: Gain control for ADC FOR FIRST SAMPLE
;*****
GAIN_CNT: MOVW    #0,GN_PNT1
        LDAA    GAIN0
        JSR     GN_ADC

```

```

STD      X_SAMPL0      ; Store sample for gain 000
CPD      #51491        ; +9.8(*0.8)
LBHS     NO_GN
CPD      #14044        ; -9.8(*0.8)
LBLS     NO_GN
MOVB     #1,GN_PNT1
LDAA     GAIN1
JSR      GN_ADC
STD      X_SAMPL1      ; Store sample for X gain
CPD      #43375        ; +5(*0.8)
LBHS     NO_GN
CPD      #22160        ; -5(*0.8)
LBLS     NO_GN
MOVB     #2,GN_PNT1
LDAA     GAIN2
JSR      GN_ADC
STD      X_SAMPL2      ; Store sample for X gain
CPD      #38174        ; +2.5(*0.7)
LBHS     NO_GN
CPD      #27361        ; -2.5(*0.7)
LBLS     NO_GN
MOVB     #3,GN_PNT1
LDAA     GAIN3
JSR      GN_ADC
STD      X_SAMPL3      ; Store sample for X gain
CPD      #34888        ; +0.98(*0.7)
LBHS     NO_GN
CPD      #30647        ; -0.98(*0.7)
LBLS     NO_GN
MOVB     #4,GN_PNT1
LDAA     GAIN4
JSR      GN_ADC
STD      X_SAMPL4      ; Store sample for X gain
CPD      #34358        ; +0.735(*0.7)
LBHS     NO_GN
CPD      #31177        ; -0.735(*0.7)
LBLS     NO_GN
MOVB     #5,GN_PNT1
LDAA     GAIN5
JSR      GN_ADC
STD      X_SAMPL5      ; Store sample for X gain
CPD      #33849        ; +0.5(*0.7)
LBHS     NO_GN
CPD      #31686        ; -0.5(*0.7)
LBLS     NO_GN
MOVB     #6,GN_PNT1
LDAA     GAIN6
JSR      GN_ADC
STD      X_SAMPL6      ; Store sample for X gain
CPD      #33308        ; +0.25(*0.7)
LBHS     NO_GN
CPD      #32227        ; -0.25(*0.7)
LBLS     NO_GN
MOVB     #7,GN_PNT1
LDAA     GAIN7
JSR      GN_ADC
STD      X_SAMPL7      ; Store sample for X gain
NO_GN:   RTS
;*****
;* Subroutine:  GN_CNT2
;*
;*      Note:  Gain control for ADC FOR SECOND SAMPLE
;*****
GN_CNT2: MOVB     #0,GN_PNT2
LDAA     GAIN0
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #51491        ; +9.8(*0.8)
LBHS     NO_GN1
CPD      #14044        ; -9.8(*0.8)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #1,GN_PNT2
LDAA     GAIN1
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000
CPD      #43375        ; +5(*0.8)
LBHS     NO_GN1
CPD      #22160        ; -5(*0.8)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #2,GN_PNT2
LDAA     GAIN2
JSR      GN_ADC
STD      X_SAMPLB      ; Store sample for gain 000

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```

CPD      #38174          ; +2.5(*0.7)
LBHS     NO_GN1
CPD      #27361          ; -2.5(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #3,GN_PNT2
LDAA     GAIN3
JSR      GN_ADC
STD      X_SAMPLB        ; Store sample for gain 000
CPD      #34888          ; +0.98(*0.7)
LBHS     NO_GN1
CPD      #30647          ; -0.98(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #4,GN_PNT2
LDAA     GAIN4
JSR      GN_ADC
STD      X_SAMPLB        ; Store sample for gain 000
CPD      #34358          ; +0.735(*0.7)
LBHS     NO_GN1
CPD      #31177          ; -0.735(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #5,GN_PNT2
LDAA     GAIN5
JSR      GN_ADC
STD      X_SAMPLB        ; Store sample for gain 000
CPD      #33849          ; +0.5(*0.7)
LBHS     NO_GN1
CPD      #31686          ; -0.5(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #6,GN_PNT2
LDAA     GAIN6
JSR      GN_ADC
STD      X_SAMPLB        ; Store sample for gain 000
CPD      #33308          ; +0.25(*0.7)
LBHS     NO_GN
CPD      #32227          ; -0.25(*0.7)
LBLS     NO_GN1
LDAA     GN_PNT1
CMPA     GN_PNT2
LBLS     NO_GN1
MOVB     #7,GN_PNT2
LDAA     GAIN7
JSR      GN_ADC
STD      X_SAMPLB        ; Store sample for X gain
NO_GN1:   RTS
;*****
; SUBROUTINE:  D_CHAR
; FUNCTION:
;*****
D_CHAR:   JSR      PRNLCD
          RTS
;*****
; SUBROUTINE:  IN_CHAR
; FUNCTION:    Receives typed character into register A.
;*****
IN_CHAR:  LDAA     SC0SR1          ; Check status reg (RDRF in bit 5)
          ANDA     #BIT5          ; Check if receive buffer full
          BEQ      IN_CHAR        ; Wait until data present
          LDAA     SC0DRL         ; Data -> A register
          STAA     CHAR
          RTS                    ; Return from subroutine
;*****
; SUBROUTINE:  OUT_CHAR
; FUNCTION:    Receives typed character into register A.
;*****
OUT_CHAR: NOP
LP_LP:    BRCLR   SC0SR1,$80,LP_LP
          STAA     SC0DRL
          RTS                    ; Return from subroutine
;*****
; SUBROUTINE:  INIT_SCI
; INFO:        Baud rate 4800, 8 data bits, 1 stop
; PASS:        No
; RETURNE:     No
;*****
INIT_SCI: BSET     DDRL,$00000010 ; Set data direction to output for
          BCLR     DDRL,$00000001 ; PortS bit1 (Tx) and input PortS bit0 (Rx)
          LDAA     #$01           ; Set baud rate to 4800

```

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        STAA    SC0BDH        ; (25)16MHz/2 / 16 / 104 = 4.800kHz
        LDAA    #$46          ; SC1:SCP0=11 SCR2:SCR1:SCR0=011
        STAA    SC0BDL        ; set baud rate to 4800
        LDAA    #0            ; 1 start/stop bit, 8 data bits
        STAA    SC0CR1        ; no wakeup
        LDAA    #BIT32        ; Enable Tx and Rx;
        STAA    SC0CR2        ; all interrupts disabled
        LDAA    SC0SR1
        STD     SC0DRH
        RTS

;*****
;*      SUBROUTINE: CLR_LCD
;*      INFO:      Clear LCD
;*      PASS:      No
;*      RETURNE:   No
;*****
CLR_LCD: LDAA    #%00000001    ; Clear LCD
        JSR     CNTLCT
        RTS

;*****
;*      SUBROUTINE: LINE_LCD
;*      INFO:      Next Line (LCD)
;*      PASS:      No
;*      RETURNE:   No
;*****
LINE_LCD: LDAA    #%11000000    ; Next line
        JSR     CNTLCT
        RTS

;*****
;*      SUBROUTINE: CNTLCT
;*      INFO:      Control output to LCD
;*      PASS:      Register-A, data
;*      RETURNE:   No
;*****
CNTLCT:  LDAB    #%00000000    ; CONTROL: (E=0,R/W=0,RS=0)
        STAB    PORTP
        STAA    PORTH
        JSR     DELAYLCD
        LDAB    #%00000100    ; CONTROL: (E=1,R/W=0,RS=0)
        STAB    PORTP
        JSR     DELAYLCD
        RTS

;*****
;*      SUBROUTINE: PRNLCD
;*      INFO:      Data output to LCD
;*      PASS:      Register-A, data
;*      RETURNE:   No
;*****
PRNLCD:  LDAB    #%00010000    ; CONTROL: (E=0,R/W=0,RS=0)
        STAB    PORTP
        STAA    PORTH
        JSR     DELAYLCD
        LDAB    #%00010100    ; CONTROL: (E=1,R/W=0,RS=1)
        STAB    PORTP
        JSR     DELAYLCD
        RTS

;*****
;*      SUBROUTINE: DELAY50
;*      INFO:      Delay for 50ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY50: PSHA
        LDAA    #5            ; 5 x 10msec DELAY
LOOP50:  JSR     DELAY10
        DECA
        CMPA    #0
        BHI     LOOP50
        PULA
        RTS

;*****
;*      SUBROUTINE: DELAY10
;*      INFO:      Delay for 10ms
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAY10: LDX     #40625        ;10msec execution time
LOOP10:  DEX
        CFX     #$00
        BHI     LOOP10
        LDX     #REGBS
        RTS

;*****
;*      SUBROUTINE: DELAYLCD
;*      INFO:      Delay for LCD operation
;*      PASS:      No
;*      RETURNE:   No
;*****
DELAYLCD: JSR     DELAY10      ;10msec execution time

```

```

RTS
;*****
;* SUBROUTINE: READADC
;* INFO:      Read ADC Converter
;* PASS:      No
;* RETURNE:   Register-D
;*****
READADC:      BSET      PORTP,##10000000 ; Initial stage (Conversion=OFF)
              JSR        DELAY01
              BCLR      PORTP,##10000000 ; Conversion=ON
              NOP
              NOP
              NOP
              BSET      PORTP,##10000000 ; Conversion=OFF
              JSR        DELAY01 ; Wait for BUSY signal
              LDAA      PORTA ; Read MSByte
              LDAB      PORTAD1 ; Read LSByte
              RTS
;*****
;* SUBROUTINE: DELAY01
;* INFO:      Wait for 100usec
;* PASS:      No
;* RETURNE:   No
;*****
DELAY01:      LDX        #1016 ; 100 usec execution time
LOOP25:       DEX
              CPX        #$00
              BHI        LOOP25
              RTS
;*****
;* SUBROUTINE: DELAY001
;* INFO:      Small recovery delay
;* PASS:      No
;* RETURNE:   No
;*****
DELAY001:     nop ; 40 nsec execution time each
              nop
              nop
              nop
              nop
              nop ; 200 nsec overall execution time
              rts
;*****
;* SUBROUTINE: DELAY02
;* INFO:      Wait for 770usec
;* PASS:      No
;* RETURNE:   No
;*****
DELAY02:      LDX        #3125 ; 770 usec execution time
LOOP77:       DEX
              CPX        #$00
              BHI        LOOP77
              RTS
;*****
;* SUBROUTINE: CONV
;* INFO:      Convert decimal number to ASCII
;* PASS:      Register-D
;* RETURNE:   DIGIT1,DIGIT2,DIGIT3,DIGIT4,DIGIT5.
;*****
CONV:         CLR        DIGIT1 ; Clear all digits variables
              CLR        DIGIT2
              CLR        DIGIT3
              CLR        DIGIT4
              CLR        DIGIT5
              CPD        #0
              BEQ        LP
              LDX        #10
              IDIV
              STAB      DIGIT1 ; Check first digit
              STX        RESULTS
              LDD        RESULTS
              CPD        #0
              BEQ        LP
              LDX        #10
              IDIV
              STAB      DIGIT2 ; Check second digit
              STX        RESULTS
              LDD        RESULTS
              CPD        #0
              BEQ        LP
              LDX        #10
              IDIV
              STAB      DIGIT3 ; Check third digit
              STX        RESULTS
              LDD        RESULTS
              CPD        #0
              BEQ        LP
              LDX        #10
              IDIV
              STAB      DIGIT4 ; Check fourth digit

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```

        STX      RESULTS
        LDD      RESULTS
        STAB     DIGIT5          ; Check fifth digit
LP:      BSET     DIGIT1,%%00110000; ASCII conversion
        BSET     DIGIT2,%%00110000; ASCII conversion
        BSET     DIGIT3,%%00110000; ASCII conversion
        BSET     DIGIT4,%%00110000; ASCII conversion
        BSET     DIGIT5,%%00110000; ASCII conversion
        RTS
;*****
;*      SUBROUTINE: TIMER
;*      INFO:      Count Deposition time
;*      PASS:      TIMER_60
;*      RETURNE:   None
;*****
TIMER:   JSR      CLR_LCD          ; Clear LCD
        LDY      #MSG-Ta          ; TEXT "Wait: "
        JSR      CHAR_STR
        LDD      TIMER_60; Load Timer
        JSR      CONV
        LDAA     DIGIT3          ; No of digit on LCD 8/20
        JSR      PRNLCD
        LDAA     DIGIT2          ; No of digit on LCD 7/20
        JSR      PRNLCD
        LDAA     DIGIT1          ; No of digit on LCD 8/20
        JSR      PRNLCD
        LDY      #MSG-Tb          ; TEXT " sec "
        JSR      CHAR_STR
        RTS
;*****
;*      SUBROUTINE: NEGPOS
;*      INFO:      Negative and positive shift
;*      PASS:      Register-D
;*      RETURNE:   Register-D
;*****
NEGPOS:  CPD      #$7FFF          ; 01111111-FF (negative)
        BLE      POS            ; Positive number
        COMA     ; A complement
        COMB     ; B complement
        STD      ADD_M          ; ADD_M
        LDD      #$7FFF
        SUBD     ADD_M          ; Obtain shift
        BRA      NEG
POS:     ADDD     #$7FFF          ; Shift UP
NEG:     RTS
;*****
;*      SUBROUTINE: ENT_BTN
;*      INFO:      Wait to press Enter button
;*****
ENT_BTN: NOP
INTROD8: LDAA     PORTM          ; Read ENTER bout-on
        ANDA     %%00001000      ; READ M4 PIN
        CMPA     %%00001000
        BNE     INTROD8
        RTS
;*****
;*      SUBROUTINE: CHARACT
;*      INFO:      Print Characterisation results on LCD
;*      PASS:      MAX, THRES, POTEN, PBMIN, PBMAX....
;*      RETURNE:   No
;*****
CHARACT: CLR      CHR_FLG
        LDD      CNT_PR          ; Check for Pb
        CPD      PBMIN
        BLO     END011A
        CPD      PBMAX
        BHI     END011A
        JSR      CLR_LCD          ; Clear LCD
        MOVB     #1,CHR_FLG
        LDY      #MSG_CHRa        ; Display "Contmin. LEAD (Pb) "
        JSR      CHAR_STR
        LDD      #1137            ; A=1.137 X 1000
        JSR      PRN_PPM
END011A: LDD      CNT_PR          ; Check for Cd
        CPD      CDMIN
        BLO     END011B
        CPD      CDMAX
        BHI     END011B
        JSR      CLR_LCD          ; Clear LCD
        MOVB     #1,CHR_FLG
        LDY      #MSG_CHRb        ; Display "Contm. CADMIUM (Cd) "
        JSR      CHAR_STR
        LDD      #2084            ; A=2.084 X 1000
        JSR      PRN_PPM
END011B: LDD      CNT_PR          ; Cheak for Hg
        CPD      HGMIN
        BLO     END011C
        CPD      HGMAX
        BHI     END011C

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JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRc              ; Display "Contmin. MERCURY (Hg) "
JSR    CHAR_STR
LDD    #983                    ; A=0.983 X 1000
JSR    PRN_PPM
END011C: LDD    CNT_PR        ; Cheak for Zn
CPD    ZNMIN
BLO    END011D
CPD    ZNMAX
BHI    END011D
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRd              ; Display "Contmin. ZINK (Zn) "
JSR    CHAR_STR
LDD    #718                    ; A=0.718 X 1000
JSR    PRN_PPM
END011D: LDD    CNT_PR        ; Cheak for Ni-1
CPD    NI1MIN
BLO    END011E
CPD    NI1MAX
BHI    END011E
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRe              ; Display "Contmin. NICKEL (Ni-1) "
JSR    CHAR_STR
LDD    #698                    ; A=0.698 X 1000
JSR    PRN_PPM
END011E: LDD    CNT_PR        ; Cheak for Ni-2
CPD    NI2MIN
BLO    END011F
CPD    NI2MAX
BHI    END011F
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRf              ; Display "Contmin. NICKEL (Ni-2) "
JSR    CHAR_STR
LDD    #570                    ; A=0.57 X 1000
JSR    PRN_PPM
END011F: LDD    CNT_PR        ; Cheak for Cu-1
CPD    CU1MIN
BLO    END011G
CPD    CU1MAX
BHI    END011G
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRg              ; Display "Contmin. COPPER (Cu-1) "
JSR    CHAR_STR
END011G: LDD    CNT_PR        ; Cheak for Cu-2
CPD    CU2MIN
BLO    END011H
CPD    CU2MAX
BHI    END011H
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRh              ; Display "Contmin. COPPER (Cu-2) "
JSR    CHAR_STR
END011H: LDD    CNT_PR        ; Cheak for Cu-3
CPD    CU3MIN
BLO    END011Z
CPD    CU3MAX
BHI    END011Z
JSR    CLR_LCD                ; Clear LCD
MOVB   #1,CHR_FLG
LDY    #MSG_CHRi              ; Display "Contmin. COPPER (Cu-3) "
JSR    CHAR_STR
LDD    #505                    ; A=0.505 X 1000
JSR    PRN_PPM
END011Z: LDAA   CHR_FLG
CMPA   #0
BNE    END011ZZ
JSR    CLR_LCD                ; Clear LCD
LDY    #MSG_CHRz              ; Display "No recognised "
JSR    CHAR_STR
END011ZZ: RTS
*****
* Subroutine: CHAR_STR
* Description: This subroutine prints
*              a character string
*****
CHAR_STR: NOP
TXT_LOOP: LDAA   0,Y
          CMPA   #$FF
          BEQ    TXT_END1
          JSR    PRN_LCD
          INY
          BRA    TXT_LOOP
TXT_END1: RTS
*****

```

```

;*      SUBROUTINE: PRN_PPM
;*      INFO:      Display PPM
;*      PASS:
;*      RETURNE:
;*****
PRN_PPM: LDY      AMPLITUDE      ; In uA X 10;
          EMUL      ; A*AMP*10=(Y:D)
          LDX      #10000
          EDIV      ; (Y:D)/10000=Y.D
          STY      RES_PPM      ; Store results
          JSR      LINE_LCD     ; Next line
          LDD      RES_PPM      ; Load variable to print
          JSR      CONV
          LDAA     DIGIT3       ; No of digit on LCD 15/20
          JSR      PRNLCD
          LDAA     DIGIT2       ; No of digit on LCD 16/20
          JSR      PRNLCD
          LDAA     DIGIT1       ; No of digit on LCD 17/20
          JSR      PRNLCD
          LDAA     #'          ; No of digit on LCD 20/20
          JSR      PRNLCD
          LDAA     #'p         ; No of digit on LCD 18/20
          JSR      PRNLCD
          LDAA     #'p         ; No of digit on LCD 19/20
          JSR      PRNLCD
          LDAA     #'m         ; No of digit on LCD 20/20
          JSR      PRNLCD
          LDAA     #'          ; No of digit on LCD 20/20
          JSR      PRNLCD
          JSR      ENT_BTN      ; Read ENTER bout-on
          RTS
;*****
;*      SUBROUTINE: ALGO1
;*      INFO:      Peak detection Algorithm
;*      PASS:
;*      RETURNE:
;*****
ALGO1:   NOP
;*****
;* Four Points moving average
;*****
          LDAA     FLAG
          CMPA     #1
          BNE     BR_1
          LDD      SAMPLE_M
          STD      DATA_1
          JMP      BR_NXT
BR_1:    LDAA     FLAG
          CMPA     #2
          BNE     BR_2
          LDD      SAMPLE_M
          STD      DATA_2
          JMP      BR_NXT
BR_2:    LDAA     FLAG
          CMPA     #3
          BNE     BR_3
          LDD      SAMPLE_M
          STD      DATA_3
          JMP      BR_NXT
BR_3:    LDAA     FLAG
          CMPA     #4
          LBNE     BR_NXT
          LDD      SAMPLE_M
          STD      DATA_4
          LDD      DATA_1
          LSRD
          LSRD
          STD      ADATA_1
          LDD      DATA_2
          LSRD
          LSRD
          STD      ADATA_2
          LDD      DATA_3
          LSRD
          LSRD
          STD      ADATA_3
          LDD      DATA_4
          LSRD
          LSRD
          STD      ADATA_4
          LDD      ADATA_1
          ADDD     ADATA_2
          ADDD     ADATA_3
          ADDD     ADATA_4
          STD      F           ; Four Points moving average variable
;*****
;* Process 1 - detection of min and max
;*****
          LDD      CNT_X      ; Check if first point

```

```

CPD      #1
BNE      BRN_1
LDD      F                      ; If first point then all variable = F
STD      OLD_DATA
STD      MAX
STD      MIN
STD      MAX_1
STD      MIN_1
BRN_1:   LDAA      P              ; Check if P = 0
CMPA     #1
BNE      BRN_2
LDD      OLD_DATA              ; If P = 0 then continue
CPD      F
BHI      BRN_3
LDAA     #1
STAA     P
LDD      OLD_DATA
STD      MAX
BRN_3:   LDD      OLD_DATA
CPD      F
BLS      BRN_2
ldd      MAX
cpd      MIN
blo      GOMAN1
LDD      MAX
SUBD     MIN
STD      AMP
bra      GOMAN2
GOMAN1:  LDD      #0
STD      AMP
GOMAN2:  LDD      AMP
CPD      ALG1_THR              ; Threshold 1.0uA
BLS      BRN_5
LDAA     #1
STAA     P_2
LDD      MAX
STD      MAX_1
LDD      CNT_X
STD      CNT_1
LDD      MINPOS
STD      MINPOS_1
LDD      MIN
STD      MIN_1
BRN_5:   CLR      P
BRN_2:   LDAA     P              ; Check if P is still 0
CMPA     #0
LBNE     BRN_6                  ; IF P not 0 leave process (min-max-min)
LDD      OLD_DATA              ; IF P = 0 continue
CPD      F
BLS      BRN_7
CLR      P
LDD      OLD_DATA
STD      MIN
LDD      CNT_X
STD      MINPOS
BRN_7:   LDD      OLD_DATA
CPD      F
LBHI     BRN_6                  ; 8
LDAA     P_2
CMPA     #1
LBNE     BRN_9
ldd      MAX
cpd      MIN
blo      GOMAN3
LDD      MAX
SUBD     MIN
STD      DEF
GOMAN3:  BRA      GOMAN4
LDD      #0
STD      DEF
GOMAN4:  LDD      MIN_1          ; 1st min point
;LSRD                      ; divide by 2
STD      A_MIN_1              ; store 1st min point
LDD      MIN                  ; 2nd min point
;LSRD                      ; divide by 2
STD      A_MIN                ; store 2nd min point
LDD      A_MIN_1
;ADDD                      ; Add 1st and 2nd min points
STD      AV_MIN              ; Store average min
ldd      MAX_1
cpd      AV_MIN
blo      GOMAN5
LDD      MAX_1
SUBD     AV_MIN
STD      AMP_2
BRA      GOMAN6
GOMAN5:  ldd      #0
GOMAN6:  std      AMP_2
LDD      DEF

```

```

        CPD      ALG1_THR      ; Threshold 1.0uA
        BLS      BRN_9        ;10
;*****
;* Calculate & convert max potential
;*****
        LDD      CNT_1
        LDY      #244          ; Counter x 2.44V x 100
        EMUL                     ; Multiplication: DxY=Y:D
        LDX      #10
        EDIV                     ; 32bit division: Y:D/X=Y.D
        STY      CNT_PR        ; Current counter potential
        LDD      CNT_PR        ; Load COUNTMAX
        CPD      #14000        ; Compare with 1.4V
        BLO      NNNEG         ; If lower then is negative
        SUBD     #14000        ; If not is positive
        STD      POTEN         ; Shift down 1.1V and leave
        MOVB     #$01,SINFLAG  ; Set SIGNFLAG to 1 (positive)
        JMP      EEEND         ; Leave
NNNEG:   LDD      #14000        ; Calculate offset
        SUBD     CNT_PR
        CLR      SINFLAG      ; Set SIGNFLAG to 0 (negative)
        STD      POTEN
EEEND:   LDD      POTEN
        LDX      #10
        IDIV                     ; 16bit division
        STX      POTEN
        LDD      AMP_2         ; Save to PRINT AMP_2 and POTEN
        STD      AMPLITUDE
        LDY      POINTER
        LDAA     SINFLAG
        STAA     0,Y           ;One place (8bit) $0000
        LDD      POTEN
        STD      1,Y           ;Two places (16bits) $0001-$0002
        LDD      AMPLITUDE
        STD      3,Y           ;Two places (16bits) $0003-$0004
        LDD      CNT_PR
        STD      5,Y           ;Two places (16bits) $0005-$0006
        LDD      POINTER
        ADDD     #7
        STD      POINTER
        CLR      P_2
BRN_9:   LDD      OLD_DATA
        STD      MAX
        LDAA     #1
        STAA     P
BRN_6:   LDD      F
        STD      OLD_DATA
;*****
;* Ready to continue for next sample
;*****
        LDD      CNT_X
        ADDD     #1
        STD      CNT_X
        LDD      DATA_2
        STD      DATA_1
        LDD      DATA_3
        STD      DATA_2
        LDD      DATA_4
        STD      DATA_3
        LDAA     #4
        STAA     FLAG
BR_NXT:  LDAA     FLAG
        CMPA     #4
        BHS     NXT
        LDAA     FLAG
        INCA
        STAA     FLAG
NXT:     RTS
;*****
;*      SUBROUTINE: PRDATA
;*      INFO:      Print on LCD max current & potential
;*
;*****
PRDATA:  JSR      CLR_LCD      ; Clear LCD
        LDAA     #'P          ; No of digit on LCD 1/20
        JSR      PRNLCD
        LDAA     #'e          ; No of digit on LCD 2/20
        JSR      PRNLCD
        LDAA     #'a          ; No of digit on LCD 3/20
        JSR      PRNLCD
        LDAA     #'k          ; No of digit on LCD 4/20
        JSR      PRNLCD
        LDAA     #'('         ; No of digit on LCD 5/20
        JSR      PRNLCD
        LDAA     #0
        LDAB     PEAK          ; Load PEAK variable to print
        JSR      CONV
        LDAA     DIGIT2        ; No of digit on LCD 6/20
        JSR      PRNLCD

```



```

LDAA DIGIT1 ; No of digit on LCD 7/20
JSR PRNLCD
LDAA #' ) ; No of digit on LCD 8/20
JSR PRNLCD
LDAA #' ; No of digit on LCD 9/20
JSR PRNLCD
LDAA #' I ; No of digit on LCD 10/20
JSR PRNLCD
LDAA #' = ; No of digit on LCD 11/20
JSR PRNLCD
LDD AMPLITUDE ; Load MAX variable to print
JSR CONV
LDAA DIGIT5 ; No of digit on LCD 12/20
JSR PRNLCD
LDAA DIGIT4 ; No of digit on LCD 13/20
JSR PRNLCD
LDAA DIGIT3 ; No of digit on LCD 15/20
JSR PRNLCD
LDAA DIGIT2 ; No of digit on LCD 16/20
JSR PRNLCD
LDAA #' . ; No of digit on LCD 14/20
JSR PRNLCD
LDAA DIGIT1 ; No of digit on LCD 17/20
JSR PRNLCD
LDAA #' u ; No of digit on LCD 18/20
JSR PRNLCD
LDAA #' A ; No of digit on LCD 19/20
JSR PRNLCD
LDAA #' ; No of digit on LCD 20/20
JSR PRNLCD
JSR LINE_LCD ; Next line
LDAA #' @ ; No of digit on LCD 1/20
JSR PRNLCD
LDAA #' ; No of digit on LCD 2/20
JSR PRNLCD
LDD POTEN
JSR CONV
LDAA SINFLAG ; Check sign
CMPA #0 ; If 0 then negative
BNE BARAS
LDAA #' - ; No of digit on LCD 3/20
JSR PRNLCD
BRA BARAS2
LDAA #' + ; No of digit on LCD 3/20
JSR PRNLCD
BARAS2: LDAA DIGIT5 ; No of digit on LCD 4/20
JSR PRNLCD
LDAA DIGIT4 ; No of digit on LCD 5/20
JSR PRNLCD
LDAA #' . ; No of digit on LCD 6/20
JSR PRNLCD
LDAA DIGIT3 ; No of digit on LCD 7/20
JSR PRNLCD
LDAA DIGIT2 ; No of digit on LCD 8/20
JSR PRNLCD
LDAA DIGIT1 ; No of digit on LCD 9/20
JSR PRNLCD
LDAA #' V ; No of digit on LCD 10/20
JSR PRNLCD
LDAA #00010000 ; Finish printing
JSR PRNLCD
RTS

;*****
; * CHARACTERS FOR DISPLAY
;*****
MSG_1a FCC "Deposition time,"
FCB $FF
MSG_1b FCC "wait 60 sec "
FCB $FF
MSG_2 FCC "System working! "
FCB $FF
MSG_3 FCC "End of process "
FCB $FF
MSG_Ta FCC "Wait: "
FCB $FF
MSG_Tb FCC " sec "
FCB $FF
MSG_Wa FCC "Volt. Analyser-I "
FCB $FF
MSG_Wb FCC "R.G.U. 2004. "
FCB $FF
MSG_CHRa FCC "Contmin. LEAD (Pb) "
FCB $FF
MSG_CHRb FCC "Contm. CADMIUM (Cd) "
FCB $FF
MSG_CHRc FCC "Contm. MERCURY (Hg) "
FCB $FF
MSG_CHRd FCC "Contm. ZINK (Zn) "
FCB $FF

```

```

MSG_CHRe FCC      "Contm. NICKEL (Ni-1) "
FCB               $FF
MSG_CHRf FCC      "Contm. NICKEL (Ni-2) "
FCB               $FF
MSG_CHRg FCC      "Contm. COPPER (Cu-1) "
FCB               $FF
MSG_CHRh FCC      "Contm. COPPER (Cu-2) "
FCB               $FF
MSG_CHRi FCC      "Contm. COPPER (Cu-3) "
FCB               $FF
MSG_CHRz FCC      "No recognised "
FCB               $FF
MSG_TR1           FCC      "No Match"
FCB               $FF
MSG_IA3           FCC      "RETURN "
FCB               $FF
MSG_Sam           FCC      "Sample: <> "
FCB               $FF
MSG_5a            FCC      "Ready for GPS: "
FCB               $FF
MSG_5b            FCC      "Connect GPS module "
FCB               $FF
MSG_6a            FCC      "Ready for identif. "
FCB               $FF
MSG_6b            FCC      "Press <ENTER> "
FCB               $FF
MSG_pha           FCC      "Ready to Measure pH"
FCB               $FF
MSG_phb           FCC      "Press <ENTER> "
FCB               $FF
MSG_phc           FCC      "Measure Acidity"
FCB               $FF
MSG_phd           FCC      "Please wait... "
FCB               $FF
MSG_RSa           FCC      "Sensor Resting "
FCB               $FF
MSG_Rsb           FCC      "Please wait... "
FCB               $FF
;*****
;*               END OF CODE
;*****

```

Appendix C

Software developed in C language

Serial Communication with the Analyser

```
/******
* Name:      Konstantinos Christidis
* Date:      11-October-2005
* Filename:  comp_2.CPP (working)
*
* Description: Serial Communication
* Note: Compile this program with Test Stack Overflow OFF.
*****/
#include <dos.h>
#include <conio.h>
#include <stdio.h>
#include <string.h>
#include "serial.h"
#include <math.h>
#include <graphics.h>
#include <stdlib.h>
#include <iostream.h>
#define VERSION 0x0101
#define FALSE 0
#define TRUE (!FALSE)
#define NOERROR 0 /* No error */
#define BUFOVFL 1 /* Buffer overflowed */
#define ESC 0x1B /* ASCII Escape character */
#define ASCII 0x007F /* Mask ASCII characters */
#define SBUFSIZ 0x4000 /* Serial buffer size */
int Error = NOERROR;
int portbase = 0;
void interrupt(*oldvects[2])(...);
static char ccbuf[SBUFSIZ];
unsigned int startbuf = 0;
unsigned int endbuf = 0;

/* Handle communications interrupts and put them in ccbuf */
void interrupt com_int(...)
{
    disable();
    if ((inportb(portbase + IIR) & RX_MASK) == RX_ID)
    {
        if ((endbuf + 1) & SBUFSIZ - 1) == startbuf)
            Error = BUFOVFL;
        ccbuf[endbuf++] = inportb(portbase + RXR);
        endbuf &= SBUFSIZ - 1;
    }
    /* Signal end of hardware interrupt */
    outportb(ICR, EOI);
    enable();
}

/* Output a character to the serial port */
serial& serial::operator<<( char x )
{
    long int timeout = 0x0000FFFFL;
    outportb(portbase + MCR, MC_INT | DTR | RTS);
    *
```

```

/* Wait for Clear To Send from modem */
while ((inportb(portbase + MSR) & CTS) == 0)
    if (!(--timeout))
        return *this;
timeout = 0x0000FFFF;
/* Wait for transmitter to clear */
while ((inportb(portbase + LSR) & XMTRDY) == 0)
    if (!(--timeout))
        return *this;
disable();
outportb(portbase + TXR, x);
enable();
return *this;
}

/* Output a string to the serial port */
serial& serial::operator<<( char *string )
{
    while (*string)
    {
        (*this) << *string;
        string++;
    }
    return *this;
}

/* This routine returns the current value in the buffer */
serial& serial::operator>>( char &ch )
{
    if (endbuf == startbuf)
    {
        ch = -1;
        return *this;
    }
    ch = ccbuf[startbuf];
    startbuf++;
    startbuf %= SBUFSIZ;
    return *this;
}

/* Install our functions to handle communications */
void setvects(void)
{
    oldvects[0] = getvect(0x0B);
    oldvects[1] = getvect(0x0C);
    setvect(0x0B, com_int);
    setvect(0x0C, com_int);
}

/* Uninstall our vectors before exiting the program */
void resvects(void)
{
    setvect(0x0B, oldvects[0]);
    setvect(0x0C, oldvects[1]);
}

/* Turn on communications interrupts */
void i_enable(int pnum)
{
    int c;
    disable();
    c = inportb(portbase + MCR) | MC_INT;
    outportb(portbase + MCR, c);
    outportb(portbase + IER, RX_INT);
    c = inportb(IMR) & (pnum == COM1 ? IRQ4 : IRQ3);
    outportb(IMR, c);
    enable();
}

/* Turn off communications interrupts */
void i_disable(void)
{
    int c;
    disable();
    c = inportb(IMR) | ~IRQ3 | ~IRQ4;
    outportb(IMR, c);
    outportb(portbase + IER, 0);
    c = inportb(portbase + MCR) & ~MC_INT;
    outportb(portbase + MCR, c);
    enable();
}

/* Tell modem that we're ready to go */

```

```

void comm_on(void)
{
    int c, pnum;
    pnum = (portbase == COM1BASE ? COM1 : COM2);
    i_enable(pnum);
    c = inportb(portbase + MCR) | DTR | RTS;
    outportb(portbase + MCR, c);
}
/* Go off-line */
void serial::comm_off(void)
{
    i_disable();
    outportb(portbase + MCR, 0);
}
void serial::init_serial(void)
{
    endbuf = startbuf = 0;
    setvects();
    comm_on();
}
serial::~~serial()
{
    comm_off();
    resvects();
}
/* Set the port number to use */
int serial::SetPort(int Port)
{
    int Offset, far *RS232_Addr;
    switch (Port)
    { /* Sort out the base address */
        case COM1 : Offset = 0x0000;
                    break;
        case COM2 : Offset = 0x0002;
                    break;
        default  : return (-1);
    }
    RS232_Addr = (int far *)MK_FP(0x0040, Offset); /* Find out where the port is. */
    if (*RS232_Addr == NULL) return (-1); /* If NULL then port not used. */
    portbase = *RS232_Addr; /* Otherwise set portbase */
    return (0);
}
/* This routine sets the speed; will accept funny baud rates. */
/* Setting the speed requires that the DLAB be set on. */
int serial::SetSpeed(int Speed)
{
    char c;
    int divisor;
    if (Speed == 0) /* Avoid divide by zero */
        return (-1);
    else
        divisor = (int) (115200L/Speed);
    if (portbase == 0)
        return (-1);
    disable();
    c = inportb(portbase + LCR);
    outportb(portbase + LCR, (c | 0x80)); /* Set DLAB */
    outportb(portbase + DLH, (divisor & 0x00FF));
    outportb(portbase + DLH, ((divisor >> 8) & 0x00FF));
    outportb(portbase + LCR, c); /* Reset DLAB */
    enable();
    return (0);
}
/* Set other communications parameters */
int serial::SetOthers(int Parity, int Bits, int StopBit)
{
    int setting;
    if (portbase == 0) return (-1);
    if (Bits < 5 || Bits > 8) return (-1);
    if (StopBit != 1 && StopBit != 2) return (-1);
    if (Parity != NO_PARITY && Parity != ODD_PARITY && Parity != EVEN_PARITY)
        return (-1);

    setting = Bits-5;
    setting |= ((StopBit == 1) ? 0x00 : 0x04);
    setting |= Parity;
    disable();
    outportb(portbase + LCR, setting);
    enable();
}

```



```

    return (0);
}
/* Set up the port */
serial::serial(int Port, int Speed, int Parity, int Bits, int StopBit)
{
    flag = 0;
    if (SetPort(Port))
        flag = -1;
    if (SetSpeed(Speed))
        flag = -1;
    if (SetOthers(Parity, Bits, StopBit))
        flag = -1;
    if (!flag)
        init_serial();
}
/* Control-Break interrupt handler */
int c_break(void)
{
    i_disable();
    fprintf(stderr, "\nStill online.\n");
    return(0);
}

void main()
{
    /*****
    * Variables declaration: Communication
    *****/
    int port = COM1;
    int speed = 9600;
    int parity = NO_PARITY;
    int bits = 8;
    int stopbits = 1;
    /*****
    * Variables declaration: Graphs and presentation
    *****/
    int driver, mode; //Driver and mode variables
    FILE *outfile;
    /*****
    * Variable declaration: Data manipulation
    *****/
    int i_counter=1, prs_1=1, prs_2=1;
    char c; //Input character
    unsigned char cc;
    unsigned char array_data[40];
    unsigned int DT_0,DT_1,DT_2,DT_3,DT_4,DT_5,DT_6,DT_7;
    unsigned int DT_8, DT_9;
    unsigned long DT,DTT,DTT1,DTT2,DTT3;
    /*****
    * Variables for graphical output
    *****/
    int i,selection;
    float range;
    int flag_plot=0;
    float y_point,y1_point, y2_point, y_old_point;
    int cnt_plot=1;
    int x_point;
    serial comport(port, speed, parity, bits, stopbits);
    ctrlbrk(c_break);
    outfile=fopen("ncr_data.txt","w");
    if (outfile==NULL)
    {
        printf("Cannot open file");
        exit(0);
    }
    driver = DETECT;
    initgraph(&driver, &mode, "c:\\turboc\\bgi\\");
    /*****
    * Say hello...
    *****/
    cleardevice();
    setbkcolor(15);
    setcolor(4);
    moveto(200, 80);
    outtext("The Robert Gordon University");
    moveto(200, 100);
    outtext("Data Logging-Upload MEM DATA");
    moveto(240, 120);

```

```

outtext("by K. Christidis");
moveto(220, 160);
outtext("Press any Key to start");
getch();
/*****
*****
* Input range
*****
cleardevice();
setbkcolor(1);
setcolor(4);
for (i=1; i<=17; i++)
{
    printf("\n");
}
printf("                ");
moveto(20, 80);
outtext("Voltage Range Selection");
moveto(20, 95);
outtext("_____");
moveto(20, 125);
outtext("Selection: [1] Range 0 - 500mV");
moveto(20, 145);
outtext("                [2] Range 0 - 1000mV");
moveto(20, 165);
outtext("                [3] Range 0 - 2000mV");
moveto(20, 185);
outtext("                [4] Range 0 - 5000mA");
moveto(20, 226);
outtext("Enter range:");
cin >> selection;
while (selection > 5)
{
    printf("Try again:");
    cin >> selection;
}
cleardevice();
setbkcolor(15);
range = 0.352;          /* Defult range 0-5000mV */
if (selection == 1)
{
    range = 0.352*10; //0.352*0.1;    // 360/1024=0.352
/***** Labeling Y-axis *****/
    setcolor(5);
    moveto(30,260+150-50);
    outtext("71");
    moveto(30,260+150-100);
    outtext("143");
    moveto(30,260+150-150);
    outtext("214");
    moveto(30,260+150-200);
    outtext("286");
    moveto(30,260+150-250);
    outtext("357");
    moveto(30,260+150-300);
    outtext("429");
    moveto(30,260+150-350);
    outtext("500");
/*****
}
if (selection == 2)
{
    range = 0.352*5; //0.352*0.2;    // 360/1024=0.352
/***** Labeling Y-axis *****/
    setcolor(5);
    moveto(30,260+150-50);
    outtext("142");
    moveto(30,260+150-100);
    outtext("286");
    moveto(30,260+150-150);
    outtext("428");
    moveto(30,260+150-200);
    outtext("572");
    moveto(30,260+150-250);
    outtext("714");
    moveto(30,260+150-300);
    outtext("858");
    moveto(30,260+150-350);

```

```

    outtext("1000");
/*****
}

if (selection == 3)
{
    range = 0.352*2.5; //0.352*0.4;    //360/1024=0.352
/***** Labeling Y-axis *****/
    setcolor(5);
    moveto(30,260+150-50);
    outtext("284");
    moveto(30,260+150-100);
    outtext("572");
    moveto(30,260+150-150);
    outtext("856");
    moveto(30,260+150-200);
    outtext("1144");
    moveto(30,260+150-250);
    outtext("1428");
    moveto(30,260+150-300);
    outtext("1716");
    moveto(30,260+150-350);
    outtext("2000");
/*****
}

if (selection == 4)
{
    range = 0.352;    // 360/1024=0.352
/***** Labeling Y-axis *****/
    setcolor(5);
    moveto(30,260+150-50);
    outtext("710");
    moveto(30,260+150-100);
    outtext("1430");
    moveto(30,260+150-150);
    outtext("2140");
    moveto(30,260+150-200);
    outtext("2860");
    moveto(30,260+150-250);
    outtext("3570");
    moveto(30,260+150-300);
    outtext("4290");
    moveto(30,260+150-350);
    outtext("5000");
/*****
}

/*****
* Plot the Axis      *
*****/
setcolor(1);
setlinestyle(0,0,3);
line (50,260+150,630,260+150);    /* X-axis */
line (630,260+150,630-10,260+150-10); /* X-axis (arrow) */
line (630,260+150,630-10,260+150+10); /* X-axis (arrow) */
line (70,280+150,70,10);          /* Y-axis */
line (70,10,70-10,10+10);
line (70,10,70+10,10+10);
moveto(350+100, 280+150);
outtext("Number of Samples");
moveto(10, 30);
outtext("Voltage [mV]");
/***** Labeling X-axis *****/
setcolor(5);
moveto(50+0,265+150);
outtext("0");
moveto(50+100-20,265+150);
outtext("100");
moveto(50+200-20,265+150);
outtext("200");
moveto(50+300-20,265+150);
outtext("300");
moveto(50+400-20,265+150);
outtext("400");
moveto(50+500-20,265+150);
outtext("500");
/*****
setcolor(4);
moveto(220, 30); //310+150);

```

```

outtext("Data Logging Voltage Vs No Samples");
setcolor(4);
line (220,445,430,445);
line (220,460,430,460);
line (220,445,220,460);
line (430,445,430,460);
moveto(230, 450);
outtext("STATUS:");
moveto(300, 450);
outtext("Program Running");
setcolor(5); /* Colour for data */
//*****PROCESS - FIRST PART*****
//*****
//printf("Waiting for Data....\n");
do{
    comports >> c;

    if(c != -1)
    {
        cc=c;
        DT=c;

    if (DT == 11)    //Start Word
    {
        //printf("Transferring Started....\n");
        do {
            comports >> c;
            if(c != -1)
            {
                cc=c;
                DT=c;
                if (DT !=12)    //Stop Word
                {
                    array_data[i_counter]=cc;
                    printf("bit(%d)=%ld \n", i_counter, DT);
                    i_counter=i_counter+1;
                    if (i_counter == 17)    //8+8+(1)
                    {
                        DT_0=array_data[1];
                        DT_1=array_data[2];
                        DT_2=array_data[3];
                        DT_3=array_data[4];
                        DT_4=array_data[5];
                        DT_5=array_data[6];
                        DT_6=array_data[7];
                        DT_7=array_data[8];
                        DTT1=(DT_0*1)+(DT_1*2)+(DT_2*4)+(DT_3*8);
                        DTT2=(DT_4*16)+(DT_5*32)+(DT_6*64)+(DT_7*128);
                        DTT = DTT1 + DTT2;

                        DT_8=array_data[9];
                        DT_9=array_data[10];
                        DTT3=(DT_8*256)+(DT_9*512);
                        DTT = DTT + DTT3;
                        //printf("data=%ld \n", DTT);

                        i_counter = 1;

                        //*****
                        //****Plot Data*****

                        flag_plot=flag_plot+1;
                        y_point=260+150-(DTT*range);

                        if (flag_plot == 1)
                        {
                            y_old_point=y_point;
                        }
                        else if (flag_plot == 2)
                        {
                            x_point=cnt_plot+70;
                            y_point=(y_point+y_old_point)/2;
                            setcolor(5);
                            moveto(x_point,y_point);
                            outtext(".");
                            fprintf(outfile, "%d \n", DTT);
                            cnt_plot=cnt_plot+1;

```

```

        flag_plot = 0;
    }
    //*****
    //***End Plot Data***
}
}
else if (c == 12)    // If DATA = 12
{
    prs_1=0;
    prs_2=0;
    //printf("Stop Transferring.....");
    setcolor(15);
    moveto(300, 450);
    outtext("Program Running");
    setcolor(4);
    moveto(300, 450);
    outtext("End of Process");
}
}
}while(prs_2 != 0);
}
}
}while(prs_1 != 0);
getchar();
fclose(outfile);
closegraph();
}

```


Appendix D

Technical Information

D.1: 12 bit DAC - AD7541A

D.2: Operational Amplifier – OP07

D.3: Program. Ref. Voltage Device – TL431

D.4: 1-to-8 Analogue Multiplexer – 4052B

D.5: 16 bit ADC – LTC1605

D.6: 2 x 20 Alphanumerical Display

D.7: 64 x 128 Graphic Display

D.8: 512 Kbit IC2 Serial EEPROM – 24AA512

D.9: Voltage Regulator – LM2940

D.10: Voltage Regulator – LM2940

D.11: DC-to-DC Converter – TEN 5-0522

D.12. RS232 driver – MAX323

D.1: 12 bit DAC – AD7541A

CMOS
12-Bit Monolithic Multiplying DAC

FEATURES

Improved Version of AD 7541
Full Four-Quadrant Multiplication
12-Bit Linearity (Endpoint)
All Parts Guaranteed Monotonic
TTL/CMOS Compatible
Low Cost
Protection Schottky Diodes Not Required
Low Logic Input Leakage

GENERAL DESCRIPTION

The Analog Devices AD7541A is a low cost, high performance, 12-bit monolithic multiplying digital-to-analog converter. It is fabricated using advanced, low noise, thin film on CMOS technology and is available in a standard 16-lead DIP and in 20-terminal surface mount packages.

The AD7541A is functionally and pin compatible with the industry standard AD7541 device and offers improved specifications and performance. The improved design ensures that the device is latch-up free to no output protection. Schottky diodes are required.

This new device uses laser trimming to provide full 120-endpoint linearity with several new high performance grades.

ORDERING GUIDE

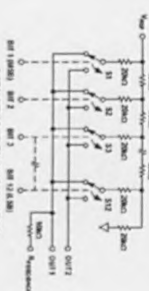
Material	Temperature Range	Accuracy T _{max} ± 1%	Repeatability Error ± 0.2%	Units
AD741AN	0°C ~ +10°C	±1.15%	±0.15%	0-10
AD741AN	0°C ~ +10°C	±1.12.5%	±1.15%	N-10
AD741ANP	0°C ~ +10°C	±1.15%	±0.15%	P-20A
AD741AN	0°C ~ +10°C	±1.15%	±0.15%	P-20A
AD741AN	0°C ~ +10°C	±1.12.5%	±1	N-10
AD741AN	-25°C ~ +10°C	±1.15%	±0.15%	0-10
AD741AN	-25°C ~ +10°C	±1.12.5%	±0.15%	0-10
AD741ANQ	-25°C ~ +10°C	±1.15%	±0.15%	0-10
AD741ANQ	-25°C ~ +10°C	±1.12.5%	±0.15%	0-10
AD741AN	-55°C ~ +125°C	±1.15%	±0.15%	E-20A
AD741AN	-55°C ~ +125°C	±1.12.5%	±0.15%	E-20A

[illegible]

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PRODUCT HIGHLIGHTS

Compatibility: The AD7541A can be used as a direct replacement for any AD7541-type device. As with the Analog Device AD7541, the digital inputs are TTL/CMOS compatible and have been designed to have a ± 1 V maximum input current requirement at no load to avoid the driving circuitry.

Improvements: The AD7541A offers the following improvements over the AD7541:

1. Gaskets for all gaskets have been replaced with premium grade stainless steel gaskets with a maximum leak error of 2.1 LBS.
2. Gasket thermal expansion coefficient has been reduced to 2 ppm/°C and 3 ppm/°C maximum.
3. Digital-to-analog charge injection energy for this new device is typically 20% less than the standard AD7341 part.
4. Launch-up proof.
5. Improved results in burst testing (typical 1.125 LBS in differential mode) for top grade sensors with operating temperature range (°C) 11.25 to 85 (older 7541 (Tppm)).
6. All gaskets are guaranteed/matched to 12 bolts over the operating temperature range.

AD7541A-SPECIFICATIONS

($V_{GS} = +15$ V, $V_{DS} = +10$ V, $I_{D1} = I_{D2} = I_{ND} = 0$ V unless otherwise noted)

Parameter	Variable	T ₁ , °C +12°C	T ₂ , °C +30 °C	Units	Test Conditions or Comments
ACCURACY	Resolution	Δt, s	12	12	
	Resolution	ΔK, %	2.1	2.1	1: L28 = 20 (45%) of P22 Sub
	Relative Accuracy	ΔK, %	2.1	2.1	1: L28 = 20 (45%) of P22 Sub
	Differential Accuracy	ΔK, %	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
Gain Error	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
Gain Temperature Coefficient	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
Output Leakage Current	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
COTF (P=2)	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
REPRODUCTION	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
DIGITAL ERRORS	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
POWER SUPPLY	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
ANALOG SUPPLY	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
TEMPERATURE	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
HUMIDITY	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
VIBRATION	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
SHOCK	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
ELECTROMAGNETIC INTERFERENCE	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
ELECTROSTATIC DISCHARGE	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
RADIATION	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
MECHANICAL STRESS	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
THERMAL SHOCK	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub
	ΔK, %	2.1	2.1	2.1	ΔK (Copper) = 20 (45%) of P22 Sub

AC PERFORMANCE CHARACTERISTICS

These Characteristics are included for Region Guidance only and are not subject to test. $V_{in} = +15\text{ V}$, $V_{gs} = +10\text{ V}$ except where noted. $Q_{UT1} = 0.12$, 6 MO , 0 V , Output Imp is $AD544$ except where noted.

Parameter	Vendor ^a	T _g , °C ^b +25°C	T _{on} , T _{off} ^c	Units	Test Conditions/Comments
PROJECTION BRISTLE (from Digital Image Charge to sets of Feed Anode Charge)	AI	164	—	no TP	(D/T 7 Load = 100 V, C _{set} = 11 pF Digital Image = 5 V, V _{off} = V _{on} to 5 V, V _{on} = 5 V AI Aerial pickup = V to V _{on} or V _{off} to 5 V
DIGITAL TO ANALOG (D/TCH) BRISTLE	AI	1609	—	60° sec, TP	Measured using Tekadirect as input amplifier
MULTI-VISING PHOTOGRAPHIC BRISTLE ^d (V _{on} to (D/TCH))	AI	1.8	—	mV p-p TP	V _{on} = 0.1 V, V _{off} 200 mV on V _{on} T _g is 10% of the each sweep (D/T 7 Load = 100 V, C _{set} = 11 pF Digital Image = 5 V to V _{off} or V _{on} to 5 V
OUTPUT CHANNEL SETTLING TIME	AI	0.4	—	ns	
SUPPLY CHARACTERISTICS					
Cons. (P _{in} 1)	AI	200	200	gF, max	Digital Image
Cons. (P _{in} 2)	AI	74	74	gF, max	Digital Image
Cons. (P _{in} 3)	AI	74	74	gF, max	Digital Image
Cons. (P _{in} 21)	AI	290	290	gF, max	V _{on} = V _{off}

^a Temperature range in which ΔT is $\pm 1^\circ\text{C}$. A, 0 heating; ΔT is $\pm 1^\circ\text{C}$. B, 1 heating; ΔT is $\pm 1^\circ\text{C}$. C, 2 heating; ΔT is $\pm 1^\circ\text{C}$. D, 3 heating; ΔT is $\pm 1^\circ\text{C}$. E, 4 heating; ΔT is $\pm 1^\circ\text{C}$. F, 5 heating; ΔT is $\pm 1^\circ\text{C}$. G, 6 heating; ΔT is $\pm 1^\circ\text{C}$. H, 7 heating; ΔT is $\pm 1^\circ\text{C}$. I, 8 heating; ΔT is $\pm 1^\circ\text{C}$. J, 9 heating; ΔT is $\pm 1^\circ\text{C}$. K, 10 heating; ΔT is $\pm 1^\circ\text{C}$. L, 11 heating; ΔT is $\pm 1^\circ\text{C}$. M, 12 heating; ΔT is $\pm 1^\circ\text{C}$. N, 13 heating; ΔT is $\pm 1^\circ\text{C}$. O, 14 heating; ΔT is $\pm 1^\circ\text{C}$. P, 15 heating; ΔT is $\pm 1^\circ\text{C}$. Q, 16 heating; ΔT is $\pm 1^\circ\text{C}$. R, 17 heating; ΔT is $\pm 1^\circ\text{C}$. S, 18 heating; ΔT is $\pm 1^\circ\text{C}$. T, 19 heating; ΔT is $\pm 1^\circ\text{C}$. U, 20 heating; ΔT is $\pm 1^\circ\text{C}$. V, 21 heating; ΔT is $\pm 1^\circ\text{C}$. W, 22 heating; ΔT is $\pm 1^\circ\text{C}$. X, 23 heating; ΔT is $\pm 1^\circ\text{C}$. Y, 24 heating; ΔT is $\pm 1^\circ\text{C}$. Z, 25 heating; ΔT is $\pm 1^\circ\text{C}$.

Specifications subject to change without notice.

AD7541A

ABSOLUTE MAXIMUM RATINGS*

$T_A = +25^\circ\text{C}$ (unless otherwise noted)	
V_{DD} to GND	+17 V
V_{EE} to GND	-25 V
V_{EE} to V_{DD}	-25 V
Digital Input Voltage to GND	-0.3 V, $V_{DD} + 0.3$ V
Digital Input Voltage to V_{DD}	-0.3 V, $V_{DD} + 0.3$ V
Power Dissipation (Derating Factor)	450 mW
Operating Temperature	0 to $+70^\circ\text{C}$
Storage Temperature	-55 to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)	$+300^\circ\text{C}$

CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the AD7541A features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



TERMINOLOGY

RELATIVE ACCURACY
Relative accuracy or endpoint nonlinearity is a measure of the error in the output code relative to the ideal output code. It is expressed in % of full-scale range or (sub) multiples of 1 LSB.

DIFFERENTIAL NONLINEARITY
Differential nonlinearity is the difference between the *measured* change and the *ideal* 1LSB change between any two adjacent codes. A specified differential nonlinearity of ± 1 LSB max over the operating temperature range insures monotonicity.

GAIN ERROR
Gain error is a measure of the output error between an ideal DAC and the actual device output. For the AD7541A, ideal maximum output is

$$- \left(\frac{4095}{4096} \right) (V_{EE})$$

Gain error is adjustable to zero using external trim as shown in Figures 1, 2, and 3.

Operating Temperature Range

Commercial (J, K Version)	0 to $+70^\circ\text{C}$
Industrial (A, B Version)	-55 to $+85^\circ\text{C}$
Extended (S, T Version)	-55 to $+125^\circ\text{C}$
Storage Temperature	-55 to $+150^\circ\text{C}$
Lead Temperature (Soldering, 10 sec)	$+300^\circ\text{C}$

*Values shown above lead solder. Maximum Ratings are stated pursuant to the manufacturer's specifications. The maximum operating temperature of the device is specified for the maximum power dissipation. The maximum junction temperature is not specified. Excess power dissipation may lead to device failure.

OUTPUT LEAKAGE CURRENT

Current which appears at OUT1 with the DAC loaded to all 0s or at OUT2 with the DAC loaded to all 1s.

MULTIPLYING PREDETERMINED ERROR

AC error due to capacitive feedthrough from V_{EE} terminal to OUT1 with DAC loaded to all 0s.

OUTPUT CURRENT SETTLING TIME

Time required for the output function of the DAC to settle to within 1/2 LSB for a given digital input stimulus, i.e., 0 to full scale.

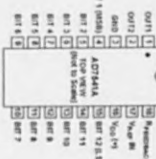
PROPAGATION DELAY

This is a measure of the internal delay of the circuit and is measured from the time a digital input changes to the point at which the analog output at OUT1 reaches 90% of its final value.

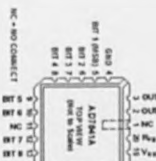
DIGITAL-TO-ANALOG CHARGE INJECTION (QDI)

This is a measure of the amount of charge injected from the digital inputs to the analog outputs when the inputs change state. It is usually specified as the error of the glitch in mV and is measured with $V_{EE} = \text{GND}$ and a Model 50K at the output op amp. CI (charge compensation) ≈ 0 pF.

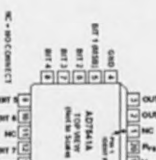
DIPOLOC



PLCC



LCCC



AD7541A

GENERAL CIRCUIT INFORMATION

The simplified D/A circuit is shown in Figure 1. An inverted R-2R ladder structure is used—that is, the binary weighted currents are switched between the OUT1 and OUT2 bus lines, thus maintaining a constant current in each ladder leg independent of the switch state.

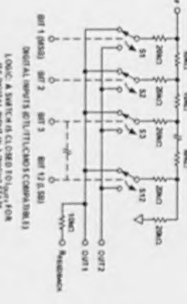


Figure 1. Functional Diagram (Inputs HIGH)

The input resistance at V_{EE} (Figure 1) is always equal to R_{2R} (Data Sheet B-2R ladder). The input resistance at V_{DD} is equal to $R_{2R}/4$. Since R_{2R} at the V_{EE} pin is constant, the reference current, I_{REF} , or $I_{REF}/4$, of positive or negative polarity. (If a current source is used, a low temperature coefficient external R_{2R} is recommended to define scale factor.)

EQUIVALENT CIRCUIT ANALYSIS

The equivalent circuits for all digital inputs LOW and all digital inputs HIGH are shown in Figures 2 and 3. In Figure 2 with all digital inputs LOW, the reference current is switched to OUT2. The current source I_{REF} is composed of current sources and junction diodes to the substrate, while the I_{REF} current source represents a constant 1-bit current drawn through the termination resistor on the R-2R ladder. The ON capacitance of the output N-channel switch is 200 pF, as shown on the OUT2 terminal. The OFF switch capacitance is 70 pF, as shown on the OUT1 terminal. Analysis of the circuit for all digital inputs HIGH, as shown in Figure 3 is similar to Figure 2; however, the ON switches are now on terminal OUT1, hence the 200 pF at that terminal.

Figure 2. DAC Equivalent Circuit All Digital Inputs LOW

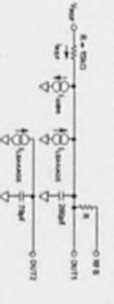


Figure 3. DAC Equivalent Circuit All Digital Inputs HIGH

APPLICATIONS

UNIPOLAR BINARY OPERATION

Figure 4 shows the analog circuit connections required for unipolar binary (2-quadrant multiplication) operation. With a dc reference voltage or current (positive or negative polarity) applied at Pin 17, the circuit is a complete D/A converter. With an ac reference voltage or current (ac current source), a 2-quadrant multiplier (digital-to-analog current product). The input-output relationship is shown in Table II.

BI-POLAR BINARY OPERATION
The AD7541A can be configured for bi-polar binary operation. This is achieved by connecting Pin 17 to a reference voltage or current (positive or negative polarity) and Pin 18 to a reference voltage or current (positive or negative polarity). The input-output relationship is shown in Table II.

AMPLIFIER A1 should be selected or trimmed to provide V_{EE} 5% of the voltage resolution at V_{EE} . Additionally, the amplifier should exhibit a bias current which is low over the temperature range of interest (bias current causes output offset at V_{EE} equal to I_b , times the DAC feedback resistance, nominally 111k Ω). The AD7541C is a high speed amplified 1 BIT input op amp with low factory-trimmed V_{EE} .

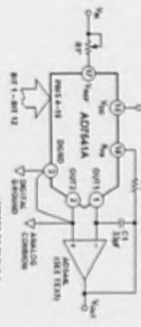


Figure 4. Unipolar Binary Operation

Table I. Recommended Trim Resistor Values vs. Grades

Trim Resistor	JNAQSD	KNRQTD
R1	100 Ω	100 Ω
R2	47 Ω	33 Ω

Table II. Unipolar Binary Code Table for Circuit of Figure 4

Binary Number in DAC	Analog Output, V_{OUT}
MSB	LSB
1111	1111
1111	1111
1000	0000
0000	0000
0000	0001
0000	0000
0000	0000

BIPOLAR OPERATION

(4-Q) QUADRANT MULTIPLICATION)
 Figure 5 and Table III illustrate the circuitry and code relationship for bipolar operation. With a dc reference (positive or negative polarity) the circuit provides full 4-quadrant multiplication. With an ac reference the circuit provides full 4-quadrant multiplication. With the DAC loaded to 1000 0000 0000, adjust R1 for $V_{REF} = 0$ V. Alternatively, one can omit R1 and R2 and adjust the ratio of R3 to R4 for $V_{REF} = 0$ V. Full-scale trimming can be accomplished by adjusting the amplitude of V_{REF} or by varying the value of R3.
 As in unipolar operation, A1 must be chosen for low V_{OS} and low I_n . R3, R4 and R5 must be selected for matching and tracking. Mismatch of R3 to R4 causes both offset and full-scale error. Mismatch of R5 to R4 or 2R3 causes full-scale error. Compensation (10 pF to 50 pF) may be required for stability, depending on amplifier used.

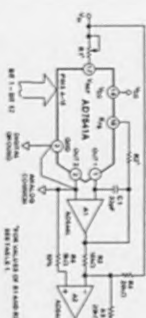


Figure 5. Bipolar Operation (4-Quadrant Multiplication)

Table III. Bipolar Code Table for 0-Bias Binary Currents of Figure 5

Binary Number in DAC	Analog Output, V_{OUT}
MSB	LSB
1111 1111 1111	$+V_{REF} \left(\frac{2047}{2048} \right)$
1000 0000 0001	$+V_{REF} \left(\frac{1}{2048} \right)$
1000 0000 0000	0 V (bias)
0111 1111 1111	$-V_{REF} \left(\frac{1}{2048} \right)$
0000 0000 0000	$-V_{REF} \left(\frac{2048}{2048} \right)$

Figure 6 and Table IV show an alternative method of achieving bipolar output. The circuit operates with sign plus magnitude code and has the advantage of giving 12-bit resolution in each quadrant, compared with 11-bit resolution per quadrant for the circuit of Figure 5. The AD7541A is a fully protected CMOS charge-coupled device with data inputs, R4 and R5 should match each other to 0.01% to maintain the accuracy of the D/A converter. Mismatch between R4 and R5 introduces a gain error.

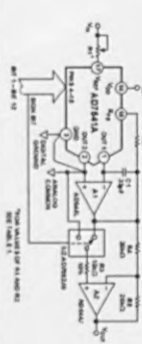


Figure 6. 12-Bit Plus Sign Magnitude Operation

Table IV. 12-Bit Plus Sign Magnitude Code Table for Circuit of Figure 6

Sign Bit	Binary Number in DAC	Analog Output, V_{OUT}
MSB	LSB	
0	1111 1111 1111	$+V_{REF} \times \left(\frac{4095}{4096} \right)$
0	0000 0000 0000	0 V (bias)
1	0000 0000 0000	0 V (bias)
1	1111 1111 1111	$-V_{REF} \times \left(\frac{4095}{4096} \right)$

Note: Sign bit of "0" assumes R3 to GND.

APPLICATIONS HINTS

Output Offset: CMOS D/A converters exhibit a code-dependent output resistance which in turn can cause a code-dependent error voltage at the output of the amplifier. The maximum amplitude of this offset, which adds to the D/A converter nonlinearity, is $0.57 V_{REF}$, where V_{REF} is the amplifier input offset voltage. To maintain maximum operating accuracy it is recommended that the output resistance of the D/A converter be less than the input resistance of the amplifier. Suitable op ampers are AD511T, and AD544L. The AD511T, a low offset for fixed reference applications with low bandwidth requirement, it has extremely low offset (50 nV) and, in most applications, will not require an offset trim. The AD544L, has a much wider bandwidth and higher slew rate and is recommended for multiplying and other applications requiring fast settling. An offset trim on the AD544L may be necessary in some circuits.

Digital Glitches: One cause of digital glitches is capacitive coupling from the digital lines to the QOUT1 and QOUT2 terminals. This should be minimized by screening the analog pins of the AD7541A (Pins 1, 2, 17, 18) from the digital pins by a ground or wet run between Pins 2 and 3 and between Pins 16 and 17 of the AD7541A. Note how the analog pins are at one end of the package and separated from the digital pins by V_{REF} and GND in the AD7541A. On-chip capacitive coupling can also give rise to cross-talk from the digital-to-analog sections of the AD7541A, particularly in circuits with high currents and fast rise and fall times.

Temperature Coefficients: The gain temperature coefficient of the AD7541A has a maximum value of 5 ppm/°C and a typical value of 2 ppm/°C. This corresponds to worst case gain ability of 12.5% and 0.8125%, respectively, over a 100°C temperature range. When trim resistors R1 and R2 are used to adjust full-scale range, the temperature coefficient of R1 and R2 should also be taken into account. The reader is referred to Analog Devices Application Note "Gain Error and Gain Temperature Coefficient of CMOS Multiplying DACs," Publication Number EN000-9-3-86.

SINGLE SUPPLY OPERATION

Figure 7 shows the AD7541A connected in a voltage switching mode. QOUT1 is connected to the reference voltage and QOUT2 is connected to GND. The D/A converter output voltage is available at the V_{REF} pin (Pin 17) and has a constant output impedance equal to R_{OUT} . The feedback resistor R_{FB} is not used in this circuit.

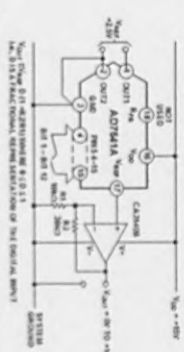


Figure 7. Single Supply Operation Using Voltage Switching Mode

The reference voltage must always be positive. If QOUT1 goes more than 0.3 V from GND, an internal diode will be turned on, and a heavy current may flow causing device damage (the AD7541A is, however, protected from the SCR latch-up phenomenon prevalent in many CMOS devices). Suitable references include the AD580 and AD584.

The loading on the reference voltage source is code-dependent and the response time of the circuit is often determined by the behavior of the reference voltage with changing load conditions. To maintain linearity, the voltage at QOUT1 should remain within 2.5 V of GND, for a V_{REF} of 15 V. If V_{REF} is reduced within 2.5 V of the reference voltage at QOUT1 increased to more than 2.5 V, the differential nonlinearity of the DAC will increase and the linearity of the DAC will be degraded.

SUPPLEMENTAL APPLICATION MATERIAL

For further information on CMOS multiplying D/A converters, the reader is referred to the following texts:
 CMOS DAC Application Guide, Publication Number G8728-6-1-89 available from Analog Devices.
 Gain Error and Gain Temperature Coefficient of CMOS Multiplying DACs Application Note, Publication Number EN000-5-1-86 available from Analog Devices.
 Analog-Digital Conversion Handbook—available from Analog Devices.

D.2: Operational Amplifier - OP07



Ultralow Offset Voltage Operational Amplifier

OP07

FEATURES

- Low V_{os} 25 μ V Max
- Low V_{os} Drift 0.5 μ V/°C Max
- Ultra-Stable vs Time 1.0 μ V/month Max
- Low Noise 8.0 μ V \sqrt{Hz} Max
- Wide Input Voltage Range ± 1 V
- Wide Supply Voltage Range ± 3 V to ± 15 V
- Pin 725, 100k Ω , 741, AD575 Sockets
- 125°C Temperature-Biased Die

ORDERING INFORMATION¹

V_{os} MAX	TEMP	PACKAGE	LOC	TEMPERATURE RANGE
25	TO-18	8-PIN	30-CONTACT	MIN
75	OP07A ²	OP07Z ²	OP07P ²	MAX
150	OP07C	OP07D	OP07E	MAX
150	OP07A	OP07C	OP07D	MAX
150	OP07A	OP07C	OP07D	MAX
150	OP07A	OP07C	OP07D	MAX

¹ For detailed product and ordering information, see the OP07 data sheet.

² For detailed product and ordering information, see the OP07 data sheet.

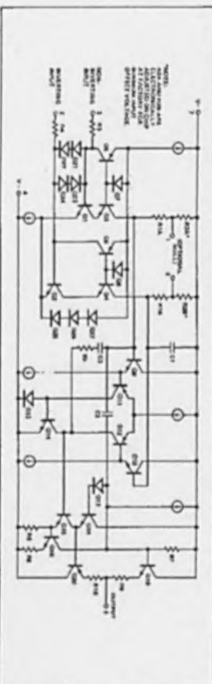
³ For detailed product and ordering information, see the OP07 data sheet.

GENERAL DESCRIPTION

The OP-07 has very low input offset voltage (25 μ V max. for OP-07A) which is obtained by trimming at the wafer stage. These low offset voltages generally eliminate any need for external nulling. The OP-07 also features low input bias current (25 nA for OP-07A) and high open-loop gain (130 dB for OP-07A). The low offset and high open-loop gain make the OP-07 particularly useful for high-gain instrumentation applications.

The wide input voltage range of ± 1.3 V minimum combined with high common-mode rejection ratio (CMRR) provides high accuracy in the noninverting configuration. Excellent linearity and gain accuracy can be maintained.

SIMPLIFIED SCHEMATIC



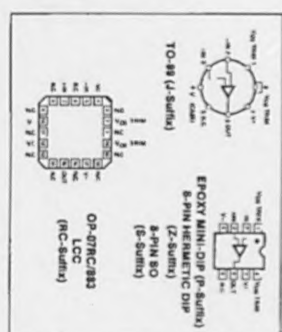
even at high closed-loop gains.

Stability of offset and gain with time or variations in temperature is excellent. The accuracy and stability of the OP-07, even at high gain, combined with the freedom from external nulling have made the OP-07 a new industry standard for instrumentation and military applications.

The OP-07 is available in the standard performance grades. The OP-07A and the OP-07 are specified for operation over the full military range of -55°C to $+125^{\circ}\text{C}$. The OP-07E is specified for operation -40°C to $+125^{\circ}\text{C}$, and the OP-07C and OP-07D are -40°C to $+125^{\circ}\text{C}$.

The OP-07 is available in hermetically sealed TO-18 metal can or ceramic 8-pin Mini-DIP, and a second 8-pin Mini-DIP. It is a direct replacement for 725, 100k, and OP-05 amplifiers. 741 types may be directly replaced by removing the 741 nulling potentiometer. The OP-07, a dual OP-07, is available for applications requiring close matching of two OP-07 amplifiers. For improved specifications, see the OP-07C or OP-07D.

PIN CONNECTIONS



OP07

ABSOLUTE MAXIMUM RATINGS (Note 1)

Supply Voltage	± 22 V
Differential Input Voltage	± 30 V
Input Voltage (Note 2)	± 22 V
Output Short-Circuit Duration	Indefinite
Storage Temperature Range	-65°C to $+150^{\circ}\text{C}$
1. RJC and 2. Package	-65°C to $+150^{\circ}\text{C}$

Operating Temperature Range
OP-07A, OP-07, OP-07B -55°C to $+125^{\circ}\text{C}$
OP-07C, OP-07D -40°C to $+125^{\circ}\text{C}$
OP-07E -40°C to $+125^{\circ}\text{C}$
Lead Temperature (Soldering, 30 sec) $+300^{\circ}\text{C}$
Junction Temperature (T_j) $+150^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS at $V_S = \pm 15$ V, $T_A = 25^{\circ}\text{C}$, unless otherwise noted.

PARAMETER	SYMBOL	CONDITIONS	OP-07A	OP-07	OP-07C	OP-07D	OP-07E	UNIT
Input Offset Voltage	V_{os}	(Note 1)	—	25	75	150	150	μ V
Long-Term Input Offset Voltage Stability	$\Delta V_{os}/T$	(Note 2)	—	0.1	1.0	—	0.1	μ V/°C
Input Bias Current	I_{b1}	(Note 3)	—	0.1	2.0	—	0.1	nA
Input Bias Current	I_{b2}	(Note 3)	—	0.1	2.0	—	0.1	nA
Input Noise Voltage	e_{n1}	(Note 4)	—	8.0	11.0	—	8.0	μ V \sqrt{Hz}
Input Noise Voltage	e_{n2}	(Note 4)	—	8.0	11.0	—	8.0	μ V \sqrt{Hz}
Input Noise Current	i_{n1}	(Note 5)	—	0.1	0.5	—	0.1	pA \sqrt{Hz}
Input Noise Current	i_{n2}	(Note 5)	—	0.1	0.5	—	0.1	pA \sqrt{Hz}
Input Common-Mode Rejection Ratio	$CMRR$	(Note 6)	—	110	100	—	110	dB
Common-Mode Rejection Ratio	$CMRR$	(Note 6)	—	110	100	—	110	dB
Power Supply Rejection Ratio	$PSRR$	(Note 7)	—	110	100	—	110	dB
Large-Signal Voltage Gain	A_{v0}	(Note 8)	—	200	200	—	200	dB
Output Voltage Swing	V_{o1}	(Note 9)	—	1.0	1.0	—	1.0	V
Output Voltage Swing	V_{o2}	(Note 9)	—	1.0	1.0	—	1.0	V
Common-Mode Input Resistance	R_{ic1}	(Note 10)	—	100	100	—	100	Ω
Common-Mode Input Resistance	R_{ic2}	(Note 10)	—	100	100	—	100	Ω
Open-Loop Output Resistance	R_{o1}	(Note 11)	—	100	100	—	100	Ω
Open-Loop Output Resistance	R_{o2}	(Note 11)	—	100	100	—	100	Ω
Power Consumption	P_D	(Note 12)	—	100	100	—	100	mW
Power Consumption	P_D	(Note 12)	—	100	100	—	100	mW

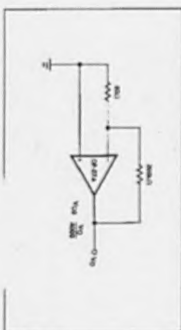
NOTES:
1. Input offset voltage V_{os} is measured at zero input signal and zero output signal. It is the average of the input offset voltages of all amplifiers in the package.
2. Long-term input offset voltage stability refers to the average of the input offset voltages of all amplifiers in the package.
3. Input bias current I_{b1} and I_{b2} are measured at zero input signal and zero output signal.
4. Input noise voltage e_{n1} and e_{n2} are measured at zero input signal and zero output signal.
5. Input noise current i_{n1} and i_{n2} are measured at zero input signal and zero output signal.
6. Common-mode rejection ratio $CMRR$ is measured at zero input signal and zero output signal.
7. Power supply rejection ratio $PSRR$ is measured at zero input signal and zero output signal.
8. Large-signal voltage gain A_{v0} is measured at zero input signal and zero output signal.
9. Output voltage swing V_{o1} and V_{o2} are measured at zero input signal and zero output signal.
10. Common-mode input resistance R_{ic1} and R_{ic2} are measured at zero input signal and zero output signal.
11. Open-loop output resistance R_{o1} and R_{o2} are measured at zero input signal and zero output signal.
12. Power consumption P_D is measured at zero input signal and zero output signal.

0P07

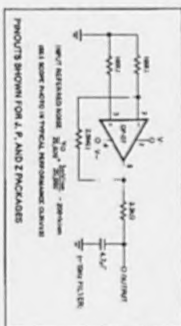
PARAMETER	OP-57A			OP-57		
	MIN	TPP	MAX	MIN	TPP	MAX
Input Current Voltage	V_{in}	(Note 1)	—	25	60	—
Average Input Current	I_{in}	(Note 2)	—	0.1	0.8	—
Storage Discharge Time	T_{SD}	(Note 2)	—	0.2	0.8	—
Input Current Temperature	T_{in}	(Note 3)	—	0.2	0.8	—
Input Current Current	I_{in}	(Note 2)	—	0.8	4	—
Average Input Current	I_{in}	(Note 2)	—	0.2	0.8	—
Input Bias Current	I_{b}	(Note 2)	—	0.1	20	—
Average Input Bias Current	I_{b}	(Note 2)	—	0.1	20	—
Input Voltage Range	V_{in}	(Note 2)	—	8	20	—
Common-Mode Rejection Ratio	CMR	(Note 2)	—	210	110	—
Power Supply Rejection Ratio	$PSRR$	(Note 2)	—	90	120	—
Input Voltage Temperature	T_{in}	(Note 2)	—	0.2	0.8	—
Input Voltage Bias	V_{in}	(Note 2)	—	0.2	0.8	—

1. On 40-60 grade Vias is measured approximately one minute after application of power. For all other grade Vias is measured spread evenly 0.5 seconds after application of power.
2. Samples tested.
3. Determined by design.

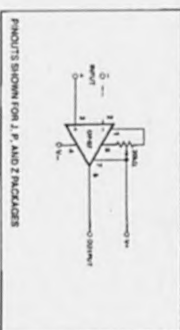
TYPICAL OFFSET VOLTAGE TEST CIRCUIT



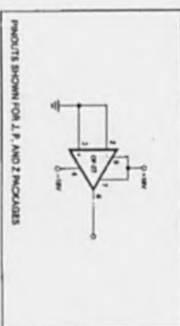
TYPICAL LOW-FREQUENCY NOISE TEST CIRCUIT



OPTIONAL OFFSET NULLING CIRCUIT



BURN-IN CIRCUIT



ELECTRICAL CHARACTERISTICS at $V_S = \pm 15V$, $T_A = 25^\circ C$, unless otherwise noted

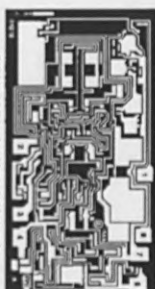
PARAMETERS		SYMBOL		CONDITIONS		OP-07C		OP-07C		MIN		TYP		MAX		LIMITS	
						MIN		TYP		MAX		MIN		TYP		MAX	
Input Drive Voltage	V_{DD}	(max 1)	—	20	15	—	64	100	—	64	100	—	64	100	—	64	100
Input Drive Voltage Sensitivity	V_{DD}/I_{DD}	(max 2)	—	63	3.8	—	63	2.0	—	63	2.0	—	63	2.0	—	63	2.0
Input Drive Current	I_{DD}	(max 3)	—	6.3	3.4	—	6.3	6.0	—	6.3	6.0	—	6.3	6.0	—	6.3	6.0
Input Bias Current	I_b	(max 4)	—	21.2	5.65	—	21.8	27.0	—	22.0	27.0	—	22.0	27.0	—	22.0	27.0
Input Noise Voltage	V_{nnp}	(max 5)	—	935	6.4	—	938	655	—	938	655	—	938	655	—	938	655
Input Noise Density	e_n	(max 6)	—	90.9	10.6	—	90.9	20.0	—	90.9	20.0	—	90.9	20.0	—	90.9	20.0
Output Noise Density	e_o	(max 7)	—	90.2	10.6	—	90.2	10.6	—	90.2	10.6	—	90.2	10.6	—	90.2	10.6
Output Noise Current	I_{nnp}	(max 8)	—	9.8	11.2	—	9.8	11.5	—	9.8	11.5	—	9.8	11.5	—	9.8	11.5
Input Noise Current	I_{npi}	(max 9)	—	14	30	—	15	30	—	15	30	—	15	30	—	15	30
Input Resistance – Common Mode	R_{in}	(max 10)	—	0.32	0.80	—	0.32	0.80	—	0.32	0.80	—	0.32	0.80	—	0.32	0.80
Input Resistance – Differential Mode	R_{in}	(max 11)	—	0.16	0.25	—	0.16	0.27	—	0.16	0.27	—	0.16	0.27	—	0.16	0.27
Input Resistance – Common Mode	R_{in}	(max 12)	—	0.17	0.17	—	0.17	0.19	—	0.17	0.19	—	0.17	0.19	—	0.17	0.19
Input Resistance – Differential Mode	R_{in}	(max 13)	—	16	30	—	6	33	—	7	33	—	7	33	—	7	33
Input Resistance – Common Mode	R_{in}	(max 14)	—	300	—	—	300	—	—	300	—	—	300	—	—	300	—
Input Voltage Range	V_{in}	(max 15)	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4
Common Mode	C_{in}	(max 16)	—	508	103	—	508	100	—	64	108	—	64	108	—	64	108
Power Supply Rejection Ratio	$PSRR$	(max 17)	—	6	20	—	7	33	—	7	33	—	7	33	—	7	33
Low Signal Voltage Gain	A_{v0}	(max 18)	—	200	300	—	150	400	—	150	400	—	150	400	—	150	400
Wideband Voltage Gain	A_{v0}	(max 19)	—	160	400	—	160	400	—	160	400	—	160	400	—	160	400
Bandwidth	f_{-3dB}	(max 20)	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4	—	2.0	5.4
Input Impedance	Z_{in}	(max 21)	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0
Output Impedance	Z_{out}	(max 22)	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0	—	1.0	1.0
Power Consumption	P_D	(max 23)	—	4	8	—	4	8	—	4	8	—	4	8	—	4	8
Power Dissipation	P_D	(max 24)	—	4	8	—	4	8	—	4	8	—	4	8	—	4	8
Power Regulation	ρ_{reg}	(max 25)	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—
Temperature Coefficient	α_{TC}	(max 26)	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—
Temperature Coefficient	α_{TC}	(max 27)	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—
Temperature Coefficient	α_{TC}	(max 28)	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—	—	0.4	—

1. Input Output Voltage requirements are performed by automated test equipment approximately 2.5 seconds after application of power.
2. Run Time Input Output Voltage Stability refers to the averaged input line of Volts. When over extended periods after the first 20 days of operation, excluding the initial hour of operation, averages in Volts during the first 30 operating days are typically 2.5V — refer to typical performance.
3. Parameter is specific model.
4. Storage status.
5. Output tested by design.
6. Quiescent load and tested.

ELECTRICAL CHARACTERISTICS at $V_g = \pm 15V$, $0^\circ C \leq T_A \leq 70^\circ C$ for OP-07E, and $-40^\circ C \leq T_A \leq 85^\circ C$ for OP-07CD, unless otherwise noted.

[illegible]

1. Input circuit voltage measurements are performed by automated test equipment approximately 0.5 seconds after application of power.
2. Sample tested.
3. Quarantined by design.



DIE SIZE 0.700 x 0.035 inches, 5500 sq. mils
(2.84 x 1.40 mm, 3.54 sq. mm)

1. BALANCE
2. INVERTING INPUT
3. NONINVERTING INPUT
4. V-
5. OUTPUT
6. V+
7. BALANCE

WAFER TEST LIMITS at $V_B = \pm 15V$, $T_A = 25^\circ C$ for OP-07N, OP-07G and OP-07R devices; $T_A = 125^\circ C$ for OP-07T and OP-07T devices, unless otherwise noted.

[illegible]

1. For 20°C characteristics of C9-Q10T and C9-Q10L, see C9-Q10N and C9-Q10 characteristics, respectively.
2. Quantified by analysis.

Electrical tests are performed at under-pulse to the limits shown. Due to variations in assembly methods and normal yield loss, part after processing is guaranteed to meet the limits shown. Current factory to regulate substitutions based on give for qualification through sample lot assembly and testing guaranteed for standard products only. Current factory to regulate substitutions based on give for qualification through sample lot assembly and testing

TYPICAL ELECTRICAL CHARACTERISTICS at $V_g = \pm 15$ V, $T_A = +25^\circ$ C, unless otherwise noted

[illegible]

D.3: Program. Ref. Voltage Device – TL431

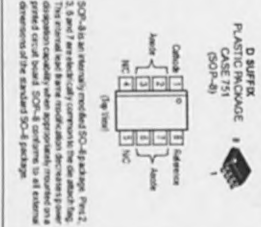
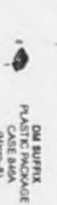
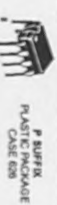
PROGRAMMABLE PRECISION REFERENCES

The TL431, A, B integrated circuits are three-terminal programmable shunt regulator devices. These monolithic IC voltage references operate as a low temperature coefficient zener which is programmable from V_{REF} to 36 V with two external resistors. These devices exhibit a wide operating current range of 1.0 mA to 100 mA with a typical dynamic impedance of 0.22 Ω . The characteristics of these references make them excellent replacements for zener diodes in many applications such as digital voltmeters, power supplies, and op amp circuitry. The 2.5 V reference makes it convenient to obtain a stable reference from 5.0 V logic supplies, and since the TL431, A, B operates as a shunt regulator, it can be used as either a positive or negative voltage reference.

- Programmable Output Voltage to 36 V
- Voltage Reference Tolerance $\pm 0.4\%$, Typ @ 25°C (TL431B)
- Low Dynamic Output Impedance, 0.22 Ω Typical
- Load Current Capability of 1.0 mA to 100 mA
- Equivalent Full-Range Temperature Coefficient of 50 ppm/°C Typical
- Temperature Compensated for Operation over Full Rated Operating Temperature Range
- Low Output Noise Voltage

TL431, A, B Series

PROGRAMMABLE PRECISION REFERENCES SEMICONDUCTOR TECHNICAL DATA

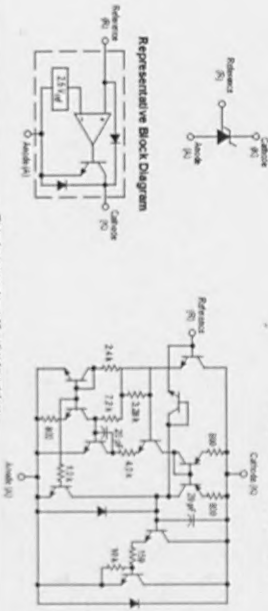


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Rev E

TL431, A, B Series

Representative Schematic Diagram Component values are nominal



MAXIMUM RATINGS (Full operating ambient temperature range unless otherwise noted)

Rating	Symbol	Value	Unit
Cathode to Anode Voltage	V_{CA}	37	V
Cathode Current (Continuous)	I_C	-100 to +150	mA
Balance Current Range (Continuous)	I_{BI}	-0.05 to +10	mA
Operating Junction Temperature	T_J	150	°C
Operating Ambient Temperature Range	T_A	-40 to +85 -40 to +125 TL431C, TL431AC, TL431BC	°C
Storage Temperature Range	T_{stg}	-45 to +150	°C
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	0.20 1.10 0.52	W
Power Dissipation @ $T_A = 25^\circ\text{C}$	P_D	1.5 3.0	W

NOTE: ESD data applies upon request.

RECOMMENDED OPERATING CONDITIONS

Condition	Symbol	Min	Max	Unit
Cathode to Anode Voltage	V_{CA}		36	V
Cathode Current	I_C	1.0	100	mA

THERMAL CHARACTERISTICS

Characteristic	Symbol	D-Suffix Package	P-Suffix Package	DM-Suffix Package	Unit
Thermal Resistance Junction-to-Ambient	R_{JA}	178	114	240	°C/W
Thermal Resistance Junction-to-Case	R_{JC}	83	41	—	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$, unless otherwise noted)

Characteristic	Symbol	TL431				TL431C			
		Min	Typ	Max	Unit	Min	Typ	Max	Unit
Reference Input Voltage (Figure 1) $V_{IA} = V_{ref}$, $I_K = 10 \text{ mA}$ $T_A = 25^\circ\text{C}$ $I_A = \text{Load to } T_{jpin} (\text{Note 1})$	V_{ref}	2.44 2.41	2.495	-	V	2.44 2.423	2.495	-	V
Reference Input Voltage Deviation Over Temperature (Figure 1, Note 1, 2) $V_{IA} = V_{ref}$, $I_K = 10 \text{ mA}$	ΔV_{ref}	-	7.0	-	mV	-	3.0	-	mV
Ratio of Change in Reference Input Voltage to Change in Cathode to Anode Voltage $I_K = 10 \text{ mA}$ (Figure 2) $\Delta V_{KA} = 10 \text{ V to } V_{Aof}$ $\Delta V_{KA} = 20 \text{ V to } 10 \text{ V}$	$\frac{\Delta V_{ref}}{\Delta V_{KA}}$	- -1.4 -1.0	-2.7 -2.0	-	mV/V	-1.4 -1.0	-2.7 -2.0	-	mV/V
Reference Input Current (Figure 2) $I_K = 10 \text{ mA}$, $R_1 = 10 \text{ k}\Omega$, $R_2 = \infty$ $T_A = 25^\circ\text{C}$ $I_A = \text{Load to } T_{jpin} (\text{Note 1})$	I_{ref}	-	1.8	4.0	μA	-	1.8	4.0	μA
Reference Input Current Deviation Over Temperature Range (Figure 2, Note 1, 4) $I_K = 10 \text{ mA}$, $R_1 = 10 \text{ k}\Omega$, $R_2 = \infty$	ΔI_{ref}	-	0.6	2.5	μA	-	0.4	1.2	μA
Maximum Cathode Current For Regulation $V_{KA} = V_{Aof}$ (Figure 1)	I_{Kmax}	-	0.5	1.0	mA	-	0.5	1.0	mA
Off-State Cathode Current (Figure 2) $V_{KA} = 20 \text{ V}$, $V_{IA} = 0 \text{ V}$	I_{off}	-	260	1000	nA	-	2.8	1000	nA
Dynamic Impedance at Input, Note 3 $V_{KA} = V_{Aof}$, $\Delta I_K = 1.0 \text{ mA}$ to 100 mA $f = 10 \text{ kHz}$	$Z_i(\text{k}\Omega)$	-	0.22	0.5	Ω	-	0.22	0.5	Ω

[illegible]

The average temperature coefficient of the reference input voltage, α_{Vref} is defined as

$$\frac{V_{red}}{V_{red}^0} = \frac{\exp\left(\frac{V_{red}}{0.25 \text{ V}}\right) \times 10^6}{\Delta V_{red} \times 10^6} = \frac{\exp\left(\frac{V_{red}}{0.25 \text{ V}}\right)}{\Delta V_{red}}$$

Example: $\Delta V_{\text{cell}} = 0.0 \text{ mV}$ and slope is positive.

$$V_{\text{red}} @ 25^{\circ}\text{C} = 2.405 \text{ V} \cdot \Delta T_A = 70^{\circ}\text{C} \quad \bullet \quad V_{\text{red}} = \frac{0.026 \text{ V} \cdot 10^6}{\frac{5000 \cdot 70}{5000}} = 45.8 \text{ ppm}/^{\circ}\text{C}$$

$$2. \text{ The dynamic impedance } Z_{\text{dyn}} \text{ is defined as } Z_{\text{dyn}} = \frac{dV_{\text{BE}}}{dI_{\text{C}}}.$$

$$I_{\text{SCA}}^{-1} = I_{\text{SCA}}^{-1} \left(1 + \frac{R1}{R2} \right)$$

When the device is programmed with two subroutines, R1 and R2, (refer to Figure 2) the total dynamic impedance of the circuit is defined as

Figure 30 Output Control for a

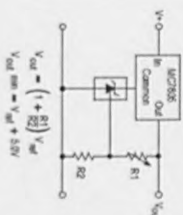


Figure 22. Constant Current Source

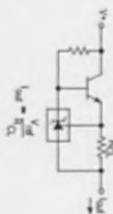


Figure 23. Constant Current Sink

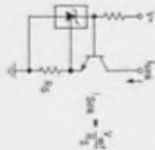


Figure 24. TRIAC Crowbar

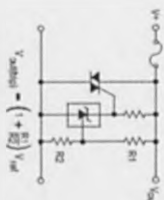
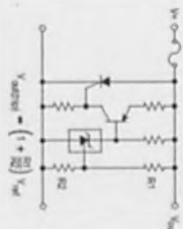


Figure 25. SRC Crowbar



D.4: 1-8 Analogue Multiplexer - 4052B

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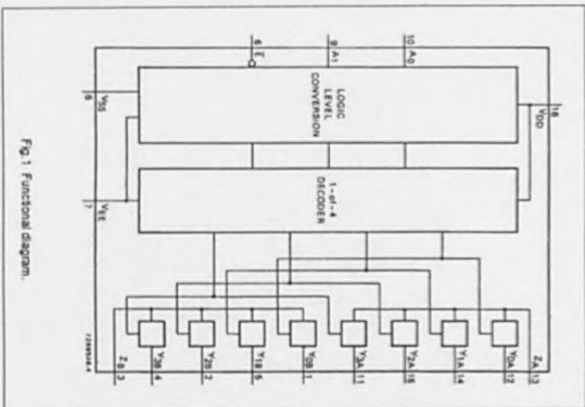


Fig. 1 Functional diagram.

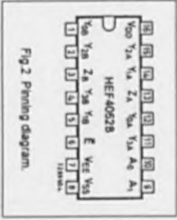


Fig. 2 Pinning diagram.

- HEF4052B(P): 16-lead DIL plastic (SOT18-1)
- HEF4052B(CP): 16-lead DIL ceramic (SOT7)
- HEF4052B(TO): 16-lead SO plastic (SOT108-1)
- (1) Package Designator North America

FUNCTIONING
Y₀ to Y₃ independent inputs/outputs
Y₀ to Y₃ independent inputs/outputs
A₀, A₁ address inputs
E enable input (active LOW)
Z₀, Z₁ common inputs/outputs

PACKAGING DATA
See Family category MSI
See Family Specifications

DESCRIPTION
The HEF4052B is a dual 4-channel analogue multiplexer/demultiplexer with common channel select logic. Each multiplexer/demultiplexer has four independent inputs/outputs (Y₀ to Y₃) and a common input/output (Z₀ to Z₁). The common channel select logic includes two address inputs (A₀ and A₁) and an active LOW enable input (E).
Both multiplexer/demultiplexers contain four bidirectional analogue switches, each with one side connected to an independent input/output (Y₀ to Y₃) and the other side connected to a common input/output (Z₀ to Z₁). With E LOW, one of the four switches is selected (low impedance ON-state) by A₀ and A₁. With E HIGH, all switches are in the high impedance OFF-state, independent of A₀ and A₁.

V_{CC} and V_{EE} are the supply voltage connections for the digital control inputs (A₀, A₁, and E). The V_{CC} to V_{EE} range is 3 to 15 V. The analogue inputs/outputs (Y₀ to Y₃, and Z₀ and Z₁) can swing between V_{CC} as a positive limit and V_{EE} as a negative limit. V_{CC} - V_{EE} may not exceed 15 V. For operation as a signal multiplexer/demultiplexer, V_{EE} is connected to V_{SS} (typically ground).

Philips Semiconductors
Dual 4-channel analogue multiplexer/demultiplexer
HEF4052B
MSI

Product specification

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FUNCTION TABLE			
INPUTS		CHANNEL	
E	A ₁ A ₀	ON	
L	L L	Y ₀ - Z ₀ , Y ₀ - Z ₁	
L	L H	Y ₁ - Z ₀ , Y ₁ - Z ₁	
L	H L	Y ₂ - Z ₀ , Y ₂ - Z ₁	
L	H H	Y ₃ - Z ₀ , Y ₃ - Z ₁	
H	X X	none	

Notes
1. H = HIGH state (the more positive voltage)
L = LOW state (the less positive voltage)
X = state is immaterial

RATINGS
Limiting values in accordance with the Absolute Maximum System (IEC 134)
Supply voltage (with reference to V_{EE}) V_{CC} -18 to +0.5 V
Note
1. To avoid drawing V_{CC} current out of terminal Z₀ when switch current flows into terminal Y₀, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z₀, no V_{CC} current will flow out of terminal Y₀. In this case there is no limit for the voltage drop across the switch, but the voltages at Y₀ and Z₀ may not exceed V_{CC} or V_{EE}.

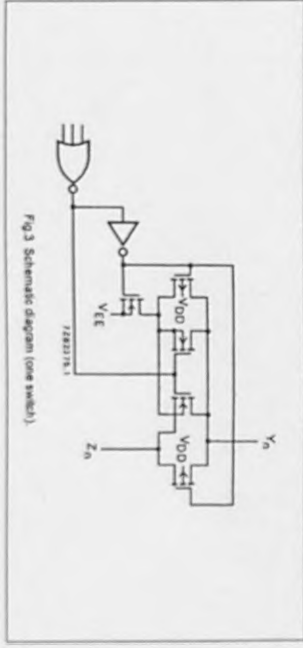


Fig. 3 Schematic diagram (one switch).

Philips Semiconductors
Dual 4-channel analogue multiplexer/demultiplexer
HEF4052B
MSI

Product specification

Dual 4-channel analogue multiplexer/demultiplexer

HEF4052B
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AC CHARACTERISTICS

$V_{EE} = V_{SS} = 0\text{ V}$; $T_{amb} = 25^\circ\text{C}$; input transition times $\leq 20\text{ ns}$

	V_{DD} V	TYPICAL FORMULA FOR P (µW)	where
DYNAMIC power dissipation per package (P)	5 10 15	$1300 (1 + 2I(C_i)) > V_{DD}^2$ $6100 (1 + 2I(C_i)) > V_{DD}^2$ $15600 (1 + 2I(C_i)) > V_{DD}^2$	I = input freq. (MHz) f_o = output freq. (MHz) C_i = load capacitance (pF) $2I(C_i)$ = sum of outputs V_{DD} = supply voltage (V)

AC CHARACTERISTICS

$V_{EE} = V_{SS} = 0\text{ V}$; $T_{amb} = 25^\circ\text{C}$; input transition times $\leq 20\text{ ns}$

	V_{DD} V	SYMBOL	TYP.	MAX.	
Propagation delays $V_{in} \rightarrow V_{out}$ HIGH to LOW	5 10 15	t_{PHL}	10 5 5	20 10 10	ns note 1
LOW to HIGH	5 10 15	t_{PLH}	10 5 5	20 10 10	ns note 1
$A_v = V_{out}/V_{in}$ HIGH to LOW	5 10 15	t_{PHL}	150 50 50	300 100 100	ns note 2
LOW to HIGH	5 10 15	t_{PLH}	150 75 50	300 150 100	ns note 2
Output disable times $E \rightarrow V_{in}$ HIGH	5 10 15	t_{WZ}	95 90 180	190 180 ns	ns note 3
LOW	5 10 15	t_{WZ}	100 90 90	200 180 180	ns note 3
Output enable times $E \rightarrow V_{in}$ HIGH	5 10 15	t_{PH}	130 55 45	260 115 85	ns note 3
LOW	5 10 15	t_{PL}	120 50 35	240 100 75	ns note 3

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Dual 4-channel analogue multiplexer/demultiplexer

HEF4052B
MSI

	V_{DD} V	SYMBOL	TYP.	MAX.	
Distortion, sine-wave response	5 10 15		0.25 0.04 0.04	%	note 4
Cross-talk between any two channels	5 10 15		-	1	dBHz note 5
Cross-talk, enable or address input to output	5 10 15		-	50	mV mV note 6
Off-state feed-through	5 10 15		-	1	dBHz note 7
On-state frequency response	5 10 15		13 40 70	dBHz	note 8

Notes

V_{in} is the input voltage at a Y or Z terminal, whichever is assigned as input.

V_{out} is the output voltage at a Y or Z terminal, whichever is assigned as output.

1. $R_L = 10\text{ k}\Omega$ to V_{EE} ; $C_L = 50\text{ pF}$ to V_{EE} ; $E = V_{EE}$; $V_{in} = V_{DD}$ (square-wave); see Fig. 8.

2. $R_L = 10\text{ k}\Omega$ to V_{DD} ; $C_L = 50\text{ pF}$ to V_{DD} ; $E = V_{DD}$; $A_v = V_{DD}$ (square-wave); $V_{in} = V_{DD}$ and R_L to V_{EE} for t_{PHL} ; $V_{in} = V_{EE}$ and R_L to V_{DD} for t_{PLH} ; see Fig. 8.

3. $R_L = 10\text{ k}\Omega$; $C_L = 50\text{ pF}$ to V_{EE} ; $E = V_{DD}$ (square-wave); $V_{in} = V_{DD}$ and R_L to V_{EE} for t_{PHL} and t_{PLH} ; see Fig. 8.

4. $R_L = 10\text{ k}\Omega$; $C_L = 15\text{ pF}$; channel ON; $V_{in} = 1/2 V_{DD}$ (sine-wave, symmetrical about $1/2 V_{DD}$); $f_o = 1\text{ MHz}$; see Fig. 9.

5. $R_L = 1\text{ k}\Omega$; $V_{in} = 1/2 V_{DD}$ (sine-wave, symmetrical about $1/2 V_{DD}$); $20\log \frac{V_{out}}{V_{in}} = -50\text{ dB}$; see Fig. 10.

6. $R_L = 10\text{ k}\Omega$ to V_{EE} ; $C_L = 15\text{ pF}$ to V_{EE} ; E or $A_v = V_{DD}$ (square-wave); cross-talk is $|V_{out}|$ (peak value); see Fig. 8.

7. $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; channel OFF; $V_{in} = 1/2 V_{DD}$ (sine-wave, symmetrical about $1/2 V_{DD}$); $20\log \frac{V_{out}}{V_{in}} = -50\text{ dB}$; see Fig. 8.

8. $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; channel ON; $V_{in} = 1/2 V_{DD}$ (sine-wave, symmetrical about $1/2 V_{DD}$); $20\log \frac{V_{out}}{V_{in}} = -3\text{ dB}$; see Fig. 9.

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DYNAMIC ACCURACY

(Notes 5, 14)

SYMBOL	PARAMETER	CONDITIONS	LIC166SLT1035A		
			MIN	TYP	MAX
V _{in}	Acting Input Range (Notes 8)	4.75V < V _{in} < 5.25V; 4.75V < V _{in} < 5.25V		±0	V
I _{in}	Acting Input Leakage Current	ES = High		±1	μA
C _{in}	Acting Input Capacitance			10	pF
I _{in}	Acting Input Impedance			20	kΩ

INTERNAL REFERENCE CHARACTERISTICS
(Note 5)

SYMBOL	PARAMETER	CONDITIONS	LTC1060/LTC1060A			UNITS
			MIN	TYP	MAX	
$S_{IN} \pm D$	Signal-to-(Noise + Distortion) Ratio	10mV Input Signal (Note 14) 10mV Input Signal 20mHz – 4000Hz Input Signal	87	81.5	68	dB
THD	Total Harmonic Distortion	10mV Input Signal, First 5 Harmonics	39	–102	68	dB
		10mV Input Signal, First 5 Harmonics	–84	–84	–84	dB
		10mV Input Signal	–102	–84	68	dB
	Peak-to-Peak or Sinusoidal Noise	10mV Input Signal	273	–84	68	dB
		10mV Input Signal	48	–84	68	dB
		10mV Input Signal	273	–84	68	dB
	Full-Power Bandwidth	(Note 15)	48		Hz	
	Asymmetry Duty				μs	
	Asymmetry Slope				μs	
	Transient Response				μs	
	Overload Recovery	Full-Rate Step (Note 8)			μs	
		(Note 16)	150		Hz	

DIGITAL INPUTS AND DIGITAL OUTPUTS
(Notes)

SYMBOL	PARAMETER	CONDITIONS	11C100A/C100BA			UNIT
			MIN	TYP	MAX	
V_{in}	High Level Input Voltage	$V_{DD} = 5.25V$	2.4		0.8	V
V_L	Low Level Input Voltage	$V_{DD} = 4.75V$			≥ 0	V
I_{in}	Digital Input Current	$V_{in} = 0V$ to V_{DD}		5		μA
V_{OH}	Digital Output Voltage	$I_O = -10\mu A$				V
V_{OL}	High Level Output Voltage	$I_O = -200\mu A$	4.8	4.5		V
V_{OH}	Low Level Output Voltage	$I_O = 1.6mA$		0.05		V
V_{OL}	Low Level Output Voltage	$V_{DD} = 4.75V$		0.10	0.4	V

TIMING CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	LTC1604/LC1605A		UNIT
			MIN	TYP	
I_{CC}	Full-Supply Leakage D15 to D05	V _{DD1} = 8V to V _{DD3} (FS)		±0	μA
C _{SD}	Pin-2 Output Capacitance D15 to D05	(FS High Imped B)		15	pF
I _{OSOURCE}	Output Source Current	V _{DD1} = 8V		±10	mA
I _{SENSE}	Output Sink Current	V _{DD1} = V _{DD3}		10	mA

POWER REQUIREMENTS

[illegible]

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LTC1605

APPLICATIONS INFORMATION

Internal Voltage Reference

The LTC1605 has an on-chip, temperature compensated, curvature corrected, bandgap reference, which is factory trimmed to 2.50V. The full-scale range of the ADC is equal to $(4 \times V_{REF})$ or nominally $\pm 10V$. The output of the reference is connected to the input of a unity-gain buffer through a 4k resistor (see Figure 3). The input to the buffer or the output of the reference is available at REF (Pin 3). The internal reference can be overdriven with an external reference if more accuracy is needed. The buffer output drives the internal DAC and is available at CAP (Pin 4). The CAP pin can be used to drive a steady DC load of less than 2mA. Driving an AC load is not recommended because it can cause the performance of the converter to degrade.

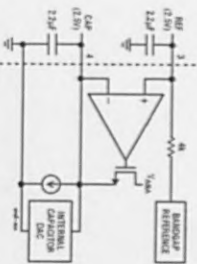


Figure 3. Internal or External Reference Source

For minimum code transition noise the REF pin and the CAP pin should each be decoupled with a capacitor to filter wideband noise from the reference and the buffer (2.2 μF tantalum).

Offset and Gain Adjustments

The LTC1605 offset and full-scale errors have been trimmed at the factory with the external resistors shown in Figure 4. This allows for external adjustment of offset and full scale in applications where absolute accuracy is important. See Figure 5 for the offset and gain trim circuit. First adjust the offset to zero by adjusting resistor R3. Apply an input voltage of $-152.6mV$ ($-0.5LSB$) and adjust R3 so the code is changing between 1111 1111 1111 1111 and 0000 0000 0000 0000. The gain error is trimmed by adjusting resistor R4. An input voltage of 9999.42V ($4FS - 1.5LSB$) is

applied to V_{IN} and R4 is adjusted until the output code is changing between 0111 1111 1111 1110 and 0111 1111 1111 1111. Figure 6 shows the bipolar transfer characteristic of the LTC1605.

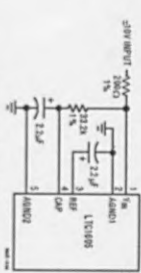


Figure 4. -10V Input With Offset Trim

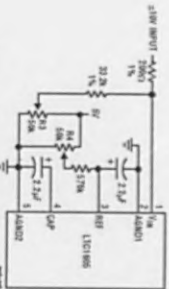


Figure 5. -10V Input with Offset and Gain Trim



Figure 6. LTC1605 Bipolar Transfer Characteristics

DC Performance

One way of measuring the transition noise associated with a high resolution ADC is to use a technique where a DC

LTC1605

APPLICATIONS INFORMATION

signal is applied to the input of the ADC and the resulting output codes are collected over a large number of conversions. For example in Figure 7 the distribution of output code is shown for a DC input that has been digitized 10000 times. The distribution is Gaussian and the RMS code transition is about 1LSB.

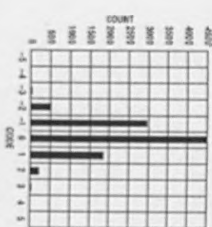


Figure 7. Histogram for 10000 Conversions

DIGITAL INTERFACE

Internal Clock

The ADC has an internal clock that is trimmed to achieve a typical conversion time of 7 μs . No external adjustments are required and, with the typical acquisition time of 1 μs , throughput performance of 100ksp/s is assured.

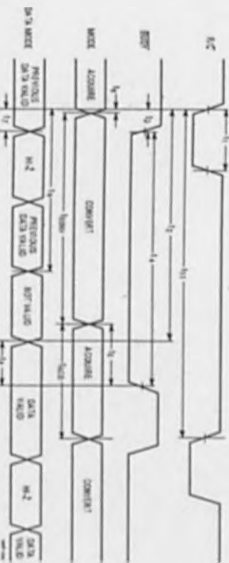


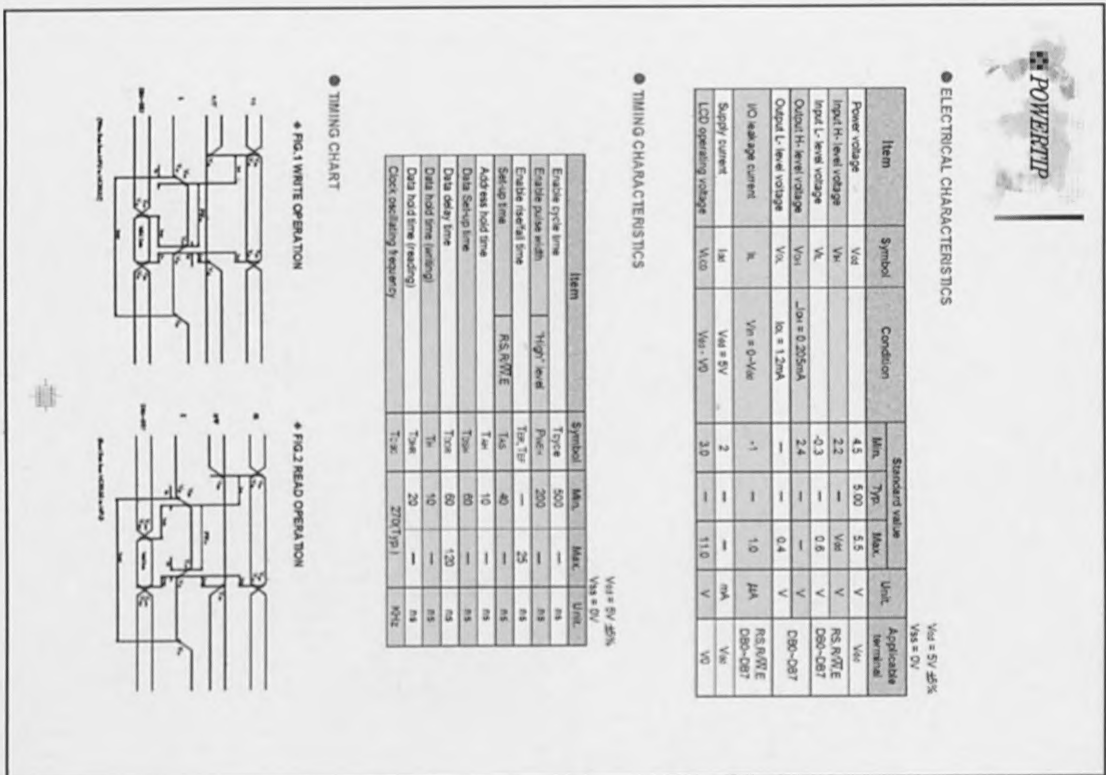
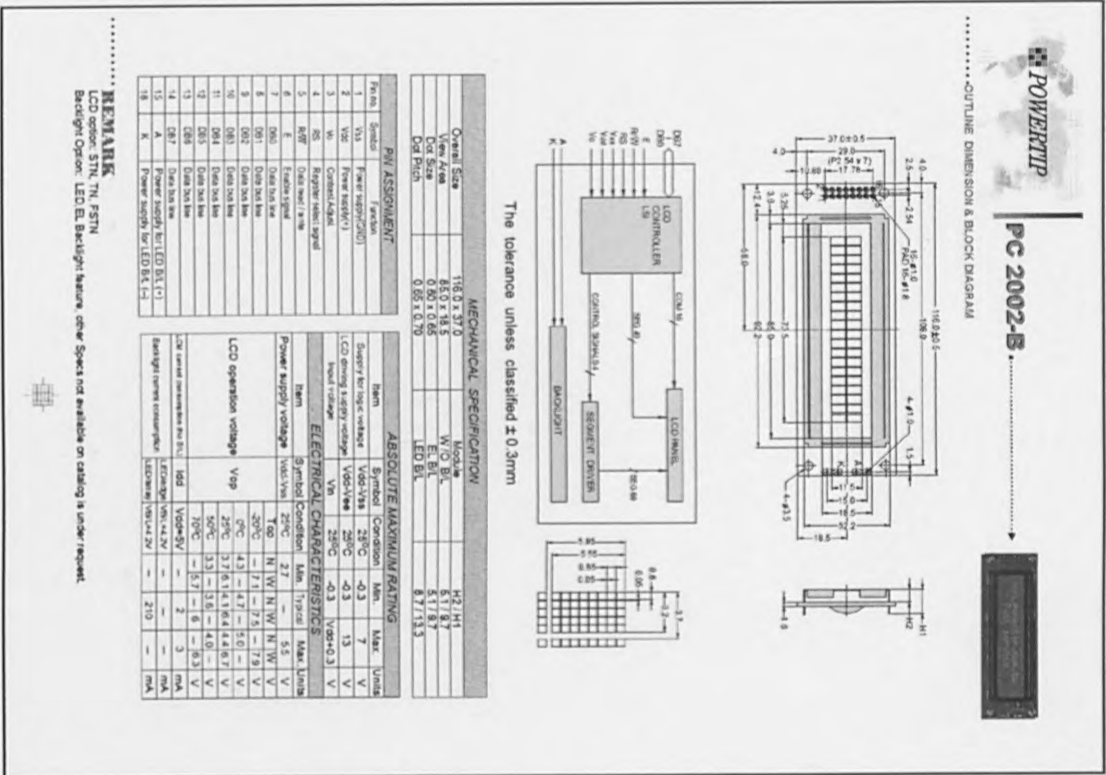
Figure 8. Conversion Timing with Outputs Enabled After Conversion (CS Tri-Level)

Timing and Control

Conversion start and data read are controlled by two digital inputs: CS and R/C. To start a conversion and put the sample-and-hold into the hold mode bring CS and R/C low for no less than 40ns. Once initiated it cannot be restarted until the conversion is complete. Converter status is indicated by the BUSY output and this is low while the conversion is in progress.

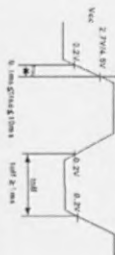
There are two modes of operation. The first mode is shown in Figure 8. The digital input R/C is used to control the start of conversion. CS is tied low. When R/C goes low the sample-and-hold goes into the hold mode and a conversion is started. BUSY goes low and stays low during the conversion and will go back high after the conversion has been completed and the internal output shift registers have been updated. R/C should remain low for no less than 40ns. During the time R/C is low the digital outputs are in a Hi-Z state. R/C should be brought back high within 3 μs after the start of the conversion to ensure that no errors occur in the digitized result. The second mode shown in Figure 9, uses the CS signal to control the start of a conversion and the reading of the digital output. In this mode the R/C input signal should be brought low no less than 10ns before the falling edge of CS. The minimum pulse width for CS is 40ns. When CS falls, BUSY goes low and will stay low until the end of the conversion. BUSY will go high after the conversion has been completed. The new data is valid when CS is brought back low again to initiate

D.6: 2 x 20 Alphanumeric Display



● POWER SUPPLY RESET

The internal reset circuit will be operating properly when the following power supply conditions are satisfied. If it isn't operated properly, please perform the initial setting along with the instruction.



Item	Symbol	Measuring Condition	Standard Value Min./Typ./Max.	Unit
Power Supply Rise Time	t _{rise}	—	0.1 — 10	nS
Power Supply ClrP Time	t _{off}	—	1 — —	nS

Reset Function

➤ Initialization Mode by Internal Reset Circuit

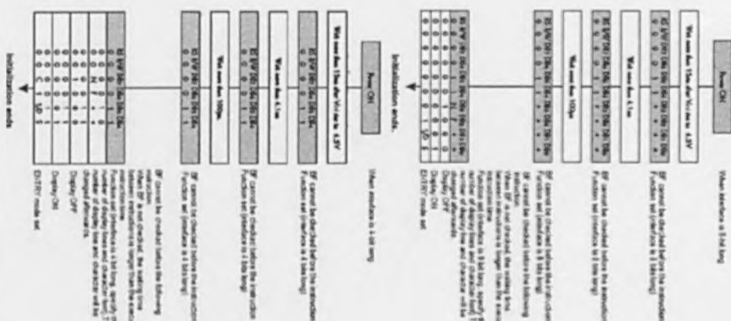
The counter and/or locally initialized (resets) when power is supplied (built-in internal reset circuit). The following instructions are executed during initialization. The busy flag (BF) is kept in busy state until initialization ends (BF=1). The busy state is 10ms after Vdd reaches 4.5V.

- (1) Display clear
- (2) Function set
 - DL=1 8 bit long interface data
 - DL=0 4 bit F=0.5 x 7 dots character font
 - N=1 2 lines
 - N=0 1 line
- (3) Display ON/OFF control
 - D=0 Display OFF
 - D=1 Cursor OFF
 - B=0 Blank OFF
- (4) Entry mode set
 - I / D = 1 = 1 (increment)

Note: When using internal reset circuit is not satisfied in power supply conditions, the internal reset circuit will not function properly and initialization will not be performed. Please initialize using the MPU along with the instruction set.

- ◆ Initialization along with instruction

If power supply conditions are not satisfied, which for proper operation of internal rest circuit, it is required to make initialization along with instruction.

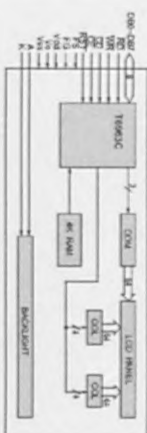
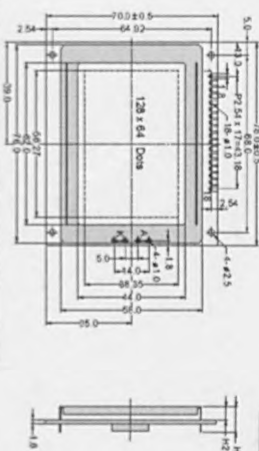


D.7: 64 x 128 Graphic Display



PG 12864-F

***** OUTLINE DESIGN & BLOCK DIAGRAM *****



The tolerance unless classified $\pm 0.3\text{mm}$



MECHANICAL SPECIFICATION		
Overall Size	78.0 x 70.0	Module
View Areas	62.0 x 44.0	HxHxH
Dot Size	0.39 x 0.35	W/O BL
Dot Pitch	0.44 x 0.60	EL BL
		LED BL
		9.2/15.6

PIN ASSIGNMENT	
Pin	Function
1	V _{DD}
2	V _{SS} (Power supply)
3	V _{SS} (Power supply)
4	V _{DD} (Power supply)
5	V _{SS} (Power supply)
6	V _{DD} (Power supply)
7	V _{SS} (Power supply)
8	V _{DD} (Power supply)
9	V _{SS} (Power supply)
10-17	V _{DD} (Power supply)
18	V _{SS} (Power supply)

[illegible]

REFERENCES

LCD option: STN, TN, FSTN
Backlight Option: LED/EL Backlight feature, other Specs not available on catalog is under request



TOSHIBA

T6963

COMMAND DEFINITION

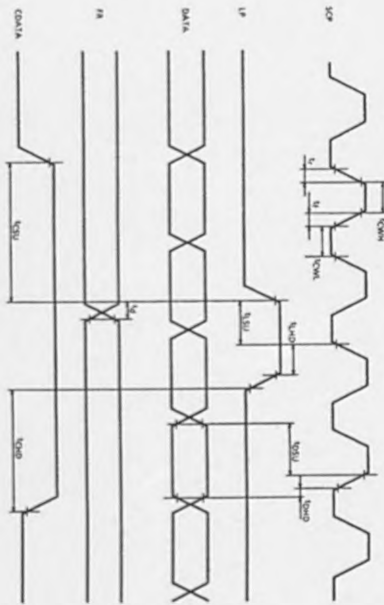
COMMAND	CODE	D1	D2	FUNCTION
REGISTERS SETTING	00100001 00100010 00100100	X address Data Low address	Y address 00H High address	Set Cursor Pointer Set Offset Register Set Address Pointer
SET CONTROL WORD	01000000 01000010 01000010 01000111	Low address Columns Low address	High address 00H High address 00H	Set Text Home Address Set Text Area Set Graphic Home Address Set Graphic Area
MODE SET	10001000 10000011 10000100 10000000 10001000	— — — — —	— — — — —	ON mode EXOR mode AND mode Text Attribute mode Internal CG ROM mode External CG RAM mode
DISPLAY MODE	10010000 10010010 10010011 10010100 10011000 10011100	— — — — — —	— — — — — —	Display off Cursor on, blink off Cursor on, blink on Text on, graphic off Text off, graphic on Text on, graphic on
CURSOR POSITION SELECT	10100000 10100001 10100010 10100011 10100100 10100101 10100110 10100111	— — — — — — — —	— — — — — — — —	1-line cursor 2-line cursor 3-line cursor 4-line cursor 5-line cursor 6-line cursor 7-line cursor 8-line cursor
DATA AUTO READ / WRITE	10110000 10110001 10110010 10110011	— — — —	— — — —	Set Data Auto Write Set Data Auto Read Auto Read
DATA READ / WRITE	11000000 11000010 11000011 11000100 11000101	Data — — Data —	— — — — —	Data Write and Increment ADP Data Read and Increment ADP Data Write and Decrement ADP Data Read and Decrement ADP Data Write and Nonvolatile ADP Data Read and Nonvolatile ADP
SCREEN RELIC	11100000 11100001 11101000 11101001	— — — —	— — — —	Screen Test
SCREEN COPY	11101000 11101001 11101010	— — —	— — —	Screen Copy

X : invall

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AC CHARACTERISTICS

- Switching Characteristics (1)

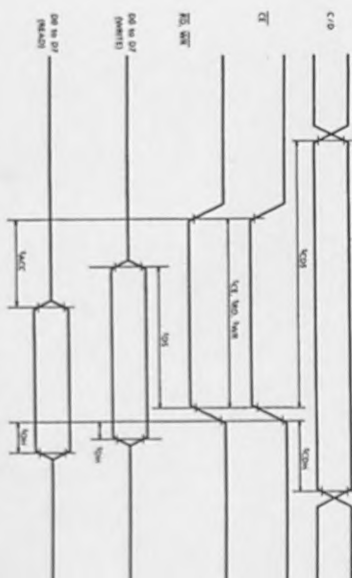


TEST CONDITIONS (Unless otherwise noted, $V_{DD} = 5.0V \pm 10\%$, $V_{SS} = 0V$, $T_a = -20$ to $70^\circ C$)

ITEM	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
Operating Frequency	f_{OP}	$T_a = -10 \sim 70^\circ C$	—	2.75	MHz
SCP Pulse Width	t_{CWH}, t_{CWL}	—	150	—	ns
SCP Rise/Fall Time	t_r, t_f	—	—	30	ns
LP Setup Time	t_{LSU}	—	150	290	ns
LP Hold Time	t_{LHD}	—	5	40	ns
Data Setup Time	t_{DSU}	—	170	—	ns
Data Hold Time	t_{DHD}	—	80	—	ns
RA Delay Time	t_d	—	0	90	ns
COMA Setup Time	t_{CSU}	—	450	850	ns
COMA Hold Time	t_{CHD}	—	450	950	ns

- Switching Characteristics (2)

Bus Timing



TEST CONDITIONS (Unless otherwise noted, $V_{DD} = 5.0V \pm 10\%$, $V_{SS} = 0V$, $T_a = -20$ to $75^\circ C$)

ITEM	SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
C/D Setup Time	t_{CDS}	—	100	—	ns
C/D Hold Time	t_{CDH}	—	10	—	ns
CE, RD, WR Pulse Width	t_{CE}, t_{RD}, t_{WR}	—	80	—	ns
Data Setup Time	t_{DS}	—	80	—	ns
Data Hold Time	t_{DH}	—	40	—	ns
Access Time	t_{ACC}	—	—	150	ns
Output Hold Time	t_{OHH}	—	10	50	ns

D.8: 512 Kbit IC2 Serial EEPROM – 24AA512



MICROCHIP 24AA512/24LC512/24FC512 512K I²C™ CMOS Serial EEPROM

Device Selection Table

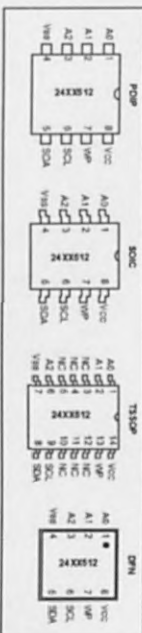
Part Number	VCC Range	Max Clock Frequency	Temp. Range
24AA512	1.8-5.5V	400 kHz (†)	—
24LC512	2.5-5.5V	400 kHz	—1E
24FC512	2.5-5.5V	1 MHz	—

Note 1: 100 kHz for VCC < 2.5V

Features:

- Low-power CMOS technology.
- Maximum write current 5 mA at 5.5V
- Maximum read current 400 μ A at 5.5V
- Standby current 100 nA typical at 5.5V
- 2-wire serial interface bus, I²C™ compatible
- Configurable for up to eight devices
- Self-timed erase/write cycle
- 128-byte Page Write mode available
- 6 ms max. write cycle time
- Hardware write protect for entire array
- Schmitt Trigger inputs for noise suppression
- 1,000,000 erase/write cycles
- Electrostatic discharge protection > 4000V
- Data retention > 200 years
- 8-pin PDIP, SOIC (208 mil), and DFN packages
- 14-lead TSSOP package
- Standard and Pin-Free finishes available
- Temperature range:
 - 40°C to +85°C
 - Industrial (I)
 - Automotive (E)
 - 40°C to +125°C

Package Type



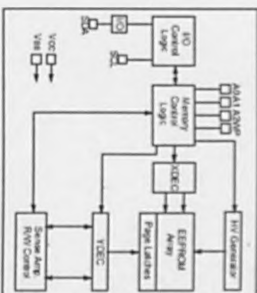
* 24LC512 is used in this document as a generic part number for the 24AA512/24LC512/24FC512 devices.

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Description:
The Microchip Technology Inc. 24AA512/24LC512/24FC512 (24XX512) is a 512K x 8 (512 Kbit) Serial Electrically Erasable Programmable Memory (EEPROM) device. It is capable of operation across a broad voltage range (1.8V to 5.5V). It has been developed for advanced, low-power applications such as personal communications and data acquisition. This device also has a page write capability of up to 128 bytes of data. This device is capable of both random and sequential reads up to the 512K boundary. For more information on the 512K boundary, please refer to the 512K address on the same bus. For up to 4 Mbit address, the device is available in the standard 8-pin plastic DIP, SOIC, DFN and 14-lead TSSOP packages.

Block Diagram



24AA512/24LC512/24FC512

1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings (†)

VCC	5.5V
All inputs and outputs w.r.t. VSS	-0.6V to VCC +1.0V
Storage temperature	-65°C to +150°C
Ambient temperature with power applied	-40°C to +125°C
ESD protection on all pins	2 kV

†NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This device is not intended for use in applications where exposure to such stresses is expected. Exposure to maximum rating conditions for extended periods may affect device reliability.

TABLE 1-1: DC CHARACTERISTICS

DC CHARACTERISTICS				Electrical Characteristics:	
Param. No.	Symbol	Characteristic	Min	Max	Units
D1	—	At A1, A2, SCL, SDA and WP pins	—	—	—
D2	V _{IH}	High-level input voltage	0.7 VCC	—	V
D3	V _{IL}	Low-level input voltage	—	0.3 VCC	V
D4	V _{IS}	Tri-state input voltage of Schmitt Trigger inputs (SCL, SDA pins)	0.05 VCC	—	V
D5	V _{OL}	Low-level output voltage	—	0.40	V
D6	I _I	Input leakage current	—	±1	μ A
D7	I _O	Output leakage current	—	±1	μ A
D8	C _{OUT}	Pin capacitance (all inputs/outputs)	—	10	pF
D9	I _{CC} Read	Operating current	—	400	μ A
D10	I _{CC} Write	Operating current	—	5	mA
D10	I _{CC} Standby	Standby current	—	1	μ A

Note: This parameter is periodically sampled and not 100% tested.

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24AA512/24LC512/24FC512

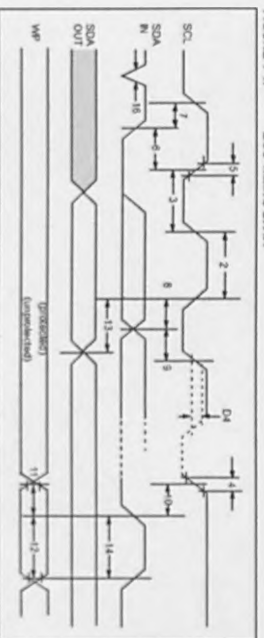
TABLE 1-2: AC CHARACTERISTICS

AC CHARACTERISTICS				Electrical Characteristics: Industrial (1) VCC = +1.8V to 5.5V Automotive (E) VCC = +2.5V to 5.5V		Ta = -40°C to +85°C Tb = -40°C to +125°C	
Param. No.	Sym	Characteristics	Min	Max	Units	Conditions	
1	FCLK	Clock frequency	—	400	kHz	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
2	Tsetup	Clock high time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
3	Tlow	Clock low time	—	500	ns	2.5V VCC + 5.5V 2MfCS12	
4	T1	SDA and SCL, rise time (Note 1)	—	1000	ns	1.8V VCC + 2.5V 1.8V VCC + 2.5V 2.5V VCC + 5.5V 2MfCS12	
5	T2	SDA and SCL, fall time (Note 1)	—	300	ns	2.5V VCC + 5.5V 2MfCS12	
6	T3	Start condition hold time	—	100	ns	As receive, 2MfCS12 2.5V VCC + 5.5V 2MfCS12	
7	T4	Start condition setup time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
8	T5	Data input hold time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
9	T6	Data input setup time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
10	T7	Stop condition setup time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
11	T8	Stop condition hold time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
12	T9	Write time	—	4000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
13	T10	Output valid from clock (Note 2)	—	3000	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
14	Tburst	Bus free time: Time the bus must be free before a new transmission can start	—	400	ns	1.8V VCC + 2.5V 2.5V VCC + 5.5V 2.5V VCC + 5.5V 2MfCS12	
15	T11	Input rise/fall suppression (SDA and SCL pins)	—	50	ns	As receive, 2MfCS12 (Notes 1 and 2)	
16	T12	Write cycle time (Data or page)	—	5	ns		
17	T13	Endurance	—	1,000,000	cycles	25°C (Note 4)	

- Notes:
1. T₁ and T₂ are the rise and fall times of the SDA and SCL signals. The device must provide an internal termination delay time to bridge the unbuffered region (minimum 300 ns) of the falling edge of SCL to avoid unintended generation of Start or Stop conditions.
 2. The combined T₁₀ and T₁₁ specifications are due to new I/OCS inputs which provide improved noise spike suppression. This eliminates the need for a T₁₁ specification for standard operation.
 3. This parameter is not tested but assumed by characterization. For endurance evaluation in a specific application, please consult the "Total Endurance" block which can be obtained from Microchip's web site: www.microchip.com.

24AA512/24LC512/24FC512

FIGURE 1-1: BUS TIMING DATA



D.10: Voltage Regulator – 79LM05

National Semiconductor

November 1984

LM79XX Series 3-Terminal Negative Regulators

General Description

The LM79XX series of 3-terminal regulators is available with fixed output voltages of $-5V$, $-8V$, $-10V$, and $-15V$. The LM79XX series is designed for use as a precision precision regulator at the output. The LM79XX series is packaged in the TO-220 power package and is capable of supplying 1.5A of output current.

The LM79XX series features an internal folding stage and built-in overcurrent protection. LM79XX series of fixed output voltage regulators are designed to be used in applications requiring a low quiescent current, a high output current, and a high output voltage.

Connection Diagrams

TO-220 Package

FIGURE 1

(N79000-01)

Other Popular Regulators: LM7912CT or LM7915CT
See MS Package Number: TO-220

These devices with a specified maximum output with two load and ensure good regulation in the voltage loaded. For applications requiring other voltages, see LM79XX series.

Features

- Thermal shut circuit and safe area protection
- High output regulation
- 1.5A output current
- No difference in percent output voltage

Typical Applications

(N79000-02)

The LM79XX series of 3-terminal regulators is designed to be used in applications requiring a low quiescent current, a high output current, and a high output voltage. The LM79XX series is designed to be used in applications requiring a low quiescent current, a high output current, and a high output voltage.

The LM79XX series of 3-terminal regulators is designed to be used in applications requiring a low quiescent current, a high output current, and a high output voltage.

LM79XX Series 3-Terminal Negative Regulators

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DS90C03-10, Rev. 10/84

[illegible]

D.11: DC-to-DC Converter – TEN 5-0522

TRACO
POWER

DC/DC Converter
TEL 3 Series 3 Watt

Features

- Wide 2:1/3:1 Input Ranges
- High Efficiency up to 81%
- Fall SMD-Design
- Indefinite Short-Circuit Protection
- 24-pin DIP Plastic Package
- Pin-compatible with TEL 3 / TED
- 2 Year Product Warranty

NEW
Model

With 10 – 30 VDC
Input



The TEL 3 series is a range of isolated 3 W converter in DIL24 package offering wide 2:1 input voltage range. Features include high efficiency which allows operation temperature up to 75 °C without derating and low output noise. This product series provides an economical solution for many cost critical applications in industrial and consumer electronics.

Model	Input voltage range	Output voltage	Output current max.	Efficiency typ.
TEL 3-0511	4.5 – 9.0 VDC	5 VDC	600 mA	70 %
TEL 3-0512		12 VDC	250 mA	74 %
TEL 3-0513		15 VDC	200 mA	74 %
TEL 3-0512		12 VDC	125 mA	74 %
TEL 3-0522	9 – 18 VDC	5 VDC	600 mA	76 %
TEL 3-0523		12 VDC	250 mA	80 %
TEL 3-0522		15 VDC	200 mA	80 %
TEL 3-0523		12 VDC	125 mA	80 %
TEL 3-0511	10 – 18 VDC	5 VDC	600 mA	76 %
TEL 3-0512		12 VDC	250 mA	80 %
TEL 3-0513		15 VDC	200 mA	80 %
TEL 3-0512		12 VDC	125 mA	80 %
TEL 3-0523	18 – 34 VDC	5 VDC	600 mA	77 %
TEL 3-0522		12 VDC	250 mA	81 %
TEL 3-0522		15 VDC	200 mA	81 %
TEL 3-0523		12 VDC	125 mA	81 %
TEL 3-0511	36 – 75 VDC	5 VDC	600 mA	77 %
TEL 3-0512		12 VDC	250 mA	81 %
TEL 3-0513		15 VDC	200 mA	81 %
TEL 3-0512		12 VDC	125 mA	81 %

www.tracopower.com

Page 1

TRACO
POWER

DC/DC Converter
TEL 3 Series 3 Watt

Input Specifications

Input current (no load)	5 Vin models 12 Vin models 20 Vin models 24 Vin models 48 Vin models	40 mA typ. 20 mA typ. 15 mA typ. 5 mA typ. 3 mA typ.
Input current (full load)	5 Vin models 12 Vin models 20 Vin models 24 Vin models 48 Vin models	820 mA typ. 320 mA typ. 190 mA typ. 155 mA typ. 80 mA typ.

Surge voltage (1 sec. max.)

5 Vin models	11 VDC
12 Vin models	25 VDC
20 Vin models	50 VDC
24 Vin models	50 VDC
48 Vin models	100 VDC

Reverse voltage protection

1.0 A max.

Output Specifications

Voltage set accuracy

± 1 %

Regulation

± 0.5 % max.

– Load variation 5 Vin max.

– Load variation 5 – 100 %

– Single output models

– Dual output models balanced load

– Dual output models unbalanced load

– Temperature coefficient

± 0.02 % / °C

– Ripple and noise (20 MHz Bandwidth)

80 mV p-p typ.

– Temperature coefficient

± 0.02 % / °C

– Output current limitation

> 110% load max. constant current

– Short circuit protection

Hiccup mode, indefinite (automatic recovery)

– Capacitive load

2000 µF max.

– General Specifications

1000 µF max.

– Temperature range

– Operating

–25 °C – +75 °C

– Storage

+55 °C max.

– Humidity non condensing

95 % rel. H max.

– Reliability calculated MTBF (MIL-HDBK-217 E)

> 1 Mio. h @ +25 °C

– Isolation voltage

1000 VDC

– Isolation capacity

500 pF typ.

– Isolation resistance

> 1.000 M Ohm

– Switching frequency

300 kHz typ. (Pulse frequency modulation PWM)

– Safety standards

UL 1950, EN 60950, IEC 60950

– Compliance up to 60 VDC input voltage

(SELV limit)

– Safety approvals

UL dUL, PSE, ENEC, etc.

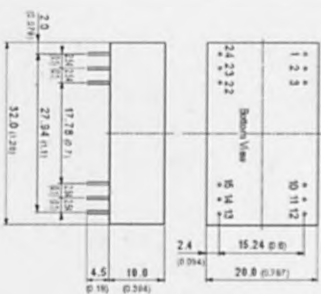
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Physical Specifications

Case material	non conductive black plastic
Plating material	silver rubber (UL94V-0 rated)
Weight	12 g (0.42 oz)
Soldering temperature	max. 250 °C / 10 min.

Outline Dimensions mm (inches)



Pin diameter: 0.5 ± 0.05 (0.02) to 0.02
Tolerances: ±0.5 (0.02)

Pin-Out

Pin	Single	Dual
1	+Vin (Nci)	+Vin (Nci)
2	No function	-Vbat
3	No function	Common
10	-Vbat	Common
11	+Vbat	+Vbat
12	-Vin (ON Di)	-Vin (ON Di)
13	-Vin (ON Di)	-Vin (ON Di)
14	+Vbat	+Vbat
15	-Vbat	Common
22	No function	Common
23	No function	-Vbat
24	+Vin (Nci)	+Vin (Nci)

Specifications can be changed without notice

TRACO

ELECTRONIC AG

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Rev. 09/02

